## Arm ${ }^{\circledR}$ Cortex $^{\circledR}$-M7 32b MCU+FPU, 462DMIPS, up to 2MB Flash/ $512+16+4 K B$ RAM, USB OTG HS/FS, 28 com IF, LCD, DSI

## Features

- Core: Arm ${ }^{\circledR}$ 32-bit Cortex ${ }^{\circledR}-\mathrm{M} 7$ CPU with DPFPU, ART Accelerator ${ }^{\text {TM }}$ and L1-cache: 16 Kbytes I/D cache, allowing 0-wait state execution from embedded Flash and external memories, up to 216 MHz , MPU, 462 DMIPS/2.14 DMIPS/MHz (Dhrystone 2.1), and DSP instructions.
- Memories
- Up to 2 Mbytes of Flash memory organized into two banks allowing read-while-write
- SRAM: 512 Kbytes (including 128 Kbytes of data TCM RAM for critical real-time data) + 16 Kbytes of instruction TCM RAM (for critical real-time routines) +4 Kbytes of backup SRAM
- Flexible external memory controller with up to 32-bit data bus: SRAM, PSRAM, SDRAM/LPSDR SDRAM, NOR/NAND memories
- Dual mode Quad-SPI
- Graphics
- Chrom-ART Accelerator ${ }^{\text {TM }}$ (DMA2D), graphical hardware accelerator enabling enhanced graphical user interface
- Hardware JPEG codec
- LCD-TFT controller supporting up to XGA resolution
- MIPI ${ }^{\circledR}$ DSI host controller supporting up to 720p 30 Hz resolution
- Clock, reset and supply management
- 1.7 V to 3.6 V application supply and I/Os
- POR, PDR, PVD and BOR
- Dedicated USB power
- 4-to-26 MHz crystal oscillator
- Internal 16 MHz factory-trimmed RC (1\% accuracy)
- 32 kHz oscillator for RTC with calibration
- Internal 32 kHz RC with calibration

- Low-power
- Sleep, Stop and Standby modes
- $V_{\text {BAT }}$ supply for RTC, $32 \times 32$ bit backup registers +4 Kbytes backup SRAM
- 3×12-bit, 2.4 MSPS ADC: up to 24 channels
- Digital filters for sigma delta modulator (DFSDM), 8 channels / 4 filters
- $2 \times 12$-bit D/A converters
- General-purpose DMA: 16-stream DMA controller with FIFOs and burst support
- Up to 18 timers: up to thirteen 16-bit ( $1 \times$ lowpower 16-bit timer available in Stop mode) and two 32-bit timers, each with up to 4 IC/OC/PWM or pulse counter and quadrature (incremental) encoder input. All 15 timers running up to 216 MHz . 2 x watchdogs, SysTick timer
- Debug mode
- SWD \& JTAG interfaces
- Cortex ${ }^{\circledR}$-M7 Trace Macrocell ${ }^{\text {TM }}$
- Up to 168 I/O ports with interrupt capability
- Up to 164 fast I/Os up to 108 MHz
- Up to 1665 V-tolerant I/Os
- Up to 28 communication interfaces
- Up to $4 I^{2} \mathrm{C}$ interfaces (SMBus/PMBus)
- Up to 4 USARTs/4 UARTs (12.5 Mbit/s, ISO7816 interface, LIN, IrDA, modem control)
- Up to 6 SPIs (up to $54 \mathrm{Mbit} / \mathrm{s}$ ), 3 with muxed simplex $I^{2} S$ for audio
- $2 \times$ SAls (serial audio interface)
- $3 \times$ CANs (2.0B Active) and $2 x$ SDMMCs
- SPDIFRX interface
- HDMI-CEC
- MDIO slave interface
- Advanced connectivity
- USB 2.0 full-speed device/host/OTG controller with on-chip PHY
- USB 2.0 high-speed/full-speed device/host/OTG controller with dedicated DMA, on-chip full-speed PHY and ULPI
- 10/100 Ethernet MAC with dedicated DMA: supports IEEE 1588v2 hardware, MII/RMII
- 8- to 14 -bit camera interface up to $54 \mathrm{Mbyte} / \mathrm{s}$
- True random number generator
- CRC calculation unit
- RTC: subsecond accuracy, hardware calendar
- 96-bit unique ID

Table 1. Device summary

| Reference | Part number |
| :--- | :--- |
| STM32F765xx | STM32F765BI, STM32F765BG, STM32F765NI, STM32F765NG, STM32F765II, <br> STM32F765IG, STM32F765ZI, STM32F765ZG, STM32F765VI, STM32F765VG |
| STM32F767xx | STM32F767BG, STM32F767BI, STM32F767IG, STM32F767II, STM32F767NG, <br> STM32F767NI, STM32F767VG, STM32F767VI, STM32F767ZG, STM32F767ZI |
| STM32F768Ax | STM32F768AI |
| STM32F769xx | STM32F769AG, STM32F769AI, STM32F769BG, STM32F769BI, STM32F769IG, <br> STM32F769II, STM32F769NG, STM32F769NI |

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## 1 Description

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices are based on the high-performance $\mathrm{Arm}^{\circledR}$ Cortex $^{\circledR}$-M7 32-bit RISC core operating at up to 216 MHz frequency. The Cortex ${ }^{\circledR}-\mathrm{M} 7$ core features a floating point unit (FPU) which supports Arm ${ }^{\circledR}$ double-precision and single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances the application security.

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices incorporate high-speed embedded memories with a Flash memory up to 2 Mbytes, 512 Kbytes of SRAM (including 128 Kbytes of Data TCM RAM for critical real-time data), 16 Kbytes of instruction TCM RAM (for critical real-time routines), 4 Kbytes of backup SRAM available in the lowest power modes, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, two AHB buses, a 32-bit multi-AHB bus matrix and a multi layer AXI interconnect supporting internal and external memories access.
All the devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve generalpurpose 16-bit timers including two PWM timers for motor control, two general-purpose 32bit timers, a true random number generator (RNG). They also feature standard and advanced communication interfaces:

- Up to four I2Cs
- Six SPIs, three I2Ss in half-duplex mode. To achieve audio class accuracy, the I2S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus four UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI)
- Three CANs
- Two SAI serial audio interfaces
- Two SDMMC host interfaces
- Ethernet and camera interfaces
- LCD-TFT display controller
- Chrom-ART Accelerator ${ }^{\text {TM }}$
- SPDIFRX interface
- HDMI-CEC

Advanced peripherals include two SDMMC interfaces, a flexible memory control (FMC) interface, a Quad-SPI Flash memory interface, a camera interface for CMOS sensors.

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices operate in the -40 to $+105^{\circ} \mathrm{C}$ temperature range from a 1.7 to 3.6 V power supply. Dedicated supply inputs for USB (OTG_FS and OTG_HS) and SDMMC2 (clock, command and 4-bit data) are available on all the packages except LQFP100 for a greater power supply choice.
The supply voltage can drop to 1.7 V with the use of an external power supply supervisor. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices offer devices in 11 packages ranging from 100 pins to 216 pins. The set of included peripherals changes with the device chosen.

These features make the STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx microcontrollers suitable for a wide range of applications:

- Motor drive and application control
- Medical equipment
- Industrial applications: PLC, inverters, circuit breakers
- Printers, and scanners
- Alarm systems, video intercom, and HVAC
- Home audio appliances
- Mobile applications, Internet of Things
- Wearable devices: smartwatches

The following table lists the peripherals available on each part number.
Table 2. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx features and

| Periph | erals | $\underset{765}{\text { STM }^{2}}$ | $\begin{aligned} & \text { M32F } \\ & 5 \mathrm{Vx} \end{aligned}$ | $\begin{array}{\|c} \text { STM3; } \\ \text { I76 } \end{array}$ | $\begin{aligned} & 2 F 767 \\ & 9 \mathrm{Vx} \end{aligned}$ | $\begin{gathered} \text { STM } \\ 765 \end{gathered}$ | [32F | $\begin{array}{r} \text { STM3 } \\ \hline 76 \end{array}$ | $\begin{aligned} & 2 F 767 \\ & 9 Z x \end{aligned}$ | $\begin{array}{r} \text { STM } \\ 769 \end{array}$ | 32F | $\underset{768 \mathrm{Ax}}{\mathrm{ST}_{2}}$ | $\begin{gathered} \text { STM } \\ 76 \end{gathered}$ | $\begin{aligned} & 132 F \\ & 51 \times \end{aligned}$ | $\begin{array}{r} \text { STM3 } \\ 176 \end{array}$ | $\underset{\text { OIv }}{2 F 767}$ |  | $\begin{aligned} & 332 F \\ & 5 \mathrm{Bx} \end{aligned}$ | $\begin{array}{\|c} \text { STM3 } \\ \hline \end{array}$ | $27767$ |  | $\begin{aligned} & 132 F \\ & { }_{5}^{2} \times \end{aligned}$ | $\begin{gathered} \text { STM32 } \\ \hline 769 \end{gathered}$ | $2 F 767$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Flash memory in | Kbytes | 1024 | 2048 | 1024 | 2048 | 1024 | 2048 | 1024 | 2048 | 1024 | 2048 | 2048 | 1024 | 2048 | 1024 | 2048 | 1024 | 2048 | 1024 | 2048 | 1024 | 2048 | 1024 | 2048 |
|  | System |  |  |  |  |  |  |  |  |  |  | 512(36 | +16+ | 128) |  |  |  |  |  |  |  |  |  |  |
| SRAM in | Instruction |  |  |  |  |  |  |  |  |  |  |  | 16 |  |  |  |  |  |  |  |  |  |  |  |
|  | Backup |  |  |  |  |  |  |  |  |  |  |  | 4 |  |  |  |  |  |  |  |  |  |  |  |
| FMC memory co | troller |  |  |  |  |  |  |  |  |  |  |  | es ${ }^{11}$ |  |  |  |  |  |  |  |  |  |  |  |
| Quad-SPI |  |  |  |  |  |  |  |  |  |  |  |  | Yes |  |  |  |  |  |  |  |  |  |  |  |
| Ethernet |  |  |  |  | Y |  |  |  |  |  | No |  |  |  |  |  |  |  | es |  |  |  |  |  |
|  | Generalpurpose |  |  |  |  |  |  |  |  |  |  |  | 10 |  |  |  |  |  |  |  |  |  |  |  |
| Timers | Advancedcontrol |  |  |  |  |  |  |  |  |  |  |  | 2 |  |  |  |  |  |  |  |  |  |  |  |
|  | Basic |  |  |  |  |  |  |  |  |  |  |  | 2 |  |  |  |  |  |  |  |  |  |  |  |
|  | Low-power |  |  |  |  |  |  |  |  |  |  |  | 1 |  |  |  |  |  |  |  |  |  |  |  |
| Random number | generator |  |  |  |  |  |  |  |  |  |  |  | Yes |  |  |  |  |  |  |  |  |  |  |  |
|  | $\mathrm{SPI} / \mathrm{I}^{2} \mathrm{~S}$ |  | 4/3 (sin | plex) ${ }^{(2)}$ |  |  |  |  |  |  |  |  |  | 6/3 ( | (implex |  |  |  |  |  |  |  |  |  |
|  | $1^{2} \mathrm{C}$ |  |  |  |  |  |  |  |  |  |  |  | 4 |  |  |  |  |  |  |  |  |  |  |  |
|  | USART/UART |  |  |  |  |  |  |  |  |  |  |  | 4/4 |  |  |  |  |  |  |  |  |  |  |  |
|  | USB OTG FS |  |  |  |  |  |  |  |  |  |  |  | Yes |  |  |  |  |  |  |  |  |  |  |  |
| ation | USB OTG HS |  |  |  |  |  |  |  |  |  |  |  | Yes |  |  |  |  |  |  |  |  |  |  |  |
| ces | CAN |  |  |  |  |  |  |  |  |  |  |  | 3 |  |  |  |  |  |  |  |  |  |  |  |
|  | SAI |  |  |  |  |  |  |  |  |  |  |  | 2 |  |  |  |  |  |  |  |  |  |  |  |
|  | SPDIFRX |  |  |  |  |  |  |  |  |  |  |  | nputs |  |  |  |  |  |  |  |  |  |  |  |
|  | SDMMC1 |  |  |  |  |  |  |  |  |  |  |  | Yes |  |  |  |  |  |  |  |  |  |  |  |
|  | SDMMC2 |  |  |  |  |  |  |  |  |  |  |  | Yes ${ }^{(3)}$ |  |  |  |  |  |  |  |  |  |  |  |
| Camera interface |  | Yes |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |
| MIPI-DSI Host ${ }^{(4)}$ |  | No |  |  |  |  |  |  |  | Yes |  |  | No |  | Yes |  | No |  | Yes |  | No |  | Yes |  |
| LCD-TFT |  | No |  | Yes |  | No |  | Yes |  |  |  |  | No |  | Yes |  | No |  | Yes |  | No |  | Yes |  |

Table 2. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx features and

| Peripherals | $\begin{gathered} \text { STM }_{765 \mathrm{~V}} \mathrm{ST} \end{gathered}$ | $\begin{gathered} \text { STM32F767 } \\ \text { I769Vx } \end{gathered}$ | $\begin{aligned} & \text { STM }{ }_{7652 F} \end{aligned}$ | $\begin{array}{\|c} \hline \text { STM32F767 } \\ \text { I769Zx } \end{array}$ | $\begin{aligned} & \text { STM32F } \\ & 769 \mathrm{Ax} \end{aligned}$ | $\begin{aligned} & \text { STM } 32 F \\ & 768 \mathrm{Ax} \end{aligned}$ | $\begin{gathered} \text { STM }{ }_{7651 x} \end{gathered}$ | $\begin{array}{\|c} \text { STM32F767 } \\ \text { I7691x } \end{array}$ | $\begin{aligned} & \text { STM } 32 \mathrm{~F} 2 \mathrm{Bx} \end{aligned}$ | $\begin{aligned} & \text { STM32F767 } \\ & \text { /769Bx } \end{aligned}$ | STM32F | $\begin{aligned} & \text { STM32F767 } \\ & \text { /769Nx } \end{aligned}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Chrom-ART Accelerator ${ }^{\text {TM }}$ (DMA2D) | Yes |  |  |  |  |  |  |  |  |  |  |  |
| JPEG codec | No | Yes | No | Yes |  |  | No | Yes | No | Yes | No | Yes |
| GPIOs | 82 |  | 114 |  | 129 |  | 140 | 132 | 168 | 159 | 168 | 159 |
| DFSDM1 | Yes (4 filters) |  |  |  |  |  |  |  |  |  |  |  |
| 12-bit ADC | 3 |  |  |  |  |  |  |  |  |  |  |  |
| Number of channels | 16 |  | 24 |  |  |  |  |  |  |  |  |  |
| 12-bit DAC Number of channels | $\begin{gathered} \text { Yes } \\ 2 \end{gathered}$ |  |  |  |  |  |  |  |  |  |  |  |
| Maximum CPU frequency | $216 \mathrm{MHz}^{(5)}$ |  |  |  |  |  |  |  |  |  |  |  |
| Operating voltage | 1.7 to $3.6 \mathrm{~V}^{(6)}$ |  |  |  |  |  |  |  |  |  |  |  |
| Operating ter | Ambient temperatures: -40 to $+85^{\circ} \mathrm{C} /-40$ to $+105^{\circ} \mathrm{C}$ |  |  |  |  |  |  |  |  |  |  |  |
|  | Junction temperature: -40 to $+125^{\circ} \mathrm{C}$ |  |  |  |  |  |  |  |  |  |  |  |
| Package | $\begin{aligned} & \text { LQFP100 } \\ & \text { TFBGA100 } \end{aligned}$ |  | LQFP144 |  | WLCSP180 |  | $\begin{gathered} \hline \text { UFBGA176 }{ }^{(7)} \\ \text { LQFP176 } \end{gathered}$ |  | LQFP208 |  | TFBGA216 |  |

[^0]
## Full compatibility throughout the family

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices are fully pin-to-pin, compatible with the STM32F4xxxx devices, allowing the user to try different peripherals, and reaching higher performances (higher frequency) for a greater degree of freedom during the development cycle.

Figure 1 gives compatible board designs between the STM32F7xx and STM32F4xx families.

Figure 1. Compatible board design for LQFP100 package


The STM32F76x LQFP144, LQFP176, LQFP208, TFBGA216, UFBGA176 packages are fully pin to pin compatible with STM32F4xx devices.

Figure 2. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx block diagram


1. The timers connected to APB2 are clocked from TIMxCLK up to 216 MHz , while the timers connected to APB1 are clocked from TIMxCLK either up to 108 MHz or 216 MHz depending on TIMPRE bit configuration in the RCC_DCKCFGR register.

## 2 Functional overview

### 2.1 $\quad$ Arm ${ }^{\circledR}$ Cortex $^{\circledR}$-M7 with FPU

The Arm ${ }^{\circledR}$ Cortex ${ }^{\circledR}-\mathrm{M} 7$ with FPU processor is the latest generation of Arm processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering an outstanding computational performance and low interrupt latency.
The Cortex ${ }^{\circledR}-\mathrm{M} 7$ processor is a highly efficient high-performance featuring:

- Six-stage dual-issue pipeline
- Dynamic branch prediction
- Harvard caches (16 Kbytes of I-cache and 16 Kbytes of D-cache)
- 64-bit AXI4 interface
- 64-bit ITCM interface
- 2x32-bit DTCM interfaces

The processor supports the following memory interfaces:

- Tightly Coupled Memory (TCM) interface.
- Harvard instruction and data caches and AXI master (AXIM) interface.
- Dedicated low-latency AHB-Lite peripheral (AHBP) interface.

The processor supports a set of DSP instructions which allow an efficient signal processing and a complex algorithm execution.

It supports single and double precision FPU (floating point unit), speeds up software development by using metalanguage development tools, while avoiding saturation.

Figure 2 shows the general block diagram of the STM32F76xxx family.
Note: $\quad$ The Cortex ${ }^{\circledR}$-M7 with FPU core is binary compatible with the Cortex ${ }^{\circledR}$-M4 core.

### 2.2 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.
The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (realtime operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

### 2.3 Embedded Flash memory

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices embed a Flash memory of up to 2 Mbytes available for storing programs and data. The Flash interface features:

- Single /or Dual bank operating modes,
- Read-While-Write (RWW) in Dual bank mode.


### 2.4 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

### 2.5 Embedded SRAM

All the devices feature:

- System SRAM up to 512 Kbytes:
- SRAM1 on AHB bus Matrix: 368 Kbytes
- SRAM2 on AHB bus Matrix: 16 Kbytes
- DTCM-RAM on TCM interface (Tighly Coupled Memory interface): 128 Kbytes for critical real-time data.
- Instruction RAM (ITCM-RAM) 16 Kbytes:
- It is mapped on TCM interface and reserved only for CPU Execution/Instruction useful for critical real-time routines.

The Data TCM RAM is accessible by the GP-DMAs and peripherals DMAs through specific AHB slave of the CPU.The instruction TCM RAM is reserved only for CPU. It is accessed at CPU clock speed with 0 wait states.

- 4 Kbytes of backup SRAM

This area is accessible only from the CPU. Its content is protected against possible unwanted write accesses, and is retained in Standby or VBAT mode.

### 2.6 AXI-AHB bus matrix

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx system architecture is based on 2 sub-systems:

- An AXI to multi AHB bridge converting AXI4 protocol to AHB-Lite protocol:
- $3 x$ AXI to 32-bit AHB bridges connected to AHB bus matrix
- $\quad 1 x$ AXI to 64-bit AHB bridge connected to the embedded Flash memory
- A multi-AHB Bus-Matrix
- The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS, LCD-TFT, and DMA2D) and the slaves (Flash memory, RAM, FMC, Quad-SPI, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

Figure 3. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx AXI-AHB bus matrix architecture ${ }^{(1)}$


1. The above figure has large wires for 64-bits bus and thin wires for 32-bits bus.

### 2.7 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They feature dedicated FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.
Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. The configuration is made by software and the transfer sizes between the source and the destination are independent.

The DMA can be used with the main peripherals:

- $\quad S P I$ and $I^{2} S$
- $\quad \mathrm{I}^{2} \mathrm{C}$
- USART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDMMC
- Camera interface (DCMI)
- ADC
- SAI
- SPDIFRX
- Quad-SPI
- HDMI-CEC
- JPEG codec
- DFSDM1


### 2.8 Flexible memory controller (FMC)

The Flexible memory controller (FMC) includes three memory controllers:

- The NOR/PSRAM memory controller
- The NAND/memory controller
- The Synchronous DRAM (SDRAM/Mobile LPSDR SDRAM) controller

The main features of the FMC controller are the following:

- Interface with static-memory mapped devices including:
- $\quad$ Static random access memory (SRAM)
- NOR Flash memory/OneNAND Flash memory
- PSRAM (4 memory banks)
- NAND Flash memory with ECC hardware to check up to 8 Kbytes of data
- Interface with synchronous DRAM (SDRAM/Mobile LPSDR SDRAM) memories
- 8-,16-,32-bit data bus width
- Independent Chip Select control for each memory bank
- Independent configuration for each memory bank
- Write FIFO
- Read FIFO for SDRAM controller
- The maximum FMC_CLK/FMC_SDCLK frequency for synchronous accesses is HCLK/2


## LCD parallel interface

The FMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build costeffective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

### 2.9 Quad-SPI memory interface (QUADSPI)

All the devices embed a Quad-SPI memory interface, which is a specialized communication interface targetting Single, Dual or Quad-SPI Flash memories. It can work in:

- Direct mode through registers
- External Flash status register polling mode
- Memory mapped mode.

Up to 256 Mbytes external Flash are memory mapped, supporting 8, 16 and 32-bit access. Code execution is supported.

The opcode and the frame format are fully programmable. The communication can be either in Single Data Rate or Dual Data Rate.

### 2.10 LCD-TFT controller

The LCD-TFT display controller provides a 24 -bit parallel digital RGB (Red, Green, Blue) and delivers all signals to interface directly to a broad range of LCD and TFT panels up to XGA (1024x768) resolution with the following features:

- 2 display layers with dedicated FIFO ( $64 \times 32$-bit)
- Color Look-Up table (CLUT) up to 256 colors (256x24-bit) per layer
- Up to 8 input color formats selectable per layer
- Flexible blending between two layers using alpha value (per pixel or constant)
- Flexible programmable parameters for each layer
- Color keying (transparency color)
- Up to 4 programmable interrupt events


### 2.11 Chrom-ART Accelerator ${ }^{\text {TM }}$ (DMA2D)

The Chrom-Art Accelerator ${ }^{\text {TM }}$ (DMA2D) is a graphic accelerator which offers advanced bit blitting, row data copy and pixel format conversion. It supports the following functions:

- Rectangle filling with a fixed color
- Rectangle copy
- Rectangle copy with pixel format conversion
- Rectangle composition with blending and pixel format conversion

Various image format codings are supported, from indirect 4bpp color mode up to 32bpp direct color. It embeds dedicated memory to store color lookup tables.

An interrupt can be generated when an operation is complete or at a programmed watermark.

All the operations are fully automatized and are running independently from the CPU or the DMAs.

### 2.12 Nested vectored interrupt controller (NVIC)

The devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 110 maskable interrupt channels plus the 16 interrupt lines of the Cortex ${ }^{\circledR}$ M7 with FPU core.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

### 2.13 JPEG codec (JPEG)

The JPEG codec provides an fast and simple hardware compressor and decompressor of JPEG images with full management of JPEG headers.

The JPEG codec main features:

- 8-bit/channel pixel depths
- Single clock per pixel encoding and decoding
- Support for JPEG header generation and parsing
- Up to four programmable quantization tables
- Fully programmable Huffman tables (two AC and two DC)
- Fully programmable minimum coded unit (MCU)
- Encode/decode support (non simultaneous)
- Single clock Huffman coding and decoding
- Two-channel interface: Pixel/Compress In, Pixel/Compressed Out
- Stallable design
- Support for single, greyscale component
- Functionality to enable/disable header processing
- Internal register interface
- Fully synchronous design
- Configured for high-speed decode mode


### 2.14 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 25 edge-detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 168 GPIOs can be connected to the 16 external interrupt lines.

### 2.15 Clocks and startup

On reset the 16 MHz internal HSI RC oscillator is selected as the default CPU clock. The 16 MHz internal RC oscillator is factory-trimmed to offer $1 \%$ accuracy. The application can then select as system clock either the RC oscillator or an external $4-26 \mathrm{MHz}$ clock source. This clock can be monitored for failure. If a failure is detected, the system automatically switches back to the internal RC oscillator and a software interrupt is generated (if enabled). This clock source is input to a PLL thus allowing to increase the frequency up to 216 MHz . Similarly, full interrupt management of the PLL clock entry is available when necessary (for example if an indirectly used external oscillator fails).
Several prescalers allow the configuration of the two AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the two AHB buses is 216 MHz while the maximum frequency of the high-speed APB domains is 108 MHz . The maximum allowed frequency of the low-speed APB domain is 54 MHz .

The devices embed two dedicated PLL (PLLI2S and PLLSAI) which allow to achieve audio class performance. In this case, the $\mathrm{I}^{2} \mathrm{~S}$ and SAI master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz .

### 2.16 Boot modes

At startup, the boot memory space is selected by the BOOT pin and BOOT_ADDx option bytes, allowing to program any boot memory address from $0 \times 00000000$ to $0 \times 3 F F F$ FFFF which includes:

- All Flash address space mapped on ITCM or AXIM interface
- All RAM address space: ITCM, DTCM RAMs and SRAMs mapped on AXIM interface
- The System memory bootloader

The boot loader is located in system memory. It is used to reprogram the Flash memory through a serial interface. Refer to STM32 microcontroller system memory boot mode application note (AN2606) for details.

### 2.17 Power supply schemes

- $\quad \mathrm{V}_{\mathrm{DD}}=1.7$ to 3.6 V : external power supply for I/Os and the internal regulator (when enabled), provided externally through $\mathrm{V}_{\mathrm{DD}}$ pins.
- $\quad V_{S S A}, V_{\text {DDA }}=1.7$ to 3.6 V : external analog power supplies for ADC, DAC, Reset blocks, RCs and PLL. $V_{D D A}$ and $V_{S S A}$ must be connected to $V_{D D}$ and $V_{S S}$, respectively.
- $\quad V_{B A T}=1.65$ to 3.6 V : power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when $\mathrm{V}_{\mathrm{DD}}$ is not present.

Note: $\quad V_{D D} / V_{D D A}$ minimum value of 1.7 V is obtained when the internal reset is OFF (refer to Section 2.18.2: Internal reset OFF). Refer to Table 3: Voltage regulator configuration mode versus device operating mode to identify the packages supporting this option.

- $\quad V_{\text {DDSDMMC }}$ can be connected either to $V_{D D}$ or an external independent power supply (1.8 to 3.6 V ) for SDMMC2 pins (clock, command, and 4-bit data). For example, when the device is powered at 1.8 V , an independent power supply 2.7 V can be connected to $\mathrm{V}_{\text {DDSDMMC }}$. When the $\mathrm{V}_{\text {DDSDMMC }}$ is connected to a separated power supply, it is independent from $V_{D D}$ or $V_{D D A}$ but it must be the last supply to be provided and the first to disappear. The following conditions $\mathrm{V}_{\text {DDSDMMC }}$ must be respected:
- During the power-on phase ( $\mathrm{V}_{\mathrm{DD}}<\mathrm{V}_{\mathrm{DD}}$ MIN $), \mathrm{V}_{\text {DDSDMMC }}$ should be always lower than $V_{D D}$
- During the power-down phase $\left(\mathrm{V}_{\mathrm{DD}}<\mathrm{V}_{\mathrm{DD} \_\mathrm{MIN}}\right), \mathrm{V}_{\text {DDSDMMC }}$ should be always lower than $\mathrm{V}_{\mathrm{DD}}$
- The $\mathrm{V}_{\text {DDSDMMC }}$ rising and falling time rate specifications must be respected
- In operating mode phase, $\mathrm{V}_{\text {DDSDMMC }}$ could be lower or higher than $\mathrm{V}_{\mathrm{DD}}$ : All associated GPIOs powered by $\mathrm{V}_{\text {DSSDMMC }}$ are operating between $V_{\text {DDSDMMC_MIN }}$ and $V_{\text {DDSDMMC_MAX. }}$
- $\quad V_{\text {DDUSB }}$ can be connected either to $\mathrm{V}_{\text {DD }}$ or an external independent power supply (3.0 to 3.6 V ) for USB transceivers (refer to Figure 4 and Figure 5). For example, when the device is powered at 1.8 V , an independent power supply 3.3 V can be connected to $V_{\text {DDUSB }}$. When the $V_{\text {DDUSB }}$ is connected to a separated power supply, it is independent from $V_{D D}$ or $V_{D D A}$ but it must be the last supply to be provided and the first to
disappear. The following conditions $V_{\text {DDUSB }}$ must be respected:
- During the power-on phase ( $\left.\mathrm{V}_{\mathrm{DD}}<\mathrm{V}_{\mathrm{DD}} \mathrm{MII}\right), \mathrm{V}_{\mathrm{DDUSB}}$ should be always lower than $V_{D D}$
- $\quad$ During the power-down phase $\left(\mathrm{V}_{\mathrm{DD}}<\mathrm{V}_{\mathrm{DD}} \mathrm{MII}\right), \mathrm{V}_{\mathrm{DDUSB}}$ should be always lower than $V_{D D}$
- The $V_{\text {DDUSB }}$ rising and falling time rate specifications must be respected (see Table 20 and Table 21)
- In operating mode phase, $\mathrm{V}_{\mathrm{DDUSB}}$ could be lower or higher than $\mathrm{V}_{\mathrm{DD}}$ : - If USB (USB OTG_HS/OTG_FS) is used, the associated GPIOs powered by $V_{\text {DDUSB }}$ are operating between $V_{\text {DDUSB_MIN }}$ and $V_{\text {DDUSB_MAX }}$.
- The VDDUSB supply both USB transceiver (USB OTG_HS and USB OTG_FS). If only one USB transceiver is used in the application, the GPIOs associated to the other USB transceiver are still supplied by $\mathrm{V}_{\text {DDUSB }}$.
- If USB (USB OTG_HS/OTG_FS) is not used, the associated GPIOs powered by $V_{\text {DDUSB }}$ are operating between $V_{D D \_M I N}$ and $V_{D D \_M A X}$.

Figure 4. $\mathrm{V}_{\text {DDUSB }}$ connected to $\mathrm{V}_{\text {DD }}$ power supply


Figure 5. $\mathrm{V}_{\text {DDUSB }}$ connected to external power supply


The DSI (Display Serial Interface) sub-system uses several power supply pins which are independent from the other supply pins:

- $\quad V_{\text {DDDSI }}$ is an independent DSI power supply dedicated for DSI Regulator and MIPI D-PHY. This supply must be connected to global $\mathrm{V}_{\mathrm{DD}}$.
- $\quad$ The $\mathrm{V}_{\text {CAPDSI }}$ pin is the output of DSI Regulator (1.2V) which must be connected externally to $\mathrm{V}_{\text {DD12DSI }}$.
- The $V_{\text {DD12DSI }}$ pin is used to supply the MIPI D-PHY, and to supply the clock and data lanes pins. An external capacitor of 2.2 uF must be connected on the $V_{\text {DD12DSI }}$ pin.
- The $\mathrm{V}_{\text {SSDSI }}$ pin is an isolated supply ground used for DSI sub-system.
- If the DSI functionality is not used at all, then:
- The $\mathrm{V}_{\text {DDDSI }}$ pin must be connected to global $\mathrm{V}_{\mathrm{DD}}$.
- The $\mathrm{V}_{\text {CAPDSI }}$ pin must be connected externally to $\mathrm{V}_{\text {DD12DSI }}$ but the external capacitor is no more needed.
- The $\mathrm{V}_{\text {SSDSI }}$ pin must be grounded.


### 2.18 Power supply supervisor

### 2.18.1 Internal reset ON

On packages embedding the PDR_ON pin, the power supply supervisor is enabled by holding PDR_ON high. On the other packages, the power supply supervisor is always enabled.

The device has an integrated power-on reset (POR)/ power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR/PDR is always active and ensures proper operation starting from 1.8 V . After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default BOR thresholds, or to disable BOR permanently. Three BOR thresholds are available through
option bytes. The device remains in reset mode when $\mathrm{V}_{\mathrm{DD}}$ is below a specified threshold, $V_{\text {POR/PDR }}$ or $\mathrm{V}_{\mathrm{BOR}}$, without the need for an external reset circuit.
The device also features an embedded programmable voltage detector (PVD) that monitors the $\mathrm{V}_{\mathrm{DD}} / \mathrm{V}_{\mathrm{DDA}}$ power supply and compares it to the $\mathrm{V}_{\mathrm{PVD}}$ threshold. An interrupt can be generated when $\mathrm{V}_{\mathrm{DD}} / \mathrm{V}_{\mathrm{DDA}}$ drops below the $\mathrm{V}_{\mathrm{PVD}}$ threshold and/or when $\mathrm{V}_{\mathrm{DD}} / \mathrm{V}_{\mathrm{DDA}}$ is higher than the $\mathrm{V}_{\mathrm{PVD}}$ threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

### 2.18.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled through the PDR_ON pin.
An external power supply supervisor should monitor $V_{D D}$ and NRST and should maintain the device in reset mode as long as $\mathrm{V}_{\mathrm{DD}}$ is below a specified threshold. PDR_ON should be connected to $\mathrm{V}_{\mathrm{SS}}$. Refer to Figure 6: Power supply supervisor interconnection with internal reset OFF.

Figure 6. Power supply supervisor interconnection with internal reset OFF


The $\mathrm{V}_{\mathrm{DD}}$ specified threshold, below which the device must be maintained under reset, is 1.7 V (see Figure 7).

A comprehensive set of power-saving mode allows to design low-power applications.
When the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry must be disabled
- The embedded programmable voltage detector (PVD) is disabled
- $\quad V_{B A T}$ functionality is no more available and $V_{B A T}$ pin should be connected to $V_{D D}$. All the packages, except for the LQFP100, allow to disable the internal reset through the PDR_ON signal when connected to $\mathrm{V}_{\mathrm{SS}}$.

Figure 7. PDR_ON control with internal reset OFF


### 2.19 Voltage regulator

The regulator has four operating modes:

- Regulator ON
- Main regulator mode (MR)
- Low power regulator (LPR)
- Power-down
- Regulator OFF


### 2.19.1 Regulator ON

On packages embedding the BYPASS_REG pin, the regulator is enabled by holding BYPASS_REG low. On all other packages, the regulator is always enabled.
There are three power modes configured by software when the regulator is ON :

- MR mode used in Run/sleep modes or in Stop modes
- In Run/Sleep modes

The MR mode is used either in the normal mode (default mode) or the over-drive mode (enabled by software). Different voltages scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption. The over-drive mode allows operating at a higher frequency than the normal mode for a given voltage scaling.

- In Stop modes

The MR can be configured in two ways during stop mode:
MR operates in normal mode (default mode of MR in stop mode) MR operates in under-drive mode (reduced leakage mode).

- LPR is used in the Stop modes:

The LP regulator mode is configured by software when entering Stop mode. Like the MR mode, the LPR can be configured in two ways during stop mode:

- LPR operates in normal mode (default mode when LPR is ON)
- LPR operates in under-drive mode (reduced leakage mode).
- Power-down is used in Standby mode.

The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost.

Refer to Table 3 for a summary of voltage regulator modes versus device operating modes.
Two external ceramic capacitors should be connected on $\mathrm{V}_{\mathrm{CAP}} 1$ and $\mathrm{V}_{\mathrm{CAP}}$ 2 pin.
All packages have the regulator ON feature.
Table 3. Voltage regulator configuration mode versus device operating mode ${ }^{(1)}$

| Voltage regulator <br> configuration | Run mode | Sleep mode | Stop mode | Standby mode |
| :---: | :---: | :---: | :---: | :---: |
| Normal mode | MR | MR | MR or LPR | - |
| Over-drive <br> mode $^{(2)}$ | MR | MR | - | - |
| Under-drive mode | - | - | MR or LPR | - |
| Power-down <br> mode | - | - | - | Yes |

1. '-' means that the corresponding configuration is not available.
2. The over-drive mode is not available when $\mathrm{V}_{\mathrm{DD}}=1.7$ to 2.1 V .

### 2.19.2 Regulator OFF

This feature is available only on packages featuring the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a $\mathrm{V}_{12}$ voltage source through $\mathrm{V}_{\mathrm{CAP}} 1$ and $\mathrm{V}_{\mathrm{CAP}}$ 2 pins.
Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. The two $2.2 \mu \mathrm{~F}$ ceramic capacitors should be replaced by two 100 nF decoupling capacitors.
When the regulator is OFF, there is no more internal monitoring on $\mathrm{V}_{12}$. An external power supply supervisor should be used to monitor the $\mathrm{V}_{12}$ of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on $\mathrm{V}_{12}$ power domain.

In the regulator OFF mode, the following features are no more supported:

- PAO cannot be used as a GPIO pin since it allows to reset a part of the $\mathrm{V}_{12}$ logic power domain which is not reset by the NRST pin.
- As long as PAO is kept low, the debug mode cannot be used under power-on reset. As a consequence, PAO and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The over-drive and under-drive modes are not available.
- The Standby mode is not available.

Figure 8. Regulator OFF


The following conditions must be respected:

- $V_{D D}$ should always be higher than $\mathrm{V}_{\text {CAP_1 }}$ and $\mathrm{V}_{\mathrm{CAP} \text { _ } 2}$ to avoid current injection between power domains.
- If the time for $\mathrm{V}_{\text {CAP_1 }}$ and $\mathrm{V}_{\text {CAP_2 }}$ to reach $\mathrm{V}_{12}$ minimum value is faster than the time for $\mathrm{V}_{\mathrm{DD}}$ to reach $1.7 \mathrm{~V}^{-}$then PA0 should be kept low to cover both conditions: until $\mathrm{V}_{\mathrm{CAP}} 1$ and $\mathrm{V}_{\mathrm{CAP} \text { _ } 2}$ reach $\mathrm{V}_{12}$ minimum value and until $\mathrm{V}_{\mathrm{DD}}$ reaches 1.7 V (see Figure 9).
- Otherwise, if the time for $\mathrm{V}_{\text {CAP }_{-1} 1}$ and $\mathrm{V}_{\text {CAP }_{-}}$to reach $\mathrm{V}_{12}$ minimum value is slower than the time for $\mathrm{V}_{\mathrm{DD}}$ to reach $\overline{1} .7 \mathrm{~V}$, then PAO could be asserted low externally (see Figure 10).
- If $V_{C A P \_1}$ and $V_{C A P \_2}$ go below $V_{12}$ minimum value and $V_{D D}$ is higher than 1.7 V , then a reset must be asserted on PA0 pin.
Note: $\quad$ The minimum value of $V_{12}$ depends on the maximum frequency targeted in the application.

Figure 9. Startup in regulator OFF: slow $\mathrm{V}_{\mathrm{DD}}$ slope - power-down reset risen after $\mathrm{V}_{\mathrm{CAP} 1}, \mathrm{~V}_{\mathrm{CAP} 2}$ stabilization


1. This figure is valid whatever the internal reset mode (ON or OFF).

Figure 10. Startup in regulator OFF mode: fast $\mathrm{V}_{\mathrm{DD}}$ slope - power-down reset risen before $\mathrm{V}_{\mathrm{CAP}}{ }_{1}, \mathrm{~V}_{\mathrm{CAP}}$ 2 stabilization


1. This figure is valid whatever the internal reset mode (ON or OFF).

### 2.19.3 Regulator ON/OFF and internal reset ON/OFF availability

Table 4. Regulator ON/OFF and internal reset ON/OFF availability

| Package | Regulator ON | Regulator OFF | Internal reset ON | Internal reset OFF |
| :---: | :---: | :---: | :---: | :---: |
| LQFP100 | Yes | No | Yes | No |
| LQFP144, <br> LQFP208 |  |  | $\begin{gathered} \text { Yes } \\ \text { PDR_ON set to } V_{D D} \end{gathered}$ | $\begin{gathered} \text { Yes } \\ \text { PDR_ON set to } V_{S S} \end{gathered}$ |
| LQFP176, UFBGA176, TFBGA100, TFBGA216 | Yes <br> BYPASS_REG set to $V_{S S}$ | Yes <br> BYPASS REG set to $V_{D D}$ |  |  |
| WLCSP180 | Yes ${ }^{(1)}$ |  |  |  |

1. Available only on dedicated part number. Refer to Section 7: Ordering information.

### 2.20 Real-time clock (RTC), backup SRAM and backup registers

The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Two programmable alarms.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock ( 50 or 60 Hz ) can be used to enhance the calendar precision.
- Digital calibration circuit with 0.95 ppm resolution, to compensate for quartz crystal inaccuracy.
- Three anti-tamper detection pins with programmable filter.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event, or by a switch to $V_{B A T}$ mode.
- 17-bit auto-reload wakeup timer (WUT) for periodic events with programmable resolution and period.

The RTC and the 32 backup registers are supplied through a switch that takes power either from the $\mathrm{V}_{\mathrm{DD}}$ supply when present or from the $\mathrm{V}_{\mathrm{BAT}}$ pin.

The backup registers are 32-bit registers used to store 128 bytes of user application data when VDD power is not present. They are not reset by a system or power reset, or when the device wakes up from Standby mode.

The RTC clock sources can be:

- A 32.768 kHz external crystal (LSE)
- An external resonator or oscillator(LSE)
- The internal low power RC oscillator (LSI, with typical frequency of 32 kHz )
- The high-speed external clock (HSE) divided by 32

The RTC is functional in $V_{B A T}$ mode and in all low-power modes when it is clocked by the LSE. When clocked by the LSI, the RTC is not functional in $V_{\text {BAT }}$ mode, but is functional in all low-power modes.

All RTC events (Alarm, WakeUp Timer, Timestamp or Tamper) can generate an interrupt and wakeup the device from the low-power modes.

### 2.21 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- Stop mode

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled.
The voltage regulator can be put either in main regulator mode (MR) or in low-power mode (LPR). Both modes can be configured as follows (see Table 5: Voltage regulator modes in stop mode):

- Normal mode (default mode when MR or LPR is enabled)
- Under-drive mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup and LPTIM1 asynchronous interrupt).

Table 5. Voltage regulator modes in stop mode

| Voltage regulator <br> configuration | Main regulator (MR) | Low-power regulator (LPR) |
| :---: | :---: | :---: |
| Normal mode | MR ON | LPR ON |
| Under-drive mode | MR in under-drive mode | LPR in under-drive mode |

- Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering

Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.
The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising or falling edge on one of the 6 WKUP pins (PA0, PA2, PC1, PC13, PI8, PI11), or an RTC alarm / wakeup / tamper /time stamp event occurs.
The Standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

### 2.22 $\quad \mathrm{V}_{\mathrm{BAT}}$ operation

The $\mathrm{V}_{\text {BAT }}$ pin allows to power the device $\mathrm{V}_{\mathrm{BAT}}$ domain from an external battery, an external supercapacitor, or from $V_{D D}$ when no external battery and an external supercapacitor are present.
$V_{B A T}$ operation is activated when $V_{D D}$ is not present.
The $\mathrm{V}_{\text {BAT }}$ pin supplies the RTC, the backup registers and the backup SRAM.
Note: $\quad$ When the microcontroller is supplied from $V_{B A T}$, external interrupts and RTC alarm/events do not exit it from $V_{B A T}$ operation.

When the PDR_ON pin is connected to $V_{S S}$ (Internal Reset OFF), the $V_{B A T}$ functionality is no more available and the $V_{B A T}$ pin should be connected to VDD.

### 2.23 Timers and watchdogs

The devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.
Table 6 compares the features of the advanced-control, general-purpose and basic timers.

Table 6. Timer feature comparison

| Timer type | Timer | Counter resolution | Counter type | Prescaler factor | DMA request generation | Capture/ compare channels | Complem entary output | ```Max interface clock (MHz)``` | $\begin{gathered} \text { Max } \\ \text { timer } \\ \text { clock } \\ (\mathrm{MHz})^{(1)} \end{gathered}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Advanced -control | TIM1, TIM8 | 16-bit | Up, Down, Up/down | Any integer between 1 and 65536 | Yes | 4 | Yes | 108 | 216 |
| General purpose | $\begin{aligned} & \text { TIM2, } \\ & \text { TIM5 } \end{aligned}$ | 32-bit | Up, Down, Up/down | Any integer between 1 and 65536 | Yes | 4 | No | 54 | 108/216 |
|  | TIM3, TIM4 | 16-bit | Up, Down, Up/down | Any integer between 1 and 65536 | Yes | 4 | No | 54 | 108/216 |
|  | TIM9 | 16-bit | Up | Any integer between 1 and 65536 | No | 2 | No | 108 | 216 |
|  | TIM10, TIM11 | 16-bit | Up | Any integer between 1 and 65536 | No | 1 | No | 108 | 216 |
|  | TIM12 | 16-bit | Up | Any integer between 1 and 65536 | No | 2 | No | 54 | 108/216 |
|  | TIM13, <br> TIM14 | 16-bit | Up | Any integer between 1 and 65536 | No | 1 | No | 54 | 108/216 |
| Basic | TIM6, TIM7 | 16-bit | Up | Any integer between 1 and 65536 | Yes | 0 | No | 54 | 108/216 |

1. The maximum timer clock is either 108 or 216 MHz depending on TIMPRE bit configuration in the RCC_DCKCFGR register.

### 2.23.1 Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0100\%).

The advanced-control timer can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

TIM1 and TIM8 support independent DMA request generation.

### 2.23.2 General-purpose timers (TIMx)

There are ten synchronizable general-purpose timers embedded in the STM32F76xxx devices (see Table 6 for differences).

- TIM2, TIM3, TIM4, TIM5

The STM32F76xxx include 4 full-featured general-purpose timers: TIM2, TIM5, TIM3, and TIM4.The TIM2 and TIM5 timers are based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The TIM3 and TIM4 timers are based on a 16bit auto-reload up/downcounter and a 16-bit prescaler. They all feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input capture/output compare/PWMs on the largest packages.
The TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together, or with the other general-purpose timers and the advanced-control timers TIM1 and TIM8 via the Timer Link feature for synchronization or event chaining.
Any of these general-purpose timers can be used to generate PWM outputs.
TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation. They are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 4 hall-effect sensors.

- TIM9, TIM10, TIM11, TIM12, TIM13, and TIM14

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10, TIM11, TIM13, and TIM14 feature one independent channel, whereas TIM9 and TIM12 have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers. They can also be used as simple time bases.

### 2.23.3 Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger and waveform generation. They can also be used as a generic 16-bit time base.
TIM6 and TIM7 support independent DMA request generation.

### 2.23.4 Low-power timer (LPTIM1)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wakeup the devices from Stop mode.
This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous / one-shot mode
- Selectable software / hardware input trigger
- Selectable clock source:
- Internal clock source: LSE, LSI, HSI or APB clock
- External clock source over LPTIM input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode


### 2.23.5 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes.

### 2.23.6 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

### 2.23.7 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source


### 2.24 Inter-integrated circuit interface $\left(I^{2} \mathrm{C}\right)$

The devices embed 4 I2C. Refer to table Table 7: I2C implementation for the features implementation.
The $I^{2} \mathrm{C}$ bus interface handles communications between the microcontroller and the serial $I^{2} \mathrm{C}$ bus. It controls all $I^{2} \mathrm{C}$ bus-specific sequencing, protocol, arbitration and timing.
The I2C peripheral supports:

- $\quad I^{2} C$-bus specification and user manual rev. 5 compatibility:
- Slave and master modes, multimaster capability
- Standard-mode (Sm), with a bitrate up to $100 \mathrm{kbit/} / \mathrm{s}$
- Fast-mode (Fm), with a bitrate up to $400 \mathrm{kbit} / \mathrm{s}$
- Fast-mode Plus (Fm+), with a bitrate up to $1 \mathrm{Mbit} / \mathrm{s}$ and 20 mA output drive I/Os
- 7-bit and 10-bit addressing mode, multiple 7-bit slave addresses
- Programmable setup and hold times
- Optional clock stretching
- System Management Bus (SMBus) specification rev 2.0 compatibility:
- Hardware PEC (Packet Error Checking) generation and verification with ACK control
- Address resolution protocol (ARP) support
- SMBus alert
- Power System Management Protocol (PMBus ${ }^{\text {TM }}$ ) specification rev 1.1 compatibility
- Independent clock: a choice of independent clock sources allowing the I2C communication speed to be independent from the PCLK reprogramming.
- Programmable analog and digital noise filters
- 1-byte buffer with DMA capability

Table 7. I2C implementation

| I2C features ${ }^{(\mathbf{1 )}}$ | 12C1 | I2C2 | I2C3 | 12C4 |
| :--- | :---: | :---: | :---: | :---: |
| Standard-mode (up to 100 kbit/s) | X | X | X | X |
| Fast-mode (up to 400 kbit/s) | X | X | X | X |
| Fast-mode Plus with 20 mA output drive I/Os (up to 1 Mbit/s) | X | X | X | X |
| Programmable analog and digital noise filters | X | X | X | X |
| SMBus/PMBus hardware support | X | X | X | X |
| Independent clock | X | X | X | X |

1. X : supported.

### 2.25 Universal synchronous/asynchronous receiver transmitters (USART)

The devices embed USART. Refer to Table 8: USART implementation for the features implementation.

The universal synchronous asynchronous receiver transmitter (USART) offers a flexible means of full-duplex data exchange with external equipment requiring an industry standard NRZ asynchronous serial data format.

The USART peripheral supports:

- Full-duplex asynchronous communications
- Configurable oversampling method by 16 or 8 to give flexibility between speed and clock tolerance
- Dual clock domain allowing convenient baud rate programming independent from the PCLK reprogramming
- A common programmable transmit and receive baud rate of up to $27 \mathrm{Mbit} / \mathrm{s}$ when the USART clock source is system clock frequency (max is 216 MHz ) and oversampling by 8 is used.
- Auto baud rate detection
- Programmable data word length (7 or 8 or 9 bits) word length
- Programmable data order with MSB-first or LSB-first shifting
- Programmable parity (odd, even, no parity)
- Configurable stop bits (1 or 1.5 or 2 stop bits)
- Synchronous mode and clock output for synchronous communications
- Single-wire half-duplex communications
- Separate signal polarity control for transmission and reception
- Swappable Tx/Rx pin configuration
- Hardware flow control for modem and RS-485 transceiver
- Multiprocessor communications
- LIN master synchronous break send capability and LIN slave break detection capability
- IrDA SIR encoder decoder supporting 3/16 bit duration for normal mode
- Smartcard mode ( T=0 and T=1 asynchronous protocols for Smartcards as defined in the ISO/IEC 7816-3 standard )
- Support for Modbus communication

Table 8 summarizes the implementation of all U(S)ARTs instances
Table 8. USART implementation

| features $^{(1)}$ | USART1/2/3/6 | UART4/5/7/8 |
| :--- | :---: | :---: |
| Data Length | 7,8 and 9 bits |  |
| Hardware flow control for modem | X | X |
| Continuous communication using DMA | X | X |
| Multiprocessor communication | X | X |
| Synchronous mode | X | C |

Table 8. USART implementation (continued)

| features $^{(1)}$ | USART1/2/3/6 | UART4/5/7/8 |
| :--- | :---: | :---: |
| Smartcard mode | X | - |
| Single-wire half-duplex communication | X | X |
| IrDA SIR ENDEC block | X | X |
| LIN mode | X | X |
| Dual clock domain | X | X |
| Receiver timeout interrupt | X | X |
| Modbus communication | X | X |
| Auto baud rate detection | X | X |
| Driver Enable | X | X |

1. X : supported.

### 2.26 Serial peripheral interface (SPI)/inter- integrated sound interfaces (I2S)

The devices feature up to six SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1, SPI4, SPI5, and SPI6 can communicate at up to $54 \mathrm{Mbits} / \mathrm{s}$, SPI2 and SPI3 can communicate at up to $25 \mathrm{Mbit} / \mathrm{s}$. The 3 -bit prescaler gives 8 master mode frequencies and the frame is configurable from 4 to 16 bits. The SPI interfaces support NSS pulse mode, TI mode and Hardware CRC calculation. All the SPIs can be served by the DMA controller.
Three standard ${ }^{2}$ S interfaces (multiplexed with SPI1, SPI2 and SPI3) are available. They can be operated in master or slave mode, in simplex communication modes, and can be configured to operate with a $16-/ 32$-bit resolution as an input or output channel. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the $I^{2} S$ interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.
All I2Sx can be served by the DMA controller.

### 2.27 Serial audio interface (SAI)

The devices embed two serial audio interfaces.
The serial audio interface is based on two independent audio subblocks which can operate as transmitter or receiver with their FIFO. Many audio protocols are supported by each block: I2S standards, LSB or MSB-justified, PCM/DSP, TDM, AC'97 and SPDIF output, supporting audio sampling frequencies from 8 kHz up to 192 kHz . Both subblocks can be configured in master or in slave mode.

In master mode, the master clock can be output to the external DAC/CODEC at 256 times of the sampling frequency.

The two sub-blocks can be configured in synchronous mode when full-duplex mode is required.

SAl1 and SAI2 can be served by the DMA controller

### 2.28 SPDIFRX Receiver Interface (SPDIFRX)

The SPDIFRX peripheral, is designed to receive an S/PDIF flow compliant with IEC-60958 and IEC-61937. These standards support simple stereo streams up to high sample rate, and compressed multi-channel surround sound, such as those defined by Dolby or DTS (up to 5.1).

The main features of the SPDIFRX are the following:

- Up to 4 inputs available
- Automatic symbol rate detection
- Maximum symbol rate: 12.288 MHz
- Stereo stream from 32 to 192 kHz supported
- Supports Audio IEC-60958 and IEC-61937, consumer applications
- Parity bit management
- Communication using DMA for audio samples
- Communication using DMA for control and user channel information
- Interrupt capabilities

The SPDIFRX receiver provides all the necessary features to detect the symbol rate, and decode the incoming data stream. The user can select the wanted SPDIF input, and when a valid signal will be available, the SPDIFRX will re-sample the incoming signal, decode the manchester stream, recognize frames, sub-frames and blocks elements. It delivers to the CPU decoded data, and associated status flags.

The SPDIFRX also offers a signal named spdif_frame_sync, which toggles at the S/PDIF sub-frame rate that will be used to compute the exact sample rate for clock drift algorithms.

### 2.29 Audio PLL (PLLI2S)

The devices feature an additional dedicated PLL for audio $I^{2} S$ and SAI applications. It allows to achieve error-free $I^{2} S$ sampling clock accuracy without compromising on the CPU performance, while using USB peripherals.

The PLLI2S configuration can be modified to manage an $I^{2}$ S/SAI sample rate change without disabling the main PLL (PLL) used for CPU, USB and Ethernet interfaces.

The audio PLL can be programmed with very low error to obtain sampling rates ranging from 8 KHz to 192 KHz .

In addition to the audio PLL, a master clock input pin can be used to synchronize the $I^{2} S / S A I$ flow with an external PLL (or Codec output).

### 2.30 Audio and LCD PLL (PLLSAI)

An additional PLL dedicated to audio and LCD-TFT is used for SAI1 peripheral in case the PLLI2S is programmed to achieve another audio sampling frequency (49.152 MHz or 11.2896 MHz ) and the audio application requires both sampling frequencies simultaneously.

The PLLSAI is also used to generate the LCD-TFT clock.

### 2.31 SD/SDIO/MMC card host interface (SDMMC)

SDMMC host interfaces are available, that support the MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

The interface allows data transfer at up to 50 MHz , and is compliant with the SD Memory Card Specification Version 2.0.
The SDMMC Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDMMC/MMC4.2 card at any one time and a stack of MMC4.1 or previous.
The SDMMC can be served by the DMA controller

### 2.32 Ethernet MAC interface with dedicated DMA and IEEE 1588 support

The devices provide an IEEE-802.3-2002-compliant media access controller (MAC) for ethernet LAN communications through an industry-standard medium-independent interface (MII) or a reduced medium-independent interface (RMII). The microcontroller requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). The PHY is connected to the device MII port using 17 signals for MII or 9 signals for RMII, and can be clocked using the 25 MHz (MII) from the microcontroller.

The devices include the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes.
- Supports hardware PTP (precision time protocol) in accordance with IEEE 15882008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time


### 2.33 Controller area network (bxCAN)

The three CANs are compliant with the 2.0A and B (active) specifications with a bit rate up to $1 \mathrm{Mbit} / \mathrm{s}$. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOS with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). 256 bytes of SRAM are allocated for CAN1 and CAN2. 512 bytes of SRAM are dedicated for CAN3.

### 2.34 Universal serial bus on-the-go full-speed (OTG_FS)

The devices embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator.
The major features are:

- Combined Rx and Tx FIFO size of 1.28 Kbytes with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 1 bidirectional control endpoint +5 IN endpoints +5 OUT endpoints
- 12 host channels with periodic OUT support
- Software configurable to OTG1.3 and OTG2.0 modes of operation
- USB 2.0 LPM (Link Power Management) support
- Battery Charging Specification Revision 1.2 support
- Internal FS OTG PHY support
- HNP/SNP/IP inside (no need for any external resistor)

For the OTG/Host modes, a power switch is needed in case bus-powered devices are connected

### 2.35 Universal serial bus on-the-go high-speed (OTG_HS)

The devices embed a USB OTG high-speed (up to $480 \mathrm{Mbit} / \mathrm{s}$ ) device/host/OTG peripheral. The USB OTG HS supports both full-speed and high-speed operations. It integrates the transceivers for full-speed operation ( $12 \mathrm{Mbit} / \mathrm{s}$ ) and features a UTMI low-pin interface (ULPI) for high-speed operation ( $480 \mathrm{Mbit} / \mathrm{s}$ ). When using the USB OTG HS in HS mode, an external PHY device connected to the ULPI is required.

The USB OTG HS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator.

The major features are:

- Combined Rx and Tx FIFO size of 4 Kbytes with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 8 bidirectional endpoints
- 16 host channels with periodic OUT support
- Software configurable to OTG1.3 and OTG2.0 modes of operation
- USB 2.0 LPM (Link Power Management) support
- Battery Charging Specification Revision 1.2 support
- Internal FS OTG PHY support
- External HS or HS OTG operation supporting ULPI in SDR mode. The OTG PHY is connected to the microcontroller ULPI port through 12 signals. It can be clocked using the 60 MHz output.
- Internal USB DMA
- HNP/SNP/IP inside (no need for any external resistor)
- for OTG/Host modes, a power switch is needed in case bus-powered devices are connected


### 2.36 High-definition multimedia interface (HDMI) - consumer electronics control (CEC)

The devices embed a HDMI-CEC controller that provides hardware support for the Consumer Electronics Control (CEC) protocol (Supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory overhead. It has a clock domain independent from the CPU clock, allowing the HDMI-CEC controller to wakeup the MCU from Stop mode on data reception.

### 2.37 Digital camera interface (DCMI)

The devices embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain a data transfer rate up to $54 \mathrm{Mbytes} / \mathrm{s}$ in 8 -bit mode at 54 MHz . It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- $\quad$ Supports 8-bit progressive video monochrome or raw bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image


### 2.38 Management Data Input/Output (MDIO) slaves

The devices embed a MDIO slave interface it includes the following features:

- $\quad 32$ MDIO Registers addresses, each of which is managed using separate input and output data registers:
- $\quad 32 \times 16$-bit firmware read/write, MDIO read-only output data registers
- $32 \times 16$-bit firmware read-only, MDIO write-only input data registers
- Configurable slave (port) address
- Independently maskable interrupts/events:
- MDIO Register write
- MDIO Register read
- MDIO protocol error
- Able to operate in and wake up from STOP mode


### 2.39 Random number generator (RNG)

All the devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

### 2.40 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

A fast I/O handling allows a maximum I/O toggling up to 108 MHz .

### 2.41 Analog-to-digital converters (ADCs)

Three 12-bit analog-to-digital converters are embedded and each ADC shares up to 16 external channels, performing conversions in the single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold

The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

To synchronize A/D conversion and timers, the ADCs could be triggered by any of TIM1, TIM2, TIM3, TIM4, TIM5, or TIM8 timer.

### 2.42 Digital filter for Sigma-Delta Modulators (DFSDM)

The devices embed one DFSDM with 4 digital filters modules and 8 external input serial channels (transceivers) or alternately 8 internal parallel inputs support. The DFSDM peripheral is dedicated to interface the external $\Sigma \Delta$ modulators to microcontroller and then to perform digital filtering of the received data streams (which represent analog value on $\Sigma \Delta$ modulators inputs). The DFSDM can also interface PDM (Pulse Density Modulation) microphones and perform PDM to PCM conversion and filtering in hardware. The DFSDM features optional parallel data stream inputs from microcontrollers memory (through DMA/CPU transfers into DFSDM). The DFSDM transceivers support several serial interface formats (to support various $\Sigma \Delta$ modulators). The DFSDM digital filter modules perform digital processing according user selected filter parameters with up to 24-bit final ADC resolution.

The DFSDM peripheral supports:

- 8 multiplexed input digital serial channels:
- Configurable SPI interface to connect various SD modulator(s)
- Configurable Manchester coded 1 wire interface support
- PDM (Pulse Density Modulation) microphone input support
- Maximum input clock frequency up to 20 MHz (10 MHz for Manchester coding)
- Clock output for SD modulator(s): $0 . .20 \mathrm{MHz}$
- Alternative inputs from 8 internal digital parallel channels (up to 16 bit input resolution):
- internal sources: device memory data streams (DMA)
- 4 digital filter modules with adjustable digital signal processing:
- Sincxfilter: filter order/type (1..5), oversampling ratio (up to 1..1024)
- integrator: oversampling ratio (1..256)
- Up to 24-bit output data resolution, signed output data format
- Automatic data offset correction (offset stored in register by user)
- Continuous or single conversion
- Start-of-conversion triggered by:
- Software trigger
- Internal timers
- External events
- Start-of-conversion synchronously with first digital filter module (DFSDMO)
- Analog watchdog feature:
- Low value and high value data threshold registers
- Dedicated configurable Sincx digital filter (order = 1..3, oversampling ratio $=1 . .32$ )
- Input from final output data or from selected input digital serial channels
- Continuous monitoring independently from standard conversion
- Short circuit detector to detect saturated analog input values (bottom and top range):
- Up to 8-bit counter to detect 1.. 256 consecutive 0 's or 1's on serial data stream
- Monitoring continuously each input serial channel
- Break signal generation on analog watchdog event or on short circuit detector event
- Extremes detector:
- Storage of minimum and maximum values of final conversion data
- Refreshed by software
- DMA capability to read the final conversion data
- Interrupts: end of conversion, overrun, analog watchdog, short circuit, input serial channel clock absence
- "regular" or "injected" conversions:
- "regular" conversions can be requested at any time or even in continuous mode without having any impact on the timing of "injected" conversions
- "injected" conversions for precise timing and with high conversion priority

Table 9. DFSDM implementation

| DFSDM features | DFSDM1 |
| :--- | :---: |
| Number of filters: x (DFSDM_FLTx) | 4 |
| Number of input transceivers/channels: y (DFSDM_CHy) | 8 |
| Internal ADC parallel input support | - |
| Number of external triggers (JEXTSEL size) | 32 |
| ID register support | - |

### 2.43 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with the temperature. The conversion range is between 1.7 V and 3.6 V . The temperature sensor is internally connected to the same input channel as $\mathrm{V}_{\mathrm{BAT}}$, $\mathrm{ADC} 1 \_I N 18$, which is used to convert the sensor output voltage into a digital value. When the temperature sensor and $\mathrm{V}_{\text {BAT }}$ conversion are enabled at the same time, only $\mathrm{V}_{\mathrm{BAT}}$ conversion is performed.
As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

### 2.44 Digital-to-analog converter (DAC)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs.

This dual digital Interface supports the following features:

- Two DAC converters: one for each output channel
- 8-bit or 12-bit monotonic output
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- Dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- External triggers for conversion
- Input voltage reference $\mathrm{V}_{\text {REF }}+$

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

### 2.45 Serial wire JTAG debug port (SWJ-DP)

The Arm SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

The debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

### 2.46 Embedded Trace Macrocell ${ }^{\text {TM }}$

The Arm embedded trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F76xxx through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or
any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

### 2.47 DSI Host (DSIHOST)

The DSI Host is a dedicated peripheral for interfacing with MIPI ${ }^{\circledR}$ DSI compliant displays. It includes a dedicated video interface internally connected to the LTDC and a generic APB interface that can be used to transmit information to the display.
These interfaces are as follows:

- LTDC interface:
- Used to transmit information in Video mode, in which the transfers from the host processor to the peripheral take the form of a real-time pixel stream (DPI).
- Through a customized for mode, this interface can be used to transmit information in full bandwidth in the Adapted Command mode (DBI).
- APB slave interface:
- Allows the transmission of generic information in Command mode, and follows a proprietary register interface.
- Can operate concurrently with either LTDC interface in either Video mode or Adapted Command mode.
- Video mode pattern generator:
- Allows the transmission of horizontal/vertical color bar and D-PHY BER testing pattern without any kind of stimuli.
The DSI Host main features:
- Compliant with MIPI ${ }^{\circledR}$ Alliance standards
- Interface with MIPI ${ }^{\circledR}$ D-PHY
- Supports all commands defined in the MIPI ${ }^{\circledR}$ Alliance specification for DCS:
- Transmission of all Command mode packets through the APB interface
- Transmission of commands in low-power and high-speed during Video mode
- Supports up to two D-PHY data lanes
- Bidirectional communication and escape mode support through data lane 0
- Supports non-continuous clock in D-PHY clock lane for additional power saving
- Supports Ultra Low-power mode with PLL disabled
- ECC and Checksum capabilities
- $\quad$ Support for End of Transmission Packet (EoTp)
- Fault recovery schemes
- 3D transmission support
- Configurable selection of system interfaces:
- AMBA APB for control and optional support for Generic and DCS commands
- Video Mode interface through LTDC
- Adapted Command mode interface through LTDC
- Independently programmable Virtual Channel ID in
- Video mode
- Adapted Command mode
- APB Slave


## Video Mode interfaces features:

- LTDC interface color coding mappings into 24-bit interface:
- 16-bit RGB, configurations 1,2 , and 3
- 18-bit RGB, configurations 1 and 2
- 24-bit RGB
- Programmable polarity of all LTDC interface signals
- Maximum resolution is limited by available DSI physical link bandwidth:
- Number of lanes: 2
- Maximum speed per lane: 500 Mbps 1 Gbps


## Adapted interface features

Support for sending large amounts of data through the memory_write_start(WMS) and memory_write_continue(WMC) DCS commands

- LTDC interface color coding mappings into 24-bit interface:
- 16-bit RGB, configurations 1,2 , and 3
- 18-bit RGB, configurations 1 and 2
- 24-bit RGB


## Video mode pattern generator:

- Vertical and horizontal color bar generation without LTDC stimuli
- BER pattern without LTDC stimuli


## 3 Pinouts and pin description

Figure 11. STM32F76xxx LQFP100 pinout


1. The above figure shows the package top view.

Figure 12. STM32F76xxx TFBGA100 pinout


1. The above figure shows the package top view.

Figure 13. STM32F76xxx LQFP144 pinout


1. The above figure shows the package top view.

Figure 14. STM32F76xxx LQFP176 pinout


1. The above figure shows the package top view.

Figure 15. STM32F769xx LQFP176 pinout


1. The above figure shows the package top view.

Figure 16. STM32F769Ax/STM32F768Ax WLCSP180 ballout


1. NC ball must not be connected to GND nor to VDD.
2. The above figure shows the package top view.

Figure 17. STM32F76xxx LQFP208 pinout


1. The above figure shows the package top view.

Figure 18. STM32F769xx LQFP208 pinout


1. The above figure shows the package top view.

Figure 19. STM32F76xxx UFBGA176 ballout


MS39130V1

1. The above figure shows the package top view.

Figure 20. STM32F76xxx TFBGA216 ballout


1. The above figure shows the package top view.

Figure 21. STM32F769xx TFBGA216 ballout


MS39125V1

1. The above figure shows the package top view.

Table 10. Legend/abbreviations used in the pinout table

| Name | Abbreviation | Definition |
| :---: | :---: | :---: |
| Pin name | Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name |  |
| Pin type | S | Supply pin |
|  | 1 | Input only pin |
|  | I/O | Input / output pin |
| I/O structure | FT | 5 V tolerant I/O |
|  | TTa | 3.3 V tolerant I/O directly connected to ADC |
|  | B | Dedicated BOOT pin |
|  | RST | Bidirectional reset pin with weak pull-up resistor |
| Notes | Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset |  |
| Alternate functions | Functions selected through GPIOx_AFR registers |  |
| Additional functions | Functions directly selected/enabled through peripheral registers |  |

Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


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Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


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Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


Table 11. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)


1. NC (not-connected) pins are not bonded. They must be configured by software to output push-pull and forced to 0 in the output data register to avoid an extra current consumption in low-power modes. list of pins: PI8, PI12, PI13, PI14, PF6, PF7, PF8, PF9, PC2, PC3, PC4, PC5, PI15, PJ0, PJ1, PJ2, PJ3, PJ4, PJ5, PH6, PH7, PJ12, PJ13, PJ14, PJ15, PG14, PK3, PK4, PK5, PK6 and PK7.
2. PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current ( 3 mA ), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited:- The speed should not exceed 2 MHz with a maximum load of 30 pF . - These I/Os must not be used as a current source (e.g. to drive an LED).
3. $\mathrm{FT}=5 \mathrm{~V}$ tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
4. If the device is in regulator OFF/internal reset ON mode (BYPASS_REG pin is set to VDD), then PAO is used as an internal reset (active low).
5. Internally connected to VDD or VSS depending on part number.

Table 12. FMC pin definition

| Pin name | NOR/PSRAM/SR AM | NOR/PSRAM Mux | NAND16 | SDRAM |
| :---: | :---: | :---: | :---: | :---: |
| PF0 | A0 | - | - | A0 |
| PF1 | A1 | - | - | A1 |
| PF2 | A2 | - | - | A2 |
| PF3 | A3 | - | - | A3 |
| PF4 | A4 | - | - | A4 |
| PF5 | A5 | - | - | A5 |
| PF12 | A6 | - | - | A6 |
| PF13 | A7 | - | - | A7 |
| PF14 | A8 | - | - | A8 |
| PF15 | A9 | - | - | A9 |
| PG0 | A10 | - | - | A10 |
| PG1 | A11 | - | - | A11 |
| PG2 | A12 | - | - | A12 |
| PG3 | A13 | - | - | - |
| PG4 | A14 | - | - | BA0 |
| PG5 | A15 | - | - | BA1 |
| PD11 | A16 | A16 | CLE | - |
| PD12 | A17 | A17 | ALE | - |
| PD13 | A18 | A18 | - | - |
| PE3 | A19 | A19 | - | - |
| PE4 | A20 | A20 | - | - |
| PE5 | A21 | A21 | - | - |
| PE6 | A22 | A22 | - | - |
| PE2 | A23 | A23 | - | - |
| PG13 | A24 | A24 | - | - |
| PG14 | A25 | A25 | - | - |
| PD14 | D0 | DA0 | D0 | D0 |
| PD15 | D1 | DA1 | D1 | D1 |
| PD0 | D2 | DA2 | D2 | D2 |
| PD1 | D3 | DA3 | D3 | D3 |
| PE7 | D4 | DA4 | D4 | D4 |
| PE8 | D5 | DA5 | D5 | D5 |
| PE9 | D6 | DA6 | D6 | D6 |
| PE10 | D7 | DA7 | D7 | D7 |

Table 12. FMC pin definition (continued)

| Pin name | NOR/PSRAM/SR AM | NOR/PSRAM Mux | NAND16 | SDRAM |
| :---: | :---: | :---: | :---: | :---: |
| PE11 | D8 | DA8 | D8 | D8 |
| PE12 | D9 | DA9 | D9 | D9 |
| PE13 | D10 | DA10 | D10 | D10 |
| PE14 | D11 | DA11 | D11 | D11 |
| PE15 | D12 | DA12 | D12 | D12 |
| PD8 | D13 | DA13 | D13 | D13 |
| PD9 | D14 | DA14 | D14 | D14 |
| PD10 | D15 | DA15 | D15 | D15 |
| PH8 | D16 | - | - | D16 |
| PH9 | D17 | - | - | D17 |
| PH10 | D18 | - | - | D18 |
| PH11 | D19 | - | - | D19 |
| PH12 | D20 | - | - | D20 |
| PH13 | D21 | - | - | D21 |
| PH14 | D22 | - | - | D22 |
| PH15 | D23 | - | - | D23 |
| PIO | D24 | - | - | D24 |
| PI1 | D25 | - | - | D25 |
| PI2 | D26 | - | - | D26 |
| PI3 | D27 | - | - | D27 |
| PI6 | D28 | - | - | D28 |
| PI7 | D29 | - | - | D29 |
| P19 | D30 | - | - | D30 |
| PI10 | D31 | - | - | D31 |
| PD7 | NE1 | NE1 | - | - |
| PG6 | NE3 | - | - | - |
| PG9 | NE2 | NE2 | NCE | - |
| PG10 | NE3 | NE3 | - | - |
| PG11 | - | - | - | - |
| PG12 | NE4 | NE4 | - | - |
| PD3 | CLK | CLK | - | - |
| PD4 | NOE | NOE | NOE | - |
| PD5 | NWE | NWE | NWE | - |
| PD6 | NWAIT | NWAIT | NWAIT | - |

Table 12. FMC pin definition (continued)

| Pin name | NOR/PSRAM/SR AM | NOR/PSRAM Mux | NAND16 | SDRAM |
| :---: | :---: | :---: | :---: | :---: |
| PB7 | NADV | NADV | - | - |
| PF6 | - | - | - | - |
| PF7 | - | - | - | - |
| PF8 | - | - | - | - |
| PF9 | - | - | - | - |
| PF10 | - | - | - | - |
| PG6 | - | - | - | - |
| PG7 | - | - | INT | - |
| PE0 | NBLO | NBLO | - | NBLO |
| PE1 | NBL1 | NBL1 | - | NBL1 |
| PI4 | NBL2 | - | - | NBL2 |
| PI5 | NBL3 | - | - | NBL3 |
| PG8 | - | - | - | SDCLK |
| PC0 | - | - | - | SDNWE |
| PF11 | - | - | - | SDNRAS |
| PG15 | - | - | - | SDNCAS |
| PH2 | - | - | - | SDCKE0 |
| PH3 | - | - | - | SDNE0 |
| PH6 | - | - | - | SDNE1 |
| PH7 | - | - | - | SDCKE1 |
| PH5 | - | - | - | SDNWE |
| PC2 | - | - | - | SDNE0 |
| PC3 | - | - | - | SDCKE0 |
| PC6 | NWAIT | NWAIT | NWAIT | - |
| PB5 | - | - | - | SDCKE1 |
| PB6 | - | - | - | SDNE1 |


| Table 13. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx alternate function mapping |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Port |  | AFO | AF1 | AF2 | AF3 | AF4 | AF5 | AF6 | AF7 | AF8 | AF9 | AF10 | AF11 | AF12 | AF13 | AF14 | AF15 |
|  |  | SYS | $\begin{aligned} & \text { I2C4/UA } \\ & \text { RT5/TIM } \\ & \text { 1/2 } \end{aligned}$ | TIM3/4/5 | TIM8/9/10/ 1/DFSDM 1/CEC | 12C1/2/3/ 1/CEC |  | $\begin{array}{\|c\|} \hline \text { SPI2/I2S } \\ \text { 2SPP1/I2 } \\ \text { S3/SA111 } \\ 12 C 4 / / 4 A \\ \text { RT4/DF } \\ \text { SDM1 } \end{array}$ | SPI2/I2S <br> 2/SPI3/12 S3/SPI6/ <br> USART1/ <br> 2/3/UART 1/SPDIF 5/DFSDM | SPI6/SAI 2/USART 6/UART4/ G_FS/SP DIF | CAN1/2/T IM12/13/ 14/QUAD LCD | SAI2/QU <br> ADSPI/S DMMC2/D TG2 HS/ OTG1_FS /LCD | 12C4/CAN 3/SDMM C2/ETH | UART7/ FMC/SD MMC1/M G2 FS | $\begin{aligned} & \mathrm{DCMI/LL} \\ & \text { CD/DSI } \end{aligned}$ | LCD | SYS |
| Port A | PAO | - | TIM2_C H1/TIM2 ETR | $\underset{\mathrm{H} 1^{-}}{\text {TII }}$ | $\underset{R}{\text { TIM8_ET }}$ | - | - | - | USART2 _CTS | $\begin{aligned} & \text { UART4_- } \\ & \text { TX } \end{aligned}$ | - | $\underset{\bar{B}}{\mathrm{SAl}_{-} \mathrm{SD}_{-}}$ | $\underset{\text { CRS }}{\text { ETH_MII }}$ | - | - | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PA1 | - | $\underset{\mathrm{H} 2 \mathrm{C}}{\mathrm{~T} \text { TIM2_C }}$ | $\underset{\mathrm{H}_{2}}{\text { TIM5_C }}$ | - | - | - | - | $\underset{\text { _RTS }}{\text { USART2 }}$ | $\begin{gathered} \text { UART4_- } \\ \text { RX } \end{gathered}$ | $\begin{aligned} & \text { QUADSP } \\ & \text { I_BK1_IO } \\ & 3 \end{aligned}$ | $\begin{gathered} \text { SAI2_MC } \\ \text { K_B }^{2} \end{gathered}$ | $\begin{aligned} & \text { ETH_MII } \\ & \text { RX_CLK } \\ & \text { ETH RMI } \\ & \text { I_REF_C } \\ & L K_{2} \end{aligned}$ | - | - | LCD_R2 | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PA2 | - | $\underset{\mathrm{H}_{3}}{\mathrm{TIM} \mathbf{N}_{2} \mathrm{C}}$ | $\begin{gathered} \text { TIM5_C } \\ \mathrm{H}_{3} \end{gathered}$ | $\underset{1}{\text { TIM9_CH }}$ | - | - | - | USART2 <br> _TX | $\underset{K_{K} \text { S_B }}{\text { SAI2SC }}$ | - | - | ETH_MDI | MDIOS MDIO | - | LCD_R1 | EVEN TOUT |
|  | PA3 | - | $\underset{\mathrm{H} 4}{\mathrm{TIM} \mathbf{L}^{-} \mathrm{C}}$ | $\underset{\mathrm{H} 4}{\mathrm{~T} \text { TIM }}$ | $\underset{2}{\mathrm{TIM} 9} \mathrm{CH}$ | - | - | - | $\begin{gathered} \text { USART2 } \\ \text { _RX } \end{gathered}$ | - | LCD_B2 | $\begin{aligned} & \text { OTG_HS } \\ & \text { ULPI_DO } \end{aligned}$ | $\begin{array}{\|l\|l\|} \text { ETH_MII_ } \\ \text { CÖL } \end{array}$ | - | - | LCD_B5 | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PA4 | - | - | - | - | - | SPI1 NS S/I2S1_ WS | SPI3_NS S/I2S3_ WS | $\begin{gathered} \text { USART2 } \\ \text { _CK } \end{gathered}$ | $\underset{\text { S }}{\text { SPI6 }}$ | - | - | - | $\begin{gathered} \text { OTG_HS } \\ \text { SOOF } \end{gathered}$ | $\begin{aligned} & \text { DCMI_H } \\ & \text { SYNC }^{2} \end{aligned}$ | $\begin{gathered} \text { LCD_VS } \\ \text { YNC } \end{gathered}$ | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PA5 | - | TIM2_C H1/TIM2 _ETR | - | $\underset{\text { TIM8_CH }}{\substack{\text { TI }}}$ | - | SPI1_SC K/I2S1_ CK | - | - | $\underset{\mathrm{K}}{\text { SPI6_SC }}$ | - | OTG_HS | - | - | - | LCD_R4 | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PA6 | - | $\underset{\text { KIN }^{\text {TIM1_B }}}{ }$ |  | ${\underset{N}{N}}_{\text {TIM8 }}$ | - | $\begin{gathered} \mathrm{SPI1} \mathrm{Ml} \\ \mathrm{SO} \end{gathered}$ | - | - | $\begin{gathered} \text { SPI6_MI } \\ \text { SO } \end{gathered}$ | $\underset{\mathrm{H} 1}{\mathrm{~T} \text { TIM13_C }}$ | - | - | MDIOS MDC | $\underset{\text { XCLK }}{\text { DCMI PI }}$ | LCD_G2 | EVEN TOUT |
|  | PA7 | - | $\underset{\text { H1N }}{\text { TIM1_C }}$ | $\underset{\mathrm{H}_{2}}{\text { TIM3_C }}$ | $\underset{1 \mathrm{~N}}{\text { TIM8_CH }}$ | - | $\begin{gathered} \text { SPI1_M } \\ \text { OSI/I2S1 } \\ \text { SD } \end{gathered}$ | - | - | $\underset{\text { SII }}{\text { SPIO }}$ | $\underset{\mathrm{H} 1}{\text { TIM14_C }}$ | - | $\begin{aligned} & \text { ETH_MII } \\ & \text { RX_DVE } \\ & \text { TH_RMII } \\ & \text { CRS_DV } \end{aligned}$ | FMC_SD NWE | - | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PA8 | MCO1 | $\underset{\mathrm{H} 1}{\boldsymbol{T} \text { TIM1_C }}$ | - | $\underset{\mathrm{N} 2}{\mathrm{TI} \mathrm{~B}} \mathrm{BKI}$ | $\underset{\text { L_S }}{12 \mathrm{C} 3 \mathrm{SC}}$ | - | - | USART1 _CK | - | - | $\begin{array}{\|c} \hline \text { OTG_FS_ } \\ \text { SOFF } \end{array}$ | $\begin{gathered} \text { CAN3_R } \\ X \end{gathered}$ | $\text { UART7_ }_{\text {RX }}$ | LCD_B3 | LCD_R6 | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PA9 | - | $\underset{\mathrm{H} 2}{\text { TIM1_C }}$ | - | - | $\underset{B \bar{A}}{12 C 3}$ | SPI2_SC K/I2S2 CK | - | $\begin{gathered} \text { USART1 } \\ \text { _TX } \end{gathered}$ | - | - | - | - | - | $\underset{0}{\text { DCMI_D }}$ | LCD_R5 | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PA10 | - | $\underset{\text { H3 }}{\substack{\text { TIM1_C }}}$ | - | - | - | - | - | USART1 | - | LCD_B4 | $\underset{\text { ID }}{\text { OTG_Fs }}$ | - | MDIOS MDIO | $\underset{1}{\text { DCMI_D }}$ | LCD_B1 | EVEN TOUT |

Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\frac{n}{i k}$ | $\stackrel{\infty}{\omega}$ | $\underset{\sim}{\text { zien }}$ | $\underset{\sim}{2} \underset{\sim}{2}$ | 永年 | 永っ |  |  | $\underset{\sim}{2} \underset{\sim}{2}$ | 発っ | $\underset{\sim}{2} \underset{\sim}{2}$ | $\underset{\sim}{3}$ | $\underset{\sim}{\text { zien }}$ | $\underset{\sim}{2} \underset{\sim}{2} \stackrel{1}{2}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\underset{\frac{\pi}{4}}{\frac{\pi}{4}}$ | O | $\begin{aligned} & \hline \stackrel{y}{\approx} \\ & \stackrel{\rightharpoonup}{O} \end{aligned}$ |  | ＇ | ＇ | ＇ | $\begin{aligned} & \bar{O}_{1} \\ & 0 \end{aligned}$ | $\begin{aligned} & O_{1} \\ & 0 \\ & \hline- \end{aligned}$ |  |  | ， | O <br> 0 <br> 0 <br> 1 | ＇ |
| $\stackrel{N}{\stackrel{N}{4}}$ | 犮㐫合 | ， | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |  | ， | ＇ | $\begin{aligned} & Q_{1}^{\prime} \\ & \sum_{0}^{\prime} 0 \end{aligned}$ | $\sum_{\substack{0 \\ 0}}^{1}$ |
| $\stackrel{N}{\dot{\mid}}$ |  | － | ， | ， | ， | $\begin{aligned} & \hat{N}^{\prime} \\ & \stackrel{\rightharpoonup}{5} \times \\ & \hline \end{aligned}$ | ， | ， | ＇ |  |  | $\begin{aligned} & 0_{1} \\ & \sum_{4}^{\prime \stackrel{u}{0}} \end{aligned}$ | $\begin{aligned} & 0_{1}^{\prime} \\ & \sum_{4}^{\prime \stackrel{u}{z}} \end{aligned}$ |
| $\underset{\underset{\sim}{4}}{\bar{U}}$ |  | ＇ | － | ＇ | ＇ |  |  |  | ， |  |  |  |  |
| $\frac{\text { 은 }}{\stackrel{1}{4}}$ |  | $\begin{aligned} & \mathbf{N}^{\prime} \\ & \omega_{1}^{\prime 2} \\ & 0_{0}^{\prime} \end{aligned}$ | $\begin{aligned} & \hline \omega^{\prime} \\ & \mathscr{N}_{10} \\ & 0_{0}^{\prime} \\ & \hline \end{aligned}$ | ＇ | ＇ | ＇ |  |  |  | $\sum_{\substack{N \\ \sum_{0} \\ N_{1} \\ \hline}}$ | $\sum_{0}^{N} \tilde{N}_{1}^{N} \tilde{o}_{1}$ |  |  |
| $\frac{8}{4}$ |  |  |  | ＇ | ， | ＇ | 雑 | $\begin{aligned} & \text { ®O } \\ & 0 \\ & \hline-1 \end{aligned}$ |  |  | ． |  | $\stackrel{\vdash_{1}^{\prime}}{{\underset{J}{\alpha}}^{\prime} \times}$ |
| $\stackrel{\infty}{4}$ |  | ＇ |  | ＇ | ， |  |  | ， | ＇ | $\begin{aligned} & 0 \\ & \omega_{1} \\ & \frac{\varrho_{0}}{\infty} \end{aligned}$ | $\begin{aligned} & \sum_{1} \\ & \varrho_{0}^{\circ} e \\ & \omega_{0} \end{aligned}$ | $\begin{aligned} & \sum_{\sum_{1}} \\ & \varrho_{0}^{\circ} \end{aligned}$ | ＇ |
| 免 |  |  |  | ＇ | ＇ |  | ， | ＇ |  | ＇ |  | ＇ |  |
| $\stackrel{\circ}{4}$ |  |  |  | ， | ， |  |  |  |  |  | $\begin{aligned} & \hline \sum_{\omega_{1}} 0 \\ & \bar{\omega}_{0} 0 \end{aligned}$ |  |  |
| $\stackrel{6}{4}$ |  |  |  | ＇ | ， |  | ， | ， | ， |  | $\begin{aligned} & \overline{\sum_{10}} \\ & \bar{n}_{0} \cong \end{aligned}$ |  | ＇ |
| 誌 | ल্⿳亠丷厂⿰㇒⿻土一𧘇 둑 | ＇ | － | ＇ | ＇ | 产首岂 | ， | ， | ＇ | ＇ | ＇ |  |  |
| 枈 |  | － | ＇ | ＇ | ＇ | ＇ | In | In ${ }_{\text {I }}^{\text {I }}$ | ， |  | ＇ | ＇ | 㪟岂 |
| N | $\begin{aligned} & \hline \frac{n}{2} \\ & \stackrel{n}{5} \\ & \stackrel{N}{n} \end{aligned}$ | ＇ | ＇ | ＇ | ＇ | ， | $\begin{aligned} & 0_{1} \\ & \sum_{i}^{N_{1}} \bar{I} \end{aligned}$ | $\begin{aligned} & U_{1}^{\prime} \\ & \sum_{i}^{m} I \end{aligned}$ | ， | ＇ | $\begin{aligned} & \hline U_{1}^{\prime} \\ & \sum_{i} \bar{I} \end{aligned}$ | $\begin{aligned} & U_{1}^{\prime} \\ & \sum_{i}{ }^{\prime} N \end{aligned}$ |  |
| 砏 |  | $\begin{aligned} & U_{1} \\ & \sum_{i}^{S_{1}}{ }^{\prime} \end{aligned}$ |  | ， | ＇ |  | $\begin{array}{\|l\|} \hline 0 \\ \sum_{i}^{\prime} z \\ \sum_{i} \underset{I}{N} \end{array}$ | $\begin{aligned} & U_{1 z} \\ & \sum_{i}^{\prime} \bar{M} \end{aligned}$ | ＇ | $\begin{aligned} & U_{1}^{\prime} \\ & {\underset{\Sigma}{N}}^{N}{ }^{\text {N }} \end{aligned}$ | ， |  | $\begin{aligned} & \stackrel{\varrho}{n}^{\prime} \\ & \frac{\alpha}{5} \times \\ & \hline \end{aligned}$ |
| 안 | $\stackrel{\infty}{\omega}$ | ＇ | ＇ | $\sum_{5}^{\infty} \sum_{j}^{\circ}$ | $\begin{aligned} & \text { 关资 } \\ & \stackrel{y y}{0} \end{aligned}$ | 믁 | ， | ＇ | ＇ |  |  | ， | ． |
| $\stackrel{\text { ̌ }}{\substack{\circ}}$ |  | $\stackrel{\text { 「 }}{\text { ¢ }}$ | $\frac{N}{\square}$ | $\stackrel{m}{\grave{\alpha}}$ | $\frac{\mathrm{t}}{\underset{\alpha}{x}}$ | $\frac{0}{\square}$ | \％ | ＂ | ๕ | ๕ | 呙 | ¢ | ๕ |
|  |  | $\begin{aligned} & \text { を } \\ & \stackrel{y}{\circ} \end{aligned}$ |  |  |  |  | $\begin{aligned} & \infty \\ & \stackrel{\rightharpoonup}{\circ} \end{aligned}$ |  |  |  |  |  |  |

Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\frac{n}{4}$ | $\stackrel{0}{\omega}$ | \|를흔 | 案各 | 永年 | 永年 | $\underset{\text { zu른 }}{2}$ | 를둔 |  | 永っ | 를는 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\stackrel{H}{\stackrel{U}{4}}$ | O | ＇ | $\begin{aligned} & \hline ⿱ 丷 天 心 \\ & \hline 1 \\ & \hline 0 \end{aligned}$ | $\begin{aligned} & \bar{\omega}_{1} \\ & \mathrm{O}_{1} \end{aligned}$ | $\begin{aligned} & \hline \text { O} \\ & \text { OU } \end{aligned}$ | $$ | ＇ | ＇ | ＇ | ＇ |
| $\frac{\stackrel{m}{4}}{\stackrel{4}{4}}$ | 릉뭉 |  | $\begin{array}{\|l\|} \hline 0 \\ \sum_{0}^{1} o \\ 0 \end{array}$ | $\begin{aligned} & \hline Q_{1}^{\prime} \\ & \sum_{0}^{1} \wedge \end{aligned}$ | ＇ |  | ＇ | ＇ | ＇ | ， |
| $\stackrel{N}{\stackrel{N}{4}}$ |  | $\begin{aligned} & z_{z_{1}^{\prime}}^{\prime} \\ & \sum_{U}^{0} \end{aligned}$ | 気䓪 | $\sum_{0}^{0} \sum_{0}^{0} 0_{1}$ | ， | ， | $\begin{aligned} & \mathbf{N}_{1} \\ & \mathbf{N}_{1} \end{aligned}$ | ＇ |  | $\begin{aligned} & \mathbf{N}_{1} \\ & 00_{1} \\ & 5 \end{aligned}$ |
|  |  |  |  | $\begin{aligned} & \hline \sum_{\infty}^{\infty} \\ & {\underset{N}{0}}^{(1 区} \\ & \hline \end{aligned}$ |  |  |  |  | ＇ | ， |
| $\stackrel{\circ}{\dot{U}}$ |  | ， | $\sum_{0}^{N} \sum_{0}^{N}$ | $\sum_{0}^{\sim} \sum_{0}^{N}$ |  |  |  |  | $\sum_{\sum_{0}}^{\substack{N \\ 0}}$ | $\sum_{\text {coid }}^{\text {No }}$ |
| 눈 |  | ＇ |  | $\begin{aligned} & F_{i}^{1} \\ & \sum_{0}^{\prime} x \end{aligned}$ |  | ＇ | $\stackrel{\substack{\alpha \\ \sum_{c}^{\prime} \\ N_{0}^{\prime}}}{ }$ | $\begin{aligned} & \stackrel{\rightharpoonup}{\prime}_{\prime}^{N_{<}^{\prime}} \times \end{aligned}$ | $\begin{aligned} & \hline U_{1}^{\prime} \\ & \sum_{i}^{N_{1}} \bar{I} \end{aligned}$ | $\begin{aligned} & U_{1} \\ & \sum_{i}^{N} \mathbb{N} \end{aligned}$ |
| $\stackrel{\infty}{4}$ |  | ， | ＇ | ＇ | ＇ | ＇ |  |  |  |  |
| 免 |  N |  | $\begin{aligned} & n^{\prime} \\ & e^{2} \times \\ & \frac{2}{5} \times{ }^{2} \times \end{aligned}$ |  |  |  |  |  |  | ＇ |
| $\stackrel{\circ}{4}$ |  |  | $\begin{array}{\|l\|} \hline \sum_{0}^{n} \\ 0 \\ 0 \\ 0 \\ 0 \end{array}$ |  |  |  |  | $\begin{aligned} & \sum_{00}^{\overline{0}} \\ & \text { 듬 } \end{aligned}$ |  | $\begin{aligned} & \sum_{0}^{5} \tilde{e n}_{0}^{0} \\ & y_{0}^{0} \end{aligned}$ |
| $\stackrel{\text { ¢ }}{4}$ |  | ， | ＇ |  |  | ＇ |  |  | $\begin{aligned} & \hline \bar{N}_{10} \\ & {\underset{N}{\omega}}^{\omega} \Theta \end{aligned}$ |  |
| 年 |  | $\begin{aligned} & \dot{o}_{1} \\ & \bar{j}_{1} \varangle \\ & \underline{\underline{n}} \end{aligned}$ | $\begin{array}{\|l\|} \hline 0 \\ 0_{1} \\ {\underset{N}{N}}^{2} \end{array}$ | $\begin{aligned} & \dot{\sigma}_{1} \\ & \tilde{j}_{1} \end{aligned}$ | $\begin{aligned} & \mathbf{N}_{1} \\ & {\underset{N N}{N}}^{\prime} \end{aligned}$ | $\begin{aligned} & \mathbf{Q}_{1} \\ & \tilde{N}^{<} \end{aligned}$ |  | ＇ |  |  |
| 皆 |  | ＇ | O ${ }_{\text {O }}$ | $\begin{aligned} & \hline I_{0}^{\prime} \\ & \sum_{i}^{I_{1}^{\prime}} \end{aligned}$ | ＇ | ， | ， | ＇ |  |  |
| N | $\begin{aligned} & \hline \frac{n}{n} \\ & \sum_{n}^{m} \\ & \sum_{1}^{m} \end{aligned}$ | $\begin{aligned} & U_{1} \\ & \dot{T}^{\prime} \mathbb{N} \\ & \sum_{1} \end{aligned}$ |  | $\begin{aligned} & U_{1}^{\prime} \\ & \sum_{i}{ }^{\prime}{ }^{\prime} \end{aligned}$ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| 둔 |  | ＇ | $\left\lvert\, \begin{aligned} & 0 \\ & 0_{1} \\ & J_{1} \\ & \underline{\underline{N}} \end{aligned}\right.$ | $\begin{aligned} & 0_{1} \\ & \mathbf{J}_{1}< \\ & \underline{\underline{n}} \end{aligned}$ | $\sum_{i}^{N^{\prime}} \text { 오 }$ | $\begin{aligned} & U_{1}^{\prime} \\ & {\underset{N}{1}}_{1}^{1} \end{aligned}$ | $\sum_{i}^{\infty} \sum_{1}^{\prime} \bar{z}$ |  | $\begin{array}{\|l\|l\|} \hline U_{1 z} \\ \sum_{i}^{\prime} \underset{N}{N} \\ \hline \end{array}$ | $\begin{aligned} & U_{1}^{\prime 2} \\ & \sum_{i}^{\prime} \bar{M} \end{aligned}$ |
| 안 | $\stackrel{\sim}{\omega}$ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |  |
| $\stackrel{\text { ² }}{\substack{\circ}}$ |  | ¢ ${ }_{\text {¢ }}$ | ® | ® ${ }_{\text {® }}$ | 음 | － | N | ¢ | $\stackrel{\mathrm{J}}{\mathrm{D}}$ | $\stackrel{\sim}{0}$ |
|  |  | $\stackrel{\text { ¢ }}{\stackrel{\text { L }}{\circ}}$ |  |  |  |  |  |  |  |  |

Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\stackrel{\text { n }}{\stackrel{n}{4}}$ | $\stackrel{\infty}{\omega}$ | $\underset{\text { zu를 }}{2}$ | 垫 | 永5 | 垫 | $\underset{\sim}{\text { z2 }}$ | $\underset{\sim}{2} \underset{\sim}{2}$ | 坔年 | $\underset{\text { zun }}{\substack{\mathrm{u} \\ \hline}}$ | 発っ | $\underset{\sim}{2} \underset{\sim}{2} \stackrel{1}{2}$ |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\frac{\underset{4}{4}}{\frac{t}{4}}$ | O |  | ＇ |  | ， | ， | ＇ |  | $\begin{aligned} & 0 \\ & 0 \\ & 0 \\ & \hline 1 \end{aligned}$ |  | $\xrightarrow{\text { ® }}$ | $\xrightarrow{\widetilde{0}}$ |
| $\frac{\stackrel{m}{4}}{\stackrel{4}{4}}$ | $\sum_{0}^{2}$ | ＇ | ， |  | ＇ | ， | ， | $\begin{aligned} & 0 \\ & \sum_{0}^{1} 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & 0_{0}^{\prime} \\ & \sum_{0}^{\prime}- \\ & \hline \end{aligned}$ | $\begin{aligned} & 0_{0}^{\prime} \\ & \sum_{0}^{\sum_{Q}} N \end{aligned}$ | $\begin{aligned} & 0 \\ & \sum_{0}^{1} m \\ & \hline \end{aligned}$ | $\begin{aligned} & 0_{0}^{1} \\ & \sum_{0}^{\infty} \infty \\ & \hline \end{aligned}$ |
| $\stackrel{N}{\stackrel{N}{4}}$ |  | $\begin{aligned} & \text { Qum } \\ & \sum_{4}^{0} \sum_{z}^{z} \end{aligned}$ | $\begin{aligned} & \operatorname{si}^{\prime} \\ & 0_{0}^{0} \frac{0}{\Sigma} \\ & \hline \end{aligned}$ | $\begin{array}{\|l} \hline Q_{1} \\ \sum_{i}^{\prime} \\ \sum_{i}^{\prime} \underline{z} \end{array}$ |  | $\begin{aligned} & \dot{\omega}_{1}^{\prime} \\ & \sum_{i}^{\prime} \stackrel{1}{z} \end{aligned}$ |  | $\sum_{0}^{0} \AA_{1}^{0}$ | $\sum_{i=0}^{0}{ }_{0}^{0}$ | $\sum_{i=1}^{0} o_{1}^{0}$ | $\sum_{i=0}^{0} \bar{O}_{1}$ | $\sum_{i=1}^{0} N_{1}$ |
| $\underset{\underset{4}{4}}{\bar{u}}$ |  | ， | $\begin{aligned} & \sum_{\Sigma}^{0} \\ & \underset{\Psi}{\Psi} \end{aligned}$ |  |  |  |  | ， | ， | ， | ＇ | ， |
| 은 |  |  | $\begin{aligned} & \sum_{i}^{\prime} \bar{z} \\ & 0 \\ & 0 \\ & 0 \\ & 0 \end{aligned}$ |  |  | ， | ， | $\sum_{0}^{N} \mathrm{~N}_{0}^{\mathrm{N}} \mathrm{O}_{1}$ | $\sum_{i=0}^{N} \widehat{N}_{1}^{N}$ | ＇ | O | ， |
| $\frac{i \pi}{4}$ |  | ． | ， |  | ， | ， | ， | $\begin{aligned} & \sum_{<1}^{2} \\ & \sum_{k}^{0 \mid} \end{aligned}$ | $\begin{aligned} & {\underset{Z}{\prime}}_{1}^{\prime} \\ & \sum_{\\|}^{\prime} \end{aligned}$ |  |  |  |
| $\stackrel{\infty}{4}$ |  |  | ， |  | ＇ |  |  | $\begin{aligned} & 0 \\ & \stackrel{0}{6} \times \\ & \underset{\substack{4 \\ 5}}{2} \end{aligned}$ |  |  | ， |  |
| 交 |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | $\begin{aligned} & \sum_{0}^{5} \underset{\sim}{m} \\ & \sum_{0}^{2} \\ & 0 \end{aligned}$ |  |  |  |  |
| $\frac{00}{4}$ |  |  |  |  | ＇ | ＇ | ＇ | ＇ | $\sum_{\operatorname{NeN}_{1}}^{\substack{0}}$ | ＇ | ＇ |  |
| $\frac{\stackrel{6}{4}}{4}$ |  | ， |  |  |  | $\begin{aligned} & \sum_{\text {NJ }}^{\text {NO }} \end{aligned}$ | ， | $\begin{aligned} & \sum_{\sim}^{\prime} \\ & \underset{\sim}{\top} \mathrm{U} \end{aligned}$ | ＇ | ， |  | ＇ |
| 蒋 | ल্র | ， | ＇ | ， | ， | ＇ | ＇ | ， | ＇ | ， |  | ＇ |
| $\stackrel{!}{4}$ |  |  |  |  | $\begin{aligned} & \sum_{0}^{1} \\ & 0 \\ & 4 \\ & 4 \\ & \hline \end{aligned}$ |  |  | $\begin{aligned} & \mathbf{I}_{0}^{\prime} \\ & \sum_{i}^{\infty^{\prime}}- \end{aligned}$ | $\sum_{i}^{\infty}{ }_{1}^{\infty} \mathbb{N}$ | $\sum_{i}^{\infty} \frac{\infty^{\prime}}{\Xi}$ | $\sum_{1}^{\infty}{ }_{1}^{\prime}$ |  |
| Nㅜㄴ | $\begin{aligned} & \hline \frac{n}{m} \\ & \stackrel{n}{N} \\ & \stackrel{m}{n} \end{aligned}$ | ， | ＇ | ＇ | ＇ | ＇ | ＇ | $\begin{aligned} & U_{1} \\ & \sum_{i}^{N_{1}} \bar{I} \end{aligned}$ | $\begin{aligned} & \hline U_{1}^{\prime} \\ & \sum_{i}^{M_{1}} \mathbb{N} \end{aligned}$ | $\begin{aligned} & \hline U_{1}^{\prime} \\ & \sum_{i}^{\prime} \frac{M}{1} \end{aligned}$ | $\begin{aligned} & U_{1} \\ & \sum_{i}^{N_{1}} T \end{aligned}$ | ， |
| $\bar{x}$ |  | ＇ | ， |  | ＇ | ＇ | ＇ |  | ， | ＇ | ＇ | ＇ |
| 운 | $\stackrel{\infty}{\omega}$ | ， | 足 |  | ， | ， | ， |  | ． | 岂 ¢ ¢ | O | ＇ |
| ！ |  | 8 | ¢ | ก | \％ | J | \％ | O | S | \％ | 8 | 은 |
|  |  | － |  |  |  |  |  |  |  |  |  |  |

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| Port |  | AFO | AF1 | AF2 | AF3 | AF4 | AF5 | AF6 | AF7 | AF8 | AF9 | AF10 | AF11 | AF12 | AF13 | AF14 | AF15 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | SYS | 12C4/UA RT5/TIM 1/2 | TIM3/4/5 | TIM8/9/10/ 11/LPTIM 1/DFSDM 1/CEC | I2C1/2/3/ <br> 4/USART 1/CEC | $\begin{array}{\|c} \text { SPI1/12S } \\ 1 / 2 \mathrm{SPI2/2} \\ \text { S2/SPI3/ } \\ 12 \mathrm{SS} / \mathrm{SPP} \\ 4 / 5 / 6 \end{array}$ | SPI2/12S 2/SPII/2 S3/SA11/ I2CT/UA RT4/DF SDM1 | SPI2/I2S 2/SPI3/I2 S3/SPI6 USART1/ 5/DFSDM 1/SPDIF | SPI6/SAI <br> 2/USART <br> 6/UART4/ <br> G FS/SP <br> DIF | CAN $1 / 2 / \mathrm{T}$ IM12/13 14/QUAD SPI/FMC/ LCD | SAI2/QU ADSPI/S DMMC2/D FSDM1/O OTG1 FS /LCD | $\begin{aligned} & \text { I2C4/CAN } \\ & \text { 3/SDMM } \\ & \text { C2/ETH } \end{aligned}$ | UART7I FMC/SD MMC1/M DIOS/OT G2_FS | $\begin{aligned} & \text { DCMI/L } \\ & \text { CD/DSI } \end{aligned}$ | LCD | SYS |
| Port C | PC11 | - | - | - | DFSDM1 DATAIN5 | - | - | $\begin{gathered} \mathrm{SPI3} 3 \mathrm{MI} \\ \mathrm{SO} \end{gathered}$ | $\begin{gathered} \text { USART3 } \\ \quad \text { RX } \end{gathered}$ | UART4_ RX | QUADSP <br> I_BK2_N CS | - | - | $\underset{-D 3}{\text { SDMMC }}$ | $\underset{4}{\text { DCMI_D }}$ | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PC12 | $\begin{array}{\|c} \hline \text { TRACED } \\ 3 \end{array}$ | - | - | - | - | - | $\begin{gathered} \text { SPI3M } \\ \text { OSI//2S3 } \end{gathered}$ | $\begin{gathered} \text { USART3 } \\ \text { CK } \end{gathered}$ | $\underset{\mathrm{X}}{\text { UART5_T }}$ | - | - | - | $\underset{\text { _CK }}{\substack{\text { SDMMC }}}$ | $\underset{9}{\text { DCMI_D }}$ | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PC13 | - | - | - | - | - | - | - | - | - | - | - | - | - | - | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PC14 | - | - | - | - | - | - | - | - | - | - | - | - | - | - | - | EVEN TOUT |
|  | PC15 | - | - | - | - | - | - | - | - | - | - | - | - | - | - | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
| Port D | PDO | - | - | - | $\begin{array}{\|c} \text { DFSDM1 } \\ \text { CKIN6 } \end{array}$ | - | - | DFSDM1 DATAIN 7 | - | $\begin{aligned} & \text { UART4_ } \\ & \text { RX } \end{aligned}$ | $\begin{gathered} \text { CAN1_R } \\ X \end{gathered}$ | - | - | FMC_D2 | - | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PD1 | - | - | - | $\begin{aligned} & \text { DFSDM1 } \\ & \text { DATAIN6- } \end{aligned}$ | - | - | DFSDM1 _CKIN7 | - | $\begin{gathered} \text { UART4_T } \\ X \end{gathered}$ | $\begin{gathered} \text { CAN1_T } \\ \times \end{gathered}$ | - | - | FMC_D3 | - | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PD2 | $\underset{2}{\text { TRACED }}$ | - | $\underset{R}{\text { TIM3_ET }}$ | - | - | - | - | - | $\begin{aligned} & \text { UART5- } \\ & \text { RX } \end{aligned}$ | - | - | - | $\begin{gathered} \text { SDMMC } \\ \text { CMD } \end{gathered}$ | $\underset{11}{\text { DCMI_D }}$ | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PD3 | - | - | - | $\begin{gathered} \text { DFSDM1- } \\ \text { CKOUT } \end{gathered}$ | - |  | $\begin{aligned} & \text { DFSDM1 } \\ & \text {-DATAIN } \\ & 0 \end{aligned}$ | $\begin{gathered} \text { USART2 } \\ \text { _CTS } \end{gathered}$ | - | - | - | - | $\underset{K}{\text { FMC_CL }}$ | $\underset{5}{\text { DCMI_D }}$ | LCD_G7 | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PD4 | - | - | - | - | - | - | DFSDM1 _CKINO | USART2 _RTS | - | - | - | - | $\underset{\mathrm{OE}}{\mathrm{FMC}}$ | - | - | EVEN TOUT |
|  | PD5 | - | - | - | - | - | - | - | $\begin{gathered} \text { USART2 } \\ \text { _TX } \end{gathered}$ | - | - | - | - | $\underset{\text { FMC_N }}{\text { WE }}$ | - | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PD6 | - | - | - | $\begin{array}{\|c} \text { DFSDM1 } \\ \text { CKIN4 } \end{array}$ | - | _SD | $\mathrm{SAl1}_{-\mathrm{A}}^{\mathrm{A}}$ | $\begin{gathered} \text { USART2 } \\ \text { _RX } \end{gathered}$ | - | - | $\begin{aligned} & \text { DFSDM1 } \\ & \text { DATAIN1 } \end{aligned}$ | $\begin{array}{\|c} \text { SDMMC2 } \\ \text { CK } \end{array}$ | $\begin{aligned} & \text { FMCN } \\ & \text { WAIT } \end{aligned}$ | $\underset{10}{\text { DCMI_D }}$ | LCD_B2 | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |
|  | PD7 | - | - | - | $\begin{array}{\|c\|} \hline \text { DFSDM1 } \\ \text { DATAIN4 } \end{array}$ | - |  | DFSDM1 _CKIN1 | $\begin{gathered} \text { USART2 } \\ \text { CKK } \end{gathered}$ | $\underset{\text { X0 }}{\text { SPDIF_R }}$ | - | - | $\begin{aligned} & \text { SDMMC2 } \\ & \text { _CMD } \end{aligned}$ | $\underset{1}{\text { FMC_NE }}$ | - | - | $\begin{aligned} & \text { EVEN } \\ & \text { TOUT } \end{aligned}$ |

Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\stackrel{n}{\stackrel{n}{4}}$ | $\stackrel{\omega}{\omega}$ | \|를을 |  |  |  |  | 永年 |  | 坔与 |  | 坔各。 | 를는 | $\mid \underset{\sim}{\text { zun }}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\stackrel{\text { I }}{\frac{1}{4}}$ | O | ， | ＇ | $\begin{aligned} & \tilde{m}_{1} \\ & 0_{1} \end{aligned}$ |  | ＇ | ＇ | ＇ | ＇ | ， | ， | ＇ | ， |
| $\stackrel{m}{4}$ | $\sum_{0}^{2}$ | ， | ， | ， |  | ＇ | ， | ， | ＇ | $\begin{aligned} & \hline 0 \\ & \sum_{0}^{1} N \\ & \sum_{0} \end{aligned}$ | $\begin{array}{\|l\|} \hline 0 \\ \sum_{0}^{1} m \\ 0 \end{array}$ | ， | ， |
| $\stackrel{N}{4}$ |  |  | $\begin{aligned} & \bar{L}_{1}^{\prime} \\ & \sum_{\sum_{u}^{\prime}} \end{aligned}$ | $\left\lvert\, \begin{aligned} & \bar{a}_{1} \\ & \sum_{i}^{0_{1}} \end{aligned}\right.$ |  |  |  | $\begin{aligned} & \mathrm{O}_{\mathrm{I}} \\ & \sum_{\Perp}^{\prime} \end{aligned}$ | $\begin{aligned} & \bar{\Sigma}_{\bar{\prime}}^{\prime} \\ & \sum_{\text {N }}^{\prime} \end{aligned}$ | $\begin{array}{\|l} \sum_{\Sigma_{10}} \\ \sum_{i}^{0} \end{array}$ | $\begin{aligned} & \sum_{N_{l}} \\ & \sum_{U}^{0} \\ & \hline \end{aligned}$ |  | $\begin{aligned} & {\underset{ভ}{c}}_{1} \\ & \sum_{i}^{0} の \end{aligned}$ |
| $\underset{\stackrel{i}{4}}{\overline{4}}$ |  | ， | ， | ， | ， | ， | ， | ， | ， | ， | ， |  | ， |
| 은 |  | ， | ， | ＇ |  |  |  | ＇ |  |  | ， | ， | ， |
| $\frac{\ddot{4}}{4}$ |  | ， | ， | ＇ |  |  |  | ， | ， | ， | ， |  | ， |
| $\stackrel{\infty}{4}$ |  |  | ， | ， |  | ＇ | ＇ |  | －${ }_{\text {on }}^{\substack{\text { cos }}}$ |  |  | ＇ | ， |
| 交 |  |  | $\begin{aligned} & \hline \begin{array}{c} m \\ \underset{c}{\alpha} \\ \underset{\sim}{n} \\ \hline \end{array} \\ & \hline \end{aligned}$ | $\begin{array}{\|l} \hline \begin{array}{l} n \\ \underset{4}{x} \\ \substack{0 \\ 0} \\ \hline \end{array} \\ \hline \end{array}$ |  |  | ， | ， | ＇ | ， | ， | ， | ＇ |
| 这 |  | ＇ | ， | ， | ＇ | ， | ， | ＇ | ， | ， | ＇ |  |  |
| $\stackrel{6}{4}$ |  | ， | ， | ， | ， | ＇ | ， | ， | ＇ | ， | ＇ | $\begin{aligned} & 0 \\ & 0_{1} \\ & \frac{\vdots}{0} \end{aligned}$ | ， |
| 誌 |  | ＇ | ， | ， |  | O $\sim_{1}$ J $^{\text {a }}$ | $\begin{aligned} & 0_{1} \\ & \mathbf{J}_{1} \varangle \\ & \underline{N} \end{aligned}$ | ， | ， | ， | ＇ | ， | ， |
| ¢ |  | $\begin{array}{\|l\|l} \hline \sum_{0}^{\prime} \\ \sum_{0}^{0} \\ \text { y } \\ 0 \\ 0 \\ \hline \end{array}$ |  | $\begin{array}{\|l\|} \hline \sum_{0}^{1} \\ 0 . \\ 00 \\ 0 \\ 0 \\ \hline \end{array}$ | ＇ | $\begin{aligned} & -1 \\ & \sum_{i}^{-1} \bar{z} \end{aligned}$ | $\sum_{a}^{\sum_{i}^{\prime}}$ | ＇ | ， |  | $\begin{aligned} & -1 \\ & \sum_{i}^{\prime} \tilde{z} \\ & \sum_{1} \end{aligned}$ | ＇ | ， |
| 攵 | $\begin{aligned} & \hline \frac{N}{N} \\ & \frac{N}{N} \\ & \stackrel{N}{1} \end{aligned}$ | ＇ | ＇ | ＇ | ＇ | $\begin{aligned} & \hline U_{1} \\ & \sum_{i}^{+} \bar{I} \end{aligned}$ | $\begin{aligned} & \hline U^{\prime} \\ & \sum_{i}^{J^{\prime}} \times 1 \end{aligned}$ | $\begin{aligned} & U \\ & U_{1}^{\prime} \\ & \sum_{i} ㅆ ㅗ \end{aligned}$ | $\begin{aligned} & U_{1} \\ & \sum_{i}^{y_{i}} \underset{I}{ } \end{aligned}$ |  | ， | ＇ | ＇ |
| 砏 |  | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ＇ |  | ＇ | ＇ | ＇ | ＇ |
| 茹 | $\stackrel{\infty}{\omega}$ | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ， |  | ， | ， | 嵳 | 号 |
| ！ |  | 응 | 몸 | 음 | $\overline{\mathrm{a}}$ | N | $\stackrel{m}{i}$ | $\stackrel{\rightharpoonup}{\mathrm{a}}$ | $\stackrel{\varrho}{\square}$ | 씀 | 员 | 뿞 | 뜸 |
|  |  | $\begin{aligned} & \stackrel{\rightharpoonup}{0} \\ & \stackrel{\rightharpoonup}{\circ} \end{aligned}$ |  |  |  |  |  |  |  | Q |  |  |  |

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Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\frac{n}{2}$ | $\stackrel{0}{\omega}$ |  | $\underset{\text { zis }}{\text { za }}$ | 穹5 |  | 를ㅇㅇㄴ |  | 를흔 |  |  |  | $\underset{\sim}{\text { za }}$ | 宕尔 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\stackrel{H}{\stackrel{U}{4}}$ | O | $\begin{aligned} & \circ \\ & \stackrel{\circ}{1} \\ & 0 \end{aligned}$ | $\begin{aligned} & 0_{1} \\ & 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & \bar{O}_{1} \\ & 0 \end{aligned}$ | ＇ | ＇ | ＇ | ＇ | $\begin{aligned} & \text { O} \\ & 0 \\ & \hline 1 \end{aligned}$ |  |  |  | $\xrightarrow{\text { Nor }}$ |
| $\frac{\stackrel{m}{4}}{\stackrel{4}{4}}$ | $\begin{aligned} & 1 \\ & \sum_{0}^{2} \\ & 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & 0 \\ & \sum_{0}^{1} \\ & \sum_{0}^{\prime} \end{aligned}$ | $\begin{aligned} & 0 \\ & \sum_{0}^{1} \\ & \sum_{0} \end{aligned}$ | $\begin{array}{\|l\|} \hline 0 \\ \sum_{0}^{1} \end{array}$ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| $\stackrel{N}{\stackrel{N}{4}}$ |  | $\begin{aligned} & \text { N } \\ & \sum_{<1}^{0} \\ & \sum_{L}^{0} \end{aligned}$ | $\begin{aligned} & \hline \tilde{S}_{1} \\ & \sum_{L}^{0}- \end{aligned}$ | $\begin{array}{\|l\|} \hline \underset{S}{N} \\ \sum_{L}^{N} N \end{array}$ | $\begin{aligned} & \mathrm{O}_{1} \\ & \sum_{L}^{\prime} \end{aligned}$ |  | $\begin{aligned} & \circ \\ & \AA_{1} \\ & \sum_{L}^{\prime} \end{aligned}$ | $\begin{aligned} & \hat{N}_{1} \\ & \sum_{k}^{0} \end{aligned}$ |  | $\begin{aligned} & \text { İ } \\ & { }_{1}^{\prime} \\ & \sum_{k}^{\prime} \end{aligned}$ |  | $\begin{aligned} & \bar{S}_{1}^{\prime} \\ & \sum_{U}^{\prime} \end{aligned}$ | $\begin{array}{\|l\|} \hline \bar{\Sigma}_{1} \\ \sum_{u}^{0^{\prime} N} \end{array}$ |
| $\underset{\text { 친 }}{\bar{i}}$ | Z | ＇ | ， | ＇ | ， | ＇ | ＇ | ， | ， | ， | ＇ | ＇ | ， |
| 은 |  |  | $\begin{aligned} & \sum_{0}^{\prime} \sum_{0}^{\prime} \\ & \sum_{4}^{\prime} \\ & 0 \end{aligned}$ | $\begin{aligned} & \sum_{\sum_{n}}^{0} m_{1} \\ & \underset{\sim}{\mathbb{1}} x^{\prime} \end{aligned}$ |  |  |  |  |  | $\begin{aligned} & \mathbf{N}_{1} \\ & \stackrel{1}{m_{1}} \\ & \underset{\mathbb{N}}{x_{1}} \end{aligned}$ | $\begin{array}{\|l\|} \hline \boldsymbol{\omega}^{\prime} \\ \stackrel{\rightharpoonup}{\mathbf{N}} \\ \stackrel{\mathbf{N}^{\infty}}{ } \end{array}$ | $\begin{aligned} & \sum_{1}^{0} m_{1} \\ & \underset{\mathbb{N}}{N_{1}^{\prime}} \end{aligned}$ | ＇ |
| 난 |  | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| $\stackrel{\infty}{4}$ |  | ＇ | ＇ | ＇ | $\begin{aligned} & \hat{N}^{\prime} \\ & \hat{e}_{5}^{x} \times{ }^{\text {co }} \end{aligned}$ |  |  | $\begin{aligned} & \text { Non } \\ & \text { 宕合 } \end{aligned}$ | ， | ＇ | ， | ＇ | ＇ |
| 年 |  | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| $\stackrel{\circ}{4}$ |  |  |  |  |  |  |  |  |  |  | $\begin{aligned} & \sum_{0}^{5}=0 \\ & 0 \\ & 0 \\ & 0 \\ & 0 \\ & 0 \end{aligned}$ | ＇ | ＇ |
| $\stackrel{\text { ¢ }}{4}$ |  | $\begin{aligned} & \begin{array}{l} \infty \\ \sum_{1} \\ j_{0} \infty \\ \infty \end{array} \end{aligned}$ |  |  | ＇ | ＇ | ＇ | ＇ | $\begin{aligned} & \begin{array}{l} \Sigma_{1} \\ \mathbf{j}_{0}^{0} \\ \infty \end{array} \end{aligned}$ |  | $\begin{aligned} & \sum_{j_{1}} \\ & \bar{J}_{0}^{\infty} \end{aligned}$ | $\begin{aligned} & \sum_{j^{\prime}} \\ & \mathbf{J}_{0}^{0} 0 \end{aligned}$ | ＇ |
| 誌 |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| 㜽 |  | ＇ |  | $\begin{aligned} & \hline \Xi^{\prime} \\ & \sum_{1} N \\ & \sum_{F} \end{aligned}$ | ＇ | ＇ | ， | ＇ | ， | ＇ | ， | ＇ | ＇ |
| 尔 |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| 「 |  | ， | ＇ | $\sum_{i}^{m_{1}} \sum_{i}^{\sum_{1}}$ |  |  | $\begin{aligned} & U_{1} \\ & \sum_{i} \bar{I} \end{aligned}$ | $\begin{aligned} & 0_{1} \\ & \sum_{i}^{\prime} \underset{1}{I} \end{aligned}$ | $\begin{array}{\|l\|} \hline U_{1} \\ \sum_{i} \\ \hline \end{array}$ | $\begin{aligned} & U_{1} \\ & \sum_{i}^{1}{ }_{i} \bar{T} \end{aligned}$ | $\begin{aligned} & U_{0} \\ & \sum_{i}^{\prime} \text { 온 } \end{aligned}$ | $\begin{aligned} & U_{1} \\ & {\underset{i}{\prime}}_{\underline{I}}^{I} \end{aligned}$ | $\left\lvert\, \begin{aligned} & \infty_{1} z \\ & \sum_{i}^{\frac{D_{1}}{1}} \end{aligned}\right.$ |
| 안 | $\stackrel{\infty}{\omega}$ |  |  |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| \％ |  | 岂 | 吕 | 追 | 凯 | 씀 | 䟧 | 음 | $\underset{\sim}{\underset{\alpha}{\mid}}$ | $\underset{\sim}{\underset{\sim}{\sim}}$ | $\stackrel{\stackrel{N}{山 己}}{\underset{\sim}{u}}$ | $\underset{\sim}{\underset{\sim}{\underset{\sim}{4}}}$ | $\stackrel{\sim}{\text { ¢ }}$ |
|  |  | $\begin{aligned} & \text { 山 } \\ & \stackrel{\rightharpoonup}{\circ} \end{aligned}$ |  |  |  |  |  |  |  |  |  |  |  |

Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\frac{n}{4}$ | $\stackrel{\infty}{\omega}$ | \|를흔 |  |  |  | $\underset{\sim}{2} \underset{\sim}{2}$ |  | 를은 | 를는 | 坔っ |  | \|를은 | 誌岩 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\frac{\underset{U}{4}}{\frac{J}{4}}$ | O | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ， | ＇ | 山 <br> O <br> O | ＇ |
| $\frac{N}{\stackrel{N}{4}}$ |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ， | ， | ＇ | $\sum_{0}^{0} \sum_{0}^{1}=$ | $\stackrel{\sim}{0}_{0}{ }_{0}^{1}$ |
| $\underset{\underset{\sim}{\mathbb{L}}}{\stackrel{N}{2}}$ |  |  | $\begin{aligned} & \overline{\widetilde{~}} \\ & \sum_{\\|}^{\prime} \\ & \hline \end{aligned}$ | $\begin{aligned} & \text { N } \\ & \sum_{1}^{\prime} \\ & \sum_{4}^{\prime} \end{aligned}$ | $\begin{aligned} & \text { N } \\ & \sum_{L}^{0} \\ & \sum_{L}^{\prime} \end{aligned}$ | $\begin{aligned} & \mathbb{K} \\ & \sum_{1}^{N} \\ & \sum_{L}^{\prime} \end{aligned}$ | $$ | ＇ | ＇ | ＇ | ＇ | ＇ | $\begin{aligned} & 0,0 \\ & 0_{1}, \\ & \sum_{4}^{0} \frac{\alpha}{2} \end{aligned}$ |
| $\underset{\stackrel{\rightharpoonup}{4}}{\overline{4}}$ |  | ＇ | ， | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ， | ， | ＇ | ， |
| $\frac{\circ}{4}$ |  | ， | ， | ＇ | ＇ | ＇ | ， | ＇ | ＇ |  |  | ＇ |  |
| 䓘 |  | ＇ | ， | ， | ＇ | ＇ | ＇ |  |  | $\begin{aligned} & 0 \\ & \sum_{i}^{m_{1}} \bar{I} \end{aligned}$ | $\begin{aligned} & U_{1}^{\prime} \\ & \sum_{i}^{J_{i}} \bar{I} \end{aligned}$ | 仿 | ， |
| $\stackrel{\infty}{4}$ |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |  |  |  |  | ＇ | ， |
| 苼 |  츤 <br>  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| $\stackrel{\circ}{4}$ | NiN Nㅡㅁ른 <br> No No | ＇ | ， | ， | ＇ | ＇ | ＇ |  | $\begin{aligned} & \sum_{1} m_{1} \\ & \bar{\kappa} \underset{1}{\vdots} \end{aligned}$ |  |  | ＇ | ＇ |
| $\stackrel{0}{4}$ |  | ， | ， | ， | ＇ | ＇ | ＇ | $\begin{aligned} & \sum_{1} \\ & \frac{\Omega_{1}}{n} \end{aligned}$ | $\begin{aligned} & 0 \\ & \omega_{1} \\ & \stackrel{n}{0}_{\omega_{n}} \end{aligned}$ | $\begin{aligned} & \overline{\sum_{1}} \\ & \frac{\varrho^{\prime}}{\omega} \\ & \infty \end{aligned}$ | $\begin{aligned} & \sum_{1} \\ & \frac{\omega}{0} \pi \\ & \infty \end{aligned}$ | ＇ | $\begin{aligned} & \sum_{1} \\ & \frac{\omega_{0}}{0} \mathrm{O} \end{aligned}$ |
| 誌 |  | $\begin{aligned} & \dot{N}_{1} \\ & \tilde{N}_{1} \varangle \\ & \underline{\underline{x}} \end{aligned}$ | U N N－1 N－ |  | ＇ | ＇ | ， | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| $\frac{\dddot{4}}{4}$ |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |  | $\begin{aligned} & \hline I^{I} \\ & \sum_{i}^{I_{i}^{\prime}}- \end{aligned}$ | ＇ | ＇ | ＇ | ＇ |
| N |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| 㐫 |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| 茄 | $\stackrel{\infty}{\omega}$ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| $\bigcirc$ |  | 암 | 乭 | 츰 | $\frac{\mathscr{L}}{\underline{\circ}}$ | 绩 | $\frac{!!}{2}$ | $\stackrel{\circ}{1}$ | 茄 | 음 | 암 | 은 | $\underset{\text { ¢ }}{\text { 듬 }}$ |
|  |  | $\begin{aligned} & \text { u } \\ & \stackrel{\rightharpoonup}{\mathrm{a}} \end{aligned}$ |  |  |  |  |  |  |  |  |  |  |  |

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|  | $\begin{array}{\|l\|l\|l\|l\|l\|l\|} \hline \frac{n}{4} \end{array}$ | $\frac{\infty}{\omega}$ |  |  |  |  | $\begin{array}{\|l\|} \hline \text { 学灾 } \end{array}$ | $\begin{array}{\|l\|} \hline \text { 2y } \\ \text { y } \end{array}$ |  | $\begin{array}{\|l\|} \hline \text { 2y } \\ \text { y } \end{array}$ |  | 学5 | $\begin{array}{\|l\|l\|} \hline \underset{y}{2} \stackrel{5}{w} \\ \hline \end{array}$ |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | $\underset{\frac{t}{4}}{\frac{t}{4}}$ | O | ＇ | ＇ | ＇ | ＇ | － | － |  | ， | ＇ | ， | 䓂 | צ ${ }_{\text {U }}^{\text {¢ }}$ |
|  | $\frac{m}{\frac{m}{4}}$ | 左皆 | ， | ＇ | ， | ＇ | ， | ＇ | ＇ | ， | ＇ | ＇ | －${ }_{\text {¢ }}^{\substack{1 \\ 0}}$ | $\stackrel{\Sigma}{0}_{0}^{0}{ }_{0}^{\prime}$ |
|  |  |  | $\begin{aligned} & \stackrel{\otimes}{<} \\ & \sum_{4}^{0} \\ & \hline \end{aligned}$ | $\begin{aligned} & \stackrel{\rightharpoonup}{\star} \\ & \sum_{1}^{\prime} \\ & N_{4} \end{aligned}$ | $\begin{aligned} & \hline \infty \\ & \sum_{<}^{\infty} \\ & \sum_{L}^{0} \end{aligned}$ | $\begin{aligned} & \text { Q } \\ & \mathbb{N}_{1} \\ & \sum_{K}^{\prime} \end{aligned}$ | $\begin{aligned} & \mathbb{S}_{1} \\ & \sum_{1}^{0} \\ & \hline \end{aligned}$ | $\begin{array}{\|l\|} \hline \mathbb{S}_{1} \\ \sum_{1}^{0} \\ \hline \end{array}$ | $\begin{array}{\|l\|} \mathbb{T}_{1} \\ {\underset{S}{1}}^{0} N \end{array}$ | $\begin{array}{\|l\|} \hline \bar{S}_{1} \\ \sum_{i N}^{0} \end{array}$ |  |  | $\begin{array}{\|l\|} \hline{\underset{\Sigma}{1}}^{\prime} \\ \sum_{u}^{0} \end{array}$ | $\begin{array}{\|l\|} \hline \underset{u}{z} \\ \sum_{4}^{0} \vdash \end{array}$ |
|  |  |  | ＇ | ＇ | － | ， | ， | ， | ， | ， | ＇ | ＇ | ， | ， |
|  | 은 |  | ＇ | ＇ | － | － | ＇ | － | ＇ | ， | ＇ | ， | ， | ， |
|  | $\stackrel{8}{4}$ |  | ＇ | ＇ | － | ＇ | ＇ | ， | ， | ， | ＇ | ， | ， | ， |
|  | $\stackrel{\infty}{\frac{\infty}{4}}$ |  | ＇ | ， | ＇ | － | ， | ， | ， | ， | ， | ＇ | ， | 道 |
|  | 砍 |  | ＇ | ＇ | － | ＇ | ＇ | ， | ＇ | ， | ＇ | ， | ， | ＇ |
|  | $\frac{0}{4}$ |  | ＇ |  |  | ＇ | ， | － | ， | － | ＇ | ， | ＇ |  |
|  | $\frac{!!}{4}$ |  | ， | ＇ | － | ＇ | ， | ， | ， | － | ＇ | ， | ， | ＇ |
|  | 荘 |  | ＇ |  |  | $\begin{array}{\|l\|} \hline \mathbf{o}_{1} \\ J^{\prime} \ll \\ \underline{\underline{N}} \\ \hline \end{array}$ | ＇ | ， | ， | ， | ＇ | ， | ， | ＇ |
|  | 枈 |  | ， | ， | － | ， | ， | ， | ， | ， | ＇ | ， | ， | ＇ |
|  | 尔 | $\begin{aligned} & \hline \frac{N}{N} \\ & \sum_{N}^{m} \\ & \sum_{1}^{m} \end{aligned}$ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ， | ， | ＇ |
|  | 㐫 |  | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ， | ＇ | ＇ | ， | ＇ |
|  | 안 | $\stackrel{\omega}{\omega}$ | ＇ | ＇ | ， | ＇ | ＇ | ， | ＇ | ＇ | ＇ | ， | ＇ | ＇ |
|  | ！ |  | $\frac{N}{\text { 든 }}$ | $\stackrel{m}{\stackrel{m}{L}}$ | $\frac{\underset{4}{4}}{\frac{t}{4}}$ | $\frac{\text { n }}{\frac{1}{a}}$ | O | ָু | N | § | \％ | セ0 | ¢ | へ |
|  |  |  | $\stackrel{\text { u }}{\text { ¢ }}$ |  |  |  | OL¢ |  |  |  |  |  |  |  |

Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\frac{n}{\dot{4}}$ | $\omega$ | \|를은 | 永年 | 発っ | 誋 | 坔与 | 発っ | $\underset{\text { 2 }}{2}$ |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\stackrel{H}{\stackrel{4}{4}}$ | O | $\begin{aligned} & \hat{O}_{1} \\ & 0 \end{aligned}$ | ＇ | $\begin{aligned} & \tilde{m}_{1}^{\prime} \\ & 0 \end{aligned}$ | $\begin{aligned} & \text { 毋 } \\ & 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & \bar{m}_{1}^{\prime} \\ & \mathrm{O}_{1} \end{aligned}$ | $\begin{aligned} & \text { ষ্́ } \\ & 0 \\ & \hline 1 \end{aligned}$ | $\begin{aligned} & \text { ó } \\ & 0 \\ & 0 \end{aligned}$ | ＇ |
| $\frac{m}{4}$ | 르웅 | ， | $\begin{aligned} & >_{10} \\ & \sum_{0}^{1} \sum_{0} \end{aligned}$ | $\begin{aligned} & 0_{0}^{1} \\ & \sum_{0}^{\prime} N \end{aligned}$ | $\begin{aligned} & 0_{0}^{1} \\ & \sum_{0}^{\prime} m \end{aligned}$ | － | ， | ， |  |
| $\stackrel{N}{\dot{4}}$ |  | $\left\lvert\, \begin{aligned} & 0_{1} \\ & \sum_{k}^{0} \\ & \sum_{u} \end{aligned}\right.$ |  |  |  | $\begin{aligned} & \sum_{\sum_{1}} \\ & \sum_{L}^{\prime} \end{aligned}$ | $\begin{aligned} & \mathbb{N}_{1}^{N} \\ & \sum_{i}^{0} \end{aligned}$ | $\begin{aligned} & {\underset{X}{X}}_{1}^{\prime} \\ & \sum_{L}^{0} \end{aligned}$ | $\begin{aligned} & 0_{0}, 0 \\ & \sum_{k}^{0} z \\ & 0_{1} z \end{aligned}$ |
| $\underset{\underset{4}{\overline{4}}}{\stackrel{F}{4}}$ |  |  | $\sum_{i=1}^{N} O_{1}^{N}$ | $\begin{aligned} & \hline \sum_{00}^{N} \bar{O}_{1} \\ & \hline 0 \end{aligned}$ |  | $\sum_{0}^{N} \sum_{0}^{N}$ |  |  | ＇ |
| $\frac{\circ}{4}$ |  | ， | $\begin{aligned} & \hline \mathscr{N}^{\prime} \\ & \stackrel{1}{\mathbb{1}} \infty \\ & \underset{\infty}{\infty} \end{aligned}$ |  | $\sum_{i=1}^{N} \tilde{N}_{1}$ | ＇ | ＇ | ， | ， |
| $\frac{10}{4}$ |  | ＇ |  | $\begin{aligned} & \text { O} \\ & \text { O} \\ & \text { O} \end{aligned}$ | ＇ | $\begin{aligned} & \mathrm{m}_{1} \\ & \text { OU } \end{aligned}$ | ， |  | ， |
| $\stackrel{\text { ® }}{4}$ |  |  |  | － |  | 为 |  |  |  |
| 交 |  |  |  | ＇ |  | $\begin{aligned} & \hline \alpha_{1} \\ & \frac{\omega_{0}}{\overline{0}} \\ & \frac{0}{\omega} \end{aligned}$ | ＇ | ＇ | ＇ |
| $\stackrel{\circ}{4}$ |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| $\stackrel{\text { ¢ }}{4}$ |  | $\begin{aligned} & \hline \sum_{n} \\ & \frac{\rho_{1} \infty}{0} \\ & \end{aligned}$ | $\begin{aligned} & \bar{\Sigma}_{10} \\ & \overline{\bar{n}}_{\infty} \circlearrowleft \end{aligned}$ |  |  | $\begin{array}{\|l} \hline \sum_{\omega_{1}} \\ \frac{\varrho_{0}}{\infty} \omega \\ \hline \end{array}$ | $\begin{aligned} & 0 \\ & \dot{N}_{1} \\ & \frac{0}{0} \\ & x_{0} \end{aligned}$ | $\begin{aligned} & \sum_{1} \overline{\varrho_{0}}{ }_{n}^{2} \end{aligned}$ | ， |
| 誌 |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ |
| ¢ |  | ＇ | ＇ | ＇ | ＇ | $\left\lvert\, \begin{aligned} & -1 \\ & \sum_{i}^{-1} \bar{z} \\ & \vdots \end{aligned}\right.$ | $\sum_{a}^{\sum_{a}^{\prime}} \stackrel{1}{0}$ |  | ＇ |
| N |  | ＇ | ＇ | ＇ | ， | ＇ | ， | ， | ＇ |
| 둔 |  | ， | ， | ＇ | ， | ＇ | ， | ， | ＇ |
| 안 | $\omega_{\omega}^{\infty}$ | ＇ | ， | ＇ | ， | ＇ |  | ¢ | ＇ |
| ！ |  | ©゚ | O | 음 | F | N | $\begin{aligned} & \text { m } \\ & \hline 0 \end{aligned}$ | $\begin{aligned} & \stackrel{7}{2} \\ & \hline \end{aligned}$ | $\begin{aligned} & \circ \\ & \hline 0 \\ & \hline 2 \end{aligned}$ |
|  |  | $\begin{aligned} & \hline \\ & \hline \text { o } \\ & \hline ⿳ 亠 口 口 又 寸 ~ \end{aligned}$ |  |  |  |  |  |  |  |

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Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\frac{n}{\dot{4}}$ | $\omega$ | \|를은 | 를는 | $\underset{\sim}{2} \underset{\sim}{2}$ | 永年 | \|를은 | 氷年 | 를은 | 坔っ | 永年 | 永5 | 热各 | \|를은 | 坔各。 | 垫 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\stackrel{H}{\stackrel{U}{4}}$ | O | $\begin{aligned} & \hline 0 \\ & 0 \\ & 0 \\ & \hline 1 \end{aligned}$ | $\begin{aligned} & \hline \stackrel{\text { O}}{1} \\ & \text { O} \end{aligned}$ | $\begin{aligned} & \hline \text { O } \\ & 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & \hline 0 \\ & 0 \\ & 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & \hat{\mathrm{O}}_{1} \\ & \mathrm{O}_{1} \end{aligned}$ | ， | $\begin{aligned} & \hline \stackrel{\rightharpoonup}{\mathrm{m}} \\ & \stackrel{1}{0} \end{aligned}$ | $\begin{aligned} & \hline \varrho_{1} \\ & 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & \hline 0 \\ & 0 \\ & \hline 1 \end{aligned}$ | $\begin{aligned} & \hat{\omega} \\ & 0 \\ & 0 \end{aligned}$ |  |  |  | ， |
| $\stackrel{m}{4}$ | $\sum_{0}^{2}$ | $\begin{array}{\|l\|} \hline 0 \\ \sum_{0}^{1} \\ \sum_{0} \end{array}$ | $\begin{aligned} & \hline 0 \\ & \sum_{0}^{\prime} F \\ & \hline \alpha \end{aligned}$ | $\stackrel{i}{0}_{\stackrel{D}{0}_{1}^{\prime}}^{m}$ | $\begin{aligned} & Q_{0}^{1} \\ & \sum_{0}^{1} \infty \end{aligned}$ | $\begin{aligned} & \hline Q_{1}^{\prime} \\ & \sum_{0}^{1} \sigma \end{aligned}$ | $\begin{aligned} & Q_{0}^{\prime} \\ & \sum_{0}^{\prime} \circ \end{aligned}$ | $\begin{aligned} & Q_{1}^{\prime} \\ & \sum_{0}^{1} n \end{aligned}$ | $\begin{aligned} & \hline>10 \\ & \sum_{0}^{n} \sum_{\omega}^{n} \end{aligned}$ | $\begin{aligned} & \hline Q_{1}^{\prime} \\ & \sum_{0}^{1} 0 \end{aligned}$ | $\begin{array}{\|l\|} \hline 0 \\ \sum_{0}^{1} \\ \hline \end{array}$ | ＇ | ＇ | ， | ， |
| $\stackrel{N}{\frac{1}{4}}$ |  | $\begin{array}{\|l\|} \hline \tilde{N}_{1} \\ \sum_{i}^{\prime} N \end{array}$ |  | $\begin{aligned} & \tilde{N}_{1}^{\prime} \\ & \sum_{L}^{\prime} \end{aligned}$ | $\begin{aligned} & \tilde{O}_{1}^{\prime} \\ & \sum_{i}^{0_{1}} \end{aligned}$ | $\begin{array}{\|l\|} \hline N_{0}^{\prime} \\ \sum_{U}^{\prime} 0 \end{array}$ | $\begin{aligned} & \tilde{O}_{1} \\ & \sum_{i}^{0_{1}^{\prime}} \end{aligned}$ | $\begin{aligned} & \sum_{\Sigma_{l}} \\ & \sum_{u}^{0} \end{aligned}$ | $\begin{aligned} & \sum_{N_{l n}} \\ & \sum_{L}^{0} \end{aligned}$ |  | $\begin{array}{\|l\|} \hline \tilde{N}^{\prime} \\ \sum_{i}^{\prime} の \\ \hline \end{array}$ | ＇ | $\begin{array}{\|l\|l} \hline{ }_{n}^{\prime} \\ \sum_{i}^{\prime} 0 \end{array}$ | $\left\lvert\, \begin{array}{\|l\|l\|} \hline 0 \\ \sum_{1}^{\prime} \\ \sum_{4} \end{array}\right.$ | ， |
| $\underset{\underset{4}{i}}{\underset{\sim}{i}}$ |  | ， | ， | ＇ | ＇ | ， | ， | ， | ， | ， | ， | ， | ， | 仿 | ， |
| 은 |  | ， | ， | － | ， | ， | ， | $\begin{aligned} & \hline \sum_{\Sigma_{1}} \\ & \underset{\widetilde{c}}{N_{1}} \end{aligned}$ |  | $\begin{aligned} & \hline a^{\prime} \\ & n^{\prime \varangle} \\ & N^{〔} \\ & \infty \end{aligned}$ | $\begin{array}{\|l\|} \hline \mathscr{N}^{\prime} \\ \stackrel{1}{1} \\ \mathfrak{N}^{\top} \\ \mathscr{\infty} \end{array}$ | ， | ， | ， |  |
| $\frac{10}{4}$ |  | $\begin{aligned} & \underset{\sim}{\infty} \\ & \sum_{0}^{\prime} x \\ & 0 \end{aligned}$ | ， | ， | ＇ | ， | ， | ， | ， | ， |  | ， |  | ＇ | 0 <br> 0 <br> 0 |
| $\stackrel{\infty}{4}$ |  |  | ， | ， | ＇ | － | ， | ， | ， | ， |  | ＇ |  | ， | ， |
| 交 |  | ＇ | ， | ＇ | ， | ， | ， | ＇ | ＇ | ＇ | ＇ | － | ， | ， | ， |
| $\frac{00}{4}$ |  | ＇ | ， | ＇ | ＇ | ， | ， | ， | ， | ＇ | ＇ | ， | ＇ | ， | ， |
| $\frac{\ddot{6}}{4}$ |  | ＇ | ， |  |  | $\begin{array}{\|l\|l} \hline \bar{N}^{\prime} O \\ \frac{N_{n}}{\infty} \\ \hline \end{array}$ |  | ， | ， | ， | ＇ | ， | ＇ | ， | ， |
| 蒋 |  | ， | ， | ＇ | ＇ | ， | ， | ＇ | ， | ， | ， | － | ， | ＇ | ＇ |
| $\frac{\mathscr{m}}{\mathbb{4}}$ |  |  | $\begin{aligned} & \mathrm{I}_{0}^{\prime} \\ & \sum_{\sum_{1}^{\prime}}^{\infty}{ }^{\circ} \mathrm{z} \end{aligned}$ | ， |  |  |  | $\left\lvert\, \begin{aligned} & \frac{\overline{\mathrm{s}}}{1} \\ & \sum_{1}^{\infty} z \\ & \sum_{1} \end{aligned}\right.$ | $\begin{array}{\|l\|} I_{0}^{\prime} \\ \sum_{i}^{\prime} \\ \sum_{1} \end{array}$ | $\begin{aligned} & I_{0}^{\prime} \\ & \sum_{1}^{\infty} N \\ & \sum_{1} \end{aligned}$ | $\begin{array}{\|l\|l} \mathrm{I}_{0} \\ \sum_{i}^{\infty} ल \\ \sum_{1} \end{array}$ | － | ， | ， | ， |
| $\frac{\text { N }}{4}$ |  | ＇ | ＇ | $\begin{aligned} & U_{1} \\ & \sum_{i}^{n} I T \end{aligned}$ | ， | ＇ | ， | ， | － | ＇ | ＇ | － | ， | ＇ | ＇ |
| 춘 |  | ＇ | － | ＇ | ＇ | ， | ＇ | ＇ | ， | ＇ |  | ， | ＇ | ， | ＇ |
| $\frac{10}{4}$ | $\omega_{\omega}^{\infty}$ | ， | ， | ＇ | ＇ | ， | ＇ | ， | ， | ， |  | ． | ＇ | ， | ， |
| ！ |  |  | $\begin{aligned} & \text { 옴 } \\ & \hline \end{aligned}$ | 은 | Г | ㅍ | 음 | $\frac{ \pm}{\square}$ | 음 | 음 | へ | ¢ | 음 | 음 | 듬 |
|  |  |  |  | $\stackrel{ \pm}{\circ}$ |  |  |  |  |  |  |  |  |  |  |  |

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Table 13．STM32F765xx，STM32F767xx，STM32F768Ax and STM32F769xx alternate

| $\frac{n}{i k}$ | $\stackrel{\infty}{\omega}$ | \|를은 | 垫 |  | 热各 |  | $\begin{aligned} & \text { zun } \\ & \text { y } \\ & \hline 10 \end{aligned}$ |  | 热各 | $\mid \underset{\sim}{\text { zu }}$ | 热各 | 誋 | 永年 | $\underset{\sim}{\text { 2 }}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\frac{\underset{4}{4}}{\frac{t}{4}}$ | O | $\begin{aligned} & \hline{ }_{\mathrm{O}}^{1} \\ & 0 \end{aligned}$ | $\begin{aligned} & \hline 0 \\ & 0 \\ & 0 \\ & \hline 1 \end{aligned}$ | $\begin{aligned} & \overline{\bar{m}_{1}^{\prime}} \\ & \stackrel{0}{0} \end{aligned}$ | $\begin{aligned} & \hline \tilde{m}_{1} \\ & 0_{1} \end{aligned}$ | $\begin{aligned} & \tilde{\omega}_{1} \\ & \stackrel{U}{1}^{\prime} \end{aligned}$ | $\begin{aligned} & \text { O} \\ & 0 \\ & 0 \\ & \hline \end{aligned}$ | $\begin{aligned} & \hline 0 \\ & 0 \\ & 0 \\ & \hline 1 \end{aligned}$ | $\begin{aligned} & \hat{O}_{1} \\ & \mathrm{O}_{1} \end{aligned}$ | $\begin{aligned} & \hline \stackrel{\rightharpoonup}{\mathrm{o}} \\ & 0 \\ & \hline \mathrm{O} \end{aligned}$ | $\begin{aligned} & \text { 品 } \\ & 0_{1}^{\prime} \end{aligned}$ |  | $\begin{aligned} & \hat{\mathrm{m}}_{1} \\ & \mathrm{o}_{1} \end{aligned}$ | $\begin{aligned} & \ddot{0}_{1} \\ & 0 \\ & 0 \end{aligned}$ |
| $\stackrel{m}{4}$ |  | ， | ， | ， | ， | ， | ， | ， | ， | ， | ， | ， | ， | ． |
| $\stackrel{N}{\dot{4}}$ |  | ， | ， | ， | ， | － | ， | ， | － | ， | － | ， | ， | ， |
| $\underset{\underset{4}{i}}{\overline{4}}$ |  | ＇ | ， | ， | ＇ | ＇ | ， | ， | ， | ， | － | － | ＇ | ， |
| $\frac{\text { 은 }}{\stackrel{1}{4}}$ |  | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ＇ | － | － | ， | ， | ＇ |
| $\frac{\ddot{4}}{4}$ |  | ， | $\begin{aligned} & \text { O} \\ & \text { OU } \\ & \text { O- } \end{aligned}$ | $\begin{aligned} & \text { 犬 } \\ & 0 \\ & \hline \mathrm{O} \end{aligned}$ | ＇ | ＇ | ， | ， | ＇ | ， | － | － | ， | ， |
| $\stackrel{\infty}{4}$ |  | ＇ | ＇ | ， | ＇ | ， | ， | － | － | － | － | － | ＇ | ＇ |
| 交 |  | ＇ | ＇ | ＇ | ＇ | ， | ， | ， | ， | ， | ， | ， | ， | ＇ |
| $\frac{00}{4}$ |  | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ＇ | ＇ | ＇ |
| $\stackrel{0}{4}$ |  | ， | ， | ， | ＇ | ， | ， | ， | ， | ， | ， | ， | ， | ＇ |
| 誌 |  | ＇ | ， | ， | ＇ | ＇ | ＇ | ＇ | ＇ | ， | ＇ | ＇ | ＇ | ＇ |
| 枈 |  | ＇ | ， | ， | ， | － | ， | ， | ， | ， | ， | － | ＇ | ＇ |
| $\frac{\mathrm{N}}{\mathbf{\alpha}}$ |  | ＇ | ， | ， | ＇ | ＇ | ＇ | ， | ， | ＇ | ， | ＇ | ＇ | ＇ |
| 砏 |  | ， | ， | ， | ＇ | ， | ， | ， | ， | ， | ， | － | ， | ＇ |
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| ！ |  | $\underset{0}{5}$ | $\stackrel{N}{2}$ | $\stackrel{\infty}{2}$ | $\stackrel{\rightharpoonup}{2}$ | $\stackrel{\infty}{2}$ | $\stackrel{\text { 옴 }}{ }$ | $\frac{\bar{y}}{\mathrm{a}}$ | $\frac{\mathfrak{y}}{\mathrm{a}}$ | 끔 | 损 | 铝 | ํํㅁ | 츰 |
|  |  | ? |  |  |  |  | 늠 |  |  |  |  |  |  |  |

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## 4 Memory mapping

The memory map is shown in Figure 22.
Figure 22. Memory map


Table 14. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx register boundary addresses ${ }^{(1)}$

| Bus | Boundary address | Peripheral |
| :---: | :---: | :---: |
| - | 0xE00F FFFF - 0xFFFFF FFFF | Reserved |
| Cortex-M7 | 0xE000 0000-0xE00F FFFF | Cortex-M7 internal peripherals |
| AHB3 | 0xD000 0000-0xDFFF FFFF | FMC bank 6 |
|  | 0xC000 0000-0xCFFFF FFFF | FMC bank 5 |
|  | 0xA000 2000-0xBFFF FFFF | Reserved |
|  | 0xA000 1000-0xA000 1FFF | Quad-SPI control register |
|  | 0xA000 0000-0xA000 0FFF | FMC control register |
|  | 0x9000 0000-0x9FFF FFFF | Quad-SPI |
|  | 0x8000 0000-0x8FFF FFFF | FMC bank 3 |
|  | 0x7000 0000-0x7FFF FFFF | FMC bank 2 |
|  | 0x6000 0000-0x6FFF FFFF | FMC bank 1 |
| - | $0 \times 5006$ 0C00-0x5FFF FFFF | Reserved |
| AHB2 | 0x5006 0800-0x5006 0BFF | RNG |
|  | 0x5005 2000-0x5005 FFFF | Reserved |
|  | $0 \times 50051000-0 \times 50051$ FFF | JPEG codec |
|  | 0x5005 0000-0x5005 03FF | DCMI |
|  | $0 \times 50040000-0 \times 5004$ FFFF | Reserved |
|  | 0x5000 0000-0x5003 FFFF | USB OTG FS |

Table 14. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx register boundary addresses ${ }^{(1)}$ (continued)

| Bus | Boundary address | Peripheral |
| :---: | :---: | :---: |
| - | 0x4008 0000-0x4FFF FFFF | Reserved |
| AHB1 | 0x4004 0000-0x4007 FFFF | USB OTG HS |
|  | 0x4002 BC00-0x4003 FFFF | Reserved |
|  | 0x4002 B000-0x4002 BBFF | Chrom-ART (DMA2D) |
|  | 0x4002 9400-0x4002 AFFF | Reserved |
|  | 0x4002 9000-0x4002 93FF | ETHERNET MAC |
|  | 0x4002 8C00-0x4002 8FFF |  |
|  | 0x4002 8800-0x4002 8BFF |  |
|  | 0x4002 8400-0x4002 87FF |  |
|  | 0x4002 8000-0x4002 83FF |  |
|  | 0x4002 6800-0x4002 7FFF | Reserved |
|  | 0x4002 6400-0x4002 67FF | DMA2 |
|  | 0x4002 6000-0x4002 63FF | DMA1 |
|  | 0x4002 5000-0X4002 5FFF | Reserved |
|  | 0x4002 4000-0x4002 4FFF | BKPSRAM |
|  | 0x4002 3C00-0x4002 3FFF | Flash interface register |
|  | 0x4002 3800-0x4002 3BFF | RCC |
|  | $0 \times 40023400-0 \times 4002$ 37FF | Reserved |
|  | 0x4002 3000-0x4002 33FF | CRC |
|  | 0x4002 2C00-0x4002 2FFF | Reserved |
|  | 0x4002 2800-0x4002 2BFF | GPIOK |
|  | 0x4002 2400-0x4002 27FF | GPIOJ |
|  | 0x4002 2000-0x4002 23FF | GPIOI |
|  | 0x4002 1C00-0x4002 1FFF | GPIOH |
|  | 0x4002 1800-0x4002 1BFF | GPIOG |
|  | 0x4002 1400-0x4002 17FF | GPIOF |
|  | 0x4002 1000-0x4002 13FF | GPIOE |
|  | 0X4002 0C00-0x4002 0FFF | GPIOD |
|  | 0x4002 0800-0x4002 0BFF | GPIOC |
|  | 0x4002 0400-0x4002 07FF | GPIOB |
|  | 0x4002 0000-0x4002 03FF | GPIOA |

Table 14. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx register boundary addresses ${ }^{(1)}$ (continued)

| Bus | Boundary address | Peripheral |
| :---: | :---: | :---: |
| - | 0x4001 7C00-0x4001 FFFF | Reserved |
| APB2 | 0x4001 7800-0x4001 7BFF | MDIOS |
|  | 0x4001 7400-0x4001 77FF | DFSDM1 |
|  | 0x4001 6C00-0x4001 73FF | DSI Host |
|  | 0x4001 6800-0x4001 6BFF | LCD-TFT |
|  | 0x4001 6000-0x4001 67FF | Reserved |
|  | 0x4001 5C00-0x4001 5FFF | SAI2 |
|  | 0x4001 5800-0x4001 5BFF | SAI1 |
|  | 0x4001 5400-0x4001 57FF | SPI6 |
|  | 0x4001 5000-0x4001 53FF | SPI5 |
|  | 0x4001 4C00-0x4001 4FFF | Reserved |
|  | 0x4001 4800-0x4001 4BFF | TIM11 |
|  | 0x4001 4400-0x4001 47FF | TIM10 |
|  | 0x4001 4000-0x4001 43FF | TIM9 |
|  | 0x4001 3C00-0x4001 3FFF | EXTI |
|  | 0x4001 3800-0x4001 3BFF | SYSCFG |
|  | 0x4001 3400-0x4001 37FF | SPI4 |
|  | 0x4001 3000-0x4001 33FF | SPI1/I2S1 |
|  | 0x4001 2C00-0x4001 2FFF | SDMMC1 |
|  | 0x4001 $2400-0 \times 4001$ 2BFF | Reserved |
|  | 0x4001 2000-0x4001 23FF | ADC1 - ADC2 - ADC3 |
|  | 0x4001 1C00-0x4001 1FFF | SDMMC2 |
|  | 0x4001 1800-0x4001 1BFF | Reserved |
|  | 0x4001 1400-0x4001 17FF | USART6 |
|  | 0x4001 1000-0x4001 13FF | USART1 |
|  | 0x4001 0800-0x4001 OFFF | Reserved |
|  | 0x4001 0400-0x4001 07FF | TIM8 |
|  | 0x4001 0000-0x4001 03FF | TIM1 |

Table 14. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx register boundary addresses ${ }^{(1)}$ (continued)

| Bus | Boundary address | Peripheral |
| :---: | :---: | :---: |
| - | 0x4000 8000-0x4000 FFFF | Reserved |
| APB1 | 0x4000 7C00-0x4000 7FFF | UART8 |
|  | 0x4000 7800-0x4000 7BFF | UART7 |
|  | 0x4000 7400-0x4000 77FF | DAC |
|  | 0x4000 7000-0x4000 73FF | PWR |
|  | 0x4000 6C00-0x4000 6FFF | HDMI-CEC |
|  | 0x4000 6800-0x4000 6BFF | CAN2 |
|  | 0x4000 6400-0x4000 67FF | CAN1 |
|  | 0x4000 6000-0x4000 63FF | I2C4 |
|  | 0x4000 5C00-0x4000 5FFF | I2C3 |
|  | 0x4000 5800-0x4000 5BFF | I2C2 |
|  | 0x4000 5400-0x4000 57FF | I2C1 |
|  | 0x4000 5000-0x4000 53FF | UART5 |
|  | 0x4000 4C00-0x4000 4FFF | UART4 |
|  | 0x4000 4800-0x4000 4BFF | USART3 |
|  | 0x4000 4400-0x4000 47FF | USART2 |
|  | 0x4000 4000-0x4000 43FF | SPDIFRX |
|  | 0x4000 3C00-0x4000 3FFF | SPI3 / I2S3 |
|  | 0x4000 3800-0x4000 3BFF | SPI2 / I2S2 |
|  | 0x4000 3400-0x4000 37FF | CAN3 |
|  | 0x4000 3000-0x4000 33FF | IWDG |
|  | 0x4000 2C00-0x4000 2FFF | WWDG |
|  | 0x4000 2800-0x4000 2BFF | RTC \& BKP Registers |
|  | 0x4000 2400-0x4000 27FF | LPTIM1 |
|  | 0x4000 2000-0x4000 23FF | TIM14 |
|  | 0x4000 1C00-0x4000 1FFF | TIM13 |
|  | 0x4000 1800-0x4000 1BFF | TIM12 |
|  | 0x4000 1400-0x4000 17FF | TIM7 |
|  | 0x4000 1000-0x4000 13FF | TIM6 |
|  | 0x4000 0C00-0x4000 0FFF | TIM5 |
|  | 0x4000 0800-0x4000 0BFF | TIM4 |
|  | 0x4000 0400-0x4000 07FF | TIM3 |
|  | 0x4000 0000-0x4000 03FF | TIM2 |

1. The gray color is used for reserved Flash memory addresses.

## 5 Electrical characteristics

### 5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to $\mathrm{V}_{\mathrm{SS}}$.

### 5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on $100 \%$ of the devices with an ambient temperature at $T_{A}=25^{\circ} \mathrm{C}$ and $\mathrm{T}_{\mathrm{A}}=\mathrm{T}_{\mathrm{A}} \max$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3 \sigma$ ).

### 5.1.2 Typical values

Unless otherwise specified, typical data are based on $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}$ (for the $1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where $95 \%$ of the devices have an error less than or equal to the value indicated (mean $\pm 2 \sigma$ ).

### 5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

### 5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 23.

### 5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in Figure 24.
Figure 23. Pin loading conditions Figure 24. Pin input voltage

### 5.1.6 Power supply scheme

Figure 25. STM32F769xx/STM32F779xx power supply scheme


Figure 26. STM32F767xx/STM32F777xx power supply scheme


1. To connect BYPASS_REG and PDR_ON pins, refer to Section 2.18: Power supply supervisor and Section 2.19: Voltage regulator.
2. The two $2.2 \mu \mathrm{~F}$ ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.
3. The $4.7 \mu \mathrm{~F}$ ceramic capacitor must be connected to one of the $\mathrm{V}_{\mathrm{DD}} \mathrm{pin}$.
4. $\mathrm{V}_{\mathrm{DDA}}=\mathrm{V}_{\mathrm{DD}}$ and $\mathrm{V}_{\mathrm{SSA}}=\mathrm{V}_{\mathrm{SS}}$.

Caution: Each power supply pair $\left(\mathrm{V}_{\mathrm{DD}} / \mathrm{V}_{\mathrm{SS}}, \mathrm{V}_{\mathrm{DDA}} / \mathrm{V}_{\mathrm{SSA}} \ldots\right)$ must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure good operation of the device. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect operation of the device.

### 5.1.7 Current consumption measurement

Figure 27. Current consumption measurement scheme


### 5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in Table 15: Voltage characteristics, Table 16: Current characteristics, and Table 17: Thermal characteristics may cause permanent damage to the device. These are stress ratings only and the functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. The device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard. Extended mission profiles are available on demand.

Table 15. Voltage characteristics

| Symbol | Ratings | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}-\mathrm{V}_{S S}$ | External main supply voltage (including $\mathrm{V}_{\mathrm{DDA}}, \mathrm{V}_{\mathrm{DD}}$, $V_{\text {BAT }}, V_{\text {DDUSB, }} V_{\text {DDDSI }}{ }^{(1)}$ and $V_{\text {DDSDMMC }}{ }^{(2)}$ | -0.3 | 4.0 | V |
| $\mathrm{V}_{\mathrm{IN}}$ | Input voltage on FT pins ${ }^{(3)}$ | $V_{S S}-0.3$ | $V_{D D}+4.0$ |  |
|  | Input voltage on TTa pins | $V_{S S}-0.3$ | 4.0 |  |
|  | Input voltage on any other pin | $V_{S S}-0.3$ | 4.0 |  |
|  | Input voltage on BOOT pin | $V_{\text {SS }}$ | 9.0 |  |
| $\left\|\Delta \mathrm{V}_{\text {DDx }}\right\|$ | Variations between different $V_{\text {DD }}$ power pins | - | 50 | mV |
| $\mid \mathrm{V}_{\text {SSX }}{ }^{-V_{S S}}$ | Variations between all the different ground pins ${ }^{(4)}$ | - | 50 |  |
| $\mathrm{V}_{\text {ESD }}$ (HBM) | Electrostatic discharge voltage (human body model) | see Section 5.3.18: Absolute maximum ratings (electrical sensitivity) |  | - |

1. Applicable only for STM32F7x9 sales types.
2. All main power ( $\left.\mathrm{V}_{\mathrm{DD}}, \mathrm{V}_{\text {DDA }}, \mathrm{V}_{\text {DDSDMMC }}, \mathrm{V}_{\text {DDUSB }}, \mathrm{V}_{\text {DDDSI }}\right)$ and ground $\left(\mathrm{V}_{\mathrm{SS}}, \mathrm{V}_{S S A}\right)$ pins must always be connected to the external power supply, in the permitted range.
3. $\mathrm{V}_{\text {IN }}$ maximum value must always be respected. Refer to Table 16 for the values of the maximum allowed injected current.
4. Include $\mathrm{V}_{\text {REF- }}$ pin.

Table 16. Current characteristics

| Symbol | Ratings | Max. | Unit |
| :---: | :---: | :---: | :---: |
| $\Sigma l_{\text {VDD }}$ | Total current into sum of all $\mathrm{V}_{\text {DD_x }}$ p power lines (source) ${ }^{(1)}$ | 420 | mA |
| $\Sigma l_{\text {VSs }}$ | Total current out of sum of all $\mathrm{V}_{\text {SS_x }}$ ground lines (sink) ${ }^{(1)}$ | -420 |  |
| $\Sigma I_{\text {VDDUSB }}$ | Total current into $V_{\text {DDUSB }}$ power line (source) | 25 |  |
| $\Sigma I_{\text {VDDSDMMC }}$ | Total current into $\mathrm{V}_{\text {DDSDMMC }}$ power line (source) | 60 |  |
| $\mathrm{I}_{\mathrm{VDD}}$ | Maximum current into each $\mathrm{V}_{\mathrm{DD}_{2} \mathrm{x}}$ power line (source) ${ }^{(1)}$ | 100 |  |
| IVDDSDMMC | Maximum current into $\mathrm{V}_{\text {DDSDMM }}$ power line (source): PG[12:9], PD[7:6] | 100 |  |
| Ivss | Maximum current out of each $\mathrm{V}_{\text {SS_x }}$ ground line (sink) ${ }^{(1)}$ | -100 |  |
|  | Output current sunk by any I/O and control pin | 25 |  |
| 10 | Output current sourced by any I/Os and control pin | -25 |  |
| $\Sigma l_{10}$ | Total output current sunk by sum of all I/O and control pins ${ }^{(2)}$ | 120 |  |
|  | Total output current sunk by sum of all USB I/Os | 25 |  |
|  | Total output current sunk by sum of all SDMMC I/Os | 120 |  |
|  | Total output current sourced by sum of all I/Os and control pins except USB I/Os ${ }^{(2)}$ | -120 |  |
| $\mathrm{I}_{\text {INJ(PIN })}$ | Injected current on FT, FTf, RST and B pins ${ }^{(3)}$ | -5/+0 |  |
|  | Injected current on TTa pins ${ }^{(4)}$ | $\pm 5$ |  |
| $\Sigma \mathrm{I}_{\mathrm{INJ}(\mathrm{PIN})}{ }^{(4)}$ | Total injected current (sum of all I/O and control pins) ${ }^{(5)}$ | $\pm 25$ |  |

1. All main power $\left(\mathrm{V}_{\mathrm{DD}}, \mathrm{V}_{\mathrm{DDA}}\right)$ and ground $\left(\mathrm{V}_{\mathrm{SS}}, \mathrm{V}_{\mathrm{SSA}}\right)$ pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{I N}>V_{D D A}$ while a negative injection is induced by $V_{I N}<V_{S S}$. $I_{I N J(P I N)}$ must never be exceeded. Refer to Table 15: Voltage characteristics for the values of the maximum allowed input voltage.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{I N J(P I N)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 17. Thermal characteristics

| Symbol | Ratings | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{T}_{\text {STG }}$ | Storage temperature range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{J}$ | Maximum junction temperature | 125 |  |

### 5.3 Operating conditions

### 5.3.1 General operating conditions

Table 18. General operating conditions

| Symbol | Parameter | Conditions ${ }^{(1)}$ |  | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\mathrm{HCLK}}$ | Internal AHB clock frequency | Power Scale 3 (VOS[1:0] bits in PWR_CR register = 0x01), Regulator ON, over-drive OFF |  | 0 | - | 144 | MHz |
|  |  | Power Scale 2 (VOS[1:0] bits in PWR_CR register $=0 \times 10$ ), Regulator ON | Overdrive OFF | 0 | - | 168 |  |
|  |  |  | Overdrive ON |  | - | 180 |  |
|  |  | Power Scale 1 (VOS[1:0] bits in PWR_CR register $=0 \times 11$ ), Regulator ON | Overdrive OFF | 0 | - | 180 |  |
|  |  |  | Overdrive ON |  | - | $216^{(2)}$ |  |
| $\mathrm{f}_{\text {PCLK } 1}$ | Internal APB1 clock frequency | Over-drive OFF |  | 0 | - | 45 |  |
|  |  | Over-drive ON |  | 0 | - | 54 |  |
| $\mathrm{f}_{\text {PCLK2 }}$ | Internal APB2 clock frequency | Over-drive OFF |  | 0 | - | 90 |  |
|  |  | Over-drive ON |  | 0 | - | 108 |  |
| $V_{D D}$ | Standard operating voltage | - |  | $1.7{ }^{(3)}$ | - | 3.6 | $\checkmark$ |
| $V_{\text {DDA }}{ }^{(4)(5)}$ | Analog operating voltage (ADC limited to 1.2 M samples) | Must be the same potential as $\mathrm{V}_{\mathrm{DD}}{ }^{(6)}$ |  | $1.7{ }^{(3)}$ | - | 2.4 |  |
|  | Analog operating voltage (ADC limited to 2.4 M samples) |  |  | 2.4 | - | 3.6 |  |
| $V_{\text {DDUSB }}$ | USB supply voltage (supply voltage for PA11,PA12, PB14 and PB15 pins) | USB not used |  | 1.7 | 3.3 | 3.6 |  |
|  |  | USB used |  | 3.0 | - | 3.6 |  |
| $V_{\text {BAT }}$ | Backup operating voltage | - |  | 1.65 | - | 3.6 |  |
| $V_{\text {DDSDMMC }}$ | SDMMC2 supply voltage (supply voltage for PG[12:9] and PD6 pins) | It can be different from VDD | - | 1.7 | - | 3.6 |  |
| $\mathrm{V}_{\text {DDDSI }}$ | DSI system operating | - |  | 1.7 | - | 3.6 |  |

Table 18. General operating conditions (continued)

| Symbol | Parameter | Conditions ${ }^{(1)}$ | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{12}$ | Regulator ON: 1.2 V internal voltage on $\mathrm{V}_{\text {CAP_1 }} / \mathrm{V}_{\text {CAP_2 }}$ pins | Power Scale 3 ((VOS[1:0] bits in PWR_CR register = 0x01), 144 MHz HCLK max frequency | 1.08 | 1.14 | 1.20 | V |
|  |  | Power Scale 2 ((VOS[1:0] bits in PWR_CR register = 0x10), 168 MHz HCLK max frequency with over-drive OFF or 180 MHz with over-drive ON | 1.20 | 1.26 | 1.32 |  |
|  |  | Power Scale 1 ((VOS[1:0] bits in PWR_CR register = 0x11), 180 MHz HCLK max frequency with over-drive OFF or 216 MHz with over-drive ON | 1.26 | 1.32 | 1.40 |  |
|  | Regulator OFF: 1.2 V external voltage must be supplied from external regulator on $\mathrm{V}_{\text {CAP_1 }} / \mathrm{V}_{\text {CAP_2 }}$ pins $^{(7)}$ | Max frequency 144 MHz | 1.10 | 1.14 | 1.20 |  |
|  |  | Max frequency 168 MHz | 1.20 | 1.26 | 1.32 |  |
|  |  | Max frequency 180 MHz | 1.26 | 1.32 | 1.38 |  |
| $\mathrm{V}_{\text {IN }}$ | Input voltage on RST and FT pins ${ }^{(8)}$ | $2 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$ | -0.3 | - | 5.5 |  |
|  |  | $\mathrm{V}_{\mathrm{DD}} \leq 2 \mathrm{~V}$ | -0.3 | - | 5.2 |  |
|  | Input voltage on TTa pins | - | -0.3 | - | $\begin{gathered} \mathrm{V}_{\mathrm{DDA}}{ }^{+} \\ 0.3 \end{gathered}$ |  |
|  | Input voltage on BOOT pin | - | 0 | - | 9 |  |
| $P_{D}$ | Power dissipation at $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ for suffix 6 or $T_{A}=105^{\circ} \mathrm{C}$ for suffix $7^{(9)}$ | LQFP100 | - | - | 465 | mW |
|  |  | WLCSP180 | - | - | 641 |  |
|  |  | LQFP144 | - | - | 500 |  |
|  |  | LQFP176 | - | - | 526 |  |
|  |  | UFBGA176 | - | - | 513 |  |
|  |  | LQFP208 | - | - | 1053 |  |
|  |  | TFBGA216 | - | - | 690 |  |
|  |  | TFBGA100 | - | - | 552 |  |
| TA | Ambient temperature for 6 suffix version | Maximum power dissipation | -40 | - | 85 | C |
|  |  | Low power dissipation ${ }^{(10)}$ | -40 | - | 105 |  |
|  | Ambient temperature for 7 suffix version | Maximum power dissipation | -40 | - | 105 | ${ }^{\circ} \mathrm{C}$ |
|  |  | Low power dissipation ${ }^{(10)}$ | -40 | - | 125 |  |
| TJ | Junction temperature range | 6 suffix version | -40 | - | 105 | ${ }^{\circ} \mathrm{C}$ |
|  |  | 7 suffix version | -40 | - | 125 |  |

1. The over-drive mode is not supported at the voltage ranges from 1.7 to 2.1 V .
2. 216 MHz maximum frequency for 6 suffix version ( 200 MHz maximum frequency for 7 suffix version).
3. $V_{D D} / V_{D D A}$ minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to Section 2.18.2: Internal reset OFF).
4. When the ADC is used, refer to Table 72: ADC characteristics.
5. If $\mathrm{V}_{\mathrm{REF}+}$ pin is present, it must respect the following condition: $\mathrm{V}_{\mathrm{DDA}}-\mathrm{V}_{\mathrm{REF}}<1.2 \mathrm{~V}$.
6. It is recommended to power $\mathrm{V}_{\mathrm{DD}}$ and $\mathrm{V}_{\mathrm{DDA}}$ from the same source. A maximum difference of 300 mV between $\mathrm{V}_{\mathrm{DD}}$ and $V_{\text {DDA }}$ can be tolerated during power-up and power-down operation.
7. The over-drive mode is not supported when the internal regulator is OFF.
8. To sustain a voltage higher than VDD+0.3, the internal Pull-up and Pull-Down resistors must be disabled
9. If $T_{A}$ is lower, higher $P_{D}$ values are allowed as long as $T_{J}$ does not exceed $T_{J m a x}$.
10. In low power dissipation state, $T_{A}$ can be extended to this range as long as $T_{J}$ does not exceed $T_{J m a x}$.

Table 19. Limitations depending on the operating power supply range

| Operating power supply range | ADC operation | Maximum Flash memory access frequency with no wait states ( $\mathrm{f}_{\text {Flashmax }}$ ) | Maximum HCLK frequency vs Flash memory wait states (1)(2) | 1/O operation | Possible Flash memory operations |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\begin{gathered} \mathrm{V}_{\mathrm{DD}}=1.7 \text { to } \\ 2.1 \mathrm{~V}^{(3)} \end{gathered}$ | Conversion time up to 1.2 Msps | 20 MHz | 180 MHz with 8 wait states and over-drive OFF | No I/O compensation | 8-bit erase and program operations only |
| $\begin{gathered} \mathrm{V}_{\mathrm{DD}}=2.1 \text { to } \\ 2.4 \mathrm{~V} \end{gathered}$ | Conversion time up to 1.2 Msps | 22 MHz | 216 MHz with 9 wait states and over-drive ON | No I/O compensation | 16-bit erase and program operations |
| $\begin{gathered} \mathrm{V}_{\mathrm{DD}}=2.4 \text { to } \\ 2.7 \mathrm{~V} \end{gathered}$ | Conversion time up to 2.4 Msps | 24 MHz | 216 MHz with 8 wait states and over-drive ON | I/O compensation works | 16-bit erase and program operations |
| $\begin{gathered} \mathrm{V}_{\mathrm{DD}}=2.7 \text { to } \\ 3.6 \mathrm{~V}^{(4)} \end{gathered}$ | Conversion time up to 2.4 Msps | 30 MHz | 216 MHz with 6 wait states and over-drive ON | I/O compensation works | 32-bit erase and program operations |

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator on ITCM interface and L1-cache on AXI interface, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator or L1-cache allows to achieve a performance equivalent to 0 -wait state program execution.
3. $V_{D D} / V_{D D A}$ minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to Section 2.18.2: Internal reset OFF).
4. The voltage range for USB full speed PHYs can drop down to 2.7 V . However the electrical characteristics of D- and D+ pins will be degraded between 2.7 and 3 V .

### 5.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor $\mathrm{C}_{\mathrm{EXT}}$ to the VCAP1/VCAP2 pins. $\mathrm{C}_{\mathrm{EXT}}$ is specified in Table 20.

Figure 28. External capacitor $\mathrm{C}_{\mathrm{EXT}}$


1. Legend: ESR is the equivalent series resistance.

Table 20. VCAP1/VCAP2 operating conditions ${ }^{(1)}$

| Symbol | Parameter | Conditions |
| :---: | :---: | :---: |
| CEXT | Capacitance of external capacitor | $2.2 \mu \mathrm{~F}$ |
| ESR | ESR of external capacitor | $<2 \Omega$ |

1. When bypassing the voltage regulator, the two $2.2 \mu \mathrm{~F} \mathrm{~V}_{\mathrm{CAP}}$ capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

### 5.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for $T_{A}$.
Table 21. Operating conditions at power-up / power-down (regulator ON)

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{VDD}}$ | $\mathrm{V}_{\mathrm{DD}}$ rise time rate | 20 | $\infty$ | $\mu \mathrm{~s} / \mathrm{V}$ |
|  | $\mathrm{V}_{\mathrm{DD}}$ fall time rate | 20 | $\infty$ |  |

### 5.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for $\mathrm{T}_{\mathrm{A}}$.
Table 22. Operating conditions at power-up / power-down (regulator OFF) ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $t_{V D D}$ | $V_{D D}$ rise time rate | Power-up | 20 | $\infty$ | $\mu \mathrm{s} / \mathrm{V}$ |
|  | $V_{D D}$ fall time rate | Power-down | 20 | $\infty$ |  |
| $t_{\text {VCAP }}$ | $\mathrm{V}_{\text {CAP_1 }}$ and $\mathrm{V}_{\text {CAP_2 }}$ rise time rate | Power-up | 20 | $\infty$ |  |
|  | $\mathrm{V}_{\text {CAP_1 }}$ and $\mathrm{V}_{\text {CAP_2 }}$ fall time rate | Power-down | 20 | $\infty$ |  |

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when $\mathrm{V}_{\mathrm{DD}}$ reach below 1.08 V .

### 5.3.5 Reset and power control block characteristics

The parameters given in Table 23 are derived from tests performed under ambient temperature and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18.

Table 23. Reset and power control block characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{PVD}}$ | Programmable voltage detector level selection | PLS[2:0]=000 (rising edge) | 2.09 | 2.14 | 2.19 | V |
|  |  | PLS[2:0]=000 (falling edge) | 1.98 | 2.04 | 2.08 | V |
|  |  | PLS[2:0]=001 (rising edge) | 2.23 | 2.30 | 2.37 | V |
|  |  | PLS[2:0]=001 (falling edge) | 2.13 | 2.19 | 2.25 | V |
|  |  | PLS[2:0]=010 (rising edge) | 2.39 | 2.45 | 2.51 | V |
|  |  | PLS[2:0]=010 (falling edge) | 2.29 | 2.35 | 2.39 | V |
|  |  | PLS[2:0]=011 (rising edge) | 2.54 | 2.60 | 2.65 | V |
|  |  | PLS[2:0]=011 (falling edge) | 2.44 | 2.51 | 2.56 | V |
|  |  | PLS[2:0]=100 (rising edge) | 2.70 | 2.76 | 2.82 | V |
|  |  | PLS[2:0]=100 (falling edge) | 2.59 | 2.66 | 2.71 | V |
|  |  | PLS[2:0]=101 (rising edge) | 2.86 | 2.93 | 2.99 | V |
|  |  | PLS[2:0]=101 (falling edge) | 2.65 | 2.84 | 2.92 | V |
|  |  | PLS[2:0]=110 (rising edge) | 2.96 | 3.03 | 3.10 | V |
|  |  | PLS[2:0]=110 (falling edge) | 2.85 | 2.93 | 2.99 | V |
|  |  | PLS[2:0]=111 (rising edge) | 3.07 | 3.14 | 3.21 | V |
|  |  | PLS[2:0]=111 (falling edge) | 2.95 | 3.03 | 3.09 | V |
| $\mathrm{V}_{\text {PVDhyst }}{ }^{(1)}$ | PVD hysteresis | - | - | 100 | - | mV |
| $\mathrm{V}_{\text {POR/PDR }}$ | Power-on/power-down reset threshold | Falling edge | 1.60 | 1.68 | 1.76 | V |
|  |  | Rising edge | 1.64 | 1.72 | 1.80 | V |
| $\mathrm{V}_{\text {PDRhyst }}{ }^{(1)}$ | PDR hysteresis | - | - | 40 | - | mV |
| $V_{\text {BOR1 }}$ | Brownout level 1 threshold | Falling edge | 2.13 | 2.19 | 2.24 | V |
|  |  | Rising edge | 2.23 | 2.29 | 2.33 | V |
| $\mathrm{V}_{\mathrm{BOR} 2}$ | Brownout level 2 threshold | Falling edge | 2.44 | 2.50 | 2.56 | V |
|  |  | Rising edge | 2.53 | 2.59 | 2.63 | V |
| $V_{\text {BOR3 }}$ | Brownout level 3 threshold | Falling edge | 2.75 | 2.83 | 2.88 | V |
|  |  | Rising edge | 2.85 | 2.92 | 2.97 | V |
| $\mathrm{V}_{\text {BORhyst }}{ }^{(1)}$ | BOR hysteresis | - - | - | 100 | - | mV |
| $\mathrm{T}_{\mathrm{RSTTE}_{(1)(2)} \mathrm{MPO}}$ | POR reset temporization | - | 0.5 | 1.5 | 3.0 | ms |
| $\mathrm{I}_{\text {RUSH }}{ }^{(1)}$ | InRush current on voltage regulator poweron (POR or wakeup from Standby) | - | - | 160 | 250 | mA |
| $\mathrm{E}_{\text {RUSH }}{ }^{(1)}$ | InRush energy on voltage regulator poweron (POR or wakeup from Standby) | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=1.7 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=105^{\circ} \mathrm{C}, \\ & \mathrm{I}_{\mathrm{RUSH}}=171 \mathrm{~mA} \text { for } 31 \mu \mathrm{~s} \end{aligned}$ | - | - | 5.4 | $\mu \mathrm{C}$ |

1. Guaranteed by design.
2. The reset temporization is measured from the power-on (POR reset or wakeup from $\mathrm{V}_{\mathrm{BAT}}$ ) to the instant when first instruction is read by the user application code.

### 5.3.6 Over-drive switching characteristics

When the over-drive mode switches from enabled to disabled or disabled to enabled, the system clock is stalled during the internal voltage set-up.

The over-drive switching characteristics are given in Table 24. They are subject to general operating conditions for $T_{A}$.

Table 24. Over-drive switching characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Tod_swen | Over_drive switch enable time | HSI | - | 45 | - | $\mu \mathrm{s}$ |
|  |  | HSE max for 4 MHz and $\min$ for 26 MHz | 45 | - | 100 |  |
|  |  | $\begin{gathered} \text { External HSE } \\ 50 \mathrm{MHz} \end{gathered}$ | - | 40 | - |  |
| Tod_swdis | Over_drive switch disable time | HSI | - | 20 | - |  |
|  |  | HSE max for 4 MHz and min for 26 MHz . | 20 | - | 80 |  |
|  |  | $\begin{gathered} \text { External HSE } \\ 50 \mathrm{MHz} \end{gathered}$ | - | 15 | - |  |

1. Guaranteed by design.

### 5.3.7 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in Figure 27: Current consumption measurement scheme.
All the run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

## Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at $\mathrm{V}_{\mathrm{DD}}$ or $\mathrm{V}_{\mathrm{SS}}$ (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted both to $f_{H C L K}$ frequency and $V_{D D}$ range (see Table 19: Limitations depending on the operating power supply range).
- When the regulator is ON, the voltage scaling and over-drive mode are adjusted to $\mathrm{f}_{\text {HCLK }}$ frequency as follows:
- $\quad$ Scale 3 for $f_{\text {HCLK }} \leq 144 \mathrm{MHz}$
- $\quad$ Scale 2 for $144 \mathrm{MHz}<\mathrm{f}_{\text {HCLK }} \leq 168 \mathrm{MHz}$
- $\quad$ Scale 1 for $168 \mathrm{MHz}<\mathrm{f}_{\text {HCLK }} \leq 216 \mathrm{MHz}$. The over-drive is only ON at 216 MHz .
- When the regulator is OFF, the V12 is provided externally as described in Table 18: General operating conditions:
- $\quad$ The system clock is HCLK, $\mathrm{f}_{\mathrm{PCLK} 1}=\mathrm{f}_{\mathrm{HCLK}} / 4$, and $\mathrm{f}_{\mathrm{PCLK} 2}=\mathrm{f}_{\mathrm{HCLK}} / 2$.
- External clock frequency is 25 MHz and PLL is ON when $\mathrm{f}_{\text {HCLK }}$ is higher than 25 MHz .
- The typical current consumption values are obtained for $1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$ voltage range and for $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise specified.
- The maximum values are obtained for $1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$ voltage range and a maximum ambient temperature $\left(\mathrm{T}_{\mathrm{A}}\right)$ unless otherwise specified.
- For the voltage range $1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$, the maximum frequency is 180 MHz .

Table 25. Typical and maximum current consumption in Run mode, code with data processing running from ITCM RAM, regulator ON

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}(\mathrm{MHz})$ | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=105^{\circ} \mathrm{C}$ |  |
| $\mathrm{I}_{\mathrm{DD}}$ | Supply current in RUN mode | All peripherals enabled ${ }^{(2)(3)}$ | 216 | 193 | $221{ }^{(4)}$ | $258{ }^{(4)}$ | - | mA |
|  |  |  | 200 | 179 | 207 | 244 | 279 |  |
|  |  |  | 180 | 159 | $176{ }^{(4)}$ | $210^{(4)}$ | $238{ }^{(4)}$ |  |
|  |  |  | 168 | 142 | 156 | 187 | 211 |  |
|  |  |  | 144 | 122 | 135 | 167 | 190 |  |
|  |  |  | 60 | 49 | 55 | 81 | 103 |  |
|  |  |  | 25 | 23 | 28 | 54 | 76 |  |
|  |  | All peripherals disabled ${ }^{(3)}$ | 216 | 95 | $107{ }^{(4)}$ | $153{ }^{(4)}$ | - |  |
|  |  |  | 200 | 88 | 100 | 146 | 180 |  |
|  |  |  | 180 | 78 | $88^{(4)}$ | $122^{(4)}$ | $147{ }^{(4)}$ |  |
|  |  |  | 168 | 70 | 78 | 109 | 133 |  |
|  |  |  | 144 | 60 | 68 | 99 | 123 |  |
|  |  |  | 60 | 24 | 29 | 55 | 76 |  |
|  |  |  | 25 | 12 | 16 | 42 | 63 |  |

[^1]2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.
4. Guaranteed by test in production.

Table 26. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Single bank mode, ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator ON

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}(\mathrm{MHz})$ | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=10{ }^{\circ} \mathrm{C}$ |  |
| $\mathrm{I}_{\mathrm{DD}}$ | Supply current in RUN mode | All peripherals enabled ${ }^{(2)(3)}$ | 216 | 190 | 219 | 255 | - | mA |
|  |  |  | 200 | 177 | 205 | 241 | 268 |  |
|  |  |  | 180 | 157 | 173 | 208 | 228 |  |
|  |  |  | 168 | 139 | 153 | 185 | 204 |  |
|  |  |  | 144 | 107 | 117 | 144 | 161 |  |
|  |  |  | 60 | 48 | 54 | 81 | 98 |  |
|  |  |  | 25 | 23 | 28 | 54 | 71 |  |
|  |  |  | 216 | 92 | 104 | 150 | - |  |
|  |  |  | 200 | 86 | 97 | 143 | 170 |  |
|  |  |  | 180 | 76 | 85 | 119 | 140 |  |
|  |  | All peripherals disabled ${ }^{(3)}$ | 168 | 67 | 75 | 107 | 126 |  |
|  |  |  | 144 | 52 | 58 | 84 | 101 |  |
|  |  |  | 60 | 23 | 28 | 54 | 71 |  |
|  |  |  | 25 | 11 | 15 | 42 | 56 |  |

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 27. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Dual bank mode, ART ON except prefetch / L1-cache ON), regulator ON

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}(\mathrm{MHz})$ | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=105^{\circ} \mathrm{C}$ |  |
| $\mathrm{I}_{\mathrm{DD}}$ | Supply current in RUN mode | All peripherals enabled ${ }^{(2)(3)}$ | 216 | 190 | 219 | 255 | - | mA |
|  |  |  | 200 | 177 | 204 | 242 | 268 |  |
|  |  |  | 180 | 157 | 173 | 208 | 228 |  |
|  |  |  | 168 | 139 | 153 | 185 | 204 |  |
|  |  |  | 144 | 107 | 117 | 144 | 161 |  |
|  |  |  | 60 | 48 | 54 | 81 | 98 |  |
|  |  |  | 25 | 23 | 28 | 54 | 71 |  |
|  |  | All peripherals disabled ${ }^{(3)}$ | 216 | 92 | 104 | 150 | - |  |
|  |  |  | 200 | 86 | 97 | 143 | 170 |  |
|  |  |  | 180 | 76 | 85 | 119 | 140 |  |
|  |  |  | 168 | 67 | 75 | 107 | 126 |  |
|  |  |  | 144 | 52 | 58 | 84 | 101 |  |
|  |  |  | 60 | 23 | 28 | 54 | 71 |  |
|  |  |  | 25 | 11 | 15 | 42 | 59 |  |

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 28. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Single bank mode) or SRAM on AXI (L1-cache disabled),
regulator ON

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}(\mathrm{MHz})$ | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | TA $=25^{\circ} \mathrm{C}$ | TA $=85{ }^{\circ} \mathrm{C}$ | TA $=10{ }^{\circ} \mathrm{C}$ |  |
| $I_{\text {DD }}$ | Supply current in RUN mode | All peripherals enabled ${ }^{(2)(3)}$ | 216 | 190 | 209 | 255 | - | mA |
|  |  |  | 200 | 177 | 194 | 241 | 268 |  |
|  |  |  | 180 | 160 | 175 | 211 | 232 |  |
|  |  |  | 168 | 144 | 156 | 189 | 209 |  |
|  |  |  | 144 | 115 | 125 | 152 | 170 |  |
|  |  |  | 60 | 56 | 62 | 89 | 107 |  |
|  |  |  | 25 | 27 | 32 | 59 | 79 |  |
|  |  | All peripherals disabled ${ }^{(3)}$ | 216 | 92 | 103 | 150 | - |  |
|  |  |  | 200 | 86 | 96 | 243 | 171 |  |
|  |  |  | 180 | 79 | 87 | 123 | 144 |  |
|  |  |  | 168 | 71 | 79 | 111 | 131 |  |
|  |  |  | 144 | 60 | 65 | 92 | 110 |  |
|  |  |  | 60 | 32 | 36 | 63 | 80 |  |
|  |  |  | 25 | 16 | 20 | 46 | 64 |  |

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 29. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Dual bank mode), regulator ON

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}(\mathrm{MHz})$ | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | TA $=25^{\circ} \mathrm{C}$ | TA $=85{ }^{\circ} \mathrm{C}$ | TA $=105^{\circ} \mathrm{C}$ |  |
| $I_{\text {DD }}$ | Supply current in RUN mode | All peripherals enabled ${ }^{(2)(3)}$ | 216 | 176 | 194 | 240 | - | mA |
|  |  |  | 200 | 164 | 181 | 227 | 255 |  |
|  |  |  | 180 | 149 | 163 | 198 | 220 |  |
|  |  |  | 168 | 133 | 145 | 178 | 198 |  |
|  |  |  | 144 | 106 | 116 | 143 | 161 |  |
|  |  |  | 60 | 54 | 60 | 87 | 105 |  |
|  |  |  | 25 | 27 | 31 | 58 | 76 |  |
|  |  | All peripherals disabled ${ }^{(3)}$ | 216 | 77 | 88 | 135 | - |  |
|  |  |  | 200 | 72 | 82 | 129 | 157 |  |
|  |  |  | 180 | 67 | 75 | 110 | 131 |  |
|  |  |  | 168 | 60 | 67 | 99 | 120 |  |
|  |  |  | 144 | 50 | 56 | 83 | 101 |  |
|  |  |  | 60 | 29 | 34 | 60 | 78 |  |
|  |  |  | 25 | 15 | 19 | 45 | 63 |  |

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 30. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Single bank mode) on ITCM interface (ART disabled), regulator ON

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}(\mathrm{MHz})$ | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | $\mathrm{TA}=25^{\circ} \mathrm{C}$ | $\mathrm{TA}=85{ }^{\circ} \mathrm{C}$ | TA $=10{ }^{\circ} \mathrm{C}$ |  |
| $I_{\text {D }}$ | Supply current in RUN mode | All peripherals enabled ${ }^{(2)(3)}$ | 216 | 215 | 242 | 281 | - | mA |
|  |  |  | 200 | 200 | 218 | 265 | 293 |  |
|  |  |  | 180 | 185 | 200 | 237 | 258 |  |
|  |  |  | 168 | 166 | 179 | 213 | 233 |  |
|  |  |  | 144 | 134 | 144 | 172 | 190 |  |
|  |  |  | 60 | 61 | 68 | 95 | 112 |  |
|  |  |  | 25 | 29 | 34 | 61 | 78 |  |
|  |  | All peripherals disabled ${ }^{(3)}$ | 216 | 118 | 129 | 177 | - |  |
|  |  |  | 200 | 110 | 120 | 168 | 196 |  |
|  |  |  | 180 | 104 | 113 | 149 | 170 |  |
|  |  |  | 168 | 94 | 102 | 135 | 155 |  |
|  |  |  | 144 | 79 | 85 | 113 | 130 |  |
|  |  |  | 60 | 37 | 42 | 69 | 86 |  |
|  |  |  | 25 | 18 | 22 | 48 | 66 |  |

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 31. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Dual bank mode) on ITCM interface (ART disabled),
regulator ON

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}$ (MHz) | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | TA $=25^{\circ} \mathrm{C}$ | TA $=85{ }^{\circ} \mathrm{C}$ | TA $=10{ }^{\circ} \mathrm{C}$ |  |
| $I_{\text {D }}$ | Supply current in RUN mode | All peripherals enabled ${ }^{(2)(3)}$ | 216 | 191 | 218 | 255 | - | mA |
|  |  |  | 200 | 178 | 195 | 241 | 269 |  |
|  |  |  | 180 | 164 | 179 | 214 | 236 |  |
|  |  |  | 168 | 147 | 160 | 192 | 212 |  |
|  |  |  | 144 | 121 | 130 | 157 | 175 |  |
|  |  |  | 60 | 60 | 66 | 93 | 111 |  |
|  |  |  | 25 | 28 | 33 | 59 | 77 |  |
|  |  | All peripherals disabled ${ }^{(3)}$ | 216 | 93 | 104 | 150 | - |  |
|  |  |  | 200 | 87 | 97 | 144 | 171 |  |
|  |  |  | 180 | 83 | 92 | 126 | 148 |  |
|  |  |  | 168 | 75 | 82 | 114 | 134 |  |
|  |  |  | 144 | 65 | 71 | 97 | 115 |  |
|  |  |  | 60 | 35 | 40 | 66 | 84 |  |
|  |  |  | 25 | 16 | 20 | 47 | 64 |  |

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 32. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Single bank mode, ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator OFF

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}$ (MHz) | Typ |  | Max ${ }^{(1)}$ |  |  |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  |  | $\mathrm{TA}=25{ }^{\circ} \mathrm{C}$ |  | $\mathrm{TA}=85{ }^{\circ} \mathrm{C}$ |  | $\mathrm{TA}=10{ }^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  | IDD12 | IDD | IDD12 | IDD | IDD12 | IDD | IDD12 | IDD |  |
| $\begin{array}{\|l} \mid \text { IDD12/ } \\ \text { IDD } \end{array}$ | Supply current in RUN mode from V12 and VDD supply | All <br> Peripherals <br> Enabled ${ }^{(2)(3)}$ | 180 | 152 | 1 | 167 | 2 | 200 | 2 | 220 | 2 | mA |
|  |  |  | 168 | 136 | 1 | 148 | 2 | 179 | 2 | 198 | 2 |  |
|  |  |  | 144 | 105 | 1 | 115 | 2 | 141 | 2 | 158 | 2 |  |
|  |  |  | 60 | 47 | 1 | 53 | 2 | 79 | 2 | 96 | 2 |  |
|  |  |  | 25 | 22 | 1 | 27 | 2 | 53 | 2 | 70 | 2 |  |
|  |  | All <br> Peripherals Disabled ${ }^{(3)}$ | 180 | 74 | 1 | 83 | 2 | 116 | 2 | 136 | 2 |  |
|  |  |  | 168 | 65 | 1 | 73 | 2 | 104 | 2 | 123 | 2 |  |
|  |  |  | 144 | 50 | 1 | 57 | 2 | 83 | 2 | 100 | 2 |  |
|  |  |  | 60 | 22 | 1 | 27 | 2 | 53 | 2 | 70 | 2 |  |
|  |  |  | 25 | 10 | 1 | 14 | 2 | 41 | 2 | 58 | 2 |  |

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 33. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Dual bank mode, ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator OFF

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}$ (MHz) | Typ |  | Max ${ }^{(1)}$ |  |  |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  |  | $\mathrm{TA}=25^{\circ} \mathrm{C}$ |  | $\mathrm{TA}=85{ }^{\circ} \mathrm{C}$ |  | $\mathrm{TA}=10{ }^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  | IDD12 | IDD | IDD12 | IDD | IDD12 | IDD | IDD12 | IDD |  |
| $\begin{array}{\|l} \text { IDD12/ } \\ \text { IDD } \end{array}$ | Supply current in RUN mode from V12 and VDD supply | All <br> Peripherals Enabled ${ }^{(2)(3)}$ | 180 | 152 | 1 | 167 | 2 | 200 | 2 | 220 | 2 | mA |
|  |  |  | 168 | 136 | 1 | 148 | 2 | 179 | 2 | 198 | 2 |  |
|  |  |  | 144 | 105 | 1 | 115 | 2 | 141 | 2 | 158 | 2 |  |
|  |  |  | 60 | 47 | 1 | 53 | 2 | 79 | 2 | 96 | 2 |  |
|  |  |  | 25 | 22 | 1 | 27 | 2 | 53 | 2 | 70 | 2 |  |
|  |  | All <br> Peripherals Disabled ${ }^{(3)}$ | 180 | 74 | 1 | 82 | 2 | 114 | 2 | 137 | 2 |  |
|  |  |  | 168 | 65 | 1 | 73 | 2 | 104 | 2 | 123 | 2 |  |
|  |  |  | 144 | 50 | 1 | 57 | 2 | 83 | 2 | 100 | 2 |  |
|  |  |  | 60 | 22 | 1 | 27 | 2 | 53 | 2 | 70 | 2 |  |
|  |  |  | 25 | 10 | 1 | 14 | 2 | 41 | 2 | 58 | 2 |  |

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 34. Typical and maximum current consumption in Sleep mode, regulator ON

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}(\mathrm{MHz})$ | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=105^{\circ} \mathrm{C}$ |  |
| $I_{\text {D }}$ | Supply current in Sleep mode | All peripherals enabled ${ }^{(2)}$ | 216 | 128 | $144{ }^{(3)}$ | $190^{(3)}$ | - | mA |
|  |  |  | 200 | 119 | 134 | 180 | 214 |  |
|  |  |  | 180 | 105 | $118^{(3)}$ | $153{ }^{(3)}$ | $178{ }^{(3)}$ |  |
|  |  |  | 168 | 93 | 105 | 136 | 156 |  |
|  |  |  | 144 | 72 | 80 | 107 | 124 |  |
|  |  |  | 60 | 33 | 39 | 65 | 82 |  |
|  |  |  | 25 | 17 | 21 | 47 | 65 |  |
|  |  | All peripherals disabled | 216 | 18 | $25^{(3)}$ | $71^{(3)}$ | - |  |
|  |  |  | 200 | 17 | 24 | 70 | 112 |  |
|  |  |  | 180 | 14 | $20^{(3)}$ | $54^{(3)}$ | $75^{(3)}$ |  |
|  |  |  | 168 | 13 | 18 | 49 | 69 |  |
|  |  |  | 144 | 10 | 14 | 40 | 58 |  |
|  |  |  | 60 | 6 | 10 | 36 | 53 |  |
|  |  |  | 25 | 4 | 8 | 34 | 51 |  |

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. Guaranteed by test in production.

Table 35. Typical and maximum current consumption in Sleep mode, regulator OFF

| Symbol | Parameter | Conditions | $\mathrm{f}_{\mathrm{HCLK}}$ (MHz) | Typ |  | Max ${ }^{(1)}$ |  |  |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  |  | $\mathrm{TA}=25^{\circ} \mathrm{C}$ |  | TA= $85{ }^{\circ} \mathrm{C}$ |  | $\mathrm{TA}=105^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  | IDD12 | IDD | IDD12 | IDD | IDD12 | IDD | IDD12 | IDD |  |
| $\begin{array}{\|l} \mid \text { IDD12/ } \\ \text { IDD } \end{array}$ | Supply current in RUN mode from V12 and $V_{D D}$ supply | All <br> Peripherals Enabled ${ }^{(2)}$ | 180 | 102 | 1 | 114 | 2 | 148 | 2 | 168 | 2 | mA |
|  |  |  | 168 | 91 | 1 | 101 | 2 | 132 | 2 | 152 | 2 |  |
|  |  |  | 144 | 71 | 1 | 78 | 2 | 105 | 2 | 122 | 2 |  |
|  |  |  | 60 | 32 | 1 | 37 | 2 | 64 | 2 | 81 | 2 |  |
|  |  |  | 25 | 16 | 1 | 20 | 2 | 46 | 2 | 64 | 2 |  |
|  |  | All Peripherals Disabled | 180 | 13 | 1 | 18 | 2 | 53 | 2 | 73 | 2 |  |
|  |  |  | 168 | 12 | 1 | 16 | 2 | 47 | 2 | 67 | 2 |  |
|  |  |  | 144 | 9 | 1 | 13 | 2 | 39 | 2 | 56 | 2 |  |
|  |  |  | 60 | 5 | 1 | 9 | 2 | 35 | 2 | 52 | 2 |  |
|  |  |  | 25 | 3 | 1 | 7 | 2 | 33 | 2 | 50 | 2 |  |

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.

Table 36. Typical and maximum current consumptions in Stop mode

| Symbol | Parameter | Conditions | Typ | Max ${ }^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $\mathrm{V}_{\mathrm{DD}}=3.6 \mathrm{~V}$ |  |  |  |
|  |  |  | $\begin{aligned} & \mathrm{T}_{\mathrm{A}}= \\ & 25^{\circ} \mathrm{C} \end{aligned}$ | $\begin{array}{r} \mathrm{T}_{\mathrm{A}}= \\ 25^{\circ} \mathrm{C} \end{array}$ | $\begin{array}{r} \mathrm{T}_{\mathrm{A}}= \\ 85^{\circ} \mathrm{C} \end{array}$ | $\begin{gathered} \mathrm{T}_{\mathrm{A}}= \\ 105^{\circ} \mathrm{C} \end{gathered}$ |  |
| IDD_STOP_NM (normal mode) | Supply current in Stop mode, main regulator in Run mode | Flash memory in Stop mode, all oscillators OFF, no IWDG | 0.55 | 3 | 18 | 27 | mA |
|  |  | Flash memory in Deep power down mode, all oscillators OFF | 0.5 | 3 | 18 | 27 |  |
|  | Supply current in Stop mode, main regulator in Low-power mode | Flash memory in Stop mode, all oscillators OFF, no IWDG | 0.42 | 2.5 | 15 | 24 |  |
|  |  | Flash memory in Deep power down mode, all oscillators OFF, no IWDG | 0.37 | 2.5 | 15 | 24 |  |
| IDD_STOP_UDM (under-drive mode) | Supply current in Stop mode, main regulator in Low voltage and underdrive modes | Regulator in Run mode, Flash memory in Deep power down mode, all oscillators OFF, no IWDG | 0.18 | 1.2 | 6 | 10 |  |
|  |  | Regulator in Low-power mode, Flash memory in Deep power down mode, all oscillators OFF, no IWDG | 0.13 | 1.1 | 6 | 10 |  |

[^2]Table 37. Typical and maximum current consumptions in Standby mode

| Symbol | Parameter | Conditions | Typ ${ }^{(1)}$ |  |  | Max ${ }^{(2)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |  | $\begin{gathered} \mathrm{T}_{\mathrm{A}}= \\ 25^{\circ} \mathrm{C} \end{gathered}$ | $\begin{aligned} & \mathrm{T}_{\mathrm{A}}= \\ & 85^{\circ} \mathrm{C} \end{aligned}$ | $\begin{gathered} \mathrm{T}_{\mathrm{A}}= \\ 105^{\circ} \mathrm{C} \end{gathered}$ |  |
|  |  |  | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}= \\ & 1.7 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & \mathrm{v}_{\mathrm{DD}}= \\ & 2.4 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}= \\ & 3.3 \mathrm{~V} \end{aligned}$ | $\mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}$ |  |  |  |
| $\mathrm{I}_{\text {DD_STBY }}$ | Supply current in Standby mode | Backup SRAM OFF, RTC and LSE OFF | 1.1 | 1.9 | 2.4 | $5^{(3)}$ | $18^{(3)}$ | $38^{(3)}$ | $\mu \mathrm{A}$ |
|  |  | Backup SRAM ON, RTC and LSE OFF | 1.9 | 2.7 | 3.2 | $6^{(3)}$ | $23^{(3)}$ | $48^{(3)}$ |  |
|  |  | Backup SRAM OFF, RTC ON and LSE in low drive mode | 1.7 | 2.7 | 3.5 | 7 | 26 | 55 |  |
|  |  | Backup SRAM OFF, RTC ON and LSE in medium low drive mode | 1.7 | 2.7 | 3.5 | 7 | 26 | 56 |  |
|  |  | Backup SRAM OFF, RTC ON and LSE in medium high drive mode | 1.8 | 2.8 | 3.6 | 8 | 28 | 57 |  |
|  |  | Backup SRAM OFF, RTC ON and LSE in high drive mode | 1.9 | 2.9 | 3.7 | 8 | 28 | 59 |  |
|  |  | Backup SRAM ON, RTC ON and LSE in low drive mode | 2.4 | 3.4 | 4.3 | 8 | 31 | 65 |  |
|  |  | Backup SRAM ON, RTC ON and LSE in Medium low drive mode | 2.4 | 3.5 | 4.3 | 8 | 31 | 65 |  |
|  |  | Backup SRAM ON, RTC ON and LSE in Medium high drive mode | 2.6 | 3.7 | 4.5 | 8 | 33 | 68 |  |
|  |  | Backup SRAM ON, RTC ON and LSE in High drive mode | 2.6 | 3.7 | 4.5 | 9 | 33 | 68 |  |

[^3]Table 38. Typical and maximum current consumptions in $\mathrm{V}_{\mathrm{BAT}}$ mode

| Symbol | Parameter | Conditions ${ }^{(1)}$ | $\begin{gathered} \text { Typ } \\ \hline \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \end{gathered}$ |  |  | Max ${ }^{(2)}$ |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  |  | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=105^{\circ} \mathrm{C}$ |  |
|  |  |  | $\begin{gathered} \mathrm{V}_{\mathrm{BAT}}= \\ 1.7 \mathrm{~V} \end{gathered}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{BAT}}= \\ & 2.4 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{BAT}}= \\ & 3.3 \mathrm{~V} \end{aligned}$ | $\mathrm{V}_{\mathrm{BAT}}=3.6 \mathrm{~V}$ |  |  |
| Idd_VBAT | Supply current in $V_{\text {BAT }}$ mode | Backup SRAM OFF, RTC and LSE OFF | 0.03 | 0.04 | 0.04 | 0.2 | 0.4 | $\mu \mathrm{A}$ |
|  |  | Backup SRAM ON, RTC and LSE OFF | 0.77 | 0.78 | 0.83 | 3.2 | 7.4 |  |
|  |  | Backup SRAM OFF, RTC ON and LSE in low drive mode | 0.62 | 0.8 | 1.13 | 4.4 | 10.2 |  |
|  |  | Backup SRAM OFF, RTC ON and LSE in medium low drive mode | 0.65 | 0.83 | 1.17 | 4.6 | 10.6 |  |
|  |  | Backup SRAM OFF, RTC ON and LSE in medium high drive mode | 0.75 | 0.94 | 1.28 | 5.0 | 11.4 |  |
|  |  | Backup SRAM OFF, RTC ON and LSE in high drive mode | 0.9 | 1.08 | 1.43 | 5.5 | 12.8 |  |
|  |  | Backup SRAM ON, RTC ON and LSE in low drive mode | 1.35 | 1.54 | 1.91 | 7.3 | 17.2 |  |
|  |  | Backup SRAM ON, RTC ON and LSE in Medium low drive mode | 1.38 | 1.57 | 1.93 | 7.9 | 18.4 |  |
|  |  | Backup SRAM ON, RTC ON and LSE in Medium high drive mode | 1.53 | 1.73 | 2.11 | 8.0 | 18.7 |  |
|  |  | Backup SRAM ON, RTC ON and LSE in High drive mode | 1.67 | 1.87 | 2.26 | 9.0 | 21.0 |  |

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a $C_{L}$ of 6 pF for typical values.
2. Guaranteed by characterization results.

## I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

## I/O static current consumption

All the I/Os used as inputs with pull-up generate a current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in Table 66: I/O static characteristics.
For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

An additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid a current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption
In addition to the internal peripheral current consumption (see Table 40: Peripheral current consumption), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$
I_{S W}=V_{D D} \times f_{S W} \times C
$$

where
$I_{\text {SW }}$ is the current sunk by a switching I/O to charge/discharge the capacitive load
$V_{D D}$ is the MCU supply voltage
$f_{S W}$ is the I/O switching frequency
$C$ is the total capacitance seen by the I/O pin: $\mathrm{C}=\mathrm{C}_{\mathrm{INT}}{ }^{+} \mathrm{C}_{\mathrm{EXT}}$
The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 39. Switching output I/O current consumption ${ }^{(1)}$

| Symbol | Parameter | Conditions | I/O toggling frequency (fsw) MHz | $\begin{gathered} \text { Typ } \\ \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \end{gathered}$ | $\begin{gathered} \text { Typ } \\ \mathrm{V}_{\mathrm{DD}}=1.8 \mathrm{~V} \end{gathered}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\text {DDIO }}$ | I/O switching Current | $\begin{gathered} C_{E X T}=0 p F \\ C=C_{I N T}+C_{S}+C_{E X T} \end{gathered}$ | 2 | 0.1 | 0.1 | mA |
|  |  |  | 8 | 0.4 | 0.2 |  |
|  |  |  | 25 | 1.1 | 0.7 |  |
|  |  |  | 50 | 2.4 | 1.3 |  |
|  |  |  | 60 | 3.1 | 1.6 |  |
|  |  |  | 84 | 4.3 | 2.4 |  |
|  |  |  | 90 | 4.9 | 2.6 |  |
|  |  |  | 100 | 5.4 | 2.8 |  |
|  |  | $\begin{gathered} \mathrm{C}_{\mathrm{EXT}}=10 \mathrm{pF} \\ \mathrm{C}=\mathrm{C}_{\mathrm{INT}}+\mathrm{C}_{\mathrm{S}}+\mathrm{C}_{\mathrm{EXT}} \end{gathered}$ | 2 | 0.2 | 0.1 |  |
|  |  |  | 8 | 0.6 | 0.3 |  |
|  |  |  | 25 | 1.8 | 1.1 |  |
|  |  |  | 50 | 3.1 | 2.3 |  |
|  |  |  | 60 | 4.6 | 3.4 |  |
|  |  |  | 84 | 9.7 | 3.6 |  |
|  |  |  | 90 | 10.12 | 5.2 |  |
|  |  |  | 100 | 14.92 | 5.4 |  |

Table 39. Switching output I/O current consumption ${ }^{(1)}$ (continued)

| Symbol | Parameter | Conditions | I/O toggling frequency (fsw) MHz | $\begin{gathered} \text { Typ } \\ \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \end{gathered}$ | $\begin{gathered} \text { Typ } \\ \mathrm{V}_{\mathrm{DD}}=1.8 \mathrm{~V} \end{gathered}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $I_{\text {DDIo }}$ | I/O switching Current | $\begin{gathered} C_{E X T}=22 \mathrm{pF} \\ \mathrm{C}=\mathrm{C}_{I N T}+\mathrm{C}_{\mathrm{S}}+\mathrm{C}_{\mathrm{EXT}} \end{gathered}$ | 2 | 0.3 | 0.1 | mA |
|  |  |  | 8 | 1.0 | 0.5 |  |
|  |  |  | 25 | 3.5 | 1.6 |  |
|  |  |  | 50 | 5.9 | 4.2 |  |
|  |  |  | 60 | 10.0 | 4.4 |  |
|  |  |  | 84 | 19.12 | 5.8 |  |
|  |  |  | 90 | 19.6 | - |  |
|  |  | $\begin{gathered} \mathrm{C}_{\mathrm{EXT}}=33 \mathrm{pF} \\ \mathrm{C}=\mathrm{C}_{\mathrm{INT}}+\mathrm{C}_{S}+\mathrm{C}_{\mathrm{EXT}} \end{gathered}$ | 2 | 0.3 | 0.2 |  |
|  |  |  | 8 | 1.3 | 0.7 |  |
|  |  |  | 25 | 3.5 | 2.3 |  |
|  |  |  | 50 | 10.26 | 5.19 |  |
|  |  |  | 60 | 16.53 | - |  |

1. $\mathrm{CINT}+\mathrm{C}_{\mathrm{S}}$, PCB board capacitance including the pad pin is estimated to 15 pF .

## On-chip peripheral current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- I/O compensation cell enabled.
- The ART/L1-cache is ON.
- Scale 1 mode selected, internal digital voltage $\mathrm{V} 12=1.32 \mathrm{~V}$.
- HCLK is the system clock. $\mathrm{f}_{\mathrm{PCLK} 1}=\mathrm{f}_{\mathrm{HCLK}} / 4$, and $\mathrm{f}_{\text {PCLK } 2}=\mathrm{f}_{\mathrm{HCLK}} / 2$.

The given value is calculated by measuring the difference of current consumption

- with all peripherals clocked off
- with only one peripheral clocked on
- $\quad \mathrm{f}_{\text {HCLK }}=216 \mathrm{MHz}$ (Scale $1+$ over-drive ON), $\mathrm{f}_{\text {HCLK }}=168 \mathrm{MHz}$ (Scale 2), $\mathrm{f}_{\mathrm{HCLK}}=144 \mathrm{MHz}$ (Scale 3)
- Ambient operating temperature is $25^{\circ} \mathrm{C}$ and $\mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}$.

Table 40. Peripheral current consumption

| Peripheral |  | $\mathrm{I}_{\mathrm{DD}}(\mathrm{Typ})^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Scale 1 | Scale 2 | Scale 3 |  |
| $\begin{gathered} \text { AHB1 } \\ \text { (up to } \\ 216 \mathrm{MHz} \text { ) } \end{gathered}$ | GPIOA | 2.9 | 2.8 | 2.2 | $\mu \mathrm{A} / \mathrm{MHz}$ |
|  | GPIOB | 3.0 | 2.9 | 2.2 |  |
|  | GPIOC | 2.9 | 2.8 | 2.2 |  |
|  | GPIOD | 3.1 | 3.0 | 2.3 |  |
|  | GPIOE | 3.1 | 3.0 | 2.3 |  |
|  | GPIOF | 2.9 | 2.8 | 2.2 |  |
|  | GPIOG | 2.9 | 2.8 | 2.2 |  |
|  | GPIOH | 3.1 | 3.1 | 2.4 |  |
|  | GPIOI | 3.0 | 2.9 | 2.2 |  |
|  | GPIOJ | 2.9 | 2.9 | 2.2 |  |
|  | GPIOK | 2.8 | 2.8 | 2.4 |  |
|  | CRC | 1.0 | 0.9 | 0.8 |  |
|  | BKPSRAM | 0.9 | 0.9 | 0.7 |  |
|  | DMA1 | $3.17 \times \mathrm{N}+11.63$ | $3.08 \times \mathrm{N}+11.39$ | $2.6 \times \mathrm{N}+9.64$ |  |
|  | DMA2 | $3.33 \times \mathrm{N}+12.84$ | $3.27 \times \mathrm{N}+11.84$ | $2.75 \times \mathrm{N}+10.10$ |  |
|  | DMA2D | 77.7 | 76.3 | 63.5 |  |
|  | ETH_MAC <br> ETH_MAC_TX <br> ETH_MAC_RX <br> ETH_MAC_PTP | 40.1 | 39.5 | 32.8 |  |
|  | OTG_HS | 58.5 | 57.4 | 48.1 |  |
|  | OTG_HS+ULPI | 58.5 | 57.4 | 48.1 |  |
| $\begin{gathered} \text { AHB2 } \\ \text { (up to } \\ 216 \mathrm{MHz} \text { ) } \end{gathered}$ | DCMI | 2.9 | 2.8 | 2.1 | $\mu \mathrm{A} / \mathrm{MHz}$ |
|  | JPEG | 74.8 | 73.4 | 61.9 |  |
|  | RNG | 6.7 | 6.7 | 5.4 |  |
|  | USB_OTG_FS | 32.4 | 31.9 | 26.7 |  |
| $\begin{gathered} \text { AHB3 } \\ \text { (up to } \\ 216 \mathrm{MHz} \text { ) } \end{gathered}$ | FMC | 18.6 | 18.2 | 15.1 | $\mu \mathrm{A} / \mathrm{MHz}$ |
|  | QSPI | 22.3 | 21.8 | 18.1 |  |
| Bus matrix ${ }^{(2)}$ |  | 3.94 | 3.25 | 2.12 | $\mu \mathrm{A} / \mathrm{MHz}$ |

Table 40. Peripheral current consumption (continued)

| Peripheral |  | $\mathrm{I}_{\mathrm{DD}}(\mathrm{Typ})^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Scale 1 | Scale 2 | Scale 3 |  |
| APB1 <br> (up to <br> 54 MHz ) | TIM2 | 19.1 | 18.7 | 14.7 | $\mu \mathrm{A} / \mathrm{MHz}$ |
|  | TIM3 | 14.6 | 14.0 | 10.6 |  |
|  | TIM4 | 15.4 | 14.7 | 11.4 |  |
|  | TIM5 | 18.1 | 17.6 | 13.6 |  |
|  | TIM6 | 3.1 | 2.7 | 1.4 |  |
|  | TIM7 | 3.0 | 2.7 | 1.1 |  |
|  | TIM12 | 8.1 | 7.8 | 5.6 |  |
|  | TIM13 | 5.4 | 5.1 | 3.1 |  |
|  | TIM14 | 5.6 | 5.3 | 3.3 |  |
|  | LPTIM1 | 9.8 | 9.6 | 6.9 |  |
|  | WWDG | 1.9 | 1.6 | 1,4 |  |
|  | SPI2/I2S2 ${ }^{(3)}$ | 3.0 | 2.9 | 1.4 |  |
|  | SPI3/I2S3 ${ }^{(3)}$ | 3.0 | 3.3 | 1.4 |  |
|  | SPDIFRX | 2.4 | 2.0 | 1.7 |  |
|  | USART2 | 12.6 | 12.7 | 9.2 |  |
|  | USART3 | 12.4 | 12.4 | 9.4 |  |
|  | UART4 | 10.7 | 10.9 | 8.1 |  |
|  | UART5 | 10.7 | 10.7 | 8.1 |  |
|  | I2C1 | 8.9 | 8.9 | 6.4 |  |
|  | I2C2 | 8.3 | 8.2 | 6.1 |  |
|  | I2C3 | 8.1 | 8.2 | 6.1 |  |
|  | I2C4 | 8.0 | 8.2 | 5.8 |  |
|  | CAN1 | 6.3 | 6.4 | 4.4 |  |
|  | CAN2 | 5.7 | 5.8 | 3.9 |  |
|  | CAN3 | 7.4 | 7.1 | 5.6 |  |
|  | HDMI-CEC | 2.2 | 1.8 | 1.4 |  |
|  | PWR | 1.3 | 0.9 | 0.8 |  |
|  | DAC ${ }^{(4)}$ | 4.8 | 4.2 | 3.6 |  |
|  | UART7 | 10.4 | 10.4 | 7.8 |  |
|  | UART8 | 11.1 | 11.3 | 8.3 |  |

Table 40. Peripheral current consumption (continued)

| Peripheral |  | $\mathrm{I}_{\mathrm{DD}}(\mathrm{Typ})^{(1)}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Scale 1 | Scale 2 | Scale 3 |  |
| $\begin{gathered} \text { APB2 } \\ \text { (up to } \\ 108 \mathrm{MHz} \text { ) } \end{gathered}$ | TIM1 | 24.1 | 23.8 | 19.6 | $\mu \mathrm{A} / \mathrm{MHz}$ |
|  | TIM8 | 24.5 | 24.2 | 20.0 |  |
|  | USART1 | 17.7 | 17.4 | 14.3 |  |
|  | USART6 | 11.9 | 11.8 | 9.4 |  |
|  | ADC1 ${ }^{(5)}$ | 4.5 | 4.7 | 3.5 |  |
|  | ADC2 ${ }^{(5)}$ | 4.5 | 4.7 | 3.3 |  |
|  | ADC3 ${ }^{(5)}$ | 4.5 | 4.6 | 3.3 |  |
|  | SDMMC1 | 8.4 | 8.3 | 6.9 |  |
|  | SDMMC2 | 8.2 | 8.2 | 6.4 |  |
|  | SPI1/I2S1 ${ }^{(3)}$ | 3.9 | 3.6 | 3.1 |  |
|  | SPI4 | 3.9 | 3.6 | 3.1 |  |
|  | SYSCFG | 2.5 | 2.2 | 1.9 |  |
|  | TIM9 | 8.0 | 8.0 | 6.2 |  |
|  | TIM10 | 5.0 | 5.1 | 3.7 |  |
|  | TIM11 | 6.9 | 6.9 | 5.3 |  |
|  | SPI5 | 2.7 | 2.8 | 1.8 |  |
|  | SPI6 | 3.1 | 3.2 | 2.2 |  |
|  | SAI1 | 3.2 | 3.3 | 2.2 |  |
|  | DFSDM1 | 10.9 | 10.7 | 9.0 |  |
|  | SAI2 | 3.9 | 3.9 | 2.8 |  |
|  | MDIO | 7.1 | 7.0 | 5.8 |  |
|  | LTDC | 51.2 | 50.3 | 41.8 |  |
|  | DSI | 8.5 | 8.4 | 8.1 |  |

1. When the $I / O$ compensation cell is $\mathrm{ON}, \mathrm{I}_{\mathrm{DD}}$ typical value increases by 0.22 mA .
2. The BusMatrix is automatically active when at least one master is $O N$.
3. To enable an I2S peripheral, first set the I2SMOD bit and then the I2SE bit in the SPI_I2SCFGR register.
4. When the DAC is ON and EN $1 / 2$ bits are set in DAC_CR register, add an additional power consumption of 0.75 mA per DAC channel for the analog part.
5. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

### 5.3.8 Wakeup time from low-power modes

The wakeup times given in Table 41 are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep modes: the wakeup event is WFE.
- WKUP (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

All timings are derived from tests performed under ambient temperature and $V_{D D}=3.3 \mathrm{~V}$.
Table 41. Low-power mode wakeup timings

| Symbol | Parameter | Conditions | Typ ${ }^{(1)}$ | Max ${ }^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $t_{\text {WUSLEEP }}{ }^{(2)}$ | Wakeup from Sleep | - | 13 | 13 | CPU clock cycles |
| $\mathrm{t}_{\text {WUSTOP }}{ }^{(2)}$ | Wakeup from Stop mode with MR/LP regulator in normal mode | Main regulator is ON | 14 | 14.9 | $\mu \mathrm{s}$ |
|  |  | Main regulator is ON and Flash memory in Deep power down mode | 104.1 | 107.6 |  |
|  |  | Low power regulator is ON | 21.4 | 24.2 |  |
|  |  | Low power regulator is ON and Flash memory in Deep power down mode | 111.5 | 116.5 |  |
| $\mathrm{t}_{\text {WUSTOP }}{ }^{(2)}$ | Wakeup from Stop mode with MR/LP regulator in Under-drive mode | Main regulator in under-drive mode (Flash memory in Deep power-down mode) | 107.4 | 113.2 |  |
|  |  | Low power regulator in under-drive mode <br> (Flash memory in Deep power-down mode ) | 112.7 | 120 |  |
| tWUSTDBY <br> (2) | Wakeup from Standby mode | Exit Standby mode on rising edge | 308 | 313 |  |
|  |  | Exit Standby mode on falling edge | 307 | 313 |  |

1. Guaranteed by characterization results.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first

### 5.3.9 External clock source characteristics

## High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the Table 66: I/O static characteristics. However, the recommended clock input waveform is shown in Figure 29.

The characteristics given in Table 42 result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in Table 18.

Table 42. High-speed external user clock characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {HSE_ext }}$ | External user clock source frequency ${ }^{(1)}$ | - | 1 | - | 50 | MHz |
| $\mathrm{V}_{\text {HSEH }}$ | OSC_IN input pin high level voltage |  | $0.7 \mathrm{~V}_{\mathrm{DD}}$ | - | $V_{D D}$ | V |
| $\mathrm{V}_{\text {HSEL }}$ | OSC_IN input pin low level voltage |  | $\mathrm{V}_{\mathrm{SS}}$ | - | $0.3 \mathrm{~V}_{\mathrm{DD}}$ |  |
| $\begin{aligned} & \mathrm{t}_{\mathrm{w}(\mathrm{HSE})} \\ & \mathrm{t}_{\mathrm{w}(\mathrm{HSE})} \end{aligned}$ | OSC_IN high or low time ${ }^{(1)}$ |  | 5 | - | - | ns |
| $\begin{aligned} & \mathrm{t}_{\mathrm{r}(\mathrm{HSE})} \\ & \mathrm{t}_{\mathrm{f}(\mathrm{HSE})} \end{aligned}$ | OSC_IN rise or fall time ${ }^{(1)}$ |  | - | - | 10 |  |
| $\mathrm{C}_{\text {in(HSE) }}$ | OSC_IN input capacitance ${ }^{(1)}$ | - | - | 5 | - | pF |
| $\mathrm{DuCy}_{(\text {(HSE) }}$ | Duty cycle | - | 45 | - | 55 | \% |
| $\mathrm{I}_{\mathrm{L}}$ | OSC_IN Input leakage current | $\mathrm{V}_{\mathrm{SS}} \leq \mathrm{V}_{\mathrm{IN}} \leq \mathrm{V}_{\mathrm{DD}}$ | - | - | $\pm 1$ | $\mu \mathrm{A}$ |

1. Guaranteed by design.

## Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the Table 66: I/O static characteristics. However, the recommended clock input waveform is shown in Figure 30.

The characteristics given in Table 43 result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in Table 18.

Table 43. Low-speed external user clock characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {LSE_ext }}$ | User External clock source frequency ${ }^{(1)}$ | - | - | 32.768 | 1000 | kHz |
| $\mathrm{V}_{\text {LSEH }}$ | OSC32_IN input pin high level voltage |  | $0.7 \mathrm{~V}_{\mathrm{DD}}$ | - | $V_{D D}$ | V |
| $V_{\text {LSEL }}$ | OSC32_IN input pin low level voltage |  | $\mathrm{V}_{\text {SS }}$ | - | $0.3 \mathrm{~V}_{\mathrm{DD}}$ |  |
| $\begin{aligned} & \left.\mathrm{t}_{\mathrm{w}(\mathrm{LSE}}\right) \\ & \mathrm{t}_{\mathrm{f}(\mathrm{LSE})} \end{aligned}$ | OSC32_IN high or low time ${ }^{(1)}$ |  | 450 | - | - | ns |
| $\begin{aligned} & \mathrm{t}_{\mathrm{r}(\mathrm{LSE})} \\ & \mathrm{t}_{\mathrm{f}(\mathrm{LSE})} \end{aligned}$ | OSC32_IN rise or fall time ${ }^{(1)}$ |  | - | - | 50 |  |
| $\mathrm{C}_{\text {in(LSE) }}$ | OSC32_IN input capacitance ${ }^{(1)}$ | - | - | 5 | - | pF |
| DuCy ${ }_{(\text {LSE) }}$ | Duty cycle | - | 30 | - | 70 | \% |
| IL | OSC32_IN Input leakage current | $\mathrm{V}_{\mathrm{SS}} \leq \mathrm{V}_{\mathrm{IN}} \leq \mathrm{V}_{\mathrm{DD}}$ | - | - | $\pm 1$ | $\mu \mathrm{A}$ |

1. Guaranteed by design.

Figure 29. High-speed external clock source AC timing diagram


Figure 30. Low-speed external clock source AC timing diagram


## High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in Table 44. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 44. HSE 4-26 MHz oscillator characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| fosc_IN | Oscillator frequency | - | 4 | - | 26 | MHz |
| $\mathrm{R}_{\mathrm{F}}$ | Feedback resistor | - | - | 200 | - | k $\Omega$ |
| IDD | HSE current consumption | $\begin{gathered} \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}, \\ \mathrm{ESR}=30 \Omega, \\ \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF} @ 25 \mathrm{MHz} \end{gathered}$ | - | 450 | - | $\mu \mathrm{A}$ |
|  |  | $\begin{gathered} \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}, \\ \mathrm{ESR}=30 \Omega, \\ \mathrm{C}_{\mathrm{L}}=10 \mathrm{pF} @ 25 \mathrm{MHz} \end{gathered}$ | - | 530 | - |  |
| $\mathrm{ACC}_{\text {HSE }}{ }^{(2)}$ | HSE accuracy | - | - 500 | - | 500 | ppm |
| $\mathrm{G}_{\mathrm{m}}$ crit_max | Maximum critical crystal $\mathrm{gm}_{\mathrm{m}}$ | Startup | - | - | 1 | mA/V |
| $\mathrm{t}_{\text {SU(HSE }}{ }^{(3)}$ | Startup time | $V_{D D}$ is stabilized | - | 2 | - | ms |

1. Guaranteed by design.
2. This parameter depends on the crystal used in the application. The minimum and maximum values must be respected to comply with USB standard specifications.
3. $t_{\text {SU(HSE) }}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is guaranteed by characterization results. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For $\mathrm{C}_{\mathrm{L} 1}$ and $\mathrm{C}_{\mathrm{L} 2}$, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see Figure 31). $\mathrm{C}_{\mathrm{L} 1}$ and $\mathrm{C}_{\mathrm{L} 2}$ are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of $\mathrm{C}_{\mathrm{L} 1}$ and $\mathrm{C}_{\mathrm{L} 2}$. The PCB and MCU pin capacitance must be included ( 10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing $\mathrm{C}_{\mathrm{L} 1}$ and $\mathrm{C}_{\mathrm{L} 2}$.
Note: $\quad$ For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 31. Typical application with an 8 MHz crystal


1. $R_{E X T}$ value depends on the crystal characteristics.

## Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in Table 45. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 45. LSE oscillator characteristics ( $\left.\mathrm{f}_{\text {LSE }}=32.768 \mathrm{kHz}\right)^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| IDD | LSE current consumption | LSEDRV[1:0]=00 <br> Low drive capability | - | 250 | - | nA |
|  |  | LSEDRV[1:0]=10 <br> Medium low drive capability | - | 300 | - |  |
|  |  | LSEDRV[1:0]=01 <br> Medium high drive capability | - | 370 | - |  |
|  |  | LSEDRV[1:0]=11 <br> High drive capability | - | 480 | - |  |

Table 45. LSE oscillator characteristics $\left(\mathbf{f}_{\text {LSE }}=32.768 \mathrm{kHz}\right){ }^{(1)}$ (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{G}_{\mathrm{m}}$ _crit_max | Maximum critical crystal $\mathrm{gm}_{\mathrm{m}}$ | LSEDRV[1:0]=00 <br> Low drive capability | - | - | 0.48 | $\mu \mathrm{A} / \mathrm{V}$ |
|  |  | LSEDRV[1:0]=10 <br> Medium low drive capability | - | - | 0.75 |  |
|  |  | LSEDRV[1:0]=01 <br> Medium high drive capability | - | - | 1.7 |  |
|  |  | LSEDRV[1:0]=11 <br> High drive capability | - | - | 2.7 |  |
| $\mathrm{t}_{\text {Su }}{ }^{(2)}$ | start-up time | $V_{D D}$ is stabilized | - | 2 | - | s |

1. Guaranteed by design.
2. Guaranteed by characterization results. $\mathrm{t}_{\mathrm{SU}}$ is the start-up time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note:
For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 32. Typical application with a 32.768 kHz crystal

Resonator with
integrated capacitors


### 5.3.10 Internal clock source characteristics

The parameters given in Table 46 and Table 47 are derived from tests performed under ambient temperature and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18.

High-speed internal (HSI) RC oscillator
Table 46. HSI oscillator characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\mathrm{HSI}}$ | Frequency | - | - | 16 | - | MHz |
| $\mathrm{ACC}_{\mathrm{HSI}}$ | Accuracy of the HSI oscillator | HSI user trimming step ${ }^{(2)}$ | - | - | - | 1 |
|  |  | $\mathrm{~T}_{\mathrm{A}}=-40$ to $105^{\circ} \mathrm{C}^{(3)}$ | -8 | - | 4.5 | $\%$ |
|  |  | -4 | - | 4 | $\%$ |  |
|  | $\mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}^{(4)}$ | -1 | - | 1 | $\%$ |  |
| $\mathrm{t}_{\text {su(HSI) }}{ }^{(2)}$ | HSI oscillator startup time | - | - | 2.2 | 4 | $\mu \mathrm{~s}$ |
| $\mathrm{I}_{\mathrm{DD}(\mathrm{HSI})}{ }^{(2)}$ | HSI oscillator power consumption | - | - | 60 | 80 | $\mu \mathrm{~A}$ |

1. $V_{D D}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40$ to $105^{\circ} \mathrm{C}$ unless otherwise specified.
2. Guaranteed by design.
3. Guaranteed by characterization results.
4. Factory calibrated, parts not soldered.

Figure 33. ACCHSI versus temperature


1. Guaranteed by characterization results.

## Low-speed internal (LSI) RC oscillator

Table 47. LSI oscillator characteristics ${ }^{(1)}$

| Symbol | Parameter | Min | Typ | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\mathrm{LSI}}{ }^{(2)}$ | Frequency | 17 | 32 | 47 | kHz |
| $\mathrm{t}_{\text {su(LSI) }}{ }^{(3)}$ | LSI oscillator startup time | - | 15 | 40 | $\mu \mathrm{~s}$ |
| $\mathrm{I}_{\mathrm{DD}(\mathrm{LSI})}{ }^{(3)}$ | LSI oscillator power consumption | - | 0.4 | 0.6 | $\mu \mathrm{~A}$ |

1. $V_{D D}=3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40$ to $105^{\circ} \mathrm{C}$ unless otherwise specified.
2. Guaranteed by characterization results.
3. Guaranteed by design.

Figure 34. LSI deviation versus temperature


### 5.3.11 PLL characteristics

The parameters given in Table 48 and Table 49 are derived from tests performed under temperature and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18.

Table 48. Main PLL characteristics

| Symbol | Parameter | Conditions |  | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {PLL_IN }}$ | PLL input clock ${ }^{(1)}$ | - |  | $0.95{ }^{(2)}$ | 1 | 2.10 | MHz |
| fPLL_OUT | PLL multiplier output clock | - |  | 24 | - | 216 |  |
| fPLL48_OUT | 48 MHz PLL multiplier output clock | - |  | - | 48 | 75 |  |
| fvco_out | PLL VCO output | - |  | 100 | - | 432 |  |
| t Lock | PLL lock time | VCO freq $=192 \mathrm{MHz}$ |  | 75 | - | 200 | $\mu \mathrm{s}$ |
|  |  | VCO freq $=432 \mathrm{MHz}$ |  | 100 | - | 300 |  |
| Jitter ${ }^{(3)}$ |  | System clock 216 MHz | RMS | - | 25 | - | ps |
|  | Cycle-to-cycle jitter |  | peak to peak | - | $\pm 150$ | - |  |
|  |  |  | RMS | - | 15 | - |  |
|  | Period Jitter |  | peak to peak | - | $\pm 200$ | - |  |
|  | Main clock output (MCO) for RMII Ethernet | Cycle to cycle at 50 MHz on 1000 samples |  | - | 32 | - |  |
|  | Main clock output (MCO) for MII Ethernet | Cycle to cycle at 25 MHz on 1000 samples |  | - | 40 | - |  |
|  | Bit Time CAN jitter | Cycle to cycle at 1 MHz on 1000 samples |  | - | 330 | - |  |
| $\mathrm{I}_{\mathrm{DD}(\mathrm{PLL})^{(4)}}$ | PLL power consumption on $\mathrm{V}_{\mathrm{DD}}$ | $\begin{aligned} & \mathrm{VCO} \text { freq }=192 \mathrm{MHz} \\ & \mathrm{VCO} \text { freq }=432 \mathrm{MHz} \end{aligned}$ |  | $\begin{aligned} & 0.15 \\ & 0.45 \end{aligned}$ | - | $\begin{aligned} & 0.40 \\ & 0.75 \end{aligned}$ | mA |
| $\mathrm{I}_{\mathrm{DDA}(\mathrm{PLL})}{ }^{(4)}$ | PLL power consumption on $\mathrm{V}_{\text {DDA }}$ | $\begin{aligned} & \mathrm{VCO} \text { freq }=192 \mathrm{MHz} \\ & \mathrm{VCO} \text { freq }=432 \mathrm{MHz} \end{aligned}$ |  | $\begin{aligned} & 0.30 \\ & 0.55 \end{aligned}$ | - | $\begin{aligned} & 0.40 \\ & 0.85 \end{aligned}$ | mA |

1. Take care of using the appropriate division factor $M$ to obtain the specified PLL input clock values. The $M$ factor is shared between PLL and PLLI2S.
2. Guaranteed by design.
3. The use of 2 PLLs in parallel could degraded the Jitter up to $+30 \%$.
4. Guaranteed by characterization results.

Table 49. PLLI2S characteristics

| Symbol | Parameter | Conditions |  | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {PLLI2S_IN }}$ | PLLI2S input clock ${ }^{(1)}$ | - |  | $0.95{ }^{(2)}$ | 1 | 2.10 | MHz |
| $\mathrm{f}_{\text {PLLI2SP_OUT }}$ | PLLI2S multiplier output clock for SPDIFRX | - |  | - | - | 216 |  |
| $\mathrm{f}_{\text {PLLI2SQ_OUT }}$ | PLLI2S multiplier output clock for SAI | - |  | - | - | 216 |  |
| $\mathrm{f}_{\text {PLLI2SR_OUT }}$ | PLLI2S multiplier output clock for I2S | - |  | - | - | 216 |  |
| $\mathrm{f}_{\mathrm{VCO}}$ _Out | PLLI2S VCO output | - |  | 100 | - | 432 |  |
| $\mathrm{t}_{\text {LOCK }}$ | PLLI2S lock time | VCO freq = 192 MHz |  | 75 | - | 200 | $\mu \mathrm{s}$ |
|  |  | VCO freq $=432 \mathrm{MHz}$ |  | 100 | - | 300 |  |
| Jitter ${ }^{(3)}$ | Master I2S clock jitter | Cycle to cycle at 12.288 MHz on 48 KHz period, $\mathrm{N}=432, \mathrm{R}=5$ | RMS | - | 90 | - | - |
|  |  |  | peak to peak | - | $\pm 280$ | - | ps |
|  |  | Average frequency of $\begin{aligned} & 12.288 \mathrm{MHz} \\ & \mathrm{~N}=432, \mathrm{R}=5 \end{aligned}$ <br> on 1000 samples |  | - | 90 | - | ps |
|  | WS I2S clock jitter | Cycle to cycle at 48 KHz on 1000 samples |  | - | 400 | - | ps |
| $\mathrm{I}_{\mathrm{DD}(\mathrm{PLLI} 2 \mathrm{~S})}{ }^{(4)}$ | PLLI2S power consumption on $V_{D D}$ | $\begin{aligned} & \hline \mathrm{VCO} \text { freq }=192 \mathrm{MHz} \\ & \mathrm{VCO} \text { freq }=432 \mathrm{MHz} \end{aligned}$ |  | $\begin{aligned} & 0.15 \\ & 0.45 \end{aligned}$ | - | $\begin{aligned} & 0.40 \\ & 0.75 \end{aligned}$ | mA |
| $\mathrm{I}_{\mathrm{DDA}(\mathrm{PLLI} 2 \mathrm{~S})}{ }^{(4)}$ | PLLI2S power consumption on $V_{\text {DDA }}$ | $\begin{aligned} & \mathrm{VCO} \text { freq }=192 \mathrm{MHz} \\ & \mathrm{VCO} \text { freq }=432 \mathrm{MHz} \end{aligned}$ |  | $\begin{aligned} & 0.30 \\ & 0.55 \end{aligned}$ | - | $\begin{aligned} & 0.40 \\ & 0.85 \end{aligned}$ | mA |

1. Take care of using the appropriate division factor $M$ to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

Table 50. PLLISAI characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :--- | :--- | :---: | :---: | :---: | :---: | :---: |
| f PLLSAI_IN $^{\text {(1) }}$ | PLLSAI input clock ${ }^{(1)}$ | - | $0.95^{(2)}$ | 1 | 2.10 |  |
| f PLLSAIP_OUT | PLLSAI multiplier output clock <br> for 48 MHz | - | - | 48 | 75 |  |
| fPLLSAIQ_OUT | PLLSAI multiplier output clock <br> for SAI | - | - | - | 216 | MHz |
| fPLLSAIR_OUT | PLLSAI multiplier output clock <br> for LCD-TFT | - | - | - | 216 |  |
| f VCO_OUT | PLLSAI VCO output | - | 100 | - | 432 |  |

Table 50. PLLISAI characteristics (continued)

| Symbol | Parameter | Conditions |  | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {LOCK }}$ | PLLSAI lock time | VCO freq $=192 \mathrm{MHz}$ |  | 75 | - | 200 |  |
|  |  | VCO freq $=432 \mathrm{MHz}$ |  | 100 | - | 300 |  |
| Jitter ${ }^{(3)}$ | Master SAI clock jitter | Cycle to cycle at 12.288 MHz on 48 KHz period, $\mathrm{N}=432, \mathrm{R}=5$ | RMS | - | 90 | - | - |
|  |  |  | peak to peak | - | $\pm 280$ | - | ps |
|  |  | Average frequency of $\begin{aligned} & 12.288 \mathrm{MHz} \\ & \mathrm{~N}=432, \mathrm{R}=5 \end{aligned}$ <br> on 1000 samples |  | - | 90 | - | ps |
|  | FS clock jitter | Cycle to cycle at 48 KHz on 1000 samples |  | - | 400 | - | ps |
| $\mathrm{I}_{\mathrm{DD}\left(\text { PLLSAI) }{ }^{(4)}\right.}$ | PLLSAI power consumption on $V_{D D}$ | $\begin{aligned} & \hline \mathrm{VCO} \text { freq }=192 \mathrm{MHz} \\ & \mathrm{VCO} \text { freq }=432 \mathrm{MHz} \end{aligned}$ |  | $\begin{aligned} & 0.15 \\ & 0.45 \end{aligned}$ | - | $\begin{aligned} & 0.40 \\ & 0.75 \end{aligned}$ | mA |
| $\mathrm{I}_{\text {DDA(PLLSAI) }}{ }^{(4)}$ | PLLSAI power consumption on $V_{\text {DDA }}$ | $\begin{aligned} & \mathrm{VCO} \text { freq }=192 \mathrm{MHz} \\ & \mathrm{VCO} \text { freq }=432 \mathrm{MHz} \end{aligned}$ |  | $\begin{aligned} & 0.30 \\ & 0.55 \end{aligned}$ |  | $\begin{aligned} & 0.40 \\ & 0.85 \end{aligned}$ | mA |

1. Take care of using the appropriate division factor $M$ to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

### 5.3.12 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see Table 62: EMI characteristics). It is available only on the main PLL.

Table 51. SSCG parameters constraint

| Symbol | Parameter | Min | Typ | Max $^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {Mod }}$ | Modulation frequency | - | - | 10 | KHz |
| md | Peak modulation depth | 0.25 | - | 2 | $\%$ |
| MODEPER * INCSTEP | - | - | - | $2^{15}-1$ | - |

1. Guaranteed by design.

## Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$
\text { MODEPER }=\operatorname{round}\left[\mathrm{f}_{\text {PLL_IN }} /\left(4 \times \mathrm{f}_{\text {Mod }}\right)\right]
$$

$\mathrm{f}_{\text {PLL_IN }}$ and $\mathrm{f}_{\text {Mod }}$ must be expressed in Hz .
As an example:

If $\mathrm{f}_{\mathrm{PLL}, \mathrm{IN}}=1 \mathrm{MHz}$, and $\mathrm{f}_{\mathrm{MOD}}=1 \mathrm{kHz}$, the modulation depth (MODEPER) is given by equation 1 :

$$
\text { MODEPER }=\operatorname{round}\left[10^{6} /\left(4 \times 10^{3}\right)\right]=250
$$

## Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$
\text { INCSTEP }=\operatorname{round}\left[\left(\left(2^{15}-1\right) \times \mathrm{md} \times \text { PLLN }\right) /(100 \times 5 \times \text { MODEPER })\right]
$$

$\mathrm{f}_{\text {VCO_OUT }}$ must be expressed in MHz .
With a modulation depth $(\mathrm{md})= \pm 2 \%$ ( $4 \%$ peak to peak), and PLLN $=240$ (in MHz):

$$
\operatorname{INCSTEP}=\operatorname{round}\left[\left(\left(2^{15}-1\right) \times 2 \times 240\right) /(100 \times 5 \times 250)\right]=126 \mathrm{md}(\text { quantitazed }) \%
$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$
\mathrm{md}_{\text {quantized }} \%=(\text { MODEPER } \times \operatorname{INCSTEP} \times 100 \times 5) /\left(\left(2^{15}-1\right) \times \text { PLLN }\right)
$$

As a result:

$$
\mathrm{md}_{\text {quantized }} \%=(250 \times 126 \times 100 \times 5) /\left(\left(2^{15}-1\right) \times 240\right)=2.002 \%(\text { peak })
$$

Figure 35 and Figure 36 show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is $f_{\text {PLL_OUT }}$ nominal.
$\mathrm{T}_{\text {mode }}$ is the modulation period.
md is the modulation depth.
Figure 35. PLL output clock waveforms in center spread mode


Figure 36. PLL output clock waveforms in down spread mode


### 5.3.13 MIPI D-PHY characteristics

The parameters given in Table 52 and Table 53 are derived from tests performed under temperature and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18.

Table 52. MIPI D-PHY characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Hi-Speed Input/Output Characteristics |  |  |  |  |  |  |
| $\mathrm{U}_{\text {INST }}$ | Ul instantaneous | - | 2 | - | 12.5 | ns |
| $\mathrm{V}_{\text {CMTX }}$ | HS transmit common mode voltage | - | 150 | 200 | 250 | mV |
| $\left\|\Delta \mathrm{V}_{\text {CMTX }}\right\|$ | $\mathrm{V}_{\text {CMTX }}$ mismatch when output is Differential-1 or Differential-0 | - | - | - | 5 |  |
| $\left\|\mathrm{V}_{\text {OD }}\right\|$ | HS transmit differential voltage | - | 140 | 200 | 270 |  |
| $\left\|\Delta \mathrm{V}_{\mathrm{OD}}\right\|$ | $V_{O D}$ mismatch when output is Differential-1 or Differential-0 | - | - | - | 14 |  |
| $\mathrm{V}_{\mathrm{OHHS}}$ | HS output high voltage | - | - | - | 360 |  |
| $\mathrm{Z}_{\mathrm{OS}}$ | Single ended output impedance | - | 40 | 50 | 62.5 | $\Omega$ |
| $\Delta \mathrm{Z}_{\text {OS }}$ | Single ended output impedance mismatch | - | - | - | 10 | \% |
| $\mathrm{t}_{\mathrm{HSr}} \& \mathrm{t}_{\mathrm{HSf}}$ | 20\%-80\% rise and fall time | - | 100 | - | 0.35*UI | ps |
| LP Receiver Input Characteristics |  |  |  |  |  |  |
| VIL | Logic 0 input voltage (not in ULP State) | - | - | - | 550 |  |
| $\mathrm{V}_{\text {IL-ULPS }}$ | Logic 0 input voltage in ULP State | - | - | - | 300 | mV |
| $\mathrm{V}_{\mathrm{IH}}$ | Input high level voltage | - | 880 | - | - |  |
| $\mathrm{V}_{\text {hys }}$ | Voltage hysteresis | - | 25 | - | - |  |
| LP Emitter Output Characteristics |  |  |  |  |  |  |

Table 52. MIPI D-PHY characteristics ${ }^{(1)}$ (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |  |
| :---: | :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{IL}}$ | Output low level voltage | - | 1.1 | 1.2 | 1.2 | V |  |
| $\mathrm{~V}_{\mathrm{IL}-\mathrm{ULPS}}$ | Output high level voltage | - | -50 | - | 50 | mV |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Output impedance of LP <br> transmitter | - | 110 | - | - | $\Omega$ |  |
| $\mathrm{V}_{\text {hys }}$ | $15 \%-85 \%$ rise and fall time | - | - | - | 25 | ns |  |
| LP Contention Detector Characteristics |  |  |  |  |  |  |  |
| $\mathrm{V}_{\mathrm{ILCD}}$ | Logic 0 contention threshold | - | - | - | 200 | mV |  |
| $\mathrm{V}_{\text {IHCD }}$ | Logic 0 contention threshold | - | 450 | - | - | m |  |

1. Guaranteed based on test during characterization.

Table 53. MIPI D-PHY AC characteristics LP mode and HS/LP

$$
\text { transitions }{ }^{(1)}
$$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{T}_{\text {LPX }}$ | Transmitted length of any LowPower state period | - | 50 | - | - |  |
| TCLK-PREPARE | Time that the transmitter drives the Clock Lane LP-00 Line state immediately before the HS-0 Line state starting the HS transmission. | - | 38 | - | 95 | ns |
| TCLK-PREPARE $+$ TCLK-ZERO | Time that the transmitter drives the HS-0 state prior to starting the clock. | - | 300 | - | - |  |
| TCLK-PRE | Time that the HS clock shall be driven by the transmitter prior to any associated Data Lane beginning the transition from LP to HS mode. | - | 8 | - | - | UI |

Table 53. MIPI D-PHY AC characteristics LP mode and HS/LP transitions ${ }^{(1)}$ (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{T}_{\text {CLK-POST }}$ | Time that the transmitter continues to send HS clock after the last associated Data Lane has transitioned to LP Mode. | - | 62+52*UI | - | - |  |
| $\mathrm{T}_{\text {CLK-TRAIL }}$ | Time that the transmitter drives the HS-0 state after the last payload clock bit of an HS transmission burst. | - | 60 | - | - |  |
| THS-PREPARE | Time that the transmitter drives the Data Lane LP-00 Line state immediately before the HS-0 Line state starting the HS transmission. | - | 40+4* UI | - | 85+6*UI |  |
| $\begin{gathered} \mathrm{T}_{\text {HS-PREPARE }} \\ + \\ \mathrm{T}_{\text {HS-ZERO }} \end{gathered}$ | THS-PREPARE+ Time that the transmitter drives the HS-0 state prior to transmitting the Sync sequence. | - | 145+10*UI | - | - | ns |
| THS-TRAIL | Time that the transmitter drives the flipped differential state after last payload data bit of a HS transmission burst. | - | $\begin{gathered} \text { Max } \\ \left(\mathrm{n}^{*} 8^{*} \mathrm{UI},\right. \\ \left.60+\mathrm{n}^{*} 4^{*} \mathrm{UI}\right) \end{gathered}$ | - | - |  |
| $\mathrm{T}_{\text {HS-EXIT }}$ | Time that the transmitter drives LP-11 following a HS burst. | - | 100 | - | - |  |
| $\mathrm{T}_{\text {REOT }}$ | $30 \%-85 \%$ rise time and fall time | - | - | - | 35 |  |
| $\mathrm{T}_{\text {EOT }}$ | Transmitted time interval from the start of $\mathrm{T}_{\text {HS-TRAIL }}$ or TCLK-TRAIL, to the start of the LP-11 state following a HS burst. | - | - | - | $\begin{gathered} \text { 105+ } \\ \text { n*12UI } \end{gathered}$ |  |

[^4]Figure 37. MIPI D-PHY HS/LP clock lane transition timing diagram


Figure 38. MIPI D-PHY HS/LP data lane transition timing diagram


### 5.3.14 MIPI D-PHY PLL characteristics

The parameters given in Table 54 are derived from tests performed under temperature and $V_{\text {DD }}$ supply voltage conditions summarized in Table 18.

Table 54. DSI-PLL characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {PLL_IN }}$ | PLL input clock | - | 4 | - | 100 | MHz |
| $\mathrm{f}_{\text {PLL_INFIN }}$ | PFD input clock | - | 4 | - | 25 |  |
| $\mathrm{f}_{\text {PLL_OUT }}$ | PLL multiplier output clock | - | 31.25 | - | 500 |  |
| $\mathrm{f}_{\text {VCO_OUT }}$ | PLL VCO output | - | 500 | - | 1000 |  |
| t Lock | PLL lock time | - | - | - | 200 | $\mu \mathrm{s}$ |

Table 54. DSI-PLL characteristics ${ }^{(1)}$ (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{DD}(\mathrm{PLL})}$ | PLL power consumption on $\mathrm{V}_{\text {DD12 }}$ | $\mathrm{f}_{\text {VCO_OUT }}=500 \mathrm{MHz}$ | - | 0.55 | 0.70 | mA |
|  |  | $\mathrm{f}_{\text {VCO_OUT }}=600 \mathrm{MHz}$ | - | 0.65 | 0.80 |  |
|  |  | $\mathrm{f}_{\text {Vco_out }}=1000 \mathrm{MHz}$ | - | 0.95 | 1.20 |  |

1. Based on test during characterization.

### 5.3.15 MIPI D-PHY regulator characteristics

The parameters given in Table 55 are derived from tests performed under temperature and $V_{D D}$ supply voltage conditions summarized in Table 18.

Table 55. DSI regulator characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {DD12DSI }}$ | 1.2 V internal voltage on $\mathrm{V}_{\text {DD12 }}$ ( ${ }^{\text {a }}$ | - | 1.15 | 1.20 | 1.30 | V |
| $\mathrm{C}_{\text {EXT }}$ | External capacitor on $\mathrm{V}_{\text {CAPDSI }}$ | - | 1.1 | 2.2 | 3.3 | $\mu \mathrm{F}$ |
| ESR | External Serial Resistor | - | 0 | 25 | 600 | $\mathrm{m} \Omega$ |
| IDDDSIREG | Regulator power consumption | - | 100 | 120 | 125 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\text {DDDSI }}$ | DSI system (regulator, PLL and D-PHY) current consumption on $V_{\text {DDDSI }}$ | Ultra Low Power Mode (Reg. ON + PLL OFF) | - | 290 | 600 | $\mu \mathrm{A}$ |
|  |  | $\begin{gathered} \text { Stop State } \\ \text { (Reg. ON + PLL OFF) } \end{gathered}$ | - | 290 | 600 |  |
| $\mathrm{I}_{\text {DDDSILP }}$ | DSI system current consumption on $V_{\text {DDDSI }}$ in LP mode communication ${ }^{(2)}$ | 10 MHz escape clock (Reg. ON + PLL OFF) | - | 4.3 | 5.0 | mA |
|  |  | 20 MHz escape clock (Reg. ON + PLL OFF) | - | 4.3 | 5.0 |  |
| IDDDSIHS | DSI system (regulator, PLL and D-PHY) current consumption on $\mathrm{V}_{\text {DDDSI }}$ in HS mode communication ${ }^{(3)}$ | 300 Mbps - 1 data lane (Reg. ON + PLL ON) | - | 8.0 | 8.8 | mA |
|  |  | 300 Mbps - 2data lane (Reg. ON + PLL ON) | - | 11.4 | 12.5 |  |
|  |  | $500 \mathrm{Mbps}-1$ data lane (Reg. ON + PLL ON) | - | 13.5 | 14.7 |  |
|  |  | 500 Mbps - 2data lane <br> (Reg. ON + PLL ON) | - | 18.0 | 19.6 |  |
|  | DSI system (regulator, PLL and D-PHY) current consumption on $V_{\text {DDDSI }}$ in HS mode with CLK like payload | 500 Mbps - 2data lane <br> (Reg. ON + PLL ON) | - | 21.4 | 23.3 |  |
| $\mathrm{t}_{\text {WAKEUP }}$ | Startup delay | $\mathrm{C}_{\text {EXT }}=2.2 \mu \mathrm{~F}$ | - | 110 | - | $\mu \mathrm{s}$ |
|  |  | $\mathrm{C}_{\text {EXT }}=3.3 \mu \mathrm{~F}$ | - | - | 160 |  |
| $\mathrm{I}_{\text {INRUSH }}$ | Inrush current on $\mathrm{V}_{\text {DDDSI }}$ | External capacitor load at start | - | 60 | 200 | mA |

1. Based on test during characterization.
2. Values based on an average traffic in LP Command Mode.
3. Values based on an average traffic ( $3 / 4 \mathrm{HS}$ traffic \& $1 / 4 \mathrm{LP}$ ) in Video Mode.

### 5.3.16 Memory characteristics

## Flash memory

The characteristics are given at TA $=-40$ to $105^{\circ} \mathrm{C}$ unless otherwise specified.
The devices are shipped to customers with the Flash memory erased.
Table 56. Flash memory characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| IDD | Supply current | Write / Erase 8-bit mode, $\mathrm{V}_{\mathrm{DD}}=1.7 \mathrm{~V}$ | - | 14 | - | mA |
|  |  | Write / Erase 16-bit mode, $\mathrm{V}_{\mathrm{DD}}=2.1 \mathrm{~V}$ | - | 17 | - |  |
|  |  | Write / Erase 32-bit mode, $\mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}$ | - | 24 | - |  |

Table 57. Flash memory programming (single bank configuration
nDBANK=1)

| Symbol | Parameter | Conditions | Min ${ }^{(1)}$ | Typ | Max ${ }^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $t_{\text {prog }}$ | Word programming time | Program/erase parallelism $(\text { PSIZE })=x 8 / 16 / 32$ | - | 16 | $100^{(2)}$ | $\mu \mathrm{s}$ |
| $t_{\text {ERASE32KB }}$ | Sector (32 KB) erase time | Program/erase parallelism $($ PSIZE $)=x 8$ | - | 400 | 800 | ms |
|  |  | Program/erase parallelism $($ PSIZE $)=x 16$ | - | 250 | 600 |  |
|  |  | Program/erase parallelism $($ PSIZE $)=x 32$ | - | 200 | 500 |  |
| terase 128 KB | Sector (128 KB) erase time | Program/erase parallelism $($ PSIZE $)=x 8$ | - | 1100 | 2400 | ms |
|  |  | Program/erase parallelism $(P S I Z E)=x 16$ | - | 800 | 1400 |  |
|  |  | Program/erase parallelism (PSIZE) $=\times 32$ | - | 500 | 1100 |  |
| terase 256 Kb | Sector (256 KB) erase time | Program/erase parallelism (PSIZE) $=x 8$ | - | 2.1 | 4 | s |
|  |  | Program/erase parallelism $($ PSIZE $)=x 16$ | - | 1.5 | 2.6 |  |
|  |  | Program/erase parallelism (PSIZE) $=\times 32$ | - | 1 | 2 |  |
| $\mathrm{t}_{\text {ME }}$ | Mass erase time | Program/erase parallelism $($ PSIZE $)=x 8$ | - | 16 | 32 | s |
|  |  | Program/erase parallelism $($ PSIZE $)=x 16$ | - | 11 | 22 |  |
|  |  | Program/erase parallelism $($ PSIZE $)=\times 32$ | - | 8 | 16 |  |

Table 57. Flash memory programming (single bank configuration nDBANK=1) (continued)

| Symbol | Parameter | Conditions | Min $^{(\mathbf{1})}$ | Typ | $\boldsymbol{M a x}^{(\mathbf{1})}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {prog }}$ | Programming voltage | 32-bit program operation | 2.7 | - | 3 | V |
|  |  | 16-bit program operation | 2.1 | - | 3.6 | V |
|  |  | 8-bit program operation | 1.7 | - | 3.6 | V |

1. Guaranteed by characterization results.
2. The maximum programming time is measured after 100 K erase operations.

Table 58. Flash memory programming (dual bank configuration nDBANK=0)

| Symbol | Parameter | Conditions | Min ${ }^{(1)}$ | Typ | Max ${ }^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $t_{\text {prog }}$ | Word programming time | Program/erase parallelism $($ PSIZE $)=x 8 / 16 / 32$ | - | 16 | $100^{(2)}$ | $\mu \mathrm{s}$ |
| terase16Kb | Sector (16 KB) erase time | Program/erase parallelism (PSIZE) $=\mathrm{x} 8$ | - | 400 | 800 | ms |
|  |  | Program/erase parallelism $($ PSIZE $)=x 16$ | - | 250 | 600 |  |
|  |  | Program/erase parallelism $($ PSIZE $)=\times 32$ | - | 200 | 500 |  |
| $t_{\text {ERASE64Kb }}$ | Sector (64 KB) erase time | Program/erase parallelism (PSIZE) $=x 8$ | - | 1100 | 2400 | ms |
|  |  | Program/erase parallelism $($ PSIZE $)=x 16$ | - | 800 | 1400 |  |
|  |  | Program/erase parallelism $($ PSIZE $)=x 32$ | - | 500 | 1100 |  |
| terase128kB | Sector (128 KB) erase time | Program/erase parallelism (PSIZE) $=\mathrm{x} 8$ | - | 2.1 | 4 | s |
|  |  | Program/erase parallelism $(P S I Z E)=x 16$ | - | 1.5 | 2.6 |  |
|  |  | Program/erase parallelism $($ PSIZE $)=\times 32$ | - | 1 | 2 |  |
| $\mathrm{t}_{\text {ME }}$ | Mass erase time | Program/erase parallelism (PSIZE) $=x 8$ | - | 16 | 32 | s |
|  |  | Program/erase parallelism $($ PSIZE $)=x 16$ | - | 11 | 22 |  |
|  |  | Program/erase parallelism $($ PSIZE $)=\times 32$ | - | 8 | 16 |  |

Table 58. Flash memory programming (dual bank configuration nDBANK=0) (continued)

| Symbol | Parameter | Conditions | Min ${ }^{(1)}$ | Typ | Max ${ }^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $t_{\text {bE }}$ | Bank erase time | Program/erase parallelism (PSIZE) $=\mathrm{x} 8$ | - | 16 | 32 | s |
|  |  | Program/erase parallelism (PSIZE) $=x 16$ | - | 11 | 22 |  |
|  |  | Program/erase parallelism (PSIZE) $=\times 32$ | - | 8 | 16 |  |
| $V_{\text {prog }}$ | Programming voltage | 32-bit program operation | 2.7 | - | 3 | V |
|  |  | 16-bit program operation | 2.1 | - | 3.6 | V |
|  |  | 8-bit program operation | 1.7 | - | 3.6 | V |

1. Guaranteed by characterization results.
2. The maximum programming time is measured after 100 K erase operations.

Table 59. Flash memory programming with $\mathrm{V}_{\mathrm{PP}}$

| Symbol | Parameter | Conditions | Min ${ }^{(1)}$ | Typ | Max ${ }^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {prog }}$ | Double word programming | $\begin{gathered} \mathrm{T}_{\mathrm{A}}=0 \text { to }+40^{\circ} \mathrm{C} \\ \mathrm{~V}_{\mathrm{DD}}=3.3 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{PP}}=8.5 \mathrm{~V} \end{gathered}$ | - | 16 | $100^{(2)}$ | $\mu \mathrm{s}$ |
| $t_{\text {ERASE32KB }}$ | Sector (32 KB) erase time |  | - | 180 | - | ms |
| terasE128KB | Sector ( 128 KB ) erase time |  | - | 450 | - |  |
| terase 256 KB | Sector (256 KB) erase time |  | - | 900 | - |  |
| $\mathrm{t}_{\text {ME }}$ | Mass erase time |  | - | 6.9 | - | s |
| $\mathrm{V}_{\text {prog }}$ | Programming voltage | - | 2.7 | - | 3.6 | V |
| $V_{P P}$ | $\mathrm{V}_{\mathrm{PP}}$ voltage range | - | 7 | - | 9 | V |
| IPP | Minimum current sunk on the $V_{\text {PP }}$ pin | - | 10 | - | - | mA |
| $\mathrm{t}_{\text {VPP }}{ }^{(3)}$ | Cumulative time during which $V_{\mathrm{Pp}}$ is applied | - | - | - | 1 | hour |

1. Guaranteed by design.
2. The maximum programming time is measured after 100 K erase operations.
3. $\mathrm{V}_{\mathrm{PP}}$ should only be connected during programming/erasing.

Table 60. Flash memory endurance and data retention

| Symbol | Parameter | Conditions | Value | Unit |
| :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min ${ }^{(1)}$ |  |
| $\mathrm{N}_{\text {END }}$ | Endurance | $\begin{aligned} & \mathrm{T}_{\mathrm{A}}=-40 \text { to }+85^{\circ} \mathrm{C}(6 \text { suffix versions }) \\ & \left.\mathrm{T}_{\mathrm{A}}=-40 \text { to }+105^{\circ} \mathrm{C} \text { (7 suffix versions }\right) \end{aligned}$ | 10 | kcycles |
| $\mathrm{t}_{\text {RET }}$ | Data retention | $1 \mathrm{kcycle}^{(2)}$ at $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ | 30 | Years |
|  |  | $1 \mathrm{kcycle}^{(2)}$ at $\mathrm{T}_{\mathrm{A}}=105^{\circ} \mathrm{C}$ | 10 |  |
|  |  | 10 ccycles $^{(2)}$ at $\mathrm{T}_{\mathrm{A}}=55^{\circ} \mathrm{C}$ | 20 |  |

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

### 5.3.17 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

## Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A burst of fast transient voltage (positive and negative) is applied to $V_{D D}$ and $V_{S S}$ through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.
A device reset allows normal operations to be resumed.
The test results are given in Table 61. They are based on the EMS levels and classes defined in application note AN1709.

Table 61. EMS characteristics

| Symbol | Parameter | Conditions | Level <br> Class |
| :--- | :--- | :--- | :---: |
| $\mathrm{V}_{\text {FESD }}$ | Voltage limits to be applied on any $\mathrm{I} / \mathrm{O}$ pin to <br> induce a functional disturbance | $\mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}, \mathrm{f}_{\mathrm{HCLK}}=$ <br> 216 MHz, conforms to IEC $61000-$ <br> $4-2$ | 2 B |
| $\mathrm{~V}_{\mathrm{FTB}}$ | Fast transient voltage burst limits to be <br> applied through 100 pF on $\mathrm{V}_{\mathrm{DD}}$ and $\mathrm{V}_{\mathrm{SS}}$ <br> pins to induce a functional disturbance | $\mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}, \mathrm{f}_{\mathrm{HCLK}}=$ <br> 168 MHz, conforms to $\mathrm{IEC} 61000-$ <br> $4-2$ | 5 A |

As a consequence, it is recommended to add a serial resistor ( $1 \mathrm{k} \Omega$ ) located as close as possible to the MCU to the pins exposed to noise (connected to tracks longer than 50 mm on PCB).

## Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.
Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

## Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)


## Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

## Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 62. EMI characteristics

| Symbol | Parameter | Conditions | Monitored frequency band | Max vs. [ $\mathrm{f}_{\mathrm{HSE}} / \mathrm{f}_{\mathrm{CPU}}$ ] | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | 8/200 MHz |  |
| $\mathrm{S}_{\text {EMI }}$ | Peak level | $\mathrm{V}_{\mathrm{DD}}=3.6 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, TFBGA216 package, conforming to IEC61967-2 ART/L1-cache ON, over-drive ON, all peripheral clocks enabled, clock dithering disabled. | 0.1 to 30 MHz | 5 | $\mathrm{dB} \mu \mathrm{V}$ |
|  |  |  | 30 to 130 MHz | 10 |  |
|  |  |  | 130 MHz to 1 GHz | 18 |  |
|  |  |  | 1 GHz to 2 GHz | 10 |  |
|  |  |  | EMI Level | 3.5 | - |
|  |  |  | 0.1 to 30 MHz | 2 |  |
|  |  | $V_{D D}=3.6 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, TFBGA216 package, conforming to IEC61967-2 ART/L1-cache ON, | 30 to 130 MHz | 9 |  |
|  |  | over-drive ON, all peripheral clocks enabled, | 130 MHz to 1 GHz | 14 |  |
|  |  |  | 1 GHz to 2 GHz | 9 |  |
|  |  |  | EMI Level | 3 | - |

### 5.3.18 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

## Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts $\times$ ( $n+1$ ) supply pins). This test conforms to the ANSI/ESDA/JEDEC JS-001-2012 and ANSI/ESD S5.3.1-2009 standards.

Table 63. ESD absolute maximum ratings

| Symbol | Ratings | Conditions | Class | $\begin{aligned} & \text { Maximum } \\ & \text { value } \end{aligned}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {ESD }}$ (HBM) | Electrostatic discharge voltage (human body model) | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ conforming to ANSI/ESDA/JEDEC JS-001-2012 | 2 | 2000 | V |
| $\mathrm{V}_{\text {ESD (CDM) }}$ | Electrostatic discharge voltage (charge device model) | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ conforming to ANSI/ESD S5.3.12009, all packages except TFBGA100 | 3 | 250 |  |
|  |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ conforming to ANSI/ESD S5.3.12009, TFBGA100 package | 4 | 500 |  |

1. Guaranteed by characterization results.

## Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.
Table 64. Electrical sensitivities

| Symbol | Parameter | Conditions | Class |
| :---: | :--- | :--- | :---: |
| LU | Static latch-up class | $\mathrm{T}_{\mathrm{A}}=+105^{\circ} \mathrm{C}$ conforming to JESD78A | II level A |

### 5.3.19 I/O current injection characteristics

As a general rule, a current injection to the I/O pins, due to external voltage below $\mathrm{V}_{\text {SS }}$ or above $\mathrm{V}_{\mathrm{DD}}$ (for standard, 3 V -capable I/O pins) should be avoided during the normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when an abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during the device characterization.

## Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $5 \mu \mathrm{~A} /+0 \mu \mathrm{~A}$ range), or other functional failure (for example reset, oscillator frequency deviation).

A negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.
The test results are given in Table 65.

Table 65. I/O current injection susceptibility

| Symbol | Description | Functional susceptibility |  | Unit |
| :---: | :---: | :---: | :---: | :---: |
|  |  | Negative injection | Positive injection |  |
| $\mathrm{I}_{\text {IN }}$ | Injected current on BOOTO, DSI_DOP, DSI_DON, DSI_D1P, DSI_D1N, DSI_CKP, DSI_CKN pin | -0 | 0 | mA |
|  | Injected current on NRST pin | -0 | $N A^{(1)}$ |  |
|  | Injected current on PC0, PC2, PH1_OSCOUT pins | -0 | $N A^{(1)}$ |  |
|  | Injected current on any other FT pin | -5 | $N A^{(1)}$ |  |
|  | Injected current on any other pins | - 5 | +5 |  |

1. Injection is not possible.

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

### 5.3.20 I/O port characteristics

## General input/output characteristics

Unless otherwise specified, the parameters given in Table 66: I/O static characteristics are derived from tests performed under the conditions summarized in Table 18. All I/Os are CMOS and TTL compliant.

Table 66. I/O static characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {IL }}$ | FT, TTa and NRST I/O input low level voltage | $1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$ | - | - | $\frac{0.35 \mathrm{~V}_{\mathrm{DD}}-0.04{ }^{(1)}}{0.3 \mathrm{~V}_{\mathrm{DD}}{ }^{(2)}}$ | V |
|  | BOOT I/O input low level voltage | $\begin{gathered} 1.75 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V},- \\ 40^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 105^{\circ} \mathrm{C} \end{gathered}$ | - | - | $0.1 \mathrm{~V}_{\mathrm{DD}}+0.1^{(1)}$ |  |
|  |  | $\begin{gathered} 1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}, \\ 0^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 105^{\circ} \mathrm{C} \end{gathered}$ | - | - |  |  |
| $\mathrm{V}_{\mathrm{IH}}$ | FT, TTa and NRST I/O input high level voltage ${ }^{(5)}$ | $1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$ | $0.45 \mathrm{~V}_{\mathrm{DD}}+0.3^{(1)}$ | - | - | V |
|  |  |  | $0.7 \mathrm{~V}_{\mathrm{DD}}{ }^{(2)}$ |  |  |  |
|  | BOOT I/O input high level voltage | $\begin{gathered} 1.75 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V},- \\ 40^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 105^{\circ} \mathrm{C} \end{gathered}$ | $0.17 \mathrm{~V}_{\mathrm{DD}}+0.7^{(1)}$ | - | - |  |
|  |  | $\begin{gathered} 1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}, \\ 0^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 105^{\circ} \mathrm{C} \end{gathered}$ |  |  |  |  |
| $\mathrm{V}_{\mathrm{HYS}}$ | FT, TTa and NRST I/O input hysteresis | $1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$ | $10 \% \mathrm{~V}_{\mathrm{DD}}{ }^{(3)}$ | - | - | V |
|  | BOOT I/O input hysteresis | $\begin{gathered} 1.75 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V},- \\ 40^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 105^{\circ} \mathrm{C} \end{gathered}$ | 0.1 | - | - |  |
|  |  | $\begin{gathered} 1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}, \\ 0^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 105^{\circ} \mathrm{C} \end{gathered}$ |  |  |  |  |

Table 66. I/O static characteristics (continued)

| Symbol | Parameter |  | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{lkg}}$ | I/O input leakage current ${ }^{(4)}$ |  | $\mathrm{V}_{\text {SS }} \leq \mathrm{V}_{\text {IN }} \leq \mathrm{V}_{\mathrm{DD}}$ | - | - | $\pm 1$ | $\mu \mathrm{A}$ |
|  | I/O FT input leakage current (5) |  | $\mathrm{V}_{\mathrm{IN}}=5 \mathrm{~V}$ | - | - | 3 |  |
| RPU | Weak pull-up equivalent resistor ${ }^{(6)}$ | All pins except for PA10/PB12 (OTG_FS_I D,OTG_HS_ ID) | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{SS}}$ | 30 | 40 | 50 | k $\Omega$ |
|  |  | PA10/PB12 (OTG_FS_I D,OTG_HS_ ID) |  | 7 | 10 | 14 |  |
| $\mathrm{R}_{\mathrm{PD}}$ | Weak pulldown equivalent resistor ${ }^{(7)}$ | All pins except for PA10/PB12 (OTG_FS_I D,OTG_HS_ ID) | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\mathrm{DD}}$ | 30 | 40 | 50 |  |
|  |  | PA10/PB12 (OTG_FS_I D,OTG_HS_ ID) |  | 7 | 10 | 14 |  |
| $\mathrm{C}_{10}{ }^{(8)}$ | I/O pin capacitance |  | - | - | 5 | - | pF |

1. Guaranteed by design.
2. Tested in production.
3. With a minimum of 200 mV .
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to Table 65: I/O current injection susceptibility
5. To sustain a voltage higher than VDD +0.3 V , the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins.Refer to Table 65: I/O current injection susceptibility
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum ( $\sim 10 \%$ order).
7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum ( $\sim 10 \%$ order).
8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in Figure 39.

Figure 39. FT I/O input characteristics


## Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to $\pm 8 \mathrm{~mA}$, and sink or source up to $\pm 20 \mathrm{~mA}$ (with a relaxed $\mathrm{V}_{\mathrm{OL}} / \mathrm{V}_{\mathrm{OH}}$ ) except PC13, PC14, PC15 and PI8 which can sink or source up to $\pm 3 \mathrm{~mA}$. When using the PC13 to PC15 and PI8 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF .

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in Section 5.2. In particular:

- The sum of the currents sourced by all the $I / O s$ on $V_{D D}$, plus the maximum Run consumption of the MCU sourced on $V_{D D}$, cannot exceed the absolute maximum rating $\Sigma \mathrm{I}_{\text {VDD }}$ (see Table 16).
- The sum of the currents sunk by all the $I / O s$ on $V_{S S}$ plus the maximum Run consumption of the MCU sunk on $\mathrm{V}_{\mathrm{SS}}$ cannot exceed the absolute maximum rating $\Sigma \mathrm{l}_{\text {VSS }}$ (see Table 16).


## Output voltage levels

Unless otherwise specified, the parameters given in Table 67 are derived from tests performed under ambient temperature and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18. All I/Os are CMOS and TTL compliant.

Table 67. Output voltage characteristics

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{OL}}{ }^{(1)}$ | Output low level voltage for an I/O pin | $\begin{gathered} \text { CMOS port }^{(2)} \\ \mathrm{I}_{\mathrm{IO}}=+8 \mathrm{~mA} \\ 2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | - | 0.4 |  |
| $\mathrm{V}_{\mathrm{OH}}{ }^{(3)}$ | Output high level voltage for an I/O pin except PC14 | CMOS port ${ }^{(2)}$ $\begin{gathered} \mathrm{I}_{\mathrm{IO}}=-8 \mathrm{~mA} \\ 2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | $V_{D D}-0.4$ | - | V |
| $\mathrm{V}_{\mathrm{OH}}{ }^{(3)}$ | Output high level voltage for PC14 | CMOS port ${ }^{(2)}$ $\begin{gathered} \mathrm{I}_{\mathrm{IO}}=-2 \mathrm{~mA} \\ 2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | $V_{D D}-0.4$ | - |  |
| $V_{O L}{ }^{(1)}$ | Output low level voltage for an I/O pin | $\begin{gathered} \mathrm{TTL}^{\text {port }}{ }^{(2)} \\ \mathrm{I}_{\mathrm{IO}}=+8 \mathrm{~mA} \\ 2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \\ \hline \end{gathered}$ | - | 0.4 | V |
| $\mathrm{V}_{\mathrm{OH}}{ }^{(3)}$ | Output high level voltage for an I/O pin except PC14 | $\begin{gathered} \text { TTL port }^{(2)} \\ \mathrm{I}_{\mathrm{O}}=-8 \mathrm{~mA} \\ 2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | 2.4 | - | $\checkmark$ |
| $\mathrm{V}_{\mathrm{OL}}{ }^{(1)}$ | Output low level voltage for an I/O pin | $\begin{gathered} \mathrm{l}_{\mathrm{O}}=+20 \mathrm{~mA} \\ 2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | - | $1.3{ }^{(4)}$ | V |
| $\mathrm{V}_{\mathrm{OH}}{ }^{(3)}$ | Output high level voltage for an I/O pin except PC14 | $\begin{gathered} \mathrm{I}_{\mathrm{OO}}=-20 \mathrm{~mA} \\ 2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | $V_{D D}-1.3^{(4)}$ | - |  |
| $\mathrm{V}_{\mathrm{OL}}{ }^{(1)}$ | Output low level voltage for an I/O pin | $\begin{gathered} \mathrm{I}_{\mathrm{IO}}=+6 \mathrm{~mA} \\ 1.8 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | - | $0.4{ }^{(4)}$ | V |
| $\mathrm{V}_{\mathrm{OH}}{ }^{(3)}$ | Output high level voltage for an I/O pin except PC14 | $\begin{gathered} \mathrm{I}_{\mathrm{IO}}=-6 \mathrm{~mA} \\ 1.8 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | $V_{D D}-0.4^{(4)}$ | - |  |
| $\mathrm{V}_{\mathrm{OL}}{ }^{(1)}$ | Output low level voltage for an I/O pin | $\begin{gathered} \mathrm{I}_{\mathrm{IO}}=+4 \mathrm{~mA} \\ 1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | - | $0.4{ }^{(5)}$ |  |
| $\mathrm{V}_{\mathrm{OH}}{ }^{(3)}$ | Output high level voltage for an I/O pin except PC14 | $\begin{gathered} \mathrm{I}_{\mathrm{O}}=-4 \mathrm{~mA} \\ 1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | $V_{D D}-0.4^{(5)}$ | - | V |
| $\mathrm{V}_{\mathrm{OH}}{ }^{(3)}$ | Output high level voltage for PC14 | $\begin{gathered} \mathrm{I}_{\mathrm{IO}}=-1 \mathrm{~mA} \\ 1.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V} \end{gathered}$ | $V_{D D}-0.4^{(5)}$ | - |  |

1. The $\mathrm{I}_{\mathrm{O}}$ current sunk by the device must always respect the absolute maximum rating specified in Table 16. and the sum of $\mathrm{I}_{\mathrm{IO}}$ (I/O ports and control pins) must not exceed $\mathrm{I}_{\text {VSs }}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The $I_{10}$ current sourced by the device must always respect the absolute maximum rating specified in Table 16 and the sum of $\mathrm{I}_{\mathrm{IO}}$ (I/O ports and control pins) must not exceed $\mathrm{I}_{\text {VDD }}$.
4. Based on characterization data.
5. Guaranteed by design.

## Input/output AC characteristics

The definition and values of input/output AC characteristics are given in Figure 40 and Table 68, respectively.

Unless otherwise specified, the parameters given in Table 68 are derived from tests performed under the ambient temperature and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18.

Table 68. I/O AC characteristics ${ }^{(1)(2)}$

| $\begin{array}{\|l\|} \hline \text { OSPEEDRy } \\ {[1: 0] \text { bit }} \\ \text { value }^{(1)} \end{array}$ | Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 00 | $\mathrm{f}_{\max (10) \text { out }}$ | Maximum frequency ${ }^{(3)}$ | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 4 | MHz |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 2 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 8 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.8 \mathrm{~V}$ | - | - | 4 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 3 |  |
|  | $\mathrm{t}_{\mathrm{f}(\mathrm{IO}) \text { out }}{ }^{\prime}$ $\mathrm{t}_{\mathrm{r}(\mathrm{IO}) \text { out }}$ | Output high to low level fall time and output low to high level rise time | $\begin{aligned} & C_{L}=50 \mathrm{pF}, \mathrm{~V}_{\mathrm{DD}}=1.7 \mathrm{~V} \text { to } \\ & 3.6 \mathrm{~V} \end{aligned}$ | - | - | 100 | ns |
| 01 | $\mathrm{f}_{\max (10) \text { out }}$ | Maximum frequency ${ }^{(3)}$ | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 25 | MHz |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.8 \mathrm{~V}$ | - | - | 12.5 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 10 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 50 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.8 \mathrm{~V}$ | - | - | 20 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 12.5 |  |
|  | $\mathrm{t}_{\mathrm{f}(\mathrm{IO}) \text { out }}{ }^{\prime}$ <br> $\mathrm{t}_{\mathrm{r}(\mathrm{IO}) \text { out }}$ | Output high to low level fall time and output low to high level rise time | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 10 | ns |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 6 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 20 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 10 |  |
| 10 | $\mathrm{f}_{\max (\mathrm{IO}) \text { out }}$ | Maximum frequency ${ }^{(3)}$ | $\mathrm{C}_{\mathrm{L}}=40 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | $50^{(4)}$ | MHz |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | $100^{(4)}$ |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=40 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 25 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.8 \mathrm{~V}$ | - | - | 50 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 42.5 |  |
|  | $\mathrm{t}_{\mathrm{f}} \mathrm{IO}$ )out ${ }^{\prime}$ <br> $\mathrm{t}_{\mathrm{r}(\mathrm{IO}) \text { out }}$ | Output high to low level fall time and output low to high level rise time | $\mathrm{C}_{\mathrm{L}}=40 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 6 | ns |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 4 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=40 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 10 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 6 |  |

Table 68. I/O AC characteristics ${ }^{(1)(2)}$ (continued)

| $\begin{aligned} & \text { OSPEEDRy } \\ & \text { [1:0] bit } \\ & \text { value }{ }^{(1)} \end{aligned}$ | Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 11 | $\mathrm{f}_{\max (\mathrm{IO}) \text { out }}$ | Maximum frequency ${ }^{(3)}$ | $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | $100^{(4)}$ | MHz |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.8 \mathrm{~V}$ | - | - | 50 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 42.5 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | $180^{(4)}$ |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.8 \mathrm{~V}$ | - | - | 100 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 72.5 |  |
|  | $\mathrm{t}_{\mathrm{f}(\mathrm{IO}) \text { out }}{ }^{\prime}$ <br> $\mathrm{t}_{\mathrm{r}(\mathrm{IO}) \text { out }}$ | Output high to low level fall time and output low to high level rise time | $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 4 | ns |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.8 \mathrm{~V}$ | - | - | 6 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 7 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 2.7 \mathrm{~V}$ | - | - | 2.5 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.8 \mathrm{~V}$ | - | - | 3.5 |  |
|  |  |  | $\mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}, \mathrm{V}_{\mathrm{DD}} \geq 1.7 \mathrm{~V}$ | - | - | 4 |  |
| - | tEXTIpw | Pulse width of external signals detected by the EXTI controller | - | 10 | - | - | ns |

1. Guaranteed by design.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F76xxx and STM32F77xxx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in Figure 40.
4. For maximum frequencies above 50 MHz and $\mathrm{V}_{\mathrm{DD}}>2.4 \mathrm{~V}$, the compensation cell should be used.

Figure 40. I/O AC characteristics definition


### 5.3.21 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, $\mathrm{R}_{\mathrm{PU}}$ (see Table 66: I/O static characteristics).
Unless otherwise specified, the parameters given in Table 69 are derived from tests performed under the ambient temperature and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18.

Table 69. NRST pin characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{R}_{\mathrm{PU}}$ | Weak pull-up equivalent resistor ${ }^{(1)}$ | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\mathrm{SS}}$ | 30 | 40 | 50 | $\mathrm{k} \Omega$ |
| $\mathrm{V}_{\mathrm{F}(\mathrm{NRST})^{(2)}}$ | NRST Input filtered pulse | - | - | - | 100 | ns |
| $\mathrm{~V}_{\text {NF(NRST) }}{ }^{(2)}$ | NRST Input not filtered pulse | $\mathrm{V}_{\mathrm{DD}}>2.7 \mathrm{~V}$ | 300 | - | - | ns |
| $\mathrm{T}_{\text {NRST_OUT }}$ | Generated reset pulse duration | Internal Reset source | 20 | - | - | $\mu \mathrm{s}$ |

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum ( $\sim 10 \%$ order).
2. Guaranteed by design.

Figure 41. Recommended NRST pin protection


1. The reset network protects the device against parasitic resets. 0.1 uF capacitor must be placed as close as possible to the chip.
2. The user must ensure that the level on the NRST pin can go below the $\mathrm{V}_{\text {IL(NRST) }}$ max level specified in Table 69. Otherwise the reset is not taken into account by the device.

### 5.3.22 TIM timer characteristics

The parameters given in Table 70 are guaranteed by design.
Refer to Section 5.3.20: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 70. TIMx characteristics ${ }^{(1)(2)}$

| Symbol | Parameter | Conditions ${ }^{(3)}$ | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {res(TIM) }}$ | Timer resolution time | AHB/APBx prescaler=1 or 2 or $4, \mathrm{f}_{\text {TIMxCLK }}=$ 216 MHz | 1 | - | $\mathrm{t}_{\text {TIMxCLK }}$ |
|  |  | AHB/APBx prescaler>4, $\mathrm{f}_{\text {TIM } \times C L K}=$ 100 MHz | 1 | - | $\mathrm{t}_{\text {TIM } \times \text { CLK }}$ |
| $\mathrm{f}_{\mathrm{EXT}}$ | Timer external clock frequency on CH 1 to CH 4 | $\mathrm{f}_{\text {TIMxCLK }}=216 \mathrm{MHz}$ | 0 | $\mathrm{f}_{\text {TIM } \times C L K} / 2$ | MHz |
| $\mathrm{Res}_{\text {TIM }}$ | Timer resolution |  | - | 16/32 | bit |
| $\mathrm{t}_{\text {MAX_COUNT }}$ | Maximum possible count with 32-bit counter | - | - | $\begin{gathered} 65536 \times \\ 65536 \end{gathered}$ | $\mathrm{t}_{\text {TIM } \times \text { CLK }}$ |

1. TIMx is used as a general term to refer to the TIM1 to TIM12 timers.
2. Guaranteed by design.
3. The maximum timer frequency on APB1 or APB2 is up to 216 MHz , by setting the TIMPRE bit in the RCC DCKCFGR register, if APBx prescaler is 1 or 2 or 4 , then TIMxCLK = HCLK, otherwise TIMxCLK = $4 x$ PC̄LKx.

### 5.3.23 RTC characteristics

Table 71. RTC characteristics

| Symbol | Parameter | Conditions | Min | Max |
| :---: | :---: | :---: | :---: | :---: |
| - | $f_{\text {PCLK1 }} /$ RTCCLK frequency ratio | Any read/write operation <br> from/to an RTC register | 4 | - |

### 5.3.24 12-bit ADC characteristics

Unless otherwise specified, the parameters given in Table 72 are derived from tests performed under the ambient temperature, $\mathrm{f}_{\text {PCLK2 }}$ frequency and $\mathrm{V}_{\text {DDA }}$ supply voltage conditions summarized in Table 18.

Table 72. ADC characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {DDA }}$ | Power supply | $\mathrm{V}_{\mathrm{DDA}}-\mathrm{V}_{\text {REF+ }}<1.2 \mathrm{~V}$ | $1.7{ }^{(1)}$ | - | 3.6 | V |
| $\mathrm{V}_{\text {REF+ }}$ | Positive reference voltage |  | $1.7{ }^{(1)}$ | - | $\mathrm{V}_{\text {DDA }}$ | V |
| $\mathrm{f}_{\text {ADC }}$ | ADC clock frequency | $\mathrm{V}_{\mathrm{DDA}}=1.7^{(1)}$ to 2.4 V | 0.6 | 15 | 18 | MHz |
|  |  | $\mathrm{V}_{\mathrm{DDA}}=2.4$ to 3.6 V | 0.6 | 30 | 36 | MHz |

Table 72. ADC characteristics (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {TRIG }}{ }^{(2)}$ | External trigger frequency | $\begin{aligned} & \hline \mathrm{f}_{\mathrm{ADC}}=30 \mathrm{MHz}, \\ & \text { 12-bit resolution } \end{aligned}$ | - | - | 1764 | kHz |
|  |  | - | - | - | 17 | $1 / \mathrm{f}_{\text {ADC }}$ |
| $\mathrm{V}_{\text {AIN }}$ | Conversion voltage range ${ }^{(3)}$ | - | $\begin{gathered} 0 \\ \left(V_{S S A} \text { or } V_{R E F-}\right. \\ \text { tied to ground }) \end{gathered}$ | - | $\mathrm{V}_{\text {REF }+}$ | V |
| $\mathrm{R}_{\text {AIN }}{ }^{(2)}$ | External input impedance | See Equation 1 for details | - | - | 50 | k $\Omega$ |
| $\mathrm{R}_{\text {ADC }}{ }^{(2)(4)}$ | Sampling switch resistance | - | 1.5 | - | 6 | k $\Omega$ |
| $\mathrm{C}_{\text {ADC }}{ }^{(2)}$ | Internal sample and hold capacitor | - | - | 4 | 7 | pF |
| $\mathrm{t}_{\text {at }}{ }^{(2)}$ | Injection trigger conversion latency | $\mathrm{f}_{\text {ADC }}=30 \mathrm{MHz}$ | - | - | 0.100 | $\mu \mathrm{s}$ |
|  |  | - | - | - | $3^{(5)}$ | $1 / \mathrm{f}_{\text {ADC }}$ |
| $t_{\text {latr }}{ }^{(2)}$ | Regular trigger conversion latency | $\mathrm{f}_{\text {ADC }}=30 \mathrm{MHz}$ | - | - | 0.067 | $\mu \mathrm{s}$ |
|  |  | - | - | - | $2^{(5)}$ | $1 / \mathrm{f}_{\text {ADC }}$ |
| $\mathrm{t}_{s}{ }^{(2)}$ | Sampling time | $\mathrm{f}_{\text {ADC }}=30 \mathrm{MHz}$ | 0.100 | - | 16 | $\mu \mathrm{s}$ |
|  |  | - | 3 | - | 480 | $1 / f_{\text {ADC }}$ |
| $\mathrm{t}_{\text {STAB }}{ }^{(2)}$ | Power-up time | - | - | 2 | 3 | $\mu \mathrm{s}$ |
| $\mathrm{t}_{\mathrm{CONV}}{ }^{(2)}$ | Total conversion time (including sampling time) | $\begin{aligned} & \hline \mathrm{f}_{\mathrm{ADC}}=30 \mathrm{MHz} \\ & \text { 12-bit resolution } \end{aligned}$ | 0.50 | - | 16.40 | $\mu \mathrm{s}$ |
|  |  | $\begin{aligned} & \mathrm{f}_{\mathrm{ADC}}=30 \mathrm{MHz} \\ & \text { 10-bit resolution } \end{aligned}$ | 0.43 | - | 16.34 | $\mu \mathrm{s}$ |
|  |  | $\begin{aligned} & \mathrm{f}_{\mathrm{ADC}}=30 \mathrm{MHz} \\ & \text { 8-bit resolution } \end{aligned}$ | 0.37 | - | 16.27 | $\mu \mathrm{s}$ |
|  |  | $\begin{aligned} & \mathrm{f}_{\mathrm{ADC}}=30 \mathrm{MHz} \\ & \text { 6-bit resolution } \end{aligned}$ | 0.30 | - | 16.20 | $\mu \mathrm{s}$ |
|  |  | 9 to 492 ( $\mathrm{t}_{\mathrm{S}}$ for sampling +n -bit resolution for successive approximation) |  |  |  | $1 / \mathrm{f}_{\mathrm{ADC}}$ |
| $\mathrm{f}_{S}{ }^{(2)}$ | Sampling rate <br> ( $\mathrm{f}_{\mathrm{ADC}}=36 \mathrm{MHz}$, and $\mathrm{t}_{\mathrm{S}}=3$ ADC cycles) | 12-bit resolution Single ADC | - | - | 2.4 | Msps |
|  |  | 12-bit resolution Interleave Dual ADC mode | - | - | 4.5 | Msps |
|  |  | 12-bit resolution Interleave Triple ADC mode | - | - | 7.2 | Msps |

Table 72. ADC characteristics (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :--- | :--- | :---: | :---: | :---: | :---: | :---: |
| IVREF $^{(2)}$ | ADC V <br> REF DC current <br> consumption in conversion <br> mode | - | - | 300 | 500 | $\mu \mathrm{~A}$ |
| IVDDA $^{(2)}$ | ADC V <br> DDA <br> consumption in current <br> mode | - | - | 1.6 | 1.8 | mA |

1. $V_{\text {DDA }}$ minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to Section 2.18.2: Internal reset OFF).
2. Guaranteed by characterization results.
3. $\mathrm{V}_{\text {REF }}$ is internally connected to $\mathrm{V}_{\mathrm{DDA}}$ and $\mathrm{V}_{\text {REF- }}$ is internally connected to $\mathrm{V}_{\mathrm{SSA}}$.
4. $R_{A D C}$ maximum value is given for $V_{D D}=1.7 \mathrm{~V}$, and minimum value for $V_{D D}=3.3 \mathrm{~V}$.
5. For external triggers, a delay of $1 / \mathrm{f}_{\text {PCLK2 }}$ must be added to the latency specified in Table 72.

Equation 1: $\mathbf{R}_{\text {AIN }} \max$ formula

$$
\mathrm{R}_{\mathrm{AIN}}=\frac{(\mathrm{k}-0.5)}{\mathrm{f}_{\mathrm{ADC}} \times \mathrm{C}_{\mathrm{ADC}} \times \ln \left(2^{\mathrm{N}+2}\right)}-\mathrm{R}_{\mathrm{ADC}}
$$

The formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below $1 / 4$ of LSB. $\mathrm{N}=12$ (from 12-bit resolution) and k is the number of sampling periods defined in the ADC_SMPR1 register.

Table 73. ADC static accuracy at $\mathrm{f}_{\text {ADC }}=18 \mathrm{MHz}$

| Symbol | Parameter | Test conditions | Typ | Max ${ }^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| ET | Total unadjusted error | $\begin{gathered} \mathrm{f}_{\mathrm{ADC}}=18 \mathrm{MHz} \\ \mathrm{~V}_{\mathrm{DDA}}=1.7 \text { to } 3.6 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{REF}}=1.7 \text { to } 3.6 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{DDA}}-\mathrm{V}_{\mathrm{REF}}<1.2 \mathrm{~V} \end{gathered}$ | $\pm 3$ | $\pm 4$ | LSB |
| EO | Offset error |  | $\pm 2$ | $\pm 3$ |  |
| EG | Gain error |  | $\pm 1$ | $\pm 3$ |  |
| ED | Differential linearity error |  | $\pm 1$ | $\pm 2$ |  |
| EL | Integral linearity error |  | $\pm 2$ | $\pm 3$ |  |

1. Guaranteed by characterization results.

Table 74. ADC static accuracy at $\mathrm{f}_{\mathrm{ADC}}=30 \mathrm{MHz}$

| Symbol | Parameter | Test conditions | Typ | Max ${ }^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| ET | Total unadjusted error | $\begin{aligned} & \mathrm{f}_{\mathrm{ADC}}=30 \mathrm{MHz}, \\ & \mathrm{R}_{\mathrm{AIN}}<10 \mathrm{k} \Omega \\ & \mathrm{~V}_{\mathrm{DDA}}=2.4 \text { to } 3.6 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{REF}}=1.7 \text { to } 3.6 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{DDA}}-\mathrm{V}_{\mathrm{REF}}<1.2 \mathrm{~V} \end{aligned}$ | $\pm 2$ | $\pm 5$ | LSB |
| EO | Offset error |  | $\pm 1.5$ | $\pm 2.5$ |  |
| EG | Gain error |  | $\pm 1.5$ | $\pm 4$ |  |
| ED | Differential linearity error |  | $\pm 1$ | $\pm 2$ |  |
| EL | Integral linearity error |  | $\pm 1.5$ | $\pm 3$ |  |

1. Guaranteed by characterization results.

Table 75. ADC static accuracy at $\mathrm{f}_{\text {ADC }}=36 \mathrm{MHz}$

| Symbol | Parameter | Test conditions | Typ | Max ${ }^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| ET | Total unadjusted error | $\begin{gathered} \mathrm{f}_{\mathrm{ADC}}=36 \mathrm{MHz}, \\ \mathrm{~V}_{\mathrm{DDA}}=2.4 \text { to } 3.6 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{REF}}=1.7 \text { to } 3.6 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{DDA}}-\mathrm{V}_{\mathrm{REF}}<1.2 \mathrm{~V} \end{gathered}$ | $\pm 4$ | $\pm 7$ | LSB |
| EO | Offset error |  | $\pm 2$ | $\pm 3$ |  |
| EG | Gain error |  | $\pm 3$ | $\pm 6$ |  |
| ED | Differential linearity error |  | $\pm 2$ | $\pm 3$ |  |
| EL | Integral linearity error |  | $\pm 3$ | $\pm 6$ |  |

1. Guaranteed by characterization results.

Table 76. ADC dynamic accuracy at $\mathrm{f}_{\text {ADC }}=18 \mathrm{MHz}$ - limited test conditions ${ }^{(1)}$

| Symbol | Parameter | Test conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| ENOB | Effective number of bits | $\begin{gathered} \mathrm{f}_{\mathrm{ADC}}=18 \mathrm{MHz} \\ \mathrm{~V}_{\mathrm{DDA}}=\mathrm{V}_{\text {REF+ }}=1.7 \mathrm{~V} \\ \text { Input Frequency }=20 \mathrm{KHz} \\ \text { Temperature }=25^{\circ} \mathrm{C} \end{gathered}$ | 10.3 | 10.4 | - | bits |
| SINAD | Signal-to-noise and distortion ratio |  | 64 | 64.2 | - | dB |
| SNR | Signal-to-noise ratio |  | 64 | 65 | - |  |
| THD | Total harmonic distortion |  | -67 | -72 | - |  |

1. Guaranteed by characterization results.

Table 77. ADC dynamic accuracy at $\mathrm{f}_{\mathrm{ADC}}=\mathbf{3 6} \mathrm{MHz}$ - limited test conditions ${ }^{(1)}$

| Symbol | Parameter | Test conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| ENOB | Effective number of bits | $\begin{gathered} \mathrm{f}_{\mathrm{ADC}}=36 \mathrm{MHz} \\ \mathrm{~V}_{\mathrm{DDA}}=\mathrm{V}_{\mathrm{REF}}=3.3 \mathrm{~V} \\ \text { Input Frequency }=20 \mathrm{KHz} \\ \text { Temperature }=25^{\circ} \mathrm{C} \end{gathered}$ | 10.6 | 10.8 | - | bits |
| SINAD | Signal-to noise and distortion ratio |  | 66 | 67 | - | dB |
| SNR | Signal-to noise ratio |  | 64 | 68 | - |  |
| THD | Total harmonic distortion |  | - 70 | -72 | - |  |

1. Guaranteed by characterization results.

Note: $\quad$ ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
Any positive injection current within the limits specified for $\mathrm{I}_{\mathrm{INJ}(\mathrm{PIN})}$ and $\Sigma l_{\mathrm{INJ}(\mathrm{PIN})}$ in Section 5.3.20 does not affect the ADC accuracy.

Figure 42. ADC accuracy characteristics


1. See also Table 74.
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. $\mathrm{E}_{\mathrm{T}}=$ Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves. EO = Offset Error: deviation between the first actual transition and the first ideal one. EG = Gain Error: deviation between the last ideal transition and the last actual one. ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one. EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 43. Typical connection diagram using the ADC


1. Refer to Table 72 for the values of $R_{\text {AIN }}, R_{A D C}$ and $C_{A D C}$.
2. $\mathrm{C}_{\text {parasitic }}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF ). A high $\mathrm{C}_{\text {parasitic }}$ value downgrades conversion accuracy. To remedy this, $\mathrm{f}_{\mathrm{ADC}}$ should be reduced.

## General PCB design guidelines

Power supply decoupling should be performed as shown in Figure 44 or Figure 45, depending on whether $\mathrm{V}_{\text {REF }}$ is connected to $\mathrm{V}_{\text {DDA }}$ or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 44. Power supply and reference decoupling ( $\mathrm{V}_{\mathrm{REF}+}$ not connected to $\mathrm{V}_{\mathrm{DDA}}$ )


1. $V_{R E F+}$ input is available on all packages except TFBGA100 whereas the $V_{R E F-} s$ available only on UFBGA176 and TFBGA216. When $V_{\text {REF }}$ is not available, it is internally connected to $V_{\text {DDA }}$ and $V_{\text {SSA }}$.

Figure 45. Power supply and reference decoupling ( $\mathrm{V}_{\text {REF+ }}$ connected to $\mathrm{V}_{\text {DDA }}$ )


1. $V_{R E F+}$ input is available on all packages except TFBGA100 whereas the $V_{\text {REF- }} s$ available only on UFBGA176 and TFBGA216. When $V_{\text {REF }}$ - is not available, it is internally connected to $V_{\text {DDA }}$ and $V_{\text {SSA }}$.

### 5.3.25 Temperature sensor characteristics

Table 78. Temperature sensor characteristics

| Symbol | Parameter | Min | Typ | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{T}_{\mathrm{L}}{ }^{(1)}$ | $\mathrm{V}_{\text {SENSE }}$ linearity with temperature | - | $\pm 1$ | $\pm 2$ | ${ }^{\circ} \mathrm{C}$ |
| Avg_Slope $^{(1)}$ | Average slope | - | 2.5 | - | $\mathrm{mV} /{ }^{\circ} \mathrm{C}$ |
| $\mathrm{V}_{25}{ }^{(1)}$ | Voltage at $25^{\circ} \mathrm{C}$ | - | 0.76 | - | V |
| $\mathrm{t}_{\text {START }}{ }^{(2)}$ | Startup time | - | 6 | 10 | $\mu \mathrm{~s}$ |
| $\mathrm{~T}_{\text {S_temp }}{ }^{(2)}$ | ADC sampling time when reading the temperature $\left(1^{\circ} \mathrm{C}\right.$ accuracy $)$ | 10 | - | - | $\mu \mathrm{s}$ |

1. Guaranteed by characterization results.
2. Guaranteed by design.

Table 79. Temperature sensor calibration values

| Symbol | Parameter | Memory address |
| :---: | :---: | :---: |
| TS_CAL1 | TS ADC raw data acquired at temperature of $30^{\circ} \mathrm{C}, \mathrm{V}_{\text {DDA }}=3.3 \mathrm{~V}$ | $0 \times 1 \mathrm{FF} 0 \mathrm{~F} 44 \mathrm{C}-0 \times 1 \mathrm{FF} 0 \mathrm{~F} 44 \mathrm{D}$ |
| TS_CAL2 | TS ADC raw data acquired at temperature of $110^{\circ} \mathrm{C}, \mathrm{V}_{\text {DDA }}=3.3 \mathrm{~V}$ | $0 \times 1$ FF0 F44E - 0x1FF0 F44F |

### 5.3.26 $\quad V_{B A T}$ monitoring characteristics

Table 80. $\mathrm{V}_{\text {BAT }}$ monitoring characteristics

| Symbol | Parameter | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| R | Resistor bridge for $\mathrm{V}_{\mathrm{BAT}}$ | - | 50 | - | $\mathrm{K} \Omega$ |
| Q | Ratio on $\mathrm{V}_{\text {BAT }}$ measurement | - | 4 | - | - |
| $E r^{(1)}$ | Error on Q | -1 | - | +1 | \% |
| $\mathrm{T}_{\text {S_vbat }}{ }^{(2)(2)}$ | ADC sampling time when reading the $\mathrm{V}_{\text {BAT }}$ 1 mV accuracy | 5 | - | - | $\mu \mathrm{s}$ |

1. Guaranteed by design.
2. Shortest sampling time can be determined in the application by multiple iterations.

### 5.3.27 Reference voltage

The parameters given in Table 81 are derived from tests performed under ambient temperature and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18.

Table 81. internal reference voltage

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {REFINT }}$ | Internal reference voltage | $-40^{\circ} \mathrm{C}<\mathrm{T}_{\mathrm{A}}<+105^{\circ} \mathrm{C}$ | 1.18 | 1.21 | 1.24 | V |
| $\mathrm{~T}_{\text {S_vrefint }}{ }^{(1)}$ | ADC sampling time when reading the <br> internal reference voltage | - | 10 | - | - | $\mu \mathrm{s}$ |
| $\mathrm{V}_{\text {REFINT_s }}{ }^{(2)}$ | Internal reference voltage spread over the <br> temperature range | $\mathrm{V}_{\mathrm{DD}}=3 \mathrm{~V} \pm 10 \mathrm{mV}$ | - | 3 | 5 | mV |

Table 81. internal reference voltage (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{T}_{\text {Coeff }}{ }^{(2)}$ | Temperature coefficient | - | - | 30 | 50 | $\mathrm{ppm} /{ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\text {START }^{(2)}}{ }^{(2)}$ | Startup time | - | - | 6 | 10 | $\mu \mathrm{~s}$ |

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design.

Table 82. Internal reference voltage calibration values

| Symbol | Parameter | Memory address |
| :---: | :---: | :---: |
| V REFIN_CAL | Raw data acquired at temperature of $30^{\circ} \mathrm{C}_{\text {VDDA }}=3.3 \mathrm{~V}$ | $0 \times 1$ FF0 F44A - 0x1FF0 F44B |

### 5.3.28 DAC electrical characteristics

Table 83. DAC characteristics

| Symbol | Parameter |  | Min | Typ | Max | Unit | Comments |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{\text {DDA }}$ | Analog supply voltage |  | $1.7{ }^{(1)}$ | - | 3.6 | V | - |
| $V_{\text {REF+ }}$ | Reference supply voltage |  | $1.7{ }^{(1)}$ | - | 3.6 | V | $\mathrm{V}_{\text {REF+ }} \leq \mathrm{V}_{\text {DDA }}$ |
| $\mathrm{V}_{\text {SSA }}$ | Ground |  | 0 | - | 0 | V | - |
| $\mathrm{R}_{\text {LOAD }}{ }^{(2)}$ | Resistive load with buffer ON | Connected to $V_{\text {SSA }}$ <br> Connected to $V_{\text {DDA }}$ | 5 25 | - | - | $\mathrm{k} \Omega$ | - |
| $\mathrm{R}_{\mathrm{O}}{ }^{(2)}$ | Impedance output with buffer OFF |  | - | - | 15 | k $\Omega$ | When the buffer is OFF, the Minimum resistive load between DAC_OUT and $V_{S S}$ to have a $1 \%$ accuracy is $1.5 \mathrm{M} \Omega$ |
| $\mathrm{C}_{\text {LOAD }}{ }^{(2)}$ | Capacitive load |  | - | - | 50 | pF | Maximum capacitive load at DAC_OUT pin (when the buffer is ON). |
| $\underset{\min ^{(2)}}{\text { DAC_OUT }}$ | Lower DAC_OUT voltage with buffer ON |  | 0.2 | - | - | V | It gives the maximum output excursion of the DAC. <br> It corresponds to 12-bit input code |
| $\underset{\max ^{(2)}}{\text { DAC_OUT }}$ | Higher DAC_OUT voltage with buffer ON |  | - | - | $\begin{array}{\|c} \mathrm{V}_{\mathrm{DDA}}- \\ 0.2 \end{array}$ | V | ( $0 \times 0 \mathrm{EO}$ ) to $(0 \mathrm{xF} 1 \mathrm{C})$ at $\mathrm{V}_{\text {REF }+}=3.6 \mathrm{~V}$ and $(0 \times 1 \mathrm{C} 7)$ to $(0 x E 38)$ at $\mathrm{V}_{\text {REF }+}=1.7 \mathrm{~V}$ |
| $\underset{\min ^{(2)}}{\text { DAC_OUT }}$ | Lower DAC_OUT voltage with buffer OFF |  | - | 0.5 | - | mV | It gives the maximum output excursion of |
| $\underset{\max ^{(2)}}{ }$ | Higher DAC_OUT voltage with buffer OFF |  | - | - | $\begin{gathered} \mathrm{V}_{\text {REF+ }+}- \\ \text { 1LSB } \end{gathered}$ | V | the DAC. |

Table 83. DAC characteristics (continued)

| Symbol | Parameter | Min | Typ | Max | Unit | Comments |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{IVREFF}^{(4)}$ | DAC DC $V_{\text {REF }}$ current consumption in quiescent mode (Standby mode) | - | 170 | 240 | $\mu \mathrm{A}$ | With no load, worst code $(0 \times 800)$ at $\mathrm{V}_{\text {REF+ }}=3.6 \mathrm{~V}$ in terms of DC consumption on the inputs |
|  |  | - | 50 | 75 |  | With no load, worst code (0xF1C) at $\mathrm{V}_{\text {REF+ }}=3.6 \mathrm{~V}$ in terms of DC consumption on the inputs |
| $\mathrm{I}_{\text {DDA }}{ }^{(4)}$ | DAC DC $V_{\text {DDA }}$ current consumption in quiescent mode ${ }^{(3)}$ | - | 280 | 380 | $\mu \mathrm{A}$ | With no load, middle code ( $0 \times 800$ ) on the inputs |
|  |  | - | 475 | 625 | $\mu \mathrm{A}$ | With no load, worst code ( $0 x \mathrm{FF} 1 \mathrm{C}$ ) at $\mathrm{V}_{\text {REF+ }}=3.6 \mathrm{~V}$ in terms of DC consumption on the inputs |
| DNL ${ }^{(4)}$ | Differential non linearity Difference between two consecutive code-1LSB) | - | - | $\pm 0.5$ | LSB | Given for the DAC in 10-bit configuration. |
|  |  | - | - | $\pm 2$ | LSB | Given for the DAC in 12-bit configuration. |
| $\mathrm{INL}{ }^{(4)}$ | Integral non linearity (difference between measured value at Code i and the value at Code ion a line drawn between Code 0 and last Code 1023) | - | - | $\pm 1$ | LSB | Given for the DAC in 10-bit configuration. |
|  |  | - | - | $\pm 4$ | LSB | Given for the DAC in 12-bit configuration. |
| Offset ${ }^{(4)}$ | Offset error <br> (difference between measured value at Code $(0 \times 800)$ and the ideal value $=$ $\mathrm{V}_{\mathrm{REF}+} / 2$ ) | - | - | $\pm 10$ | mV | Given for the DAC in 12-bit configuration |
|  |  | - | - | $\pm 3$ | LSB | Given for the DAC in 10-bit at $\mathrm{V}_{\text {REF }+}=$ 3.6 V |
|  |  | - | - | $\pm 12$ | LSB | Given for the DAC in 12-bit at $\mathrm{V}_{\text {REF+ }}=$ 3.6 V |
| $\begin{aligned} & \text { Gain } \\ & \text { error }{ }^{(4)} \end{aligned}$ | Gain error | - | - | $\pm 0.5$ | \% | Given for the DAC in 12-bit configuration |
| $\mathrm{t}_{\text {SETTLING }}{ }^{(4)}$ | Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value $\pm 4$ LSB | - | 3 | 6 | $\mu \mathrm{s}$ | $\begin{aligned} & \mathrm{C}_{\text {LOAD }} \leq 50 \mathrm{pF}, \\ & \mathrm{R}_{\text {LOAD }} \geq 5 \mathrm{k} \Omega \end{aligned}$ |
| THD ${ }^{(4)}$ | Total Harmonic Distortion Buffer ON | - | - | - | dB | $\begin{aligned} & \mathrm{C}_{\text {LOAD }} \leq 50 \mathrm{pF}, \\ & \mathrm{R}_{\text {LOAD }} \geq 5 \mathrm{k} \Omega \end{aligned}$ |
| Update rate ${ }^{(2)}$ | Max frequency for a correct DAC_OUT change when small variation in the input code (from code ito i+1LSB) | - | - | 1 | MS/s | $\begin{aligned} & \mathrm{C}_{\text {LOAD }} \leq 50 \mathrm{pF}, \\ & \mathrm{R}_{\text {LOAD }} \geq 5 \mathrm{k} \Omega \end{aligned}$ |

Table 83. DAC characteristics (continued)

| Symbol | Parameter | Min | Typ | Max | Unit | Comments |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $t_{\text {WAKEUP }}{ }^{(4)}$ | Wakeup time from off state (Setting the ENx bit in the DAC Control register) | - | 6.5 | 10 | $\mu \mathrm{s}$ | $C_{\text {LOAD }} \leq 50 \mathrm{pF}, \mathrm{R}_{\text {LOAD }} \geq 5 \mathrm{k} \Omega$ input code between lowest and highest possible ones. |
| PSRR+ ${ }^{(2)}$ | Power supply rejection ratio (to $V_{\text {DDA }}$ ) (static DC measurement) | - | -67 | -40 | dB | No $\mathrm{R}_{\text {LOAD }}, \mathrm{C}_{\text {LOAD }}=50 \mathrm{pF}$ |

1. $\mathrm{V}_{\mathrm{DDA}}$ minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to Section 2.18.2: Internal reset OFF).
2. Guaranteed by design.
3. The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
4. Guaranteed by characterization results.

Figure 46. 12-bit buffered /non-buffered DAC


1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

### 5.3.29 Communications interfaces

## $1^{2}$ C interface characteristics

The $I^{2} C$ interface meets the timings requirements of the $I^{2} \mathrm{C}$-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to $100 \mathrm{kbit} / \mathrm{s}$
- Fast-mode (Fm): with a bit rate up to $400 \mathrm{kbit} / \mathrm{s}$.
- Fast-mode Plus (Fm+): with a bit rate up to $1 \mathrm{Mbit} / \mathrm{s}$.

The $I^{2} C$ timings requirements are guaranteed by design when the I2C peripheral is properly configured (refer to RM0410 reference manual) and when the I2CCLK frequency is greater than the minimum shown in the table below:

Table 84. Minimum I2CCLK frequency in all I2C modes

| Symbol | Parameter | Condition |  | Min | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}(\mathrm{I} 2 \mathrm{CCLK})$ | I2CCLK frequency | Standard-mode | - | 2 | MHz |
|  |  | Fast-mode | Analog filter ON DNF=0 | 8 |  |
|  |  |  | Analog filter OFF DNF=1 | 9 |  |
|  |  | Fast-mode Plus | Analog filter ON DNF=0 | 16 |  |
|  |  |  | Analog filter OFF DNF=1 | 16 |  |

The SDA and SCL I/O requirements are met with the following restrictions:

- The SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and $\mathrm{V}_{\mathrm{DD}}$ is disabled, but is still present.
- The 20 mA output drive requirement in Fast-mode Plus is not supported. This limits the maximum load Cload supported in $\mathrm{Fm}+$, which is given by these formulas:

$$
\begin{aligned}
& \operatorname{Tr}(S D A / S C L)=0.8473 x R_{p} x C_{l o a d} \\
& R_{p}(\min )=\left(V D D-V_{\mathrm{OL}}(\max )\right) / I_{\mathrm{OL}}(\max )
\end{aligned}
$$

Where Rp is the I2C lines pull-up. Refer to Section 5.3.20: I/O port characteristics for the I2C I/Os characteristics.
All I ${ }^{2}$ C SDA and SCL I/Os embed an analog filter. Refer to Table 85 for the analog filter characteristics:

Table 85. I2C analog filter characteristics ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{AF}}$ | Maximum pulse width of spikes that <br> are suppressed by the analog filter | $50^{(2)}$ | $70^{(3)}$ | ns |

1. Guaranteed by characterization results.
2. Spikes with widths below $\mathrm{t}_{\mathrm{AF}(\mathrm{min})}$ are filtered.
3. Spikes with widths above $\mathrm{t}_{\mathrm{AF}(\max )}$ are not filtered.

## SPI interface characteristics

Unless otherwise specified, the parameters given in Table 86 for the SPI interface are derived from tests performed under the ambient temperature, $\mathrm{f}_{\mathrm{PCLKx}}$ frequency and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load $\mathrm{C}=30 \mathrm{pF}$
- Measurement points are done at CMOS levels: $0.5 \mathrm{~V}_{\mathrm{DD}}$

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

Table 86. SPI dynamic characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\begin{gathered} \mathrm{f}_{\mathrm{SCK}} \\ 1 / \mathrm{t}_{\mathrm{C}(\mathrm{SCK})} \end{gathered}$ | SPI clock frequency | Master mode SPI1,4,5,6 $2.7 \leq \mathrm{VDD} \leq 3.6$ | - | - | $54^{(2)}$ | MHz |
|  |  | $\begin{gathered} \text { Master mode } \\ \text { SPI1,4,5,6 } \\ 1.71 \leq \text { VDD } \leq 3.6 \end{gathered}$ |  |  | 27 |  |
|  |  | Master transmitter mode $\begin{gathered} \text { SPI1,4,5,6 } \\ 1.71 \leq \text { VDD } \leq 3.6 \end{gathered}$ |  |  | 54 |  |
|  |  | Slave receiver mode SPI1,4,5,6 <br> $1.71 \leq \mathrm{VDD} \leq 3.6$ |  |  | 54 |  |
|  |  | Slave mode transmitter/full duplex SPI1,4,5,6 $2.7 \leq$ VDD $\leq 3.6$ |  |  | $50^{(3)}$ |  |
|  |  | Slave mode transmitter/full duplex <br> SPI1,4,5,6 <br> $1.71 \leq \mathrm{VDD} \leq 3.6$ |  |  | $37^{(3)}$ |  |
|  |  | Master \& Slave mode SPI2,3 <br> $1.71 \leq \mathrm{VDD} \leq 3.6$ |  |  | 27 |  |
| tsu(NSS) | NSS setup time | Slave mode, SPI presc = 2 | $4^{*} \mathrm{~T}_{\text {PLCK }}$ | - | - |  |
| th(NSS) | NSS hold time | Slave mode, SPI presc = 2 | $2^{*} \mathrm{~T}_{\text {PLCK }}$ | - | - | ns |
| $\begin{aligned} & \mathrm{tw}(\mathrm{SCKH}) \\ & \mathrm{tw}(\mathrm{SCKL}) \end{aligned}$ | SCK high and low time | Master mode | TPLCK ${ }^{-2}$ | TPLCK | $\mathrm{T}_{\text {PLCK }}+2$ |  |

Table 86. SPI dynamic characteristics ${ }^{(1)}$ (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| tsu(MI) | Data input setup time | Master mode | $\begin{gathered} 4 \\ 9^{(4)} \end{gathered}$ | - | - | ns |
| tsu(SI) |  | Slave mode | 4.5 | - | - |  |
| th(MI) | Data input hold time | Master mode | $\begin{gathered} 3 \\ 0^{(4)} \end{gathered}$ | - | - |  |
| th(SI) |  | Slave mode | 2 | - | - |  |
| ta(SO) | Data output access time | Slave mode | 7 | - | 21 |  |
| tdis(SO) | Data output disable time | Slave mode | 5 | - | 12 |  |
| tv(SO) | Data output valid time | Slave mode $2.7 \leq \mathrm{VDD} \leq 3.6 \mathrm{~V}$ | - | 6.5 | 10 |  |
|  |  | Slave mode 1.71 $\mathrm{VVDD} \leq 3.6 \mathrm{~V}$ | - | 6.5 | 13.5 |  |
| tv(MO) |  | Master mode | - | 2 | 6 |  |
| th(SO) | Data output hold time | $\begin{gathered} \text { Slave mode } \\ 1.71 \leq \mathrm{VDD} \leq 3.6 \mathrm{~V} \end{gathered}$ | 4.5 | - | - |  |
| th(MO) |  | Master mode | 0 | - | - |  |

1. Guaranteed by characterization results.
2. Excepting SPI1 with SCK IO pin mapped on PA5. In this configuration, Maximum achievable frequency is 40 MHz .
3. Maximum Frequency of Slave Transmitter is determined by sum of Tv(SO) and Tsu(MI) intervals which has to fit into SCK level phase preceding the SCK sampling edge. This value can be achieved when it communicates with a Master having Tsu(MI) $=0$ while signal Duty(SCK) $=50 \%$.
4. Only for SPI6.

Figure 47. SPI timing diagram - slave mode and CPHA = 0


Figure 48. SPI timing diagram - slave mode and CPHA $=1^{(1)}$


1. Measurement points are done at $0.5 \mathrm{~V}_{\mathrm{DD}}$ and with external $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}$.

Figure 49. SPI timing diagram - master mode ${ }^{(1)}$


1. Measurement points are done at $0.5 \mathrm{~V}_{\mathrm{DD}}$ and with external $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}$.

## $I^{2} S$ interface characteristics

Unless otherwise specified, the parameters given in Table 87 for the $I^{2}$ S interface are derived from tests performed under the ambient temperature, $f_{P C L K x}$ frequency and $V_{D D}$ supply voltage conditions summarized in Table 18, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load $\mathrm{C}=30 \mathrm{pF}$
- Measurement points are done at CMOS levels: $0.5 \mathrm{~V}_{\mathrm{DD}}$

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output alternate function characteristics (CK, SD, WS).

Table 87. $\mathrm{I}^{2} \mathrm{~S}$ dynamic characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {MCK }}$ | I2S Main clock output | - | 256x8K | 256xFs ${ }^{(2)}$ | MHz |
| $\mathrm{f}_{\mathrm{CK}}$ | 12S clock frequency | Master data | - | 64xFs | MHz |
|  |  | Slave data | - | 64xFs |  |
| $\mathrm{D}_{\text {CK }}$ | I2S clock frequency duty cycle | Slave receiver | 30 | 70 | \% |
| $\mathrm{t}_{\mathrm{v} \text { (WS) }}$ | WS valid time | Master mode | - | 3 | ns |
| $\mathrm{t}_{\mathrm{h} \text { (WS) }}$ | WS hold time | Master mode | 0 | - |  |
| $\mathrm{t}_{\text {su }}$ (WS) | WS setup time | Slave mode | 5 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (WS) }}$ | WS hold time | Slave mode | 2 | - |  |
| $\mathrm{t}_{\text {su(SD_MR) }}$ | Data input setup time | Master receiver | 2.5 | - |  |
| $\mathrm{t}_{\text {su(SD_SR) }}$ |  | Slave receiver | 2.5 | - |  |
| $\mathrm{th}_{\text {(SD_MR) }}$ | Data input hold time | Master receiver | 3.5 | - |  |
| $\mathrm{t}_{\text {h(SD_SR) }}$ |  | Slave receiver | 2 | - |  |
| $\mathrm{t}_{\mathrm{v} \text { (SD_ST) }}$ | Data output valid time | Slave transmitter (after enable edge) | - | 12 |  |
| $\mathrm{t}_{\mathrm{v} \text { (SD_MT) }}$ |  | Master transmitter (after enable edge) | - | 3 |  |
| $\mathrm{t}_{\text {h(SD_ST) }}$ | Data output hold time | Slave transmitter (after enable edge) | 5 | - |  |
| $\mathrm{t}_{\text {h(SD_MT) }}$ |  | Master transmitter (after enable edge) | 0 | - |  |

1. Guaranteed by characterization results.
2. The maximum value of $256 x F s$ is 49.152 MHz (APB1 maximum frequency).

Note: $\quad$ Refer to RM0410 reference manual I2S section for more details about the sampling frequency $\left(F_{S}\right) . f_{M C K}, f_{C K}$, and $D_{C K}$ values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. $D_{C K}$ depends mainly on the value of $O D D$ bit. The digital contribution leads to a minimum value of (I2SDIV/(2*I2SDIV+ODD) and a maximum value of (I2SDIV+ODD)/(2*I2SDIV+ODD). $F_{S}$ maximum value is supported for each mode/condition.

Figure 50. $\mathrm{I}^{2} \mathrm{~S}$ slave timing diagram (Philips protocol) ${ }^{(1)}$


1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 51. $I^{2}$ S master timing diagram (Philips protocol) ${ }^{(1)}$


1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

## JATG/SWD characteristics

Unless otherwise specified, the parameters given in Table 88 for JTAG/SWD are derived from tests performed under the ambient temperature, $\mathrm{f}_{\text {HCLK }}$ frequency and VDD supply voltage conditions summarized in Table 18, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load $\mathrm{C}=30 \mathrm{pF}$
- Measurement points are performed at CMOS levels: $0.5 \mathrm{~V}_{\mathrm{DD}}$

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output alternate function characteristics (SCK,SD,WS).

Table 88. Dynamics characteristics: JTAG characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{F}_{\mathrm{pp}}$ |  | $2.7 \mathrm{~V}<\mathrm{VDD}<3.6 \mathrm{~V}$ | - | - | 40 |  |
| $1 / \mathrm{t}_{\mathrm{c} \text { (TCK) }}$ | TCK clock frequency | 1.71 <VDD<3.6V | - | - | 35 | MHz |
| $\mathrm{t}_{\mathrm{w} \text { (TCKH) }}$ |  |  |  |  |  | ns |
| $t_{\text {w (TCKL) }}$ |  |  |  |  |  |  |
| $\mathrm{t}_{\text {su(TMS }}$ | TMS input setup time | - | 3 | - | - |  |
| $t_{h(T M S)}$ | TMS input hold time | - | 0 | - | - |  |
| $\mathrm{t}_{\mathrm{su}(\text { TDI })}$ | TDI input setup time | - | 0.5 | - | - |  |
| $t_{\text {(TDI) }}$ | TDI input hold time | - | 2 | - | - |  |
| $\mathrm{t}_{\mathrm{ov} \text { (TDO) }}$ | TDO output valid time | $2.7 \mathrm{~V}<\mathrm{VDD}<3.6 \mathrm{~V}$ | - | 9 | 11 |  |
|  |  | 1.71 <VDD<3.6V | - | 9 | 13 |  |
| $\mathrm{t}_{\mathrm{oh}(\text { (TDO) }}$ | TDO output hold time | - | 7.5 | - | - |  |

Table 89. Dynamics characteristics: SWD characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{F}_{\mathrm{pp}}$ |  | $2.7 \mathrm{~V}<\mathrm{VDD}<3.6 \mathrm{~V}$ | - | - | 80 |  |
| $1 / \mathrm{c}_{\text {(SWCLK) }}$ | SWCLK clock frequency | 1.71 <VDD<3.6V | - | - | 50 | MHz |
| $\mathrm{t}_{\mathrm{w} \text { (SWCLKH) }}$ |  |  |  |  |  | ns |
| $\mathrm{t}_{\mathrm{w} \text { (SWCLKL) }}$ |  |  |  |  |  |  |
| $\mathrm{t}_{\text {su(SWDIO) }}$ | SWDIO input setup time | - | 3.5 | - | - |  |
| $t_{\text {(SWDIO) }}$ | SWDIO input hold time | - | 0 | - | - |  |
| $\mathrm{t}_{\mathrm{ov} \text { (SWDIO) }}$ | SWDIO output valid time | $2.7 \mathrm{~V}<\mathrm{VDD}<3.6 \mathrm{~V}$ | - | 11 | 12 |  |
|  |  | 1.71 <VDD<3.6V | - | 11 | 16.5 |  |
| $\mathrm{t}_{\text {oh(SWDIO) }}$ | SWDIO output hold time | - | 9 | - | - |  |

## JTAG/SWD timing diagrams

Figure 52. JTAG timing diagram


Figure 53. SWD timing diagram


## SAI characteristics:

Unless otherwise specified, the parameters given in Table 90 for SAI are derived from tests performed under the ambient temperature, $\mathrm{f}_{\text {PCLKx }}$ frequency and VDD supply voltage conditions summarized in Table 18, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load $\mathrm{C}=30 \mathrm{pF}$
- Measurement points are performed at CMOS levels: $0.5 \mathrm{~V}_{\mathrm{DD}}$

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output alternate function characteristics (SCK,SD,WS).

Table 90. SAI characteristics ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {MCK }}$ | SAI Main clock output | - | $256 \times 8 \mathrm{~K}$ | 256xFs | MHz |
| $\mathrm{F}_{\mathrm{CK}}$ | SAI clock frequency ${ }^{(2)}$ | Master data: 32 bits | - | $128 \times F s^{(3)}$ | MHz |
|  |  | Slave data: 32 bits | - | 128xFs |  |
|  | FS valid time | Master mode $2.7 \leq \mathrm{VDD} \leq 3.6 \mathrm{~V}$ | - | 15 | ns |
| S) |  | Master mode <br> $1.71 \leq \mathrm{VDD} \leq 3.6 \mathrm{~V}$ | - | 20 |  |
| $\mathrm{t}_{\text {su(FS) }}$ | FS setup time | Slave mode | 7 | - |  |
| $t_{\text {(FSS }}$ | FS hold time | Master mode | 1 | - |  |
|  |  | Slave mode | 1 | - |  |
| $\mathrm{t}_{\text {su(SD_A_MR) }}$ | Data input setup time | Master receiver | 3 | - |  |
| $\mathrm{t}_{\text {su(SD_B_SR) }}$ |  | Slave receiver | 3.5 | - |  |
| $\mathrm{t}_{\text {(SD_A_MR) }}$ | Data input hold time | Master receiver | 5 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (SD_B_SR) }}$ |  | Slave receiver | 1 | - |  |

Table 90. SAI characteristics ${ }^{(1)}$ (continued)

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{v} \text { (SD_B_ST) }}$ | Data output valid time | Slave transmitter (after enable edge) $2.7 \leq \mathrm{VDD} \leq 3.6 \mathrm{~V}$ | - | 12 | ns |
|  |  | Slave transmitter (after enable edge) $1.71 \leq \mathrm{VDD} \leq 3.6 \mathrm{~V}$ | - | 20 |  |
| $\mathrm{t}_{\text {h(SD_B_MT) }}$ | Data output hold time | Slave transmitter (after enable edge) | 5 | - |  |
| $\mathrm{t}_{\mathrm{v}(\mathrm{SD} \text {-MT)_A }}$ | Data output valid time | Master transmitter (after enable edge) $2.7 \leq \mathrm{VDD} \leq 3.6 \mathrm{~V}$ | - | 15 |  |
|  |  | Master transmitter (after enable edge) $1.71 \leq \mathrm{VDD} \leq 3.6 \mathrm{~V}$ | - | 20 |  |
| $\mathrm{t}_{\text {(SD_A_MT) }}$ | Data output hold time | Master transmitter (after enable edge) | 5 | - |  |

1. Guaranteed by characterization results.
2. APB clock frequency must be at least twice SAI clock frequency.
3. With $F_{S}=192 \mathrm{kHz}$.

Figure 54. SAI master timing waveforms


Figure 55. SAI slave timing waveforms


## USB OTG full speed (FS) characteristics

This interface is present in both the USB OTG HS and USB OTG FS controllers.
Table 91. USB OTG full speed startup time

| Symbol | Parameter | Max | Unit |
| :--- | :---: | :---: | :---: |
| t $_{\text {STARTUP }}{ }^{(1)}$ | USB OTG full speed transceiver startup time | 1 | $\mu \mathrm{~s}$ |

1. Guaranteed by design.

Table 92. USB OTG full speed DC electrical characteristics

| Symbol |  | Parameter | Conditions | Min. (1) | Typ. | Max. <br> (1) | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Input levels | $V_{\text {DDUSB }}$ | USB OTG full speed transceiver operating voltage | - | $3.0^{(2)}$ | - | 3.6 | V |
|  | $V_{D I}{ }^{(3)}$ | Differential input sensitivity | I(USB_FS_DP/DM, USB_HS_DP/DM) | 0.2 | - | - | V |
|  | $\mathrm{V}_{\mathrm{CM}}{ }^{(3)}$ | Differential common mode range | Includes $\mathrm{V}_{\text {DI }}$ range | 0.8 | - | 2.5 |  |
|  | $V_{S E}{ }^{(3)}$ | Single ended receiver threshold | - | 1.3 | - | 2.0 |  |
| Output levels | $\mathrm{V}_{\text {OL }}$ | Static output level low | $\mathrm{R}_{\mathrm{L}}$ of $1.5 \mathrm{k} \Omega$ to $3.6 \mathrm{~V}^{(4)}$ | - | - | 0.3 | V |
|  | $\mathrm{V}_{\mathrm{OH}}$ | Static output level high | $\mathrm{R}_{\mathrm{L}}$ of $15 \mathrm{k} \Omega$ to $\mathrm{V}_{\mathrm{SS}}{ }^{(4)}$ | 2.8 | - | 3.6 |  |

Table 92. USB OTG full speed DC electrical characteristics (continued)

| Symbol | Parameter | Conditions | Min. (1) | Typ. | Max. (1) | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{R}_{\mathrm{PD}}$ | PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM) | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}}$ | 17 | 21 | 24 | $\mathrm{k} \Omega$ |
|  | PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS) |  | 2.4 | 5.2 | 8 |  |
| RPu | PA12, PB15 (USB_FS_DP, USB_HS_DP) | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\text {SS }}$ | 1.5 | 1.8 | 2.1 |  |
|  | PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS) | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {SS }}$ | 0.55 | 0.95 | 1.35 |  |

1. All the voltages are measured from the local ground potential.
2. The USB OTG full speed transceiver functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7 -to-3.0 $\vee \mathrm{V}_{\text {DDUSB }}$ voltage range.
3. Guaranteed by design.
4. $R_{L}$ is the load connected on the USB OTG full speed drivers.

Note: $\quad$ When VBUS sensing feature is enabled, PA9 and PB13 should be left at their default state (floating input), not as alternate function. A typical $200 \mu A$ current consumption of the sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 and PB13 when the feature is enabled.

Figure 56. USB OTG full speed timings: definition of data signal rise and fall time


Table 93. USB OTG full speed electrical characteristics ${ }^{(1)}$

| Driver characteristics |  |  |  |  |  |
| :---: | :--- | :---: | :---: | :---: | :---: |
| Symbol | Parameter | Conditions | Min | Max | Unit |
| $\mathrm{t}_{\mathrm{r}}$ | Rise time $^{(2)}$ | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ | 4 | 20 | ns |
| $\mathrm{t}_{\mathrm{f}}$ | Fall time $^{(2)}$ | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ | 4 | 20 | ns |
| $\mathrm{t}_{\mathrm{rfm}}$ | Rise/ fall time matching | $\mathrm{t}_{\mathrm{r}} / \mathrm{t}_{\mathrm{f}}$ | 90 | 110 | $\%$ |
| $\mathrm{~V}_{\mathrm{CRS}}$ | Output signal crossover voltage | - | 1.3 | 2.0 | V |
| $\mathrm{Z}_{\mathrm{DRV}}$ | Output driver impedance ${ }^{(3)}$ | Driving high or <br> low | 28 | 44 | $\Omega$ |

1. Guaranteed by design.
2. Measured from $10 \%$ to $90 \%$ of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).
3. No external termination series resistors are required on DP ( $\mathrm{D}+$ ) and $\mathrm{DM}(\mathrm{D}-)$ pins since the matching impedance is included in the embedded driver.

## USB high speed (HS) characteristics

Unless otherwise specified, the parameters given in Table 96 for ULPI are derived from tests performed under the ambient temperature, $\mathrm{f}_{\text {HCLK }}$ frequency summarized in Table 95 and $V_{D D}$ supply voltage conditions summarized in Table 94, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11, unless otherwise specified
- Capacitive load $\mathrm{C}=20 \mathrm{pF}$, unless otherwise specified
- Measurement points are done at CMOS levels: $0.5 \mathrm{~V}_{\mathrm{DD}}$.

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output characteristics.

Table 94. USB HS DC electrical characteristics

| Symbol |  | Parameter | Min. ${ }^{(1)}$ | Max. $^{(1)}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Input level | $\mathrm{V}_{\mathrm{DD}}$ | USB OTG HS operating voltage | 1.7 | 3.6 | V |

1. All the voltages are measured from the local ground potential.

Table 95. USB HS clock timing parameters ${ }^{(1)}$

| Symbol | Parameter |  | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| - | $\mathrm{f}_{\text {HCLK }}$ value to guarantee proper operation of USB HS interface |  | 30 | - | - | MHz |
| FSTART_8BIT | Frequency (first transition) | 8-bit $\pm 10 \%$ | 54 | 60 | 66 | MHz |
| $\mathrm{F}_{\text {STEADY }}$ | Frequency (steady state) $\pm 500 \mathrm{ppm}$ |  | 59.97 | 60 | 60.03 | MHz |
| DSTART_8BIT | Duty cycle (first transition) | 8-bit $\pm 10 \%$ | 40 | 50 | 60 | \% |
| D ${ }_{\text {STEADY }}$ | Duty cycle (steady state) $\pm 500 \mathrm{ppm}$ |  | 49.975 | 50 | 50.025 | \% |
| $\mathrm{t}_{\text {STEAD }}$ | Time to reach the steady state frequency and duty cycle after the first transition |  | - | - | 1.4 | ms |
| tstart_DEV | Clock startup time after the de-assertion of SuspendM | Peripheral | - | - | 5.6 | ms |
| tstart_host |  | Host | - | - | - |  |
| $t_{\text {PREP }}$ | PHY preparation time after the first transition of the input clock |  | - | - | - | $\mu \mathrm{s}$ |

[^5]Figure 57. ULPI timing diagram


Table 96. Dynamic characteristics: USB ULPI ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {SC }}$ | Control in (ULPI_DIR, ULPI_NXT) setup time | - | 2 | - | - | ns |
| $\mathrm{t}_{\mathrm{HC}}$ | Control in (ULPI_DIR, ULPI_NXT) hold time | - | 1.5 | - | - |  |
| $t_{\text {SD }}$ | Data in setup time | - | 2 | - | - |  |
| $\mathrm{t}_{\mathrm{HD}}$ | Data in hold time | - | 1 | - | - |  |
| $t_{D C} / t_{D D}$ | Data/control output delay | $\begin{gathered} 2.7 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}, \\ \mathrm{C}_{\mathrm{L}}=20 \mathrm{pF} \end{gathered}$ | - | 6.5 | 8 |  |
|  |  | - | - | 6.5 | 11 |  |
|  |  | $\begin{gathered} 1.7 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}, \\ \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF} \end{gathered}$ | - |  |  |  |

1. Guaranteed by characterization results.

## Ethernet characteristics

Unless otherwise specified, the parameters given in Table 97, Table 98 and Table 99 for SMI, RMII and MII are derived from tests performed under the ambient temperature, $\mathrm{f}_{\mathrm{HCLK}}$ frequency summarized in Table 18, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] $=10$
- Capacitive load $\mathrm{C}=20 \mathrm{pF}$
- Measurement points are done at CMOS levels: $0.5 \mathrm{~V}_{\text {DD }}$.

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output characteristics.

Table 97 gives the list of Ethernet MAC signals for the SMI (station management interface) and Figure 58 shows the corresponding timing diagram.

Figure 58. Ethernet SMI timing diagram


Table 97. Dynamics characteristics: Ethernet MAC signals for SMI ${ }^{(1)}$

| Symbol | Parameter | Min | Typ | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {MDC }}$ | MDC cycle time(2.38 MHz) | 400 | 400 | 403 |  |
|  | $\mathrm{~T}_{\mathrm{d} \text { (MDIO) }}$ | Write data valid time | $\mathrm{T}_{\text {HCLK }}+1$ | $\mathrm{~T}_{\text {HCLK }}+1.5$ | $\mathrm{~T}_{\text {HCLK }}+3$ |
|  | ns |  |  |  |  |
| $\mathrm{t}_{\text {su(MDIO) }}$ |  | 12.5 | - | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (MDIO) }}$ | Read data hold time | 0 | - | - |  |

1. Guaranteed by characterization results.

Table 98 gives the list of Ethernet MAC signals for the RMII and Figure 59 shows the corresponding timing diagram.

Figure 59. Ethernet RMII timing diagram


Table 98. Dynamics characteristics: Ethernet MAC signals for RMII ${ }^{(1)}$

| Symbol | Parameter | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {su(RXD })}$ | Receive data setup time | 1 | - | - | ns |
| $\mathrm{t}_{\mathrm{in}(\mathrm{RXD})}$ | Receive data hold time | 2 | - | - |  |
| $\mathrm{t}_{\text {su( }}$ (CRS $)$ | Carrier sense setup time | 2 | - | - |  |
| $\mathrm{t}_{\mathrm{in} \text { (CRS) }}$ | Carrier sense hold time | 2 | - | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (TXEN) }}$ | Transmit enable valid delay time | 7.5 | 8 | 12 |  |
| $\mathrm{t}_{\text {( } \text { (TXD) }}$ | Transmit data valid delay time | 7 | 7.5 | 12.5 |  |

1. Guaranteed by characterization results.

Table 99 gives the list of Ethernet MAC signals for MII and Figure 59 shows the corresponding timing diagram.

Figure 60. Ethernet MII timing diagram


Table 99. Dynamics characteristics: Ethernet MAC signals for MII ${ }^{(1)}$

| Symbol | Parameter | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $t_{\text {su(RXD })}$ | Receive data setup time | 1 | - | - | ns |
| $\mathrm{tin}_{\text {(RXD }}$ ) | Receive data hold time | 2.5 | - | - |  |
| $\mathrm{t}_{\mathrm{su}(\mathrm{DV})}$ | Data valid setup time | 1.5 | - | - |  |
| $\mathrm{t}_{\text {ih( }}(\mathrm{DV})$ | Data valid hold time | 0.5 | - | - |  |
| $\mathrm{t}_{\text {su(ER) }}$ | Error setup time | 2.5 | - | - |  |
| $\mathrm{t}_{\text {ih(ER) }}$ | Error hold time | 0.5 | - | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (TXEN) }}$ | Transmit enable valid delay time | 10 | 8 | 13 |  |
| $\mathrm{t}_{\mathrm{d} \text { (TXD) }}$ | Transmit data valid delay time | 9 | 7.5 | 13 |  |

1. Guaranteed by characterization results.

Table 100. MDIO Slave timing parameters

| Symbol | Parameter | Min | Typ | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{F}_{\mathrm{sDC}}$ | Management Data clock | - | - | 40 | MHz |
| $\mathrm{t}_{\mathrm{d} \text { (MDIO) }}$ | Management Data input/output output valid time | 7 | 8 | 20 |  |
| $\mathrm{t}_{\text {su(MDIO) }}$ | Management Data input/output setup time | 4 | - | - | ns |
|  | $\mathrm{t}_{\mathrm{h} \text { (MDIO) }}$ | Management Data input/output hold time | 1 | - | - |

The MDIO controller is mapped on APB2 domain. The frequency of the APB bus should at least 1.5 times the MDC frequency: $\mathrm{F}_{\mathrm{PCLK} 2} \geq 1.5{ }^{*} \mathrm{~F}_{\mathrm{MDC}}$

Figure 61. MDIO Slave timing diagram


## CAN (controller area network) interface

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output alternate function characteristics (CANx_TX and CANx_RX).

### 5.3.30 <br> FMC characteristics

Unless otherwise specified, the parameters given in Table 101 to Table 114 for the FMC interface are derived from tests performed under the ambient temperature, $\mathrm{f}_{\text {HCLK }}$ frequency and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Measurement points are done at CMOS levels: 0.5 V DD

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output characteristics.

## Asynchronous waveforms and timings

Figure 62 through Figure 65 represent asynchronous waveforms and Table 101 through Table 108 provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- AddressSetupTime $=0 \times 1$
- AddressHoldTime $=0 \times 1$
- DataSetupTime $=0 \times 1$ (except for asynchronous NWAIT mode , DataSetupTime $=0 \times 5$ )
- BusTurnAroundDuration $=0 \times 0$
- Capcitive load CL $=30 \mathrm{pF}$

In all timing tables, the $\mathrm{T}_{\text {HCLK }}$ is the HCLK clock period
Figure 62. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms


[^6]Table 101. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings ${ }^{(1)(2)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (NE) }}$ | FMC_NE low time | $2 \mathrm{~T}_{\text {HCLK }}-1$ | $2 \mathrm{~T}_{\text {HCLK }}+1$ |  |
| $\mathrm{t}_{\mathrm{v} \text { (NOE_NE) }}$ | FMC_NEx low to FMC_NOE low | 0 | 0.5 |  |
| $\mathrm{t}_{\mathrm{w} \text { (NOE) }}$ | FMC_NOE low time | $2 \mathrm{~T}_{\text {HCLK }}-1$ | $2 \mathrm{~T}_{\text {HCLK }}+1$ |  |
| $\mathrm{t}_{\mathrm{h} \text { (NE_NOE) }}$ | FMC_NOE high to FMC_NE high hold time | 0 | - |  |
| $\mathrm{t}_{\mathrm{v} \text { (A_NE) }}$ | FMC_NEx low to FMC_A valid | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (A_NOE) }}$ | Address hold time after FMC_NOE high | 0 | - |  |
| $\mathrm{t}_{\mathrm{v}(\text { BL_NE) }}$ | FMC_NEx low to FMC_BL valid | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (BL_NOE) }}$ | FMC_BL hold time after FMC_NOE high | 0 | - |  |
| $\mathrm{t}_{\text {su(Data_NE) }}$ | Data to FMC_NEx high setup time | $\mathrm{T}_{\text {HCLK }}-1$ | - |  |
| $\mathrm{t}_{\text {su(Data_NOE) }}$ | Data to FMC_NOEx high setup time | $\mathrm{T}_{\text {HCLK }}-1$ | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (Data_NOE) }}$ | Data hold time after FMC_NOE high | 0 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (Data_NE) }}$ | Data hold time after FMC_NEx high | 0 | - |  |
| $\mathrm{t}_{\mathrm{v}(\text { NADV_NE) }}$ | FMC_NEx low to FMC_NADV low | - | 0 |  |
| $\mathrm{t}_{\mathrm{w} \text { (NADV) }}$ | FMC_NADV low time | - | $\mathrm{T}_{\text {HCLK }}+1$ |  |

1. $C_{L}=30 \mathrm{pF}$.
2. Guaranteed by characterization results.

Table 102. Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w}(\mathrm{NE})}$ | FMC_NE low time | $7 \mathrm{~T}_{\text {HCLK }}+1$ | $7 \mathrm{~T}_{\text {HCLK }}+1$ | ns |
| $\mathrm{t}_{\mathrm{w} \text { (NOE) }}$ | FMC_NWE low time | $5 \mathrm{~T}_{\text {HCLK }}-1$ | $5 \mathrm{~T}_{\text {HCLK }}+1$ |  |
| $\mathrm{t}_{\mathrm{w} \text { (NWAIT) }}$ | FMC_NWAIT low time | $\mathrm{T}_{\text {HCLK }}$-0.5 | - |  |
| $\mathrm{t}_{\text {su( }}$ (NWAIT_NE) | FMC_NWAIT valid before FMC_NEx high | $5 \mathrm{~T}_{\text {HCLK }}+1.5$ | - |  |
| $\mathrm{th}_{\text {h(NE_NWAIT) }}$ | FMC_NEx hold time after FMC_NWAIT invalid | $4 \mathrm{~T}_{\text {HCLK }}+1$ | - |  |

1. Guaranteed by characterization results.

Figure 63. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms


1. Mode 2/B, C and D only. In Mode 1, FMC_NADV is not used.

Table 103. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $t_{w(N E)}$ | FMC_NE low time | $3 \mathrm{~T}_{\text {HCLK }}-1$ | $3 \mathrm{~T}_{\text {HCLK }}+1$ | ns |
| $\mathrm{t}_{\mathrm{v} \text { (NWE_NE) }}$ | FMC_NEx low to FMC_NWE low | $\mathrm{T}_{\text {HCLK }}-1$ | $\mathrm{T}_{\text {HCLK }}+0.5$ |  |
| $\mathrm{t}_{\mathrm{w} \text { (NWE) }}$ | FMC_NWE low time | $\mathrm{T}_{\text {HCLK }}-1.5$ | $\mathrm{T}_{\text {HCLK }}+0.5$ |  |
| $\mathrm{t}_{\mathrm{h} \text { (NE_NWE) }}$ | FMC_NWE high to FMC_NE high hold time | $\mathrm{T}_{\text {HCLK }}$ | - |  |
| $\mathrm{t}_{\text {( }}(\mathrm{A}$ _NE) | FMC_NEx low to FMC_A valid | - | 0 |  |
| $t_{\text {h(A_NWE) }}$ | Address hold time after FMC_NWE high | THCLK -0.5 | - |  |
| $\mathrm{t}_{\mathrm{v} \text { (BL_NE) }}$ | FMC_NEx low to FMC_BL valid | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (BL_NWE) }}$ | FMC_BL hold time after FMC_NWE high | $\mathrm{T}_{\text {HCLK }}-0.5$ | - |  |
| $\mathrm{t}_{\text {v(Data_NE) }}$ | Data to FMC_NEx low to Data valid | - | $\mathrm{T}_{\text {HCLK }}+2$ |  |
| $t_{\text {(Data_NWE) }}$ | Data hold time after FMC_NWE high | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\mathrm{v} \text { (NADV_NE) }}$ | FMC_NEx low to FMC_NADV low | - | 0 |  |
| $\mathrm{t}_{\mathrm{w} \text { (NADV) }}$ | FMC_NADV low time | - | $\mathrm{T}_{\text {HCLK }}+1$ |  |

1. Guaranteed by characterization results.

Table 104. Asynchronous non-multiplexed SRAM/PSRAM/NOR write - NWAIT timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (NE) }}$ | FMC_NE low time | $8 \mathrm{~T}_{\text {HCLK }}-1$ | $8 \mathrm{~T}_{\text {HCLK }}+1$ |  |
| $\mathrm{t}_{\mathrm{w} \text { (NWE) }}$ | FMC_NWE low time | $6 \mathrm{~T}_{\text {HCLK }}-1.5$ | $6 \mathrm{~T}_{\text {HCLK }}+0.5$ | n |
| $\mathrm{t}_{\text {su(NWAIT_NE) }}$ | FMC_NWAIT valid before FMC_NEx high | $6 \mathrm{~T}_{\text {HCLK }}-1$ | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (NE_NWAIT) }}$ | FMC_NEx hold time after FMC_NWAIT <br> invalid | $4 \mathrm{~T}_{\text {HCLK }}+2$ | - |  |

1. Guaranteed by characterization results.

Figure 64. Asynchronous multiplexed PSRAM/NOR read waveforms


Table 105. Asynchronous multiplexed PSRAM/NOR read timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (NE) }}$ | FMC_NE low time | $3 \mathrm{H}_{\text {HCLK }}-1$ | $3 \mathrm{~T}_{\text {HCLK }}+1$ | ns |
| $\mathrm{t}_{\mathrm{v} \text { (NOE_NE) }}$ | FMC_NEx low to FMC_NOE low | $2 \mathrm{~T}_{\text {HCLK }}$ | $2 \mathrm{~T}_{\text {HCLK }}+0.5$ |  |
| $\mathrm{t}_{\mathrm{tw}(\mathrm{NOE})}$ | FMC_NOE low time | T HCLK ${ }^{-1}$ | $\mathrm{T}_{\text {HCLK }}+1$ |  |
| $\mathrm{t}_{\mathrm{h} \text { (NE_NOE) }}$ | FMC_NOE high to FMC_NE high hold time | 0 | - |  |
| $\mathrm{t}_{\text {v(A_NE) }}$ | FMC_NEx low to FMC_A valid | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{v} \text { (NADV_NE) }}$ | FMC_NEx low to FMC_NADV low | 0 | 0.5 |  |
| $\mathrm{t}_{\mathrm{w} \text { (NADV) }}$ | FMC_NADV low time | $\mathrm{T}_{\text {HCLK }}-0.5$ | $\mathrm{T}_{\text {HCLK }}{ }^{+1}$ |  |
| $\mathrm{t}_{\mathrm{h}}(\mathrm{AD}$ _NADV) | FMC_AD(address) valid hold time after FMC_NADV high) | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\mathrm{h}\left(\mathrm{A} \_ \text {NOE) }\right.}$ | Address hold time after FMC_NOE high | $\mathrm{T}_{\text {HCLK }}-0.5$ | - |  |
| $\mathrm{t}_{\mathrm{h}}$ (BL_NOE) | FMC_BL time after FMC_NOE high | 0 | - |  |
| $\mathrm{t}_{\mathrm{v} \text { (BL_NE) }}$ | FMC_NEx low to FMC_BL valid | - | 0.5 |  |
| $\mathrm{t}_{\text {su(Data_NE) }}$ | Data to FMC_NEx high setup time | $\mathrm{T}_{\text {HCLK }}-1$ | - |  |
| $\mathrm{t}_{\text {su(Data_NOE) }}$ | Data to FMC_NOE high setup time | T ${ }_{\text {HCLK }}$-1 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (Data_NE) }}$ | Data hold time after FMC_NEx high | 0 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (Data_NOE) }}$ | Data hold time after FMC_NOE high | 0 | - |  |

1. Guaranteed by characterization results.

Table 106. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w}(\mathrm{NE})}$ | FMC_NE low time | $8 \mathrm{~T}_{\text {HCLK }}-1$ | $8 \mathrm{~T}_{\text {HCLK }}+1$ | ns |
| $\mathrm{t}_{\mathrm{w} \text { (NOE) }}$ | FMC_NWE low time | $5 \mathrm{~T}_{\text {HCLK }}-1.5$ | $5 \mathrm{~T}_{\text {HCLK }}+0.5$ |  |
| $t_{\text {su(NWAIT_NE) }}$ | FMC_NWAIT valid before FMC_NEx high | $5 \mathrm{~T}_{\text {HCLK }}+1.5$ | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (NE_NWAIT) }}$ | FMC_NEx hold time after FMC_NWAIT invalid | $4 \mathrm{~T}_{\text {HCLK }}{ }^{+1}$ | - |  |

1. Guaranteed by characterization results.

Figure 65. Asynchronous multiplexed PSRAM/NOR write waveforms


Table 107. Asynchronous multiplexed PSRAM/NOR write timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (NE) }}$ | FMC_NE low time | $4 \mathrm{H}_{\text {HCLK }}-1$ | $4 \mathrm{~T}_{\text {HCLK }}+1$ | ns |
| $\mathrm{t}_{\mathrm{v} \text { (NWE_NE) }}$ | FMC_NEx low to FMC_NWE low | T ${ }_{\text {HCLK }}$-1 | $\mathrm{T}_{\text {HCLK }}+0.5$ |  |
| $\mathrm{t}_{\mathrm{w} \text { (NWE) }}$ | FMC_NWE low time | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | $2 \mathrm{~T}_{\text {HCLK }}+0.5$ |  |
| $\mathrm{t}_{\text {h( }}$ (NE_NWE) | FMC_NWE high to FMC_NE high hold time | $\mathrm{T}_{\text {HCLK }}-0.5$ | - |  |
| $\mathrm{t}_{\text {v(A_NE) }}$ | FMC_NEx low to FMC_A valid | - | 0 |  |
| $t_{\text {v(NADV_NE) }}$ | FMC_NEx low to FMC_NADV low | 0 | 0.5 |  |
| $\mathrm{t}_{\mathrm{w} \text { (NADV) }}$ | FMC_NADV low time | $\mathrm{T}_{\text {HCLK }}$ | $\mathrm{T}_{\text {HCLK }}{ }^{+1}$ |  |
| $t_{\text {( }}$ (AD_NADV) | FMC_AD(adress) valid hold time after FMC_NADV high) | THCLK ${ }^{-0.5}$ | - |  |
| $\mathrm{t}_{\mathrm{h}}$ (A_NWE) | Address hold time after FMC_NWE high | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (BL_NWE) }}$ | FMC_BL hold time after FMC_NWE high | T ${ }_{\text {HCLK }}-0.5$ | - |  |
| $\mathrm{t}_{\mathrm{v} \text { (BL_NE) }}$ | FMC_NEx low to FMC_BL valid | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{v} \text { (Data_NADV) }}$ | FMC_NADV high to Data valid | - | $\mathrm{T}_{\text {HCLK }}+2$ |  |
| $\mathrm{t}_{\text {( }}$ (Data_NWE) | Data hold time after FMC_NWE high | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |

1. Guaranteed by characterization results.

Table 108. Asynchronous multiplexed PSRAM/NOR write-NWAIT timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{t}_{\text {w(NE) }}$ | FMC_NE low time | $9 \mathrm{~T}_{\text {HCLK }}-1$ | $9 \mathrm{~T}_{\text {HCLK }}+1$ |  |
| $\mathrm{t}_{\mathrm{w} \text { (NWE) }}$ | FMC_NWE low time | $7 \mathrm{~T}_{\text {HCLK }}-0.5$ | $7 \mathrm{~T}_{\text {HCLK }}+0.5$ | n |
| $\mathrm{t}_{\text {su(NWAIT_NE) }}$ | FMC_NWAIT valid before FMC_NEx high |  |  |  |
| $\mathrm{t}_{\mathrm{h} \text { (NE_NWAIT) }}$ | $6 \mathrm{~F}_{\text {HCLK }}+2$ | - |  |  |

1. Guaranteed by characterization results.

## Synchronous waveforms and timings

Figure 66 through Figure 69 represent synchronous waveforms and Table 109 through Table 112 provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- BurstAccessMode = FMC_BurstAccessMode_Enable;
- MemoryType = FMC_MemoryType_CRAM;
- WriteBurst = FMC_WriteBurst_Enable;
- $\quad$ CLKDivision $=1$;
- DataLatency = 1 for NOR Flash; DataLatency $=0$ for PSRAM
- $\quad \mathrm{CL}=30 \mathrm{pF}$ on data and address lines. CL = 10 pF on FMC_CLK unless otherwise specified.

In all the timing tables, the $\mathrm{T}_{\text {HCLK }}$ is the HCLK clock period.

- For 2.7 V $\leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$, maximum FMC_CLK $=100 \mathrm{MHz}$ at $\mathrm{CL}=20 \mathrm{pF}$ or 90 MHz at CL=30 pF (on FMC_CLK).
- For $1.71 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}}<2.7 \mathrm{~V}$, maximum FMC_CLK $=70 \mathrm{MHz}$ at $\mathrm{CL}=10 \mathrm{pF}$ (on FMC_CLK).

Figure 66. Synchronous multiplexed NOR/PSRAM read timings


Table 109. Synchronous multiplexed NOR/PSRAM read timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (CLK) }}$ | FMC_CLK period | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NExL) }}$ | FMC_CLK low to FMC_NEx low (x=0..2) | - | 2 |  |
| $\mathrm{t}_{\mathrm{d}(\mathrm{CLKH}}^{\text {c }}$ _NEXH) | FMC_CLK high to FMC_NEx high (x=0...2) | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKL-NADVL) }}$ | FMC_CLK low to FMC_NADV low | - | 1. |  |
| $\mathrm{t}_{\text {( } \text { (CLKL-NADVH) }}$ | FMC_CLK low to FMC_NADV high | 0 | - |  |
| $\mathrm{t}_{\mathrm{d}(\mathrm{CLKL}}$-AV) | FMC_CLK low to FMC_Ax valid ( $\mathrm{x}=16 . . .25$ ) | - | 2.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKH-AIV) }}$ | FMC_CLK high to FMC_Ax invalid ( $\mathrm{x}=16 . . .25$ ) | $\mathrm{T}_{\text {HCLK }}$ | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NOEL) }}$ | FMC_CLK low to FMC_NOE low | - | 1.5 | ns |
| $\mathrm{t}_{\mathrm{d}(\text { CLKH-NOEH) }}$ | FMC_CLK high to FMC_NOE high | $\mathrm{T}_{\text {HCLK }}-0.5$ | - |  |
| $\mathrm{t}_{\text {d(CLKL-ADV) }}$ | FMC_CLK low to FMC_AD[15:0] valid | - | 3 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-ADIV) }}$ | FMC_CLK low to FMC_AD[15:0] invalid | 0 | - |  |
| $\mathrm{t}_{\text {su(ADV-CLKH) }}$ | FMC_A/D[15:0] valid data before FMC_CLK high | 1.5 | - |  |
| $\mathrm{t}_{\text {h(CLKH-ADV) }}$ | FMC_A/D[15:0] valid data after FMC_CLK high | 3.5 | - |  |
| $\mathrm{t}_{\text {su(NWAIT-CLKH) }}$ | FMC_NWAIT valid before FMC_CLK high | 2 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (CLKH-NWAIT) }}$ | FMC_NWAIT valid after FMC_CLK high | 3.5 | - |  |

1. Guaranteed by characterization results.

Figure 67. Synchronous multiplexed PSRAM write timings


Table 110. Synchronous multiplexed PSRAM write timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (CLK) }}$ | FMC_CLK period | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | - | ns |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NExL) }}$ | FMC_CLK low to FMC_NEx low (x=0..2) | - | 2 |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKH-NExH) }}$ | FMC_CLK high to FMC_NEx high (x=0...2) | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\mathrm{d}(\mathrm{CLKL}}$ (NADVL) | FMC_CLK low to FMC_NADV low | - | 1 |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKL-NADVH) }}$ | FMC_CLK low to FMC_NADV high | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-AV) }}$ | FMC_CLK low to FMC_Ax valid ( $\mathrm{x}=16 \ldots .25$ ) | - | 2.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKH-AIV) }}$ | FMC_CLK high to FMC_Ax invalid (x=16...25) | $\mathrm{T}_{\text {HCLK }}$ | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKL-NWEL) }}$ | FMC_CLK low to FMC_NWE low | - | 1.5 |  |
| $\mathrm{t}_{\text {(CLKH-NWEH) }}$ | FMC_CLK high to FMC_NWE high | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\text {d(CLKL-ADV) }}$ | FMC_CLK low to FMC_AD[15:0] valid | - | 3 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-ADIV) }}$ | FMC_CLK low to FMC_AD[15:0] invalid | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-DATA) }}$ | FMC_A/D[15:0] valid data after FMC_CLK low | - | 3.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NBLL) }}$ | FMC_CLK low to FMC_NBL low | - | 2 |  |
| $\mathrm{t}_{\mathrm{d}(\mathrm{CLKH}}$-NBLH) | FMC_CLK high to FMC_NBL high | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\text {su( }}$ (NWAIT-CLKH) | FMC_NWAIT valid before FMC_CLK high | 2 | - |  |
| $\mathrm{t}_{\text {(CLKH-NWAIT) }}$ | FMC_NWAIT valid after FMC_CLK high | 3.5 | - |  |

1. Guaranteed by characterization results.

Figure 68. Synchronous non-multiplexed NOR/PSRAM read timings


Table 111. Synchronous non-multiplexed NOR/PSRAM read timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (CLK) }}$ | FMC_CLK period | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | - | ns |
| ${ }^{\text {t }}$ (CLKL-NExL) | FMC_CLK low to FMC_NEx low ( $\mathrm{x}=0 . .2$ ) | - | 2 |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKH-NExH) }}$ | FMC_CLK high to FMC_NEx high (x=0...2) | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKL-NADVL) }}$ | FMC_CLK low to FMC_NADV low | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NADVH) }}$ | FMC_CLK low to FMC_NADV high | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-AV) }}$ | FMC_CLK low to FMC_Ax valid ( $\mathrm{x}=16 \ldots .25$ ) | - | 2.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKH-AIV) }}$ | FMC_CLK high to FMC_Ax invalid ( $\mathrm{x}=16 . . .25$ ) | $\mathrm{T}_{\text {HCLK }}$ | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NOEL) }}$ | FMC_CLK low to FMC_NOE low | - | 1.5 |  |
| $\mathrm{t}_{\text {d(CLKH-NOEH) }}$ | FMC_CLK high to FMC_NOE high | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\text {su(DV-CLKH) }}$ | FMC_D[15:0] valid data before FMC_CLK high | 1.5 | - |  |
| $\mathrm{t}_{\text {h(CLKH-DV) }}$ | FMC_D[15:0] valid data after FMC_CLK high | 3.5 | - |  |
| $\mathrm{t}_{\text {(NWAIT-CLKH) }}$ | FMC_NWAIT valid before FMC_CLK high | 2 | - |  |
| $\mathrm{t}_{\text {( }}$ (CLKH-NWAIT) | FMC_NWAIT valid after FMC_CLK high | 3.5 | - |  |

1. Guaranteed by characterization results.

Figure 69. Synchronous non-multiplexed PSRAM write timings


Table 112. Synchronous non-multiplexed PSRAM write timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| ${ }^{\text {t }}$ (CLK) | FMC_CLK period | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | - | ns |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NExL) }}$ | FMC_CLK low to FMC_NEx low (x=0..2) | - | 2 |  |
| ${ }_{\text {t }}$ (CLKH-NExH) | FMC_CLK high to FMC_NEx high (x=0...2) | $\mathrm{T}_{\text {HCLK }}+0.5$ | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKL-NADVL) }}$ | FMC_CLK low to FMC_NADV low | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKL-NADVH) }}$ | FMC_CLK low to FMC_NADV high | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-AV) }}$ | FMC_CLK low to FMC_Ax valid ( $\mathrm{x}=16 \ldots 25$ ) | - | 2.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKH-AIV) }}$ | FMC_CLK high to FMC_Ax invalid (x=16...25) | $\mathrm{T}_{\text {HCLK }}$ | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NWEL) }}$ | FMC_CLK low to FMC_NWE low | - | 1.5 |  |
| $\mathrm{t}_{\mathrm{d}(\text { CLKH-NWEH) }}$ | FMC_CLK high to FMC_NWE high | $\mathrm{T}_{\text {HCLK }}+1$ | - |  |
| $\mathrm{t}_{\text {d(CLKL-Data) }}$ | FMC_D[15:0] valid data after FMC_CLK low | - | 3.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (CLKL-NBLL) }}$ | FMC_CLK low to FMC_NBL low | - | 2 |  |
| $\mathrm{t}_{\mathrm{d}(\mathrm{CLKH}}$-NBLH) | FMC_CLK high to FMC_NBL high | $\mathrm{T}_{\text {HCLK }}+1$ | - |  |
| $\mathrm{t}_{\text {su( }}$ (NWAIT-CLKH) | FMC_NWAIT valid before FMC_CLK high | 2 | - |  |
| $\mathrm{t}_{\text {( }}$ (CLKH-NWAIT) | FMC_NWAIT valid after FMC_CLK high | 3.5 | - |  |

1. Guaranteed by characterization results.

## NAND controller waveforms and timings

Figure 70 through Figure 73 represent synchronous waveforms, and Table 113 and Table 114 provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime $=0 \times 01$;
- COM.FMC_WaitSetupTime $=0 \times 03$;
- COM.FMC_HoldSetupTime $=0 \times 02$;
- COM.FMC_HiZSetupTime $=0 \times 01$;
- ATT.FMC_SetupTime $=0 \times 01$;
- ATT.FMC_WaitSetupTime $=0 \times 03$;
- ATT.FMC_HoldSetupTime $=0 \times 02$;
- ATT.FMC_HiZSetupTime $=0 \times 01$;
- Bank = FMC_Bank_NAND;
- MemoryDataWidth = FMC_MemoryDataWidth_16b;
- ECC = FMC_ECC_Enable;
- ECCPageSize = FMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime $=0$.

In all timing tables, the $\mathrm{T}_{\text {HCLK }}$ is the HCLK clock period.

Figure 70. NAND controller waveforms for read access


Figure 71. NAND controller waveforms for write access


Figure 72. NAND controller waveforms for common memory read access


Figure 73. NAND controller waveforms for common memory write access


Table 113. Switching characteristics for NAND Flash read cycles ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w}(\mathrm{NOE})}$ | FMC_NOE low width | $4 \mathrm{~T}_{\text {HCLK }}-0.5$ | $4 \mathrm{~T}_{\text {HCLK }}+0.5$ | ns |
| $\mathrm{t}_{\text {su(D-NOE) }}$ | FMC_D[15-0] valid data before FMC_NOE high | 11 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (NOE-D) }}$ | FMC_D[15-0] valid data after FMC_NOE high | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (ALE-NOE) }}$ | FMC_ALE valid before FMC_NOE low | - | $3 \mathrm{~T}_{\text {HCLK }}+1$ |  |
| $\mathrm{t}_{\text {( }}$ (NOE-ALE) | FMC_NWE high to FMC_ALE invalid | $4 \mathrm{~T}_{\text {HCLK }}-2$ | - |  |

1. Guaranteed by characterization results.

Table 114. Switching characteristics for NAND Flash write cycles ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (NWE) }}$ | FMC_NWE low width | $4 \mathrm{~T}_{\text {HCLK }}-0.5$ | $4 \mathrm{~T}_{\text {HCLK }}+0.5$ | ns |
| $\mathrm{t}_{\mathrm{v} \text { (NWE-D) }}$ | FMC_NWE low to FMC_D[15-0] valid | 0 | - |  |
| $\mathrm{t}_{\text {( }}$ (NWE-D) | FMC_NWE high to FMC_D[15-0] invalid | $2 \mathrm{~T}_{\text {HCLK }}-1$ | - |  |
| $\mathrm{t}_{\text {d( } \mathrm{D}-\mathrm{NWE})}$ | FMC_D[15-0] valid before FMC_NWE high | $5 \mathrm{~T}_{\text {HCLK }}-1$ | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (ALE-NWE) }}$ | FMC_ALE valid before FMC_NWE low | - | $3 \mathrm{~T}_{\text {HCLK }}+1$ |  |
| $\mathrm{t}_{\mathrm{h} \text { (NWE-ALE) }}$ | FMC_NWE high to FMC_ALE invalid | $2 \mathrm{~T}_{\text {HCLK }}-2$ | - |  |

1. Guaranteed by characterization results.

## SDRAM waveforms and timings

- $\quad C L=30 \mathrm{pF}$ on data and address lines. $\mathrm{CL}=10 \mathrm{pF}$ on FMC_SDCLK unless otherwise specified.

In all timing tables, the $\mathrm{T}_{\text {HCLK }}$ is the HCLK clock period.

- For 3.0 V $\leq V_{D D} \leq 3.6 \mathrm{~V}$, maximum FMC_SDCLK $=100 \mathrm{MHz}$ at $\mathrm{CL}=20 \mathrm{pF}$ (on FMC_SDCLK).
- For $2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$, maximum FMC_SDCLK $=90 \mathrm{MHz}$ at $\mathrm{CL}=30 \mathrm{pF}$ (on FMC_SDCLK).
- For $1.71 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}}<1.9 \mathrm{~V}$, maximum FMC _SDCLK $=70 \mathrm{MHz}$ at $\mathrm{CL}=10 \mathrm{pF}$ (on FMC_SDCLK).

Figure 74. SDRAM read access waveforms (CL = 1)


Table 115. SDRAM read timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (SDCLK) }}$ | FMC_SDCLK period | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | $2 \mathrm{~T}_{\text {HCLK }}+0.5$ | ns |
| $\mathrm{t}_{\text {su(SDCLKH _Data) }}$ | Data input setup time | 1.5 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKH_Data) }}$ | Data input hold time | 1.5 | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { SDCLKL_Add) }}$ | Address valid time | - | 3.5 |  |
| $\mathrm{t}_{\text {d(SDCLKL- SDNE) }}$ | Chip select valid time | - | 1.5 |  |
| $\mathrm{t}_{\mathrm{h}}$ (SDCLKL_SDNE) | Chip select hold time | 0.5 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL_SNRAS) }}$ | SDNRAS valid time | - | 1 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL_SNRRAS) }}$ | SDNRAS hold time | 0.5 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL_SDNCAS) }}$ | SDNCAS valid time | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL_SDNCAS) }}$ | SDNCAS hold time | 0 | - |  |

1. Guaranteed by characterization results.

Table 116. LPSDR SDRAM read timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {W(SDCLK) }}$ | FMC_SDCLK period | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | $2 \mathrm{~T}_{\text {HCLK }}+0.5$ | ns |
| $\mathrm{t}_{\text {su(SDCLKH_Data) }}$ | Data input setup time | 0 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKH_Data) }}$ | Data input hold time | 4.5 | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { SDCLKL_Add) }}$ | Address valid time | - | 2.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL_SDNE) }}$ | Chip select valid time | - | 2.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL_SDNE) }}$ | Chip select hold time | 0 | - |  |
| $\mathrm{t}_{\text {d(SDCLKL_S }}$ SNRAS | SDNRAS valid time | - | 0.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL_SDNRAS) }}$ | SDNRAS hold time | 0 | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { SDCLKL_SDNCAS) }}$ | SDNCAS valid time | - | 1.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL_SDNCAS) }}$ | SDNCAS hold time | 0 | - |  |

1. Guaranteed by characterization results.

Figure 75. SDRAM write access waveforms


Table 117. SDRAM write timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (SDCLK) }}$ | FMC_SDCLK period | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | $2 \mathrm{~T}_{\text {HCLK }}+0.5$ | ns |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL _Data }}$ ) | Data output valid time | - | 3 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL_Data) }}$ | Data output hold time | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL_Add) }}$ | Address valid time | - | 3.5 |  |
| $\mathrm{t}_{\text {d(SDCLKL_S }}$ SDNWE) | SDNWE valid time | - | 1.5 |  |
| $\mathrm{t}_{\text {h(SDCLKL_SDNWE) }}$ | SDNWE hold time | 0.5 | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { SDCLKL_ }}$ SDNE) | Chip select valid time | - | 1.5 |  |
| $\mathrm{th}_{\mathrm{h} \text { (SDCLKL-_SDNE) }}$ | Chip select hold time | 0.5 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL_SDRAS) }}$ | SDNRAS valid time | - | 1 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL_SDNRAS) }}$ | SDNRAS hold time | 0.5 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL_SDNCAS) }}$ | SDNCAS valid time | - | 1 |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL_SDNCAS) }}$ | SDNCAS hold time | 0.5 | - |  |

1. Guaranteed by characterization results.

Table 118. LPSDR SDRAM write timings ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{w} \text { (SDCLK) }}$ | FMC_SDCLK period | $2 \mathrm{~T}_{\text {HCLK }}-0.5$ | $2 \mathrm{~T}_{\text {HCLK }}+0.5$ | ns |
| $\left.\mathrm{t}_{\mathrm{d}(\text { SDCLKL_ _Data }}\right)$ | Data output valid time | - | 2.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL _Data) }}$ | Data output hold time | 0 | - |  |
| $\mathrm{t}_{\mathrm{d}(\text { SDCLKL_Add) }}$ | Address valid time | - | 2.5 |  |
| $\mathrm{t}_{\text {d(SDCLKL-SDNWE) }}$ | SDNWE valid time | - | 2.5 |  |
| $\mathrm{t}_{\mathrm{h} \text { (SDCLKL-SDNWE) }}$ | SDNWE hold time | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL- SDNE) }}$ | Chip select valid time | - | 0.5 |  |
| $\mathrm{t}_{\text {( }}$ SDCLKL- SDNE) | Chip select hold time | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL-SDNRAS) }}$ | SDNRAS valid time | - | 1.5 |  |
| $\mathrm{t}_{\mathrm{h}}$ (SDCLKL-SDNRAS) | SDNRAS hold time | 0 | - |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL-SDNCAS) }}$ | SDNCAS valid time | - | 1.5 |  |
| $\mathrm{t}_{\mathrm{d} \text { (SDCLKL-SDNCAS) }}$ | SDNCAS hold time | 0 | - |  |

1. Guaranteed by characterization results.

### 5.3.31 Quad-SPI interface characteristics

Unless otherwise specified, the parameters given in Table 119 and Table 120 for Quad-SPI are derived from tests performed under the ambient temperature, $\mathrm{f}_{\text {AHB }}$ frequency and $\mathrm{V}_{\mathrm{DD}}$ supply voltage conditions summarized in Table 18: General operating conditions, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load $C=20 \mathrm{pF}$
- Measurement points are done at CMOS levels: $0.5 \times \mathrm{V}_{\mathrm{DD}}$

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output alternate function characteristics.

Table 119. Quad-SPI characteristics in SDR mode ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Fck1/t(CK) | Quad-SPI clock <br> frequency | $2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}$ <br> $\mathrm{CL}=20 \mathrm{pF}$ | - | - | 108 |  |
|  |  | $1.71 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}$ <br> $\mathrm{CL}=15 \mathrm{pF}$ | - | - | 100 | MHz |

Table 119. Quad-SPI characteristics (continued)in SDR mode ${ }^{(1)}$ (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| tw(CKH) | Quad-SPI clock high and low time | - | $\mathrm{t}(\mathrm{CK}) / 2$ - 1 | - | $\mathrm{t}(\mathrm{CK}) / 2$ | ns |
| tw(CKL) |  |  | t(CK)/2 | - | $\mathrm{t}(\mathrm{CK}) / 2+1$ |  |
| ts(IN) | Data input setup time | - | 0.5 | - | - |  |
| th( IN ) | Data input hold time |  | 3 | - | - |  |
| tv(OUT) | Data output valid time | $2.7 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}$ | - | 1.5 | 3.5 |  |
|  |  | $1.71 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}$ | - | 1.5 | 2 |  |
| th(OUT) | Data output hold time | - | 0.5 | - | - |  |

1. Guaranteed by characterization results.

Table 120. Quad SPI characteristics in DDR mode ${ }^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Fck1/t(CK) | Quad-SPI clock frequency | $\begin{gathered} 2.7 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V} \\ \mathrm{CL}=20 \mathrm{pF} \end{gathered}$ | - | - | 80 | $\begin{gathered} \mathrm{MH} \\ \mathrm{z} \end{gathered}$ |
|  |  | $\begin{gathered} 1.8 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V} \\ \mathrm{CL}=15 \mathrm{pF} \end{gathered}$ | - | - | 80 |  |
|  |  | $\begin{gathered} 1.71 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V} \\ C L=10 \mathrm{pF} \end{gathered}$ | - | - | 80 |  |
| tw(CKH) | Quad-SPI clock high and low time | - | $\mathrm{t}(\mathrm{CK}) / 2$ - 1 | - | t(CK)/2 | ns |
| tw(CKL) |  |  | $\mathrm{t}(\mathrm{CK}) / 2$ | - | $\begin{gathered} \mathrm{t}(\mathrm{CK}) / 2 \\ +1 \end{gathered}$ |  |
| ts(IN), <br> $\operatorname{tsf}(\mathrm{IN})$ | Data input setup time | $2.7 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}$ | 0.75 | - | - |  |
|  |  | $1.71 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<2 \mathrm{~V}$ | 0.5 | - | - |  |
| thr(IN), <br> thf(IN) | Data input hold time | $2.7 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}$ | 2 | - | - |  |
|  |  | $1.71 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<2 \mathrm{~V}$ | 3 | - | - |  |
| $\operatorname{tvr}(\mathrm{OUT})$, <br> tvf(OUT) | Data output valid time | $2.7 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}$ | - | 8.5 | 10 |  |
|  |  | $\begin{gathered} 1.71 \mathrm{~V}<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V} \\ \mathrm{DHHC}=0 \end{gathered}$ | - | 8 | 12 |  |
|  |  | $\begin{gathered} \text { DHHC=1 } \\ \text { Pres=1, 2... } \end{gathered}$ | - | $\underset{\substack{\mathrm{T}_{\mathrm{HCLK}} / 2}}{ }$ | $\begin{gathered} \mathrm{T}_{\mathrm{HCLK}} / 2 \\ +2.5 \end{gathered}$ |  |
| thr(OUT), thf(OUT) | Data output hold time | DHHC=0 | 7.5 | - | - |  |
|  |  | $\begin{gathered} \mathrm{DHHC}=1 \\ \text { Pres=1, } 2 \ldots \end{gathered}$ | $\begin{gathered} \mathrm{T}_{\text {HCLK }} / 2 \\ +0.5 \end{gathered}$ | - | - |  |

[^7]Figure 76. Quad-SPI timing diagram - SDR mode


Figure 77. Quad-SPI timing diagram - DDR mode


### 5.3.32 Camera interface (DCMI) timing specifications

Unless otherwise specified, the parameters given in Table 121 for DCMI are derived from tests performed under the ambient temperature, $\mathrm{f}_{\mathrm{HCLK}}$ frequency and $\mathrm{V}_{\mathrm{DD}}$ supply voltage summarized in Table 18, with the following configuration:

- DCMI_PIXCLK polarity: falling
- DCMI_VSYNC and DCMI_HSYNC polarity: high
- Data formats: 14 bits

Table 121. DCMI characteristics ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| - | Frequency ratio DCMI_PIXCLK/f ${ }_{\text {HCLK }}$ | - | 0.4 | - |
| DCMI_PIXCLK | Pixel clock input | - | 54 | MHz |
| $\mathrm{D}_{\text {Pixel }}$ | Pixel clock input duty cycle | 30 | 70 | \% |
| $\mathrm{t}_{\text {su( }}$ (DATA) | Data input setup time | 2 | - | ns |
| $\mathrm{t}_{\mathrm{h}}$ (DATA) | Data input hold time | 0.5 | - |  |
| $\mathrm{t}_{\mathrm{su}}$ (HSYNC) $\mathrm{t}_{\text {su(VSYNC) }}$ | DCMI_HSYNC/DCMI_VSYNC input setup time | 2.5 | - |  |
| $\mathrm{t}_{\mathrm{h} \text { (HSYNC) }}$ <br> $t_{h}$ (VSYNC) | DCMI_HSYNC/DCMI_VSYNC input hold time | 3 | - |  |

1. Guaranteed by characterization results.

Figure 78. DCMI timing diagram


### 5.3.33 LCD-TFT controller (LTDC) characteristics

Unless otherwise specified, the parameters given in Table 122 for LCD-TFT are derived from tests performed under the ambient temperature, $f_{H C L K}$ frequency and $V_{D D}$ supply voltage summarized in Table 18, with the following configuration:

- LCD_CLK polarity: high
- LCD_DE polarity: low
- LCD_VSYNC and LCD_HSYNC polarity: high
- Pixel formats: 24 bits

Table 122. LTDC characteristics ${ }^{(1)}$

| Symbol | Parameter | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {CLK }}$ | LTDC clock output frequency | - | 83 | MHz |
| $\mathrm{D}_{\text {CLK }}$ | LTDC clock output duty cycle | 45 | 55 | \% |
| $\mathrm{t}_{\mathrm{w} \text { (CLKH) }}$ <br> $\mathrm{t}_{\mathrm{w}(\mathrm{CLKL})}$ | Clock High time, low time | tw(CLK)/2-0.5 | tw(CLK)/2+0.5 | ns |
| $\mathrm{t}_{\mathrm{v} \text { (DATA) }}$ | Data output valid time | - | 6 |  |
| $\mathrm{t}_{\mathrm{h} \text { (DATA) }}$ | Data output hold time | 0 | - |  |
| $\mathrm{t}_{\mathrm{v} \text { (HSYNC), }}$ $\mathrm{t}_{\mathrm{v}(\mathrm{VSYNC})}$, $\mathrm{t}_{\mathrm{v} \text { (DE) }}$ | HSYNC/VSYNC/DE output valid time | - | 3.5 |  |
| $t_{h(H S Y N C)}$, <br> $t_{h(V S Y N C)}$, <br> $t_{\text {( }}$ (E) | HSYNC/VSYNC/DE output hold time | 0.5 | - |  |

1. Guaranteed by characterization results.

Figure 79. LCD-TFT horizontal timing diagram


Figure 80. LCD-TFT vertical timing diagram


### 5.3.34 Digital filter for Sigma-Delta Modulators (DFSDM) characteristics

Unless otherwise specified, the parameters given in Table 123 for DFSDM are derived from tests performed under the ambient temperature, $f_{\text {PCLK2 }}$ frequency and $V_{D D}$ supply voltage summarized in Table 18, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load $C=30 \mathrm{pF}$
- Measurement points are done at CMOS levels: $0.5 \times$ VDD

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output alternate function characteristics (DFSDM1_CKINx, DFSDM1_DATINx, DFSDM1_CKOUT for DFSDM1).

Table 123. DFSDM measured timing 1.71-3.6V
$\left.\begin{array}{|c|c|c|c|c|c|c|}\hline \text { Symbol } & \text { Parameter } & \text { Conditions } & \text { Min } & \text { Typ } & \text { Max } & \text { Unit } \\ \hline \mathrm{f}_{\text {DFSDMCLK }} & \text { DFSDM clock } & \begin{array}{c}1.71<\mathrm{V}_{\text {DD }}<3.6 \mathrm{~V}\end{array} & - & - & \mathrm{f}_{\text {SYSCLK }}\end{array}\right]$

Table 123. DFSDM measured timing 1.71-3.6V (continued)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $t_{\text {wh (CKIN) }}$ <br> $\mathrm{t}_{\mathrm{wl}}(\mathrm{CKIN})$ | Input clock high and low time | $\begin{aligned} & \text { SPI mode (SITP[1:0]=0,1), } \\ & \text { External clock mode } \\ & \text { (SPICKSEL[1:0]=0), } \\ & 1.71<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V} \end{aligned}$ | TCKIN/2-0.5 | $\mathrm{T}_{\text {CKIN }} / 2$ | - | ns |
| $\mathrm{t}_{\text {su }}$ | Data input setup time | SPI mode (SITP[1:0]=0,1), <br> External clock mode (SPICKSEL[1:0]=0), $1.71<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V}$ | 2 | - | - |  |
| $t_{\text {h }}$ | Data input hold time | $\begin{aligned} & \text { SPI mode (SITP[1:0]=0,1), } \\ & \text { External clock mode } \\ & \text { (SPICKSEL[1:0]=0), } \\ & 1.71<\mathrm{V}_{\mathrm{DD}}<3.6 \mathrm{~V} \end{aligned}$ | 3 | - | - |  |
| $\mathrm{T}_{\text {Manchester }}$ | Manchester data period (recovered clock period) | Manchester mode (SITP[1:0]=2,3), Internal clock mode (SPICKSEL[1:0] $=0$ ), $1.71<V_{D D}<3.6 \mathrm{~V}$ | $\begin{aligned} & \text { (CKOUTDIV+1) } \\ & { }^{*} \mathrm{~T}_{\text {DFSDMCLK }} \end{aligned}$ | - | (2*CKOUTDIV) <br> * ${ }_{\text {DFSDMCLK }}$ |  |

### 5.3.35 DFSDM timing diagrams

Figure 81. Channel transceiver timing diagrams

|  |  |
| :---: | :---: |
| $\infty$ 0 $\vdots$ $\vdots$ 11 4 0 0 0 0 0 0 0 0 $=$ 0 0 |  |
| Manchester timing |  |

### 5.3.36 SD/SDIO MMC card host interface (SDMMC) characteristics

Unless otherwise specified, the parameters given in Table 124 for the SDIO/MMC interface are derived from tests performed under the ambient temperature, $f_{P C L K 2}$ frequency and $V_{D D}$ supply voltage conditions summarized in Table 18, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load $\mathrm{C}=30 \mathrm{pF}$
- Measurement points are done at CMOS levels: $0.5 \mathrm{~V}_{\mathrm{DD}}$

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output characteristics.

Figure 82. SDIO high-speed mode


Figure 83. SD default mode


Table 124. Dynamic characteristics: $S D / M M C$ characteristics, $V_{D D}=2.7 \mathrm{~V}$ to $3.6 \mathrm{~V}^{(1)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\mathrm{PP}}$ | Clock frequency in data transfer mode | - | 0 | - | 50 | MHz |
| - | SDMMC_CK/fPCLK2 frequency ratio | - | - | - | 8/3 | - |
| ${ }^{\text {tw }}$ (CKL) | Clock low time | $\mathrm{fpp}=50 \mathrm{MHz}$ | 9.5 | 10.5 | - | ns |
| ${ }^{\text {W }}$ (CKKH) | Clock high time | fpp $=50 \mathrm{MHz}$ | 8.5 | 9.5 | - |  |

CMD, D inputs (referenced to CK) in MMC and SD HS mode

| $\mathrm{t}_{I S U}$ | Input setup time HS | fpp $=50 \mathrm{MHz}$ | 3.5 | - | - | ns |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{IH}}$ | Input hold time HS | fpp $=50 \mathrm{MHz}$ | 2.5 | - | - |  |

CMD, D outputs (referenced to CK) in MMC and SD HS mode

| $\mathrm{t}_{\mathrm{OV}}$ | Output valid time HS | $\mathrm{fpp}=50 \mathrm{MHz}$ | - | 11 | 12 | ns |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | $\mathrm{t}_{\mathrm{OH}}$ | Output hold time HS | $\mathrm{fpp}=50 \mathrm{MHz}$ | 9 | - |  |

CMD, D inputs (referenced to CK) in SD default mode

| tISUD | Input setup time SD | fpp $=25 \mathrm{MHz}$ | 3.5 | - | - | ns |
| :---: | :--- | :---: | :---: | :---: | :---: | :---: |
| tIHD | Input hold time SD | fpp $=25 \mathrm{MHz}$ | 2.5 | - | - |  |

CMD, D outputs (referenced to CK) in SD default mode

| tOVD | Output valid default time SD | fpp $=25 \mathrm{MHz}$ | - | 0.5 | 1.5 | ns |
| :--- | :--- | :---: | :---: | :---: | :---: | :---: |
| tOHD | Output hold default time SD | fpp $=25 \mathrm{MHz}$ | 0 | - | - |  |

1. Guaranteed by characterization results.

Table 125. Dynamic characteristics: eMMC characteristics, $\mathrm{V}_{\mathrm{DD}}=1.71 \mathrm{~V}$ to $1.9 \mathrm{~V}^{(1)(2)}$

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\mathrm{PP}}$ | Clock frequency in data transfer mode | - | 0 | - | 50 | MHz |
| - | SDMMC_CK/fPCLK2 frequency ratio | - | - | - | 8/3 | - |
| $t_{\text {W(CKL) }}$ | Clock low time | fpp $=50 \mathrm{MHz}$ | 9.5 | 10.5 | - |  |
| ${ }^{\text {tw(CKH) }}$ | Clock high time | fpp $=50 \mathrm{MHz}$ | 8.5 | 9.5 | - |  |
| CMD, D inputs (referenced to CK) in emmC mode |  |  |  |  |  |  |
| $\mathrm{t}_{\text {ISU }}$ | Input setup time HS | fpp $=50 \mathrm{MHz}$ | 3 | - | - |  |
| $\mathrm{t}_{\mathrm{H}}$ | Input hold time HS | fpp $=50 \mathrm{MHz}$ | 4 | - | - | ns |
| CMD, D outputs (referenced to CK) in eMMC mode |  |  |  |  |  |  |
| $\mathrm{t}_{\mathrm{OV}}$ | Output valid time HS | fpp $=50 \mathrm{MHz}$ | - | 11 | 15.5 | ns |
| $\mathrm{t}_{\mathrm{OH}}$ | Output hold time HS | $\mathrm{fpp}=50 \mathrm{MHz}$ | 9.5 | - | - |  |

1. Guaranteed by characterization results.
2. Cload $=20 \mathrm{pF}$.

## 6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK ${ }^{\circledR}$ packages, depending on their level of environmental compliance. ECOPACK ${ }^{\circledR}$ specifications, grade definitions and product status are available at: www.st.com. ECOPACK ${ }^{\circledR}$ is an ST trademark.

### 6.1 LQFP100 14x 14 mm, low-profile quad flat package information

Figure 84. LQFP100, $14 \times 14 \mathrm{~mm}$ 100-pin low-profile quad flat package outline


[^8]Table 126. LQPF100, $14 \times 14$ mm 100-pin low-profile quad flat package mechanical data

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| A | - | - | 1.600 | - | - | 0.0630 |
| A1 | 0.050 | - | 0.150 | 0.0020 | - | 0.0059 |
| A2 | 1.350 | 1.400 | 1.450 | 0.0531 | 0.0551 | 0.0571 |
| b | 0.170 | 0.220 | 0.270 | 0.0067 | 0.0087 | 0.0106 |
| c | 0.090 | - | 0.200 | 0.0035 | - | 0.0079 |
| D | 15.800 | 16.000 | 16.200 | 0.6220 | 0.6299 | 0.6378 |
| D1 | 13.800 | 14.000 | 14.200 | 0.5433 | 0.5512 | 0.5591 |
| D3 | - | 12.000 | - | - | 0.4724 | - |
| E | 15.800 | 16.000 | 16.200 | 0.6220 | 0.6299 | 0.6378 |
| E1 | 13.800 | 14.000 | 14.200 | 0.5433 | 0.5512 | 0.5591 |
| E3 | - | 12.000 | - | - | 0.4724 | - |
| e | - | 0.500 | - | - | 0.0197 | - |
| L | 0.450 | 0.600 | 0.750 | 0.0177 | 0.0236 | 0.0295 |
| L1 | - | 1.000 | - | - | 0.0394 | - |
| k | $0^{\circ}$ | $3.5^{\circ}$ | $7^{\circ}$ | $0^{\circ}$ | $3.5^{\circ}$ | $7^{\circ}$ |
| ccc | - | - | 0.080 | - | - | 0.0031 |

1. Values in inches are converted from mm and rounded to 4 decimal digits

Figure 85. LQFP100, $14 \times 14 \mathrm{~mm}, 100$-pin low-profile quad flat package recommended footprint


1. Dimensions are expressed in millimeters.

## LQFP100 device making

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 86. LQFP100, $14 \times 14 \mathrm{~mm}, 100$-pin low-profile quad flat package top view example


1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 6.2 TFBGA100, $8 \times 8 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package information

Figure 87. TFBGA100, $8 \times 8 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package outline


1. Drawing is not to scale.

Table 127. TFBGA100, $8 \times 8 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package mechanical data

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| A | - | - | 1.100 | - | - | 0.0433 |
| A1 | 0.150 | - | - | 0.0059 | - | - |
| A2 | - | 0.760 | - | - | 0.0299 | - |
| b | 0.350 | 0.400 | 0.450 | 0.0138 | 0.0157 | 0.0177 |

Table 127. TFBGA100, $8 \times 8 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package mechanical data (continued)

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| D | 7.850 | 8.000 | 8.150 | 0.3091 | 0.3150 | 0.3209 |
| D1 | - | 7.200 | - | - | 0.2835 | - |
| E | 7.850 | 8.000 | 8.150 | 0.3091 | 0.3150 | 0.3209 |
| E1 | - | 7.200 | - | - | 0.2835 | - |
| e | - | 0.800 | - | - | 0.0315 | - |
| F | - | 0.400 | - | - | 0.0157 | - |
| G | - | 0.400 | - | - | 0.0157 | - |
| ddd | - | - | 0.100 | - | - | 0.0039 |
| eee | - | - | 0.150 | - | - | 0.0059 |
| fff | - | - | 0.080 | - | - | 0.0031 |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 88. TFBGA100, $8 \times 8 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package recommended footprint


1. Dimensions are expressed in millimeters.

Table 128. TFBGA100 recommended PCB design rules ( 0.8 mm pitch BGA)

| Dimension | Recommended values |
| :--- | :--- |
| Pitch | 0.8 |
| Dpad | 0.400 mm |
| Dsm | 0.470 mm typ (depends on the soldermask <br> registration tolerance) |
| Stencil opening | 0.400 mm |
| Stencil thickness | Between 0.100 mm and 0.125 mm |
| Pad trace width | 0.120 mm |

## TFBGA100 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 89. TFBGA100, $8 \times 8 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package top view example


1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 6.3 LQFP144 $20 \times 20$ mm, low-profile quad flat package information

Figure 90. LQFP144, $20 \times 20 \mathrm{~mm}$, 144-pin low-profile quad flat package outline


1. Drawing is not to scale.

Table 129. LQFP144, $20 \times 20 \mathrm{~mm}$, 144-pin low-profile quad flat package mechanical data

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| A | - | - | 1.600 | - | - | 0.0630 |
| A1 | 0.050 | - | 0.150 | 0.0020 | - | 0.0059 |
| A2 | 1.350 | 1.400 | 1.450 | 0.0531 | 0.0551 | 0.0571 |
| b | 0.170 | 0.220 | 0.270 | 0.0067 | 0.0087 | 0.0106 |
| c | 0.090 | - | 0.200 | 0.0035 | - | 0.0079 |
| D | 21.800 | 22.000 | 22.200 | 0.8583 | 0.8661 | 0.874 |
| D1 | 19.800 | 20.000 | 20.200 | 0.7795 | 0.7874 | 0.7953 |
| D3 | - | 17.500 | - | - | 0.689 | - |
| E | 21.800 | 22.000 | 22.200 | 0.8583 | 0.8661 | 0.8740 |
| E1 | 19.800 | 20.000 | 20.200 | 0.7795 | 0.7874 | 0.7953 |
| E3 | - | 17.500 | - | - | 0.6890 | - |
| e | - | 0.500 | - | - | 0.0197 | - |
| L | 0.450 | 0.600 | 0.750 | 0.0177 | 0.0236 | 0.0295 |
| L1 | - | 1.000 | - | - | 0.0394 | - |
| k | $0^{\circ}$ | $3.5^{\circ}$ | $7^{\circ}$ | $0^{\circ}$ | $3.5^{\circ}$ | $7^{\circ}$ |
| ccc | - | - | 0.080 | - | - | 0.0031 |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 91. LQFP144, $20 \times 20 \mathrm{~mm}$, 144-pin low-profile quad flat package recommended footprint


1. Dimensions are expressed in millimeters.

## LQFP144 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 92. LQFP144, $20 \times 20 \mathrm{~mm}$, 144-pin low-profile quad flat package top view example


1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 6.4 LQFP176 $24 \times 24$ mm, low-profile quad flat package information

Figure 93. LQFP176, $24 \times 24 \mathrm{~mm}$, 176-pin low-profile quad flat package outline


1. Drawing is not to scale.

Table 130. LQFP176, $24 \times 24 \mathrm{~mm}$, 176-pin low-profile quad flat package mechanical data

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| A | - | - | 1.600 | - | - | 0.0630 |
| A1 | 0.050 | - | 0.150 | 0.0020 | - | 0.0059 |
| A2 | 1.350 | - | 1.450 | 0.0531 | - | 0.0060 |
| b | 0.170 | - | 0.270 | 0.0067 | - | 0.0106 |
| C | 0.090 | - | 0.200 | 0.0035 | - | 0.0079 |
| D | 23.900 | - | 24.100 | 0.9409 | - | 0.9488 |
| E | 23.900 | - | 24.100 | 0.9409 | - | 0.9488 |
| e | - | 0.500 | - | - | 0.0197 | - |
| HD | 25.900 | - | 26.100 | 1.0200 | - | 1.0276 |
| HE | 25.900 | - | 26.100 | 1.0200 | - | 1.0276 |
| L | 0.450 | - | 0.750 | 0.0177 | - | 0.0295 |
| L1 | - | 1.000 | - | - | 0.0394 | - |
| ZD | - | 1.250 | - | - | 0.0492 | - |
| ZE | - | 1.250 | - | - | 0.0492 | - |
| ccc | - | - | 0.080 | - | - | 0.0031 |
| k | $0^{\circ}$ | - | $7^{\circ}$ | $0{ }^{\circ}$ | - | $7^{\circ}$ |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 94. LQFP176, $24 \times 24 \mathrm{~mm}$, 176-pin low-profile quad flat package recommended footprint


1. Dimensions are expressed in millimeters.

## LQFP176 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 95. LQFP176, $24 \times 24 \mathrm{~mm}$, 176-pin low-profile quad flat package top view example


1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 6.5 LQFP208 $28 \times 28$ mm low-profile quad flat package information

Figure 96. LQFP208, $28 \times 28 \mathrm{~mm}$, 208-pin low-profile quad flat package outline


1. Drawing is not to scale.

Table 131. LQFP208, $28 \times 28 \mathrm{~mm}$, 208-pin low-profile quad flat package mechanical data

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| A | - | - | 1.600 | -- | - | 0.0630 |
| A1 | 0.050 | - | 0.150 | 0.0020 | - | 0.0059 |
| A2 | 1.350 | 1.400 | 1.450 | 0.0531 | 0.0551 | 0.0571 |
| b | 0.170 | 0.220 | 0.270 | 0.0067 | 0.0087 | 0.0106 |
| c | 0.090 | - | 0.200 | 0.0035 | - | 0.0079 |
| D | 29.800 | 30.000 | 30.200 | 1.1732 | 1.1811 | 1.1890 |
| D1 | 27.800 | 28.000 | 28.200 | 1.0945 | 1.1024 | 1.1102 |
| D3 | - | 25.500 | - | - | 1.0039 | - |
| E | 29.800 | 30.000 | 30.200 | 1.1732 | 1.1811 | 1.1890 |
| E1 | 27.800 | 28.000 | 28.200 | 1.0945 | 1.1024 | 1.1102 |
| E3 | - | 25.500 | - | - | 1.0039 | - |
| e | - | 0.500 | - | - | 0.0197 | - |
| L | 0.450 | 0.600 | 0.750 | 0.0177 | 0.0236 | 0.0295 |
| L1 | - | 1.000 | - | - | 0.0394 | - |
| k | $0^{\circ}$ | $3.5^{\circ}$ | $7.0^{\circ}$ | $0^{\circ}$ | $3.5^{\circ}$ | $7.0^{\circ}$ |
| ccc | - | - | 0.080 | - | - | 0.0031 |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 97. LQFP208, $28 \times 28$ mm, 208-pin low-profile quad flat package recommended footprint


1. Dimensions are expressed in millimeters.

## LQFP208 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 98. LQFP208, $28 \times 28 \mathrm{~mm}$, 208-pin low-profile quad flat package top view example


1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 6.6 WLCSP 180-bump, $5.5 \times 6$ mm, wafer level chip scale package information

Figure 99. WLCSP 180-bump, $5.5 \times 6 \mathrm{~mm}, 0.4 \mathrm{~mm}$ pitch wafer level chip scale package outline


1. Drawing is not to scale.

Table 132. WLCSP 180-bump, $5.5 \times 6 \mathrm{~mm}$, 0.4 mm pitch wafer level chip scale package mechanical data

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| A | 0.525 | 0.555 | 0.585 | 0.0207 | 0.0219 | 0.230 |
| A1 | - | 0.175 | - | - | 0.0069 | - |
| A2 | - | 0.380 | - | - | 0.0150 | - |
| A3 | - | 0.025 | - | - | 0.0010 | - |
| b $^{(2)}$ | 0.220 | 0.250 | 0.280 | 0.0087 | 0.0098 | 0.0110 |
| D | 5.502 | 5.537 | 5.572 | 0.2166 | 0.2180 | 0.2194 |
| E | 6.060 | 6.095 | 6.130 | 0.2386 | 0.2400 | 0.2413 |
| e | - | 0.400 | - | - | 0.0157 | - |
| e1 | - | 4.800 | - | - | 0.1890 | - |
| e2 | - | 5.200 | - | - | 0.2047 | - |
| F | - | 0.368 | - | - | 0.0145 | - |
| G | - | 0.477 | - | - | 0.0188 | - |
| aaa | - | 0.110 | - | - | 0.0043 | - |
| bbb | - | 0.110 | - | - | 0.0043 | - |
| ccc | - | 0.110 | - | - | 0.0043 | - |
| ddd | - | 0.050 | - | - | 0.0020 | - |
| eee | - | 0.050 | - | - | 0.0020 | - |

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Dimension is measured at the maximum bump diameter parallel to primary datum Z .

Figure 100. WLCSP 180-bump, $5.5 \times 6 \mathrm{~mm}$, 0.4 mm pitch wafer level chip scale package recommended footprint


1. Dimensions are expressed in millimeters.

Table 133. WLCSP 180-bump, $5.5 \times 6 \mathrm{~mm}$, recommended PCB design rules ( 0.4 mm pitch)

| Dimension | Recommended values |
| :--- | :--- |
| Pitch | 0.4 |
| Dpad | 0.225 mm |
| Dsm | 0.290 mm typ. (depends on the soldermask <br> registration tolerance) |
| Stencil opening | 0.250 mm |
| Stencil thickness | 0.1 mm |

## WLCSP180 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 101. WLCSP180-bump, $5.5 \times 6 \mathrm{~mm}, 0.4 \mathrm{~mm}$ pitch wafer level chip scale package top view example


1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 6.7 UFBGA176+25, $10 \times 10,0.65 \mathrm{~mm}$ ultra thin fine-pitch ball grid array package information

Figure 102. UFBGA176+25, $10 \times 10 \times 0.65 \mathrm{~mm}$ ultra thin fine-pitch ball grid array package outline


1. Drawing is not to scale.

Table 134. UFBGA176+25, $10 \times 10 \times 0.65 \mathrm{~mm}$ ultra thin fine-pitch ball grid array package mechanical data

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| A | 0.460 | 0.530 | 0.600 | 0.0181 | 0.0209 | 0.0236 |
| A1 | 0.050 | 0.080 | 0.110 | 0.002 | 0.0031 | 0.0043 |
| A2 | 0.400 | 0.450 | 0.500 | 0.0157 | 0.0177 | 0.0197 |
| b | 0.230 | 0.280 | 0.330 | 0.0091 | 0.0110 | 0.0130 |
| D | 9.950 | 10.000 | 10.050 | 0.3917 | 0.3937 | 0.3957 |
| E | 9.950 | 10.000 | 10.050 | 0.3917 | 0.3937 | 0.3957 |
| e | - | 0.650 | - | - | 0.0256 | - |
| F | 0.400 | 0.450 | 0.500 | 0.0157 | 0.0177 | 0.0197 |
| ddd | - | - | 0.080 | - | - | 0.0031 |
| eee | - | - | 0.150 | - | - | 0.0059 |
| fff | - | - | 0.080 | - | - | 0.0031 |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 103. UFBGA176+25, $10 \times 10 \mathrm{~mm} \times 0.65 \mathrm{~mm}$, ultra fine-pitch ball grid array package recommended footprint


Table 135. UFBGA176+25 recommended PCB design rules ( 0.65 mm pitch BGA)

| Dimension | Recommended values |
| :--- | :--- |
| Pitch | 0.65 mm |
| Dpad | 0.300 mm |
| Dsm | 0.400 mm typ. (depends on the soldermask reg- <br> istration tolerance) |
| Stencil opening | 0.300 mm |
| Stencil thickness | Between 0.100 mm and 0.125 mm |
| Pad trace width | 0.100 mm |

## UFBGA 176+25 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 104. UFBGA $176+25,10 \times 10 \times 0.65 \mathrm{~mm}$ ultra thin fine-pitch ball grid array package top view example


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1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 6.8 TFBGA216, $13 \times 13 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package information

Figure 105. TFBGA216, $13 \times 13 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package outline


1. Drawing is not to scale.

Table 136. TFBGA216, $13 \times 13 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package mechanical data

| Symbol | millimeters |  |  | inches ${ }^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| A | - | - | 1.100 | - | - | 0.0433 |
| A1 | 0.150 | - | - | 0.0059 | - | - |
| A2 | - | 0.760 | - | - | 0.0299 | - |
| b | 0.350 | 0.400 | 0.450 | 0.0138 | 0.0157 | 0.0177 |
| D | 12.850 | 13.000 | 13.150 | 0.5118 | 0.5118 | 0.5177 |
| D1 | - | 11.200 | - | - | 0.4409 | - |
| E | 12.850 | 13.000 | 13.150 | 0.5118 | 0.5118 | 0.5177 |
| E1 | - | 11.200 | - | - | 0.4409 | - |
| e | - | 0.800 | - | - | 0.0315 | - |
| F | - | 0.900 | - | - | 0.0354 | - |

Table 136. TFBGA216, $13 \times 13 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package mechanical data (continued)

| Symbol | millimeters |  |  | inches $^{(1)}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Typ | Max | Min | Typ | Max |
| G | - | 0.900 | - | - | 0.0354 | - |
| ddd | - | - | 0.100 | - | - | 0.0039 |
| eee | - | - | 0.150 | - | - | 0.0059 |
| fff | - | - | 0.080 | - | - | 0.0031 |

1. Values in inches are converted from mm and rounded to 4 decimal digits

Figure 106. TFBGA216, $13 \times 13 \mathrm{~mm}, 0.8 \mathrm{~mm}$ pitch, thin fine-pitch ball grid array package recommended footprint


Table 137. TFBGA216 recommended PCB design rules ( 0.8 mm pitch BGA)

| Dimension | Recommended values |
| :--- | :--- |
| Pitch | 0.8 |
| Dpad | 0.400 mm |
| Dsm | 0.470 mm typ. (depends on the soldermask reg- <br> istration tolerance $)$ |
| Stencil opening | 0.400 mm |
| Stencil thickness | Between 0.100 mm and 0.125 mm |
| Pad trace width | 0.120 mm |

## TFBGA216 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 107. TFBGA216, $13 \times 13 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package top view example


1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 6.9 Thermal characteristics

The maximum chip-junction temperature, $T_{J}$ max, in degrees Celsius, may be calculated using the following equation:
$T_{J} \max =T_{A} \max +\left(P_{D} \max x \Theta_{J A}\right)$
Where:

- $\quad \mathrm{T}_{\mathrm{A}}$ max is the maximum ambient temperature in ${ }^{\circ} \mathrm{C}$,
- $\quad \Theta_{J A}$ is the package junction-to-ambient thermal resistance, in ${ }^{\circ} \mathrm{C} / \mathrm{W}$,
- $\quad P_{D}$ max is the sum of $P_{I N T} \max$ and $P_{I / O} \max \left(P_{D} \max =P_{I N T} \max +P_{I / O} m a x\right)$,
- $\quad P_{I N T} m a x$ is the product of $I_{D D}$ and $V_{D D}$, expressed in Watts. This is the maximum chip internal power.
$\mathrm{P}_{\mathrm{I} / \mathrm{O}}$ max represents the maximum power dissipation on output pins where:

$$
\mathrm{P}_{\mathrm{I} / \mathrm{O}} \max =\Sigma\left(\mathrm{V}_{\mathrm{OL}} \times \mathrm{I}_{\mathrm{OL}}\right)+\Sigma\left(\left(\mathrm{V}_{\mathrm{DD}}-\mathrm{V}_{\mathrm{OH}}\right) \times \mathrm{I}_{\mathrm{OH}}\right),
$$

taking into account the actual $\mathrm{V}_{\mathrm{OL}} / \mathrm{I}_{\mathrm{OL}}$ and $\mathrm{V}_{\mathrm{OH}} / \mathrm{I}_{\mathrm{OH}}$ of the $\mathrm{I} / \mathrm{Os}$ at low and high level in the application.

Table 138. Package thermal characteristics

| Symbol | Parameter | Value | Unit |
| :---: | :---: | :---: | :---: |
| $\Theta_{J A}$ | Thermal resistance junction-ambient LQFP100-14 $\times 14 \mathrm{~mm} / 0.5 \mathrm{~mm}$ pitch | 43 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  | Thermal resistance junction-ambient TFBGA100-8×8 mm / 0.8 mm pitch | 36.2 |  |
|  | Thermal resistance junction-ambient WLCSP180-0.4 mm pitch | 30 |  |
|  | Thermal resistance junction-ambient LQFP144-20 $\times 20 \mathrm{~mm} / 0.5 \mathrm{~mm}$ pitch | 40 |  |
|  | Thermal resistance junction-ambient LQFP176-24 $\times 24 \mathrm{~mm} / 0.5 \mathrm{~mm}$ pitch | 38 |  |
|  | Thermal resistance junction-ambient LQFP208-28 $\times 28 \mathrm{~mm} / 0.5 \mathrm{~mm}$ pitch | 19 |  |
|  | Thermal resistance junction-ambient UFBGA176-10× $10 \mathrm{~mm} / 0.5 \mathrm{~mm}$ pitch | 39 |  |
|  | Thermal resistance junction-ambient TFBGA216-13 $\times 13 \mathrm{~mm} / 0.8 \mathrm{~mm}$ pitch | 29 |  |

## Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

## 7 Ordering information

Table 139. Ordering information scheme
Example:
Device family
STM32 = Arm-based 32-bit microcontroller

Product type
F = general-purpose

## Device subfamily

$765=$ STM32F765xx, USB OTG FS/HS, camera interface, Ethernet
767= STM32F767xx, USB OTG FS/HS, camera interface,
Ethernet, LCD-TFT
768 = STM32F768Ax, USB OTG FS/HS, camera interface,
DSI host, WLCSP with internal regulator OFF
769= STM32F769xx, USB OTG FS/HS, camera interface,
Ethernet, DSI host

Pin count
$\mathrm{V}=100$ pins
$Z=144$ pins
I = 176 pins
$\mathrm{A}=180$ pins
$B=208$ pins
$\mathrm{N}=216$ pins
Flash memory size
G = 1024 Kbytes of Flash memory
I = 2048 Kbytes of Flash memory
Package
T = LQFP
$\mathrm{K}=\mathrm{UFBGA}$
H = TFBGA
$Y=$ WLCSP
Temperature range
6 = Industrial temperature range, -40 to $85^{\circ} \mathrm{C}$.
$7=$ Industrial temperature range, -40 to $105^{\circ} \mathrm{C}$.

## Options

xxx = programmed parts
TR = tape and reel

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

## Appendix A Recommendations when using internal reset OFF

When the internal reset is OFF, the following integrated features are no longer supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry must be disabled
- The embedded programmable voltage detector (PVD) is disabled
- $\quad V_{B A T}$ functionality is no more available and VBAT pin should be connected to $V_{D D}$
- The over-drive mode is not supported


## A. 1 Operating conditions

Table 140. Limitations depending on the operating power supply range
$\begin{array}{|l|c|c|c|l|l|}\hline & & \begin{array}{c}\text { Maximum } \\ \text { Operating } \\ \text { power } \\ \text { supply } \\ \text { range }\end{array} & \begin{array}{c}\text { ADC } \\ \text { operation }\end{array} & \begin{array}{c}\text { memory } \\ \text { access } \\ \text { frequency } \\ \text { with no wait } \\ \text { states } \\ \left(f_{\text {Flashmax }}\right.\end{array} & \begin{array}{c}\text { Maximum Flash } \\ \text { memory access } \\ \text { frequency with } \\ \text { wait states (1)(2) }\end{array}\end{array}$ I/O operation $\left.\begin{array}{c}\text { Possible Flash } \\ \text { memory } \\ \text { operations }\end{array}\right]$

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator on ITCM interface and L1-cache on AXI interface, the number of wait states given here does not impact the execution speed from the Flash memory since the ART accelerator or L1cache allows to achieve a performance equivalent to 0 -wait state program execution.
3. $\mathrm{V}_{\mathrm{DD}} / \mathrm{V}_{\mathrm{DDA}}$ minimum value of 1.7 V , with the use of an external power supply supervisor (refer to Section 2.18.1: Internal reset ON).

## Revision history

Table 141. Document revision history

| Date | Revision | Changes |
| :---: | :---: | :---: |
| 21-Mar-2016 | 1 | Initial release. |
| 26-Apr-2016 | 2 | DFSDM replaced by DFSDM1 in: <br> - Table 11: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions. <br> - Table 13: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx alternate function mapping. <br> - Table 14: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx register boundary addresses. <br> - Section 5.3.34: Digital filter for Sigma-Delta Modulators (DFSDM) characteristics. <br> Updated Table 2: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx features and peripheral counts adding DFSDM1 features. <br> Updated Table 40: Peripheral current consumption adding DFSDM1 current consumption. <br> Updated cover in 2 pages. <br> Update cover replacing for SPI 'up to $50 \mathrm{Mbit} / \mathrm{s}$ ' by 'up to $54 \mathrm{Mbit} / \mathrm{s}$ '. |
| 06-May-2016 | 3 | Updated Table 2: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx features and peripheral counts GPIO number. <br> Updated Table 13: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx alternate function mapping adding CAN3_RX alternate function on PA8/AF11. |
| 22-Dec-2016 | 4 | Updated Table 98: Dynamics characteristics: Ethernet MAC signals for RMII. <br> Updated Table 72: ADC characteristics sampling rate. <br> Updated all the notes removing 'not tested in production'. <br> Updated Figure 47: SPI timing diagram - slave mode and CPHA $=0$ <br> and Figure 48: SPI timing diagram - slave mode and CPHA $=1$ (1) with modified NSS timing waveforms (among other changes). <br> Updated Table 122: LTDC characteristics clock output frequency at 65 MHz . <br> Updated Section 5.2: Absolute maximum ratings. <br> Updated Section 6: Package information adding information about other optional marking or inset/upset marks. |

Table 141. Document revision history (continued)

| Date | Revision | Changes |
| :---: | :---: | :---: |
| 09-Aug-2017 | 5 | Updated note 1 below all the package device marking figures. <br> Updated cover title. <br> Updated Section 1: Description. <br> Updated Section 2.47: DSI Host (DSIHOST) video mode interface features. <br> Added Table 9: DFSDM implementation. <br> Updated Figure 11: STM32F76xxx LQFP100 pinout pin 43 and pin 44. Updated Table 65: I/O current injection susceptibility note by 'injection is not possible'. <br> Updated Table 122: LTDC characteristics LTDC clock frequency at 83 MHz . <br> Updated Table 72: ADC characteristics $\mathrm{R}_{\mathrm{ADC}}$ min at 1.5 Kohm. <br> Updated Figure 41: Recommended NRST pin protection note about the 0.1 uF capacitor. <br> Updated Table 83: DAC characteristics $\mathrm{R}_{\text {LOAD }}$ feature. |
| 11-Sep-2017 | 6 | Added TFBGA100 package: <br> - Updated cover page. <br> - Updated Table 2: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx features and peripheral counts. <br> - Updated Table 4: Regulator ON/OFF and internal reset ON/OFF availability. <br> - Added Figure 12: STM32F76xxx TFBGA100 pinout. <br> - Updated Table 11: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions. <br> - Updated Table 18: General operating conditions. <br> - Updated Table 63: ESD absolute maximum ratings. <br> - Updated note below Figure 44: Power supply and reference decoupling (VREF+ not connected to VDDA). <br> - Updated note below Figure 45: Power supply and reference decoupling (VREF+ connected to VDDA). <br> - Added Section 6.2: TFBGA100, $8 \times 8 \times 0.8 \mathrm{~mm}$ thin fine-pitch ball grid array package information. <br> - Updated Table 138: Package thermal characteristics. |

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[^0]:    The SPI1, SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I2S audio mode.

    1. For the LQFP100 package, only FMC Bank1 is available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select.

    SDMMC2 supports a dedicated power rail for clock, command and data $0 . .4$ lines, feature available starting from 144 pin package.
    DSI host interface is only available on STM32F769x sales types.
    $V_{D D} / V_{\text {DDA }}$ minimum value of 1.7 V is obtained when the internal reset is OFF (refer to Section 2.18.2: Internal reset OFF).
    UFBGA176 is not available for STM32F769x sales types.

[^1]:    1. Guaranteed by characterization results, unless otherwise specified.
[^2]:    1. Data based on characterization, tested in production.
[^3]:    1. The typical current consumption values are given with PDR OFF (internal reset OFF). When the PDR is OFF (internal reset OFF), the typical current consumption is reduced by additional $1.2 \mu \mathrm{~A}$.
    2. Guaranteed by characterization results, unless otherwise specified.
    3. Guaranteed by test in production.
[^4]:    1. Guaranteed based on test during characterization.
[^5]:    1. Guaranteed by design.
[^6]:    1. Mode 2/B, C and D only. In Mode 1, FMC_NADV is not used.
[^7]:    1. Guaranteed by characterization results.
[^8]:    1. Drawing is not to scale.
